

Supporting Information

Synthesis of Hupehenols A, B, and E from Protopanaxadiol

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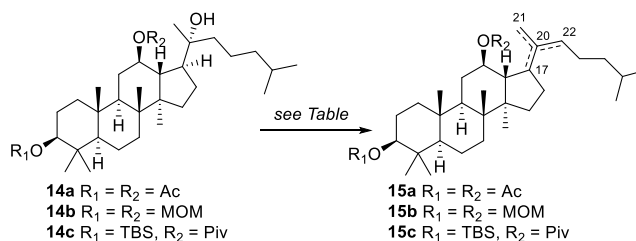
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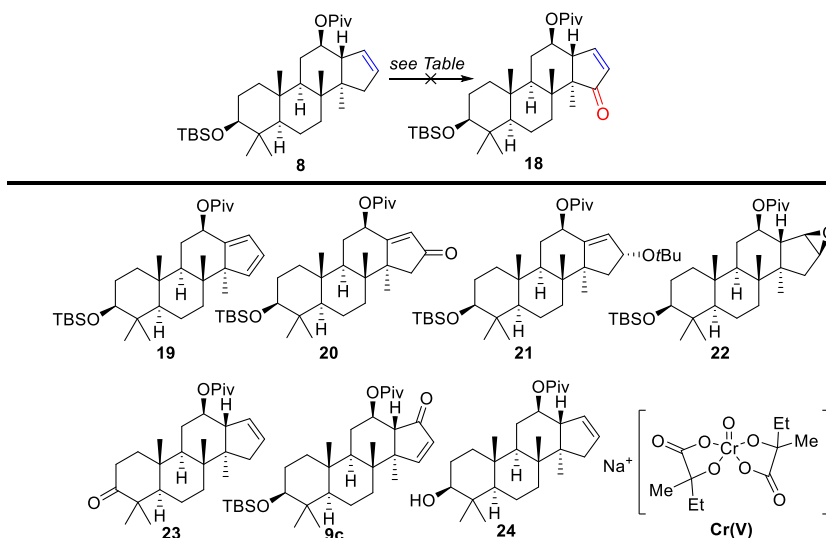
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Table S1. Attempts to Prepare $\Delta^{(17,20)}$ Olefin

entry	substrate	conditions	yield% ($\Delta^{17(20)}:\Delta^{20(22)}:\Delta^{20(21)}$) ^a
1	14a	<i>p</i> TSA(cat.), toluene, reflux, 3 h	70 (0:2.5:1)
2	14a	SOCl ₂ , pyr., 0 °C-rt, 0.5 h	70 (0:2.5:1)
3	14a	POCl ₃ , pyr., 40 °C, 6 h	85 (0:4.7:1)
4	14a	MsCl, DBU, benzene, 0-80 °C, 12 h	NR
5	14a	MsCl, TEA, DCM, 0 °C-rt, 3 h	70 (0:3:1)
6	14a	Burgess' reagent, toluene, reflux, 2 h	80 (0:1.5:1)
7	14a	BF ₃ · Et ₂ O, DCM, 0 °C, 0.5 h	65 (0:3.5:1)
8	14a	DEAD, PPh ₃ , THF, 0-50 °C, 4 h	77 (0:3:1)
9	14b	POCl ₃ , pyr., 40 °C, 8 h	80 (0:3:1)
10	14c	POCl ₃ , pyr., 40 °C, 12 h	82 (0:4:1)

^aThe ratios were determined by the isolated yields of compounds **16** and **10** after ozonolysis of olefins.

Table S2. Attempts to Achieve Allylic Oxidation of Olefin **8**

entry	conditions	products (yield%) ^a
1	SeO ₂ , 1,4-dioxane, rt, 24 h	no reaction
2	SeO ₂ , 1,4-dioxane/benzene (1:1), rt, 24 h	no reaction
3	SeO ₂ , 1,4-dioxane/benzene (1:1), 80 °C, 2 h	19 (90)
4^b	SeO ₂ , TBHP, benzene, rt-60 °C, 72 h	20 (30), 21 (35)
5^b	CrO ₃ , 3,5-dimethylpyrazole, DCM, -20 °C, 24 h	no reaction
6^b	CrO ₃ , 3,5-dimethylpyrazole, DCM, rt, 12 h	22 (42)
7	CrO ₃ , TBHP (70% aq.), DCM, rt, 8 h	23 (70)
8^b	CuCl, TBHP, benzene, 60 °C, 72 h	20 (23), 22 (12), 9c (10)
9^b	Mn(OAc) ₃ , TBHP, ethyl acetate, 3 Å MS, rt, 5 d	20 (8), 22 (5), 9c (<5)
10^b	Pd/C, TBHP, K ₂ CO ₃ , DCM, rt, 48 h	20 (<5), 22 (<5)
11^b	PDC, TBHP (70% aq.), benzene, rt, 48 h	20 (41), 22 (<5), 9c (38)
12^b	Cr(V), MnO ₂ , 15-crown-5, trifluorotoluene, 80 °C, 72 h	20 (<5), 9c (<5)
13	DDQ, DMF, H ₂ O (10 equiv.), 80 °C, 3 h	24 (quant.)

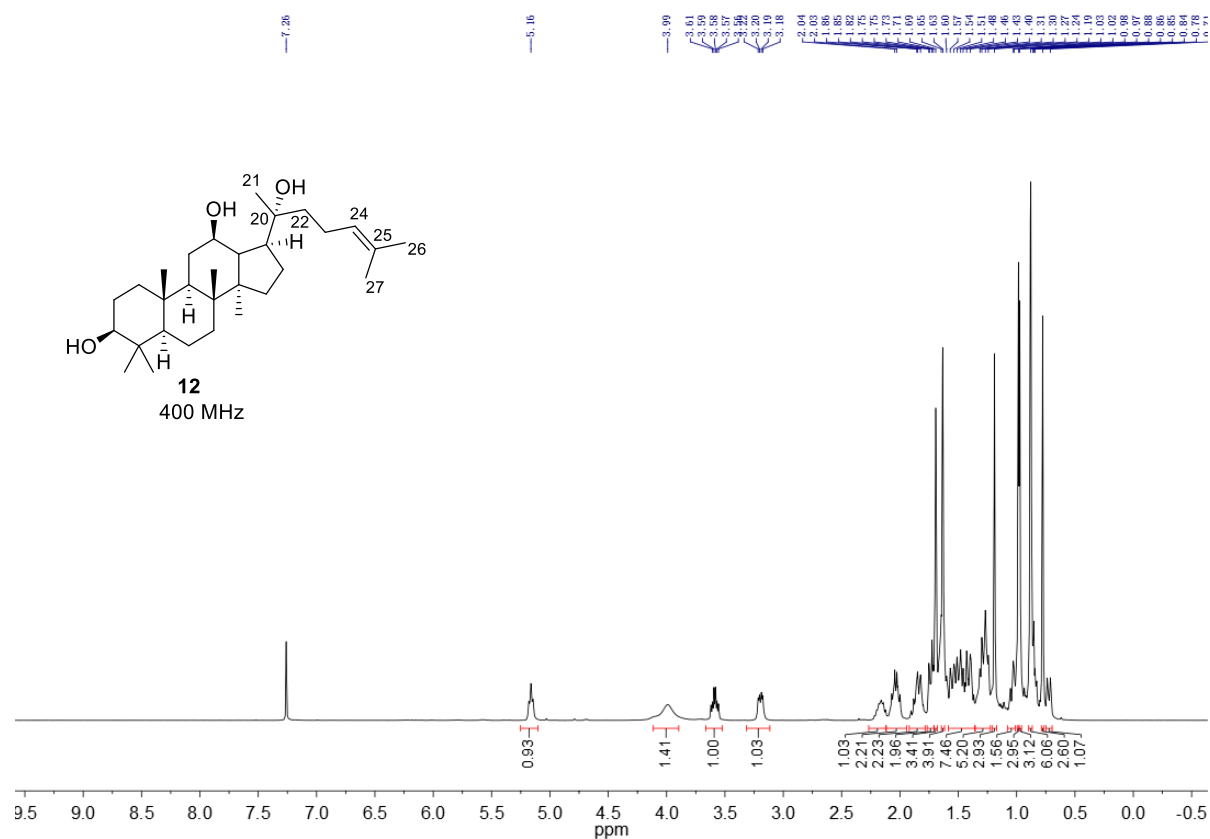
^aIsolated yields.^bRecovery of starting materials.

Table 1. 11 β -HSD1 Inhibition of Synthetic Compounds

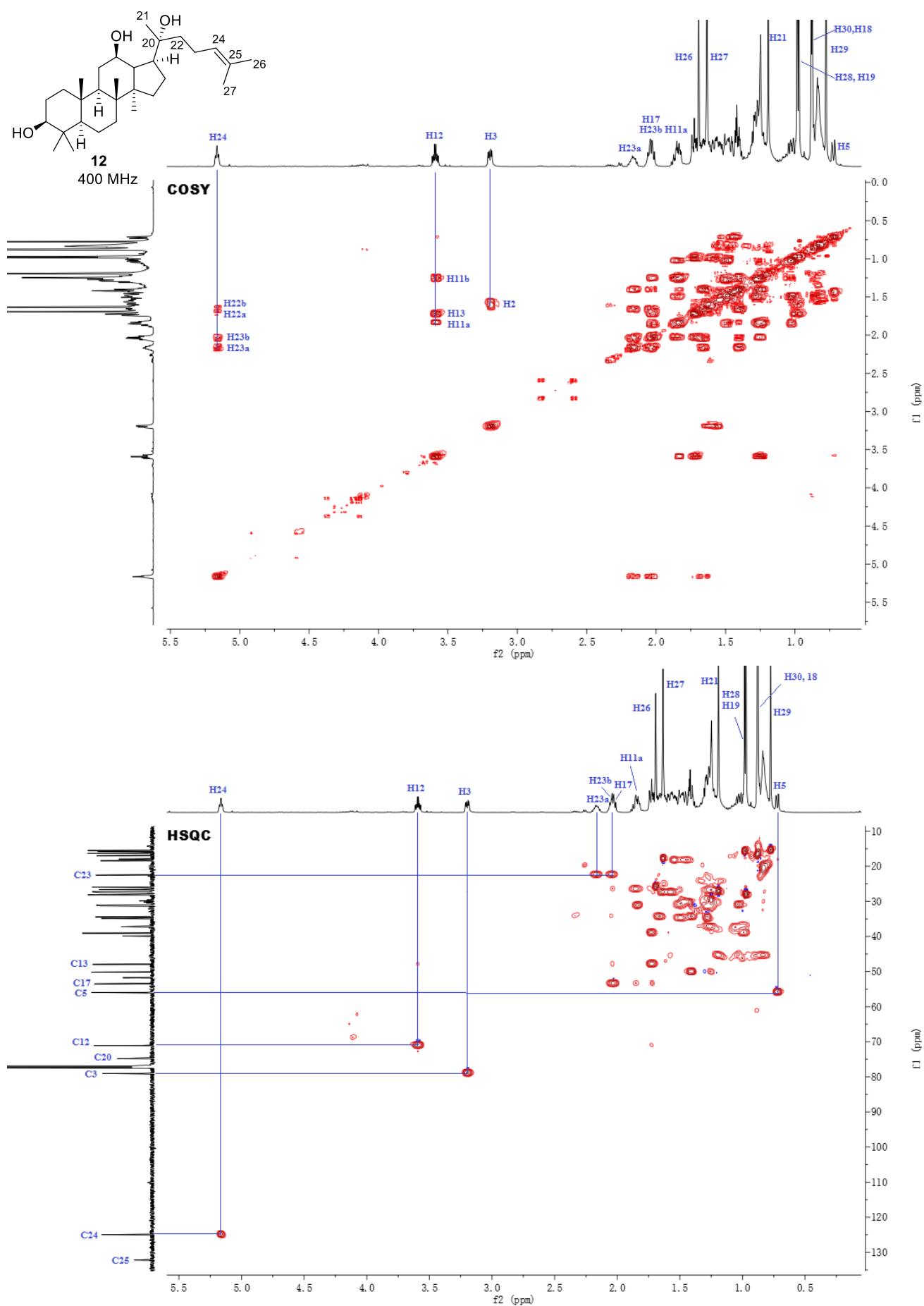
entry	1 μ M inhibitory ratio		IC ₅₀	
	human 11 β -HSD1	mouse 11 β -HSD1	human 11 β -HSD1	mouse 11 β -HSD1
12	16.13%	12.35%	ND ^b	ND
14a	13.24%	7.55%	ND	ND
14b	7.90%	7.75%	ND	ND
16a	81.12%	10.77%	0.1 μ M	ND
10a	69.36%	40.91%	0.2 μ M	ND
10b	15.43%	11.48%	ND	ND
11a	12.21%	12.53%	ND	ND
17	32.77%	17.43%	ND	ND
8	0.96%	8.74%	ND	ND
19	12.50%	10.04%	ND	ND
^a	28.86%	10.84%	ND	ND
20	32.37%	7.22%	ND	ND
21	28.29%	35.17%	ND	ND
22	2.85%	10.55%	ND	ND
23	2.61%	7.91%	ND	ND
24	33.33%	9.44%	ND	ND
27	35.64%	7.98%	ND	ND
30	88.42%	76.48%	44.0 nM ^d	0.4 μ M
hupehenol B	94.43%	27.08%	26.0 nM	3.3 μ M
GA^c	96.20%	94.91%	7.4 nM	12.1 nM

^a 3-OTBS-removed product of compound **19**.^b ND: The IC₅₀ value was not determined if the inhibitory ratio was less than 50%.^c Glycyrrhetic acid (GA) was used as a positive control.^d P > 0.05 vs hupehenol B.

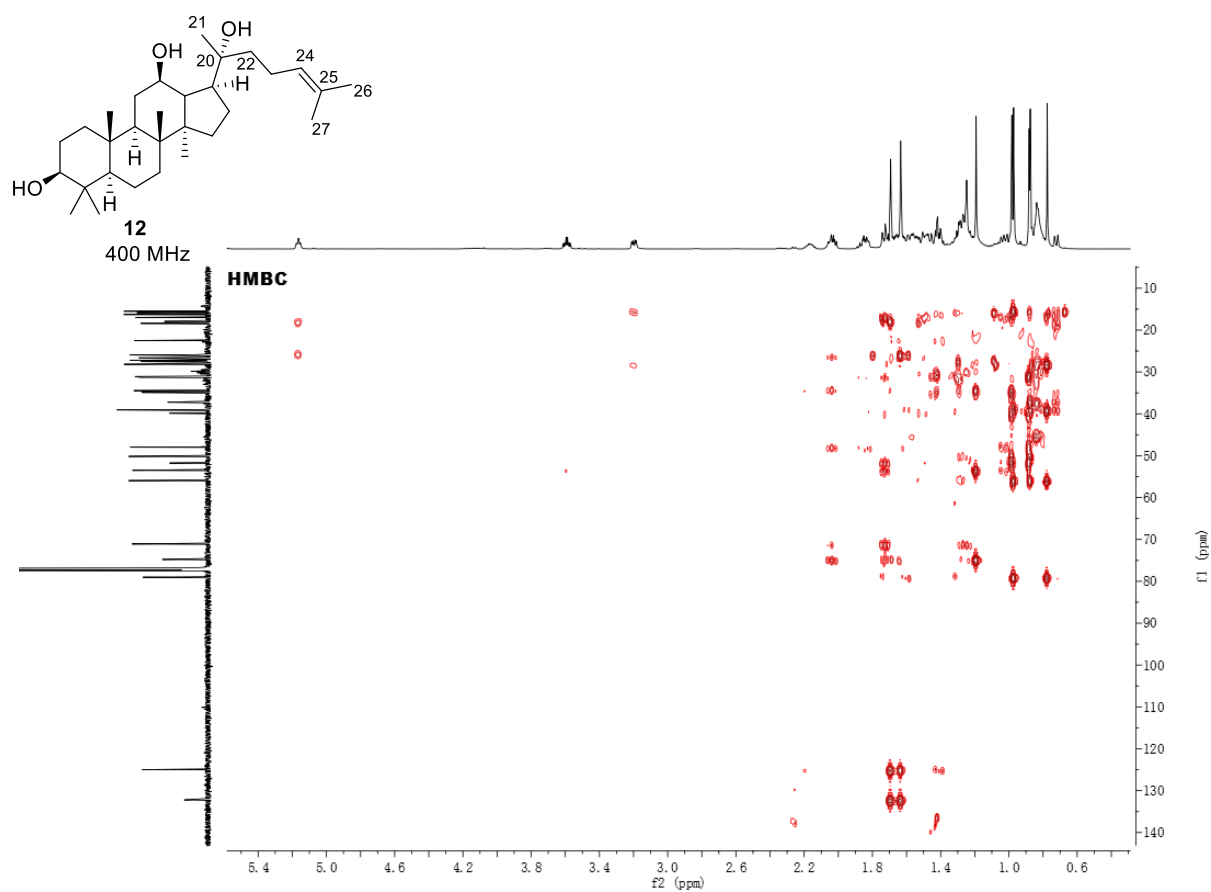
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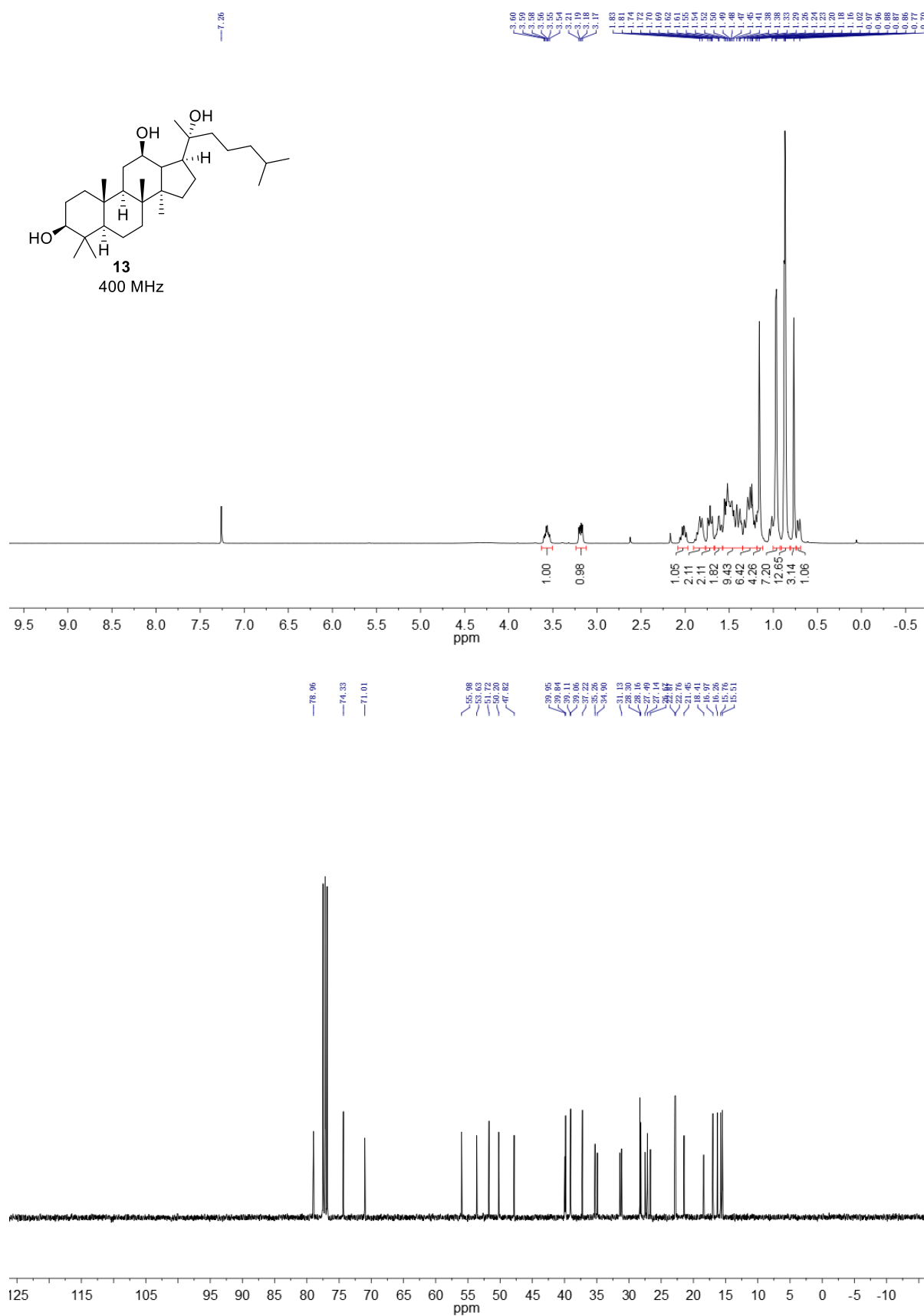
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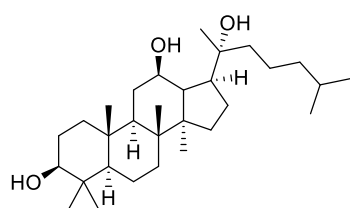
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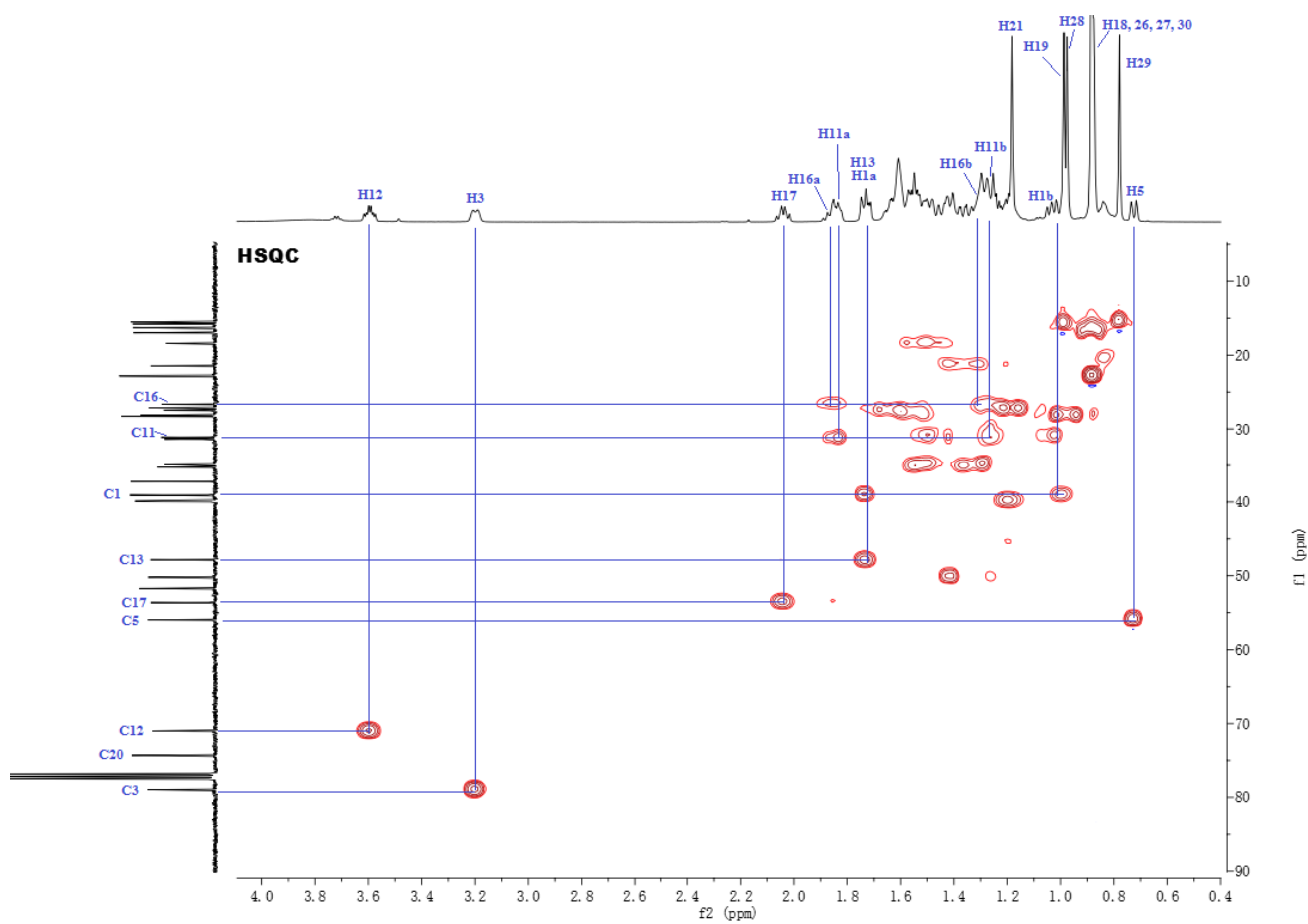
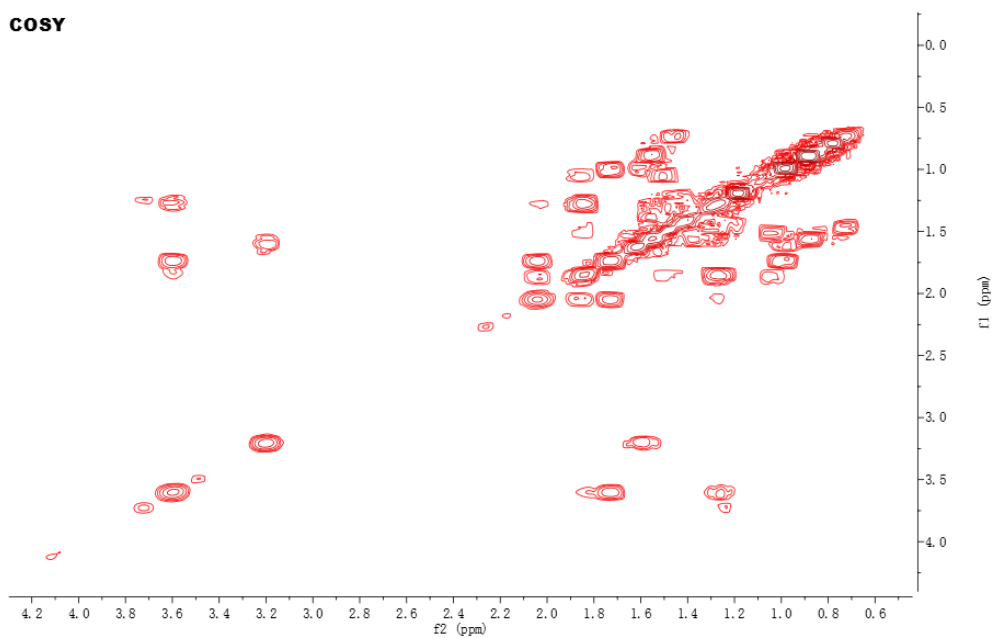


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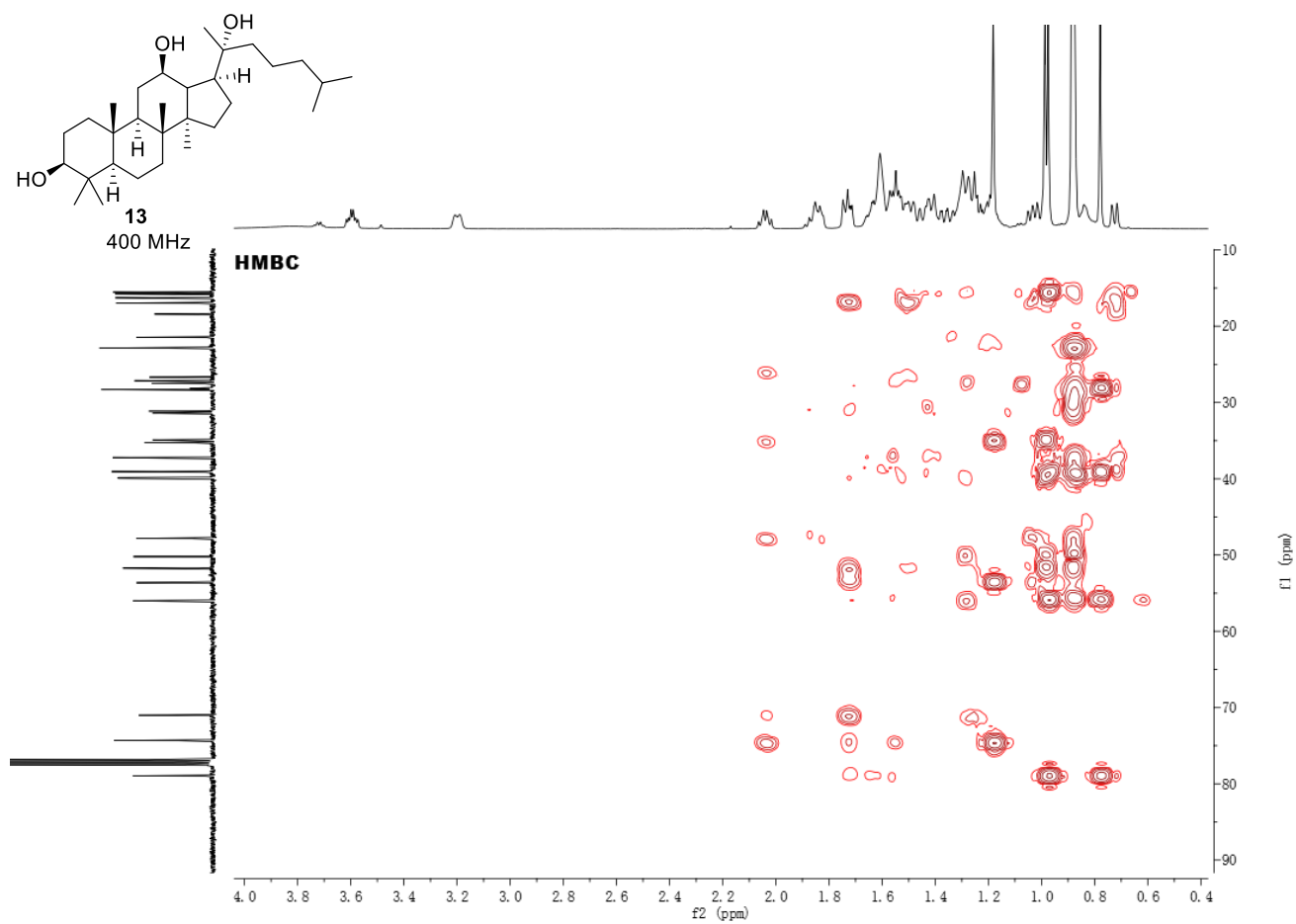


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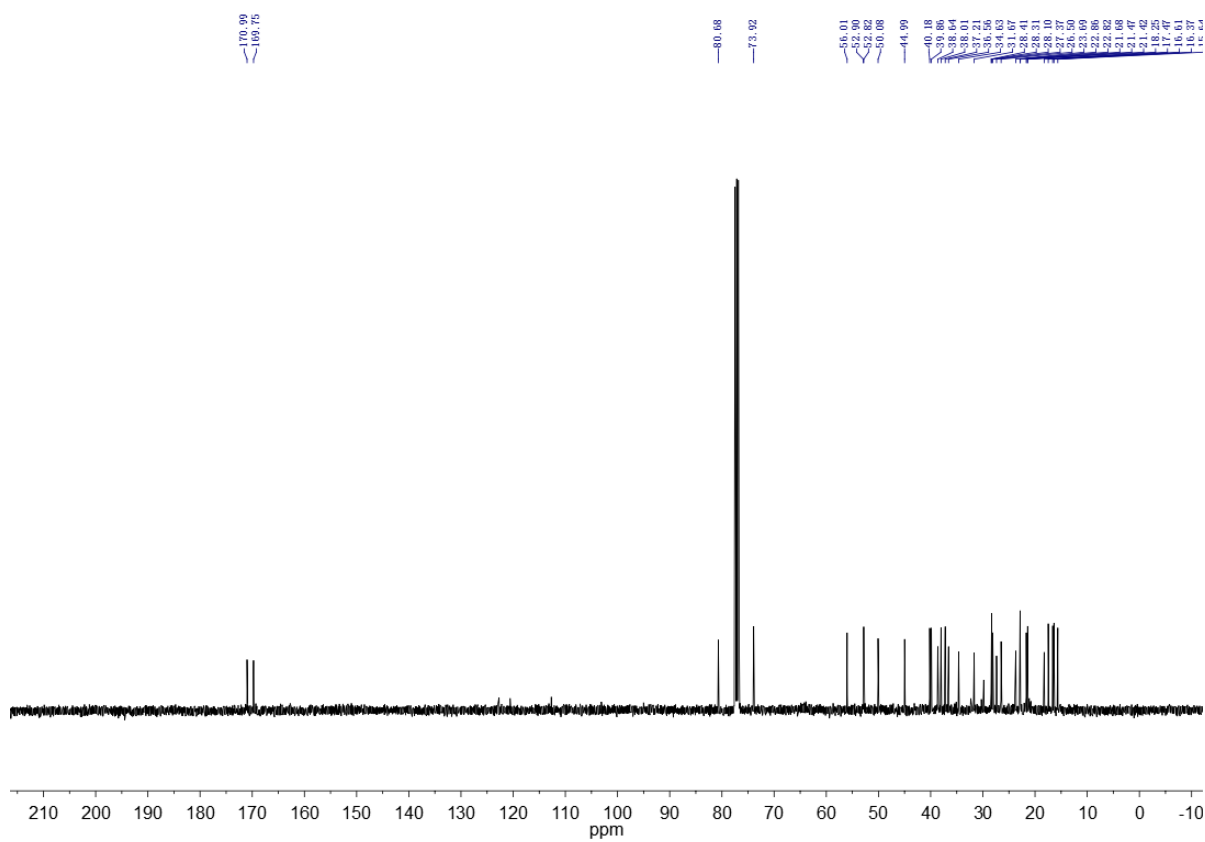
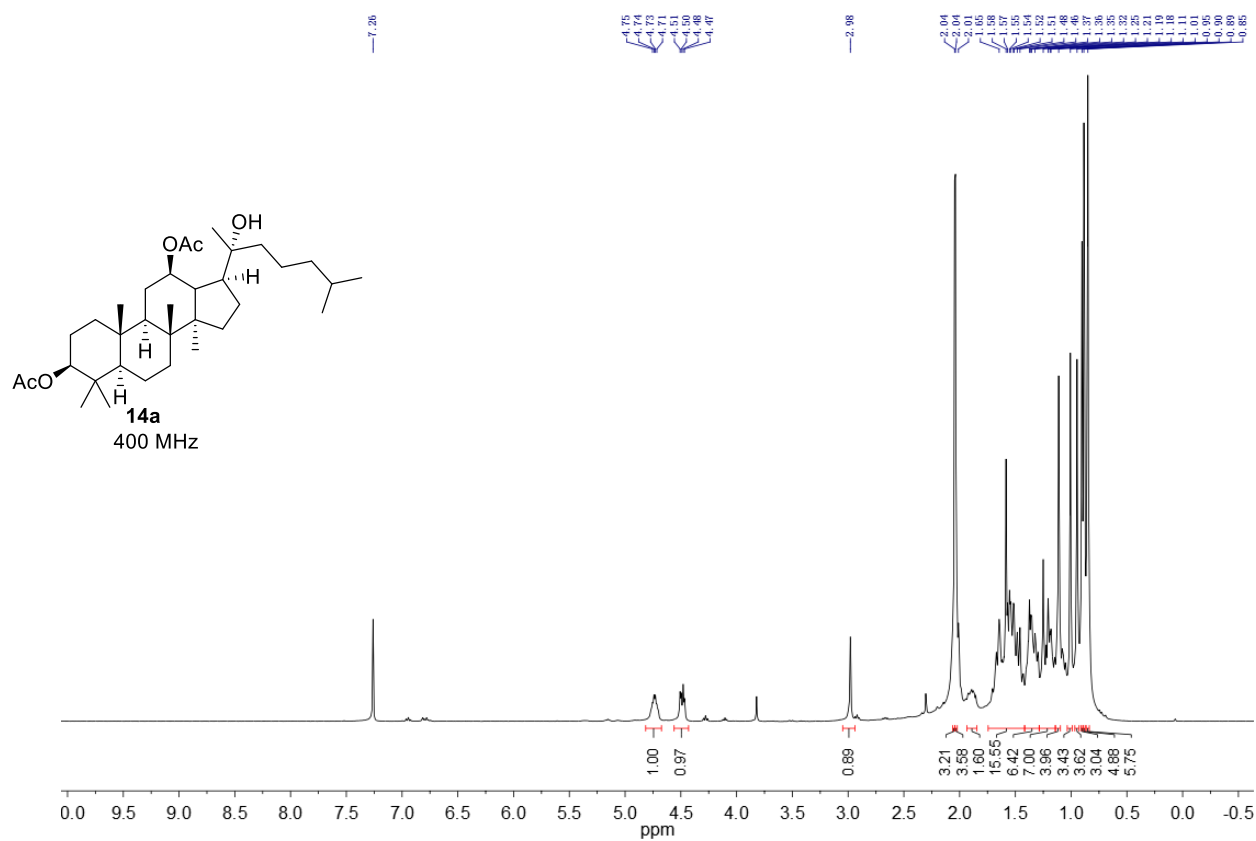
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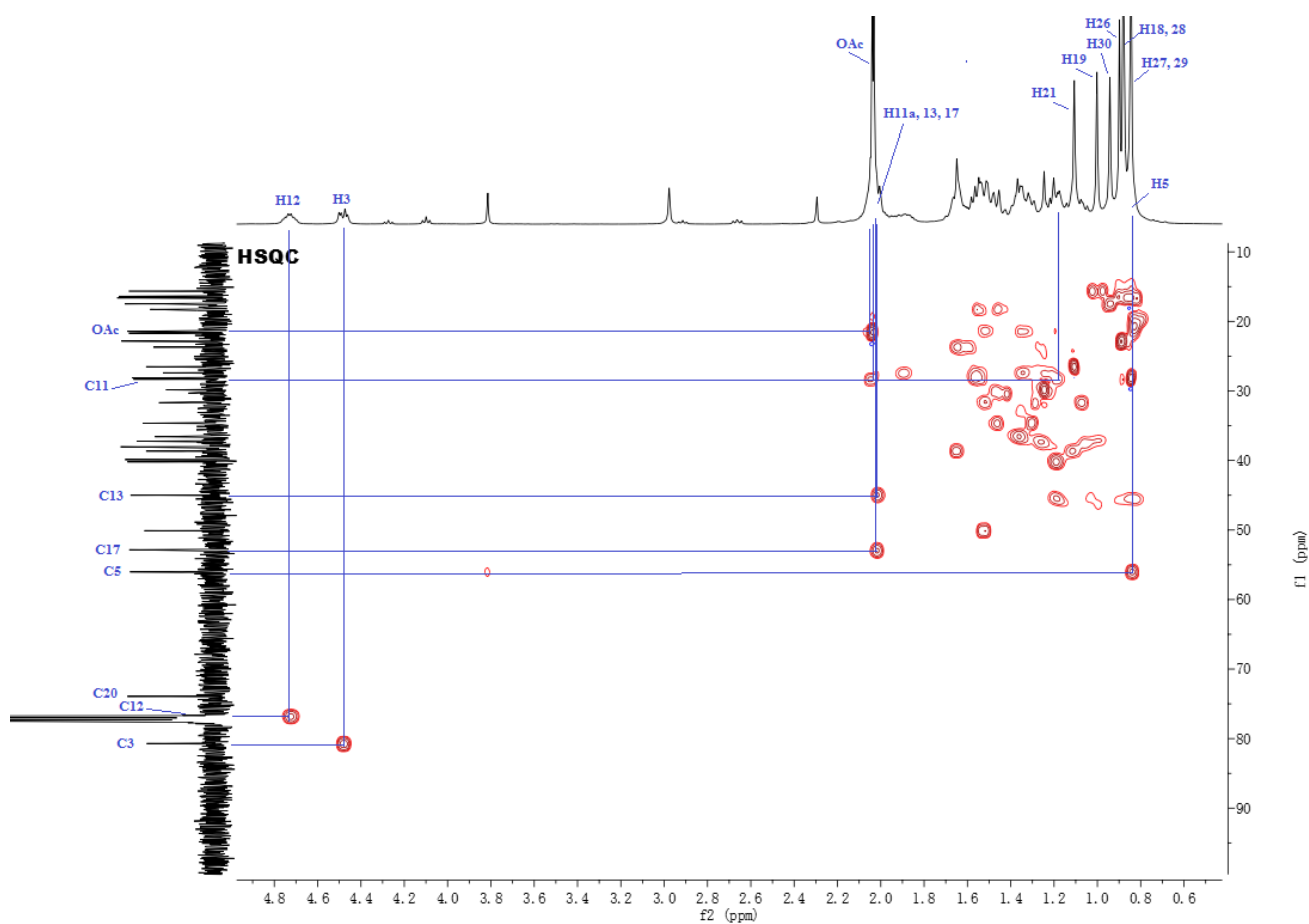
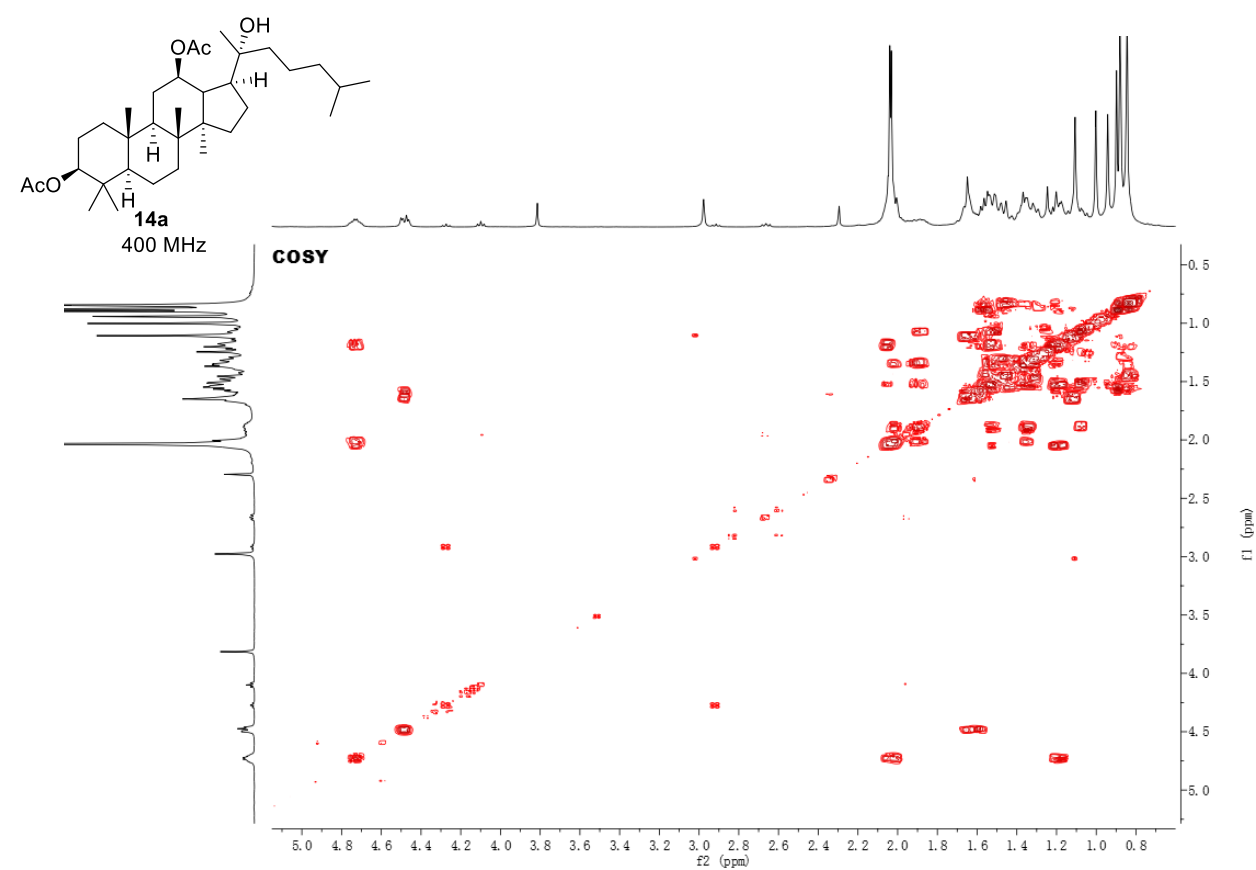
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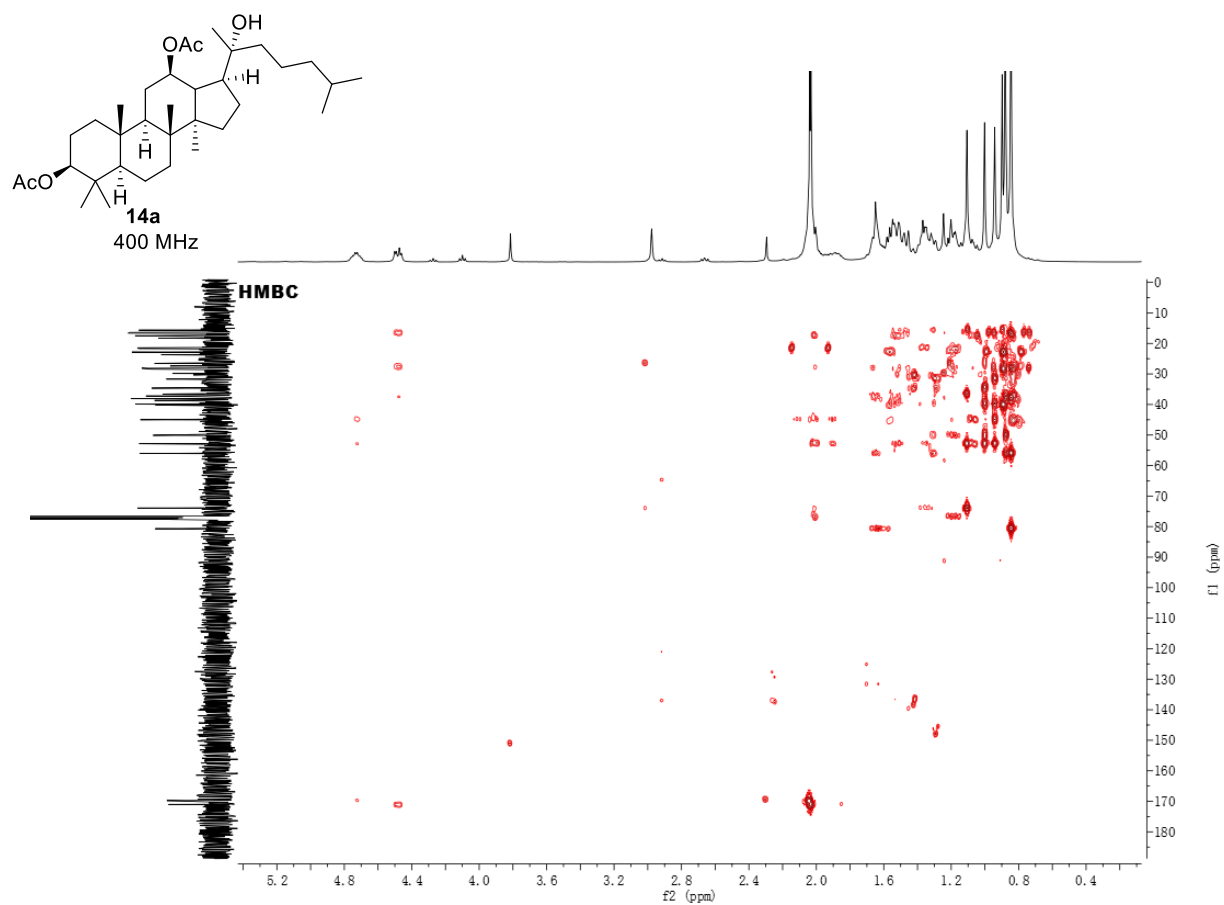
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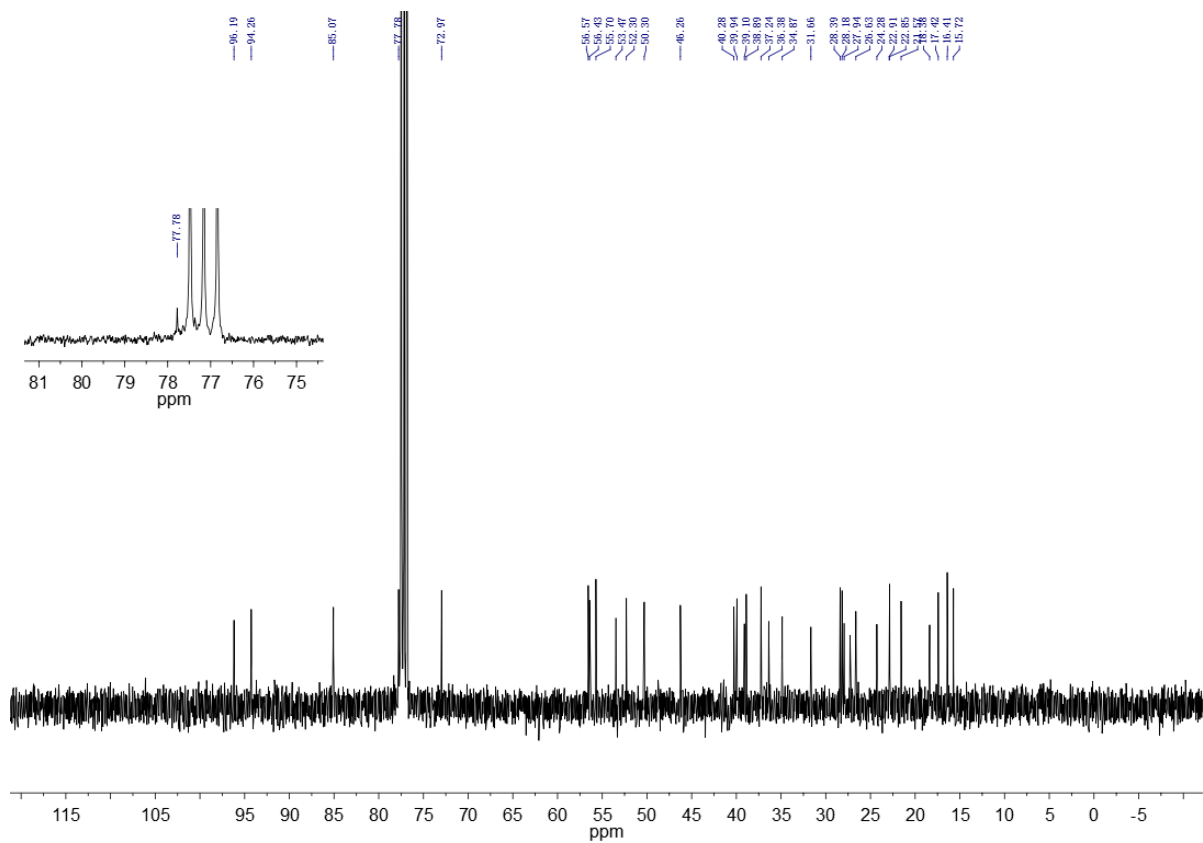
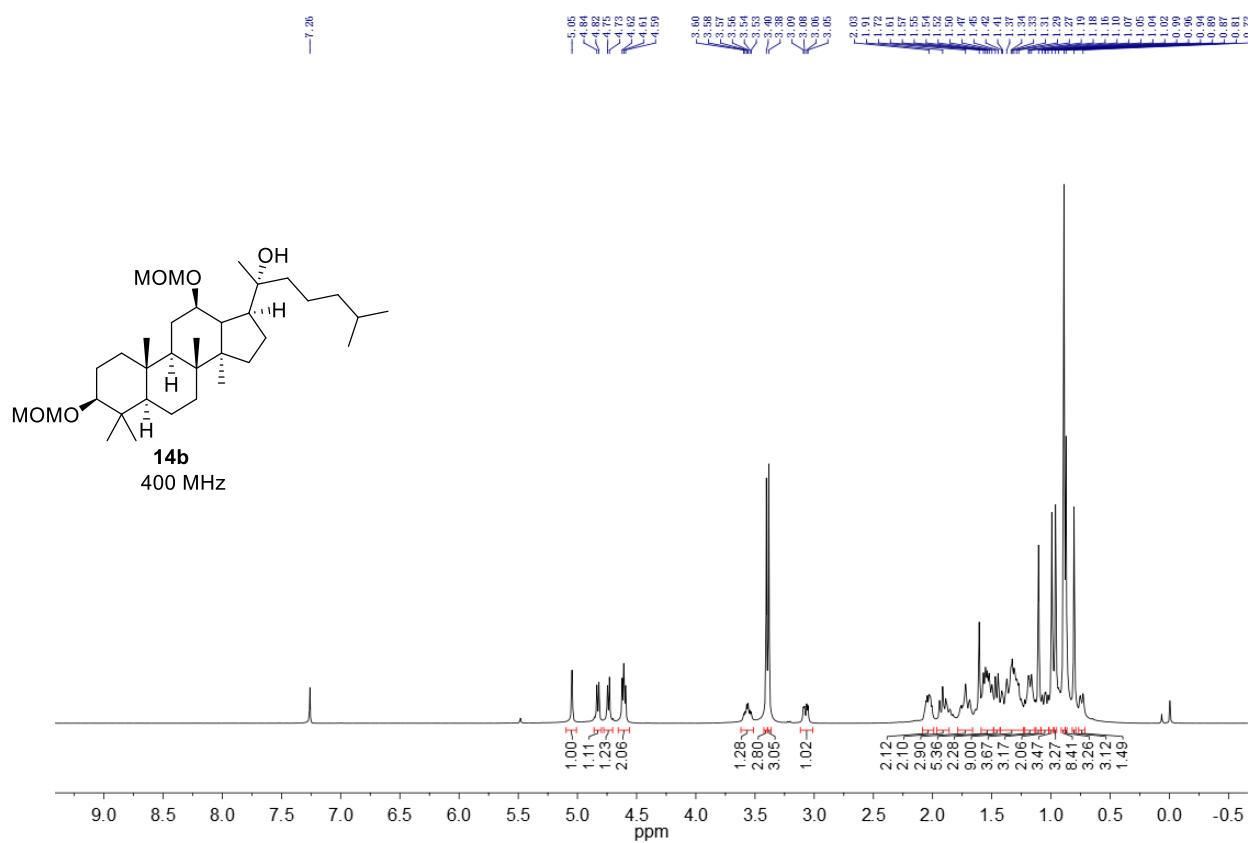
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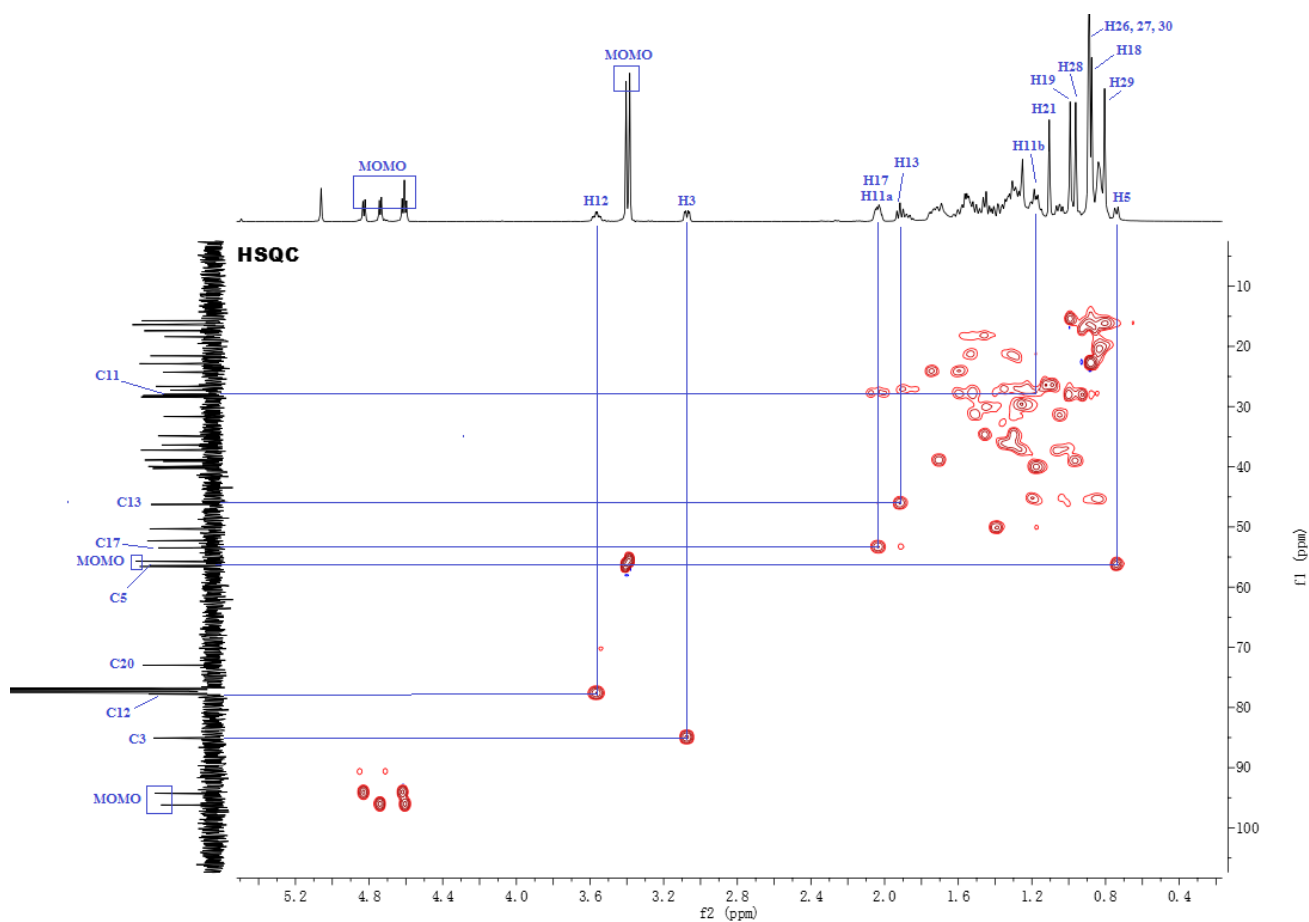
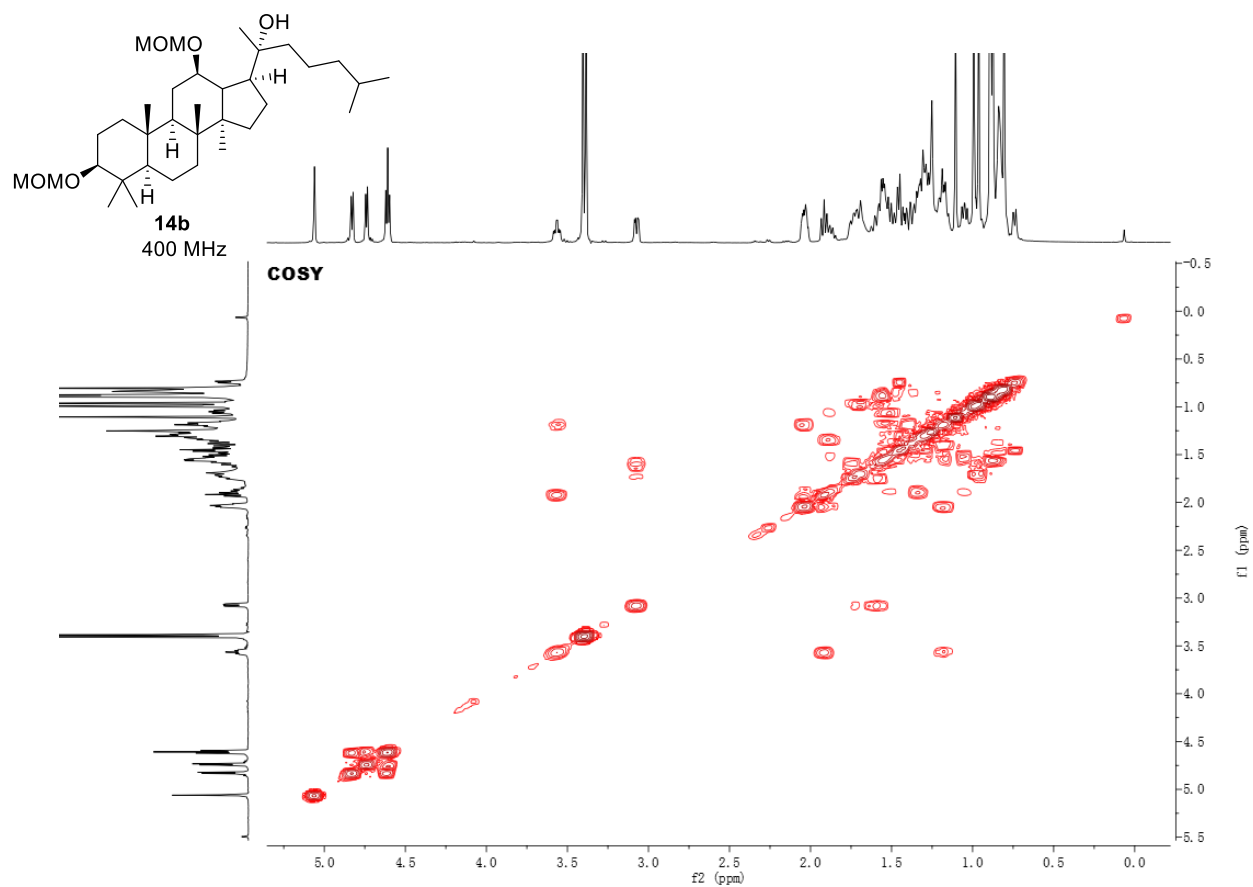
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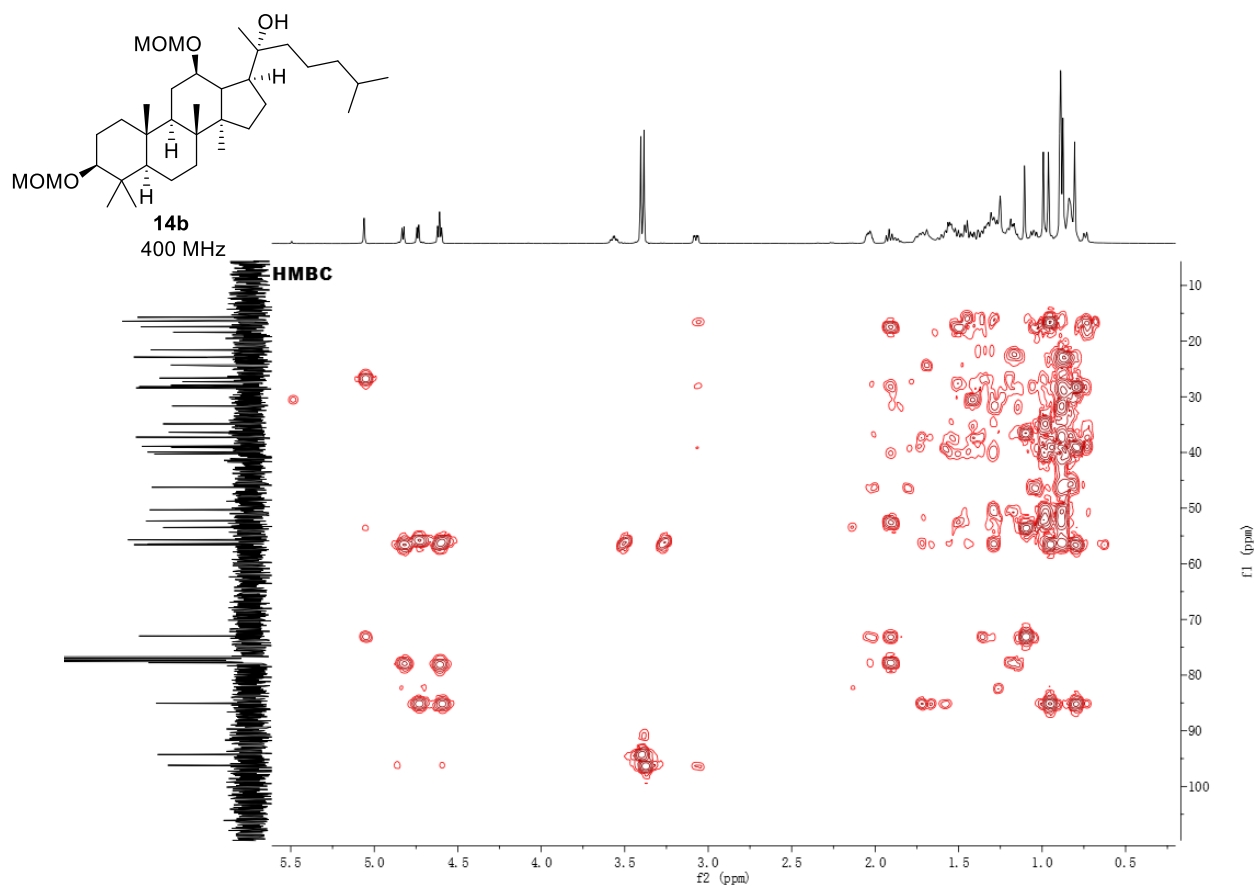
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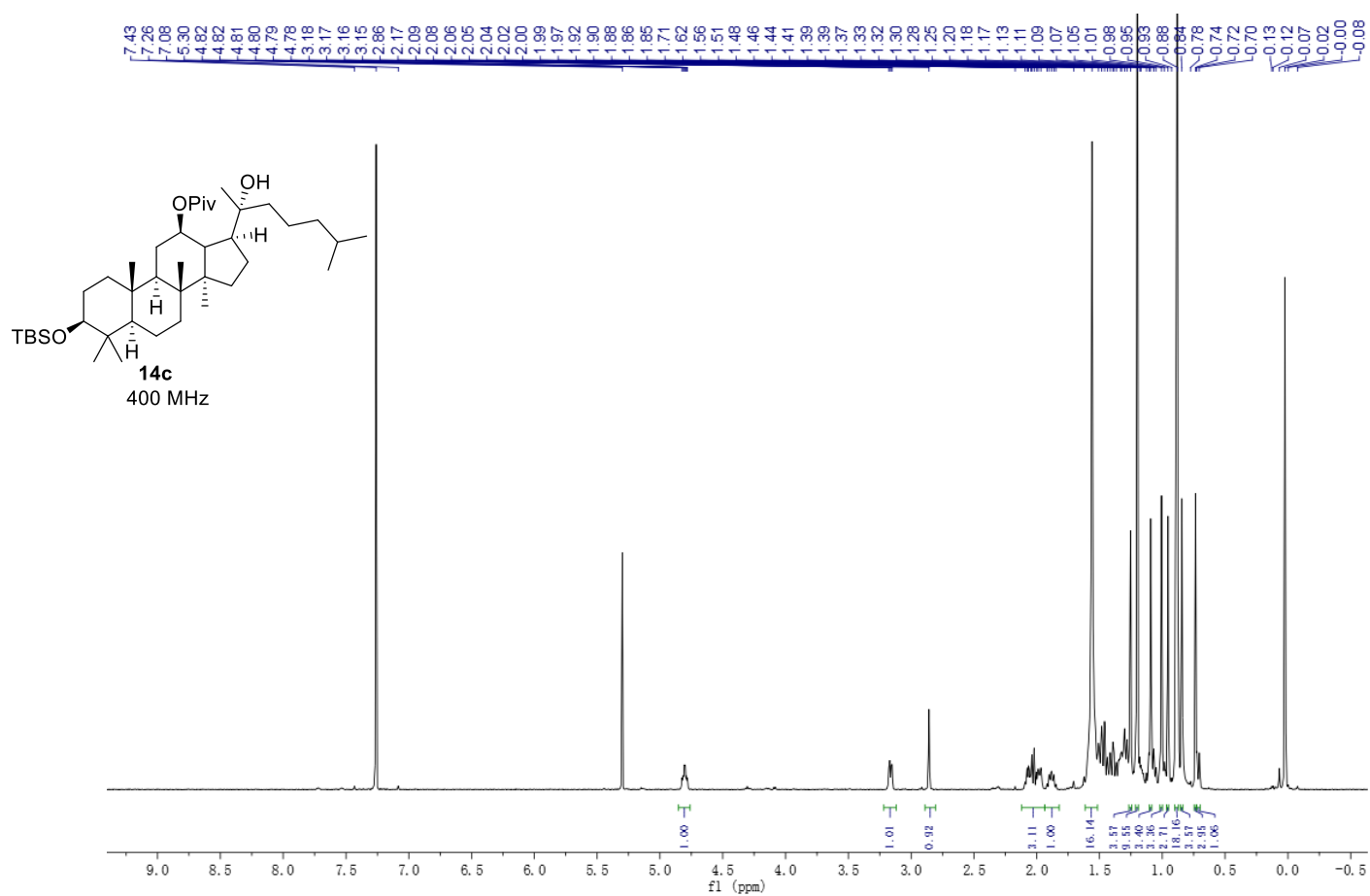
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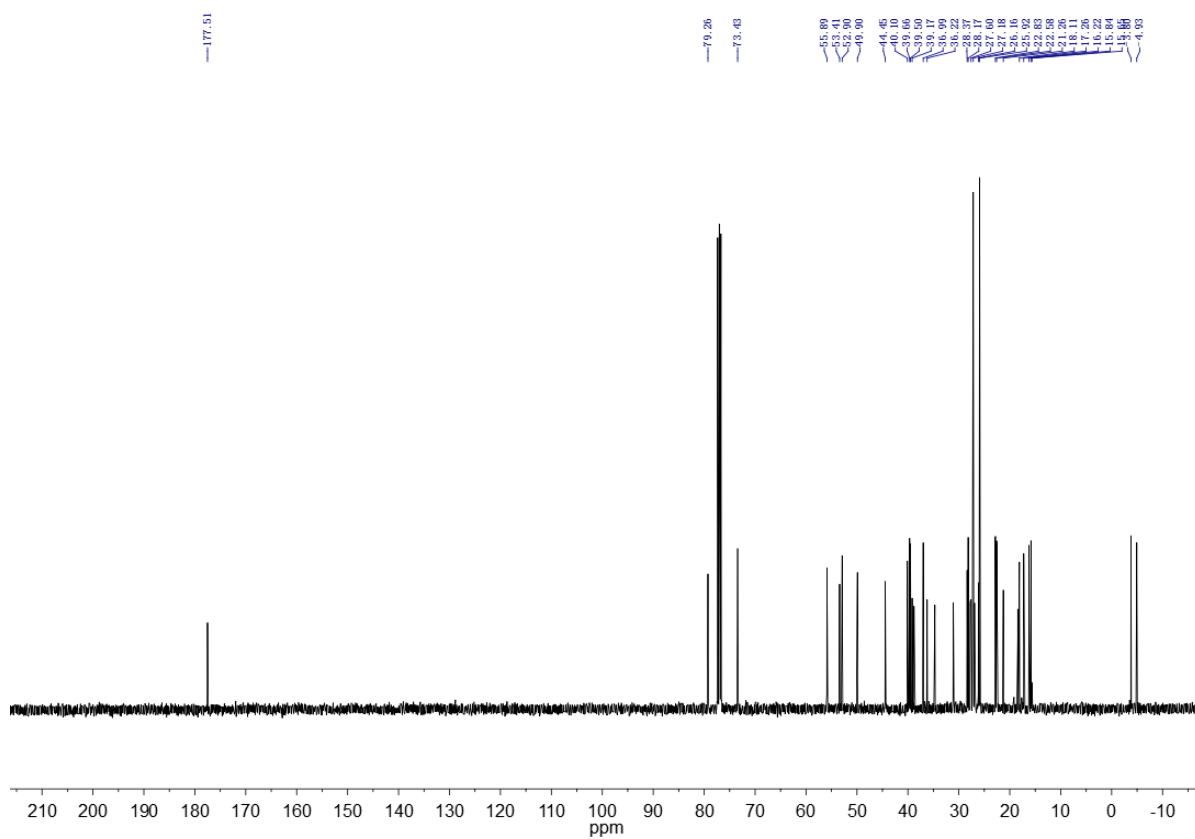
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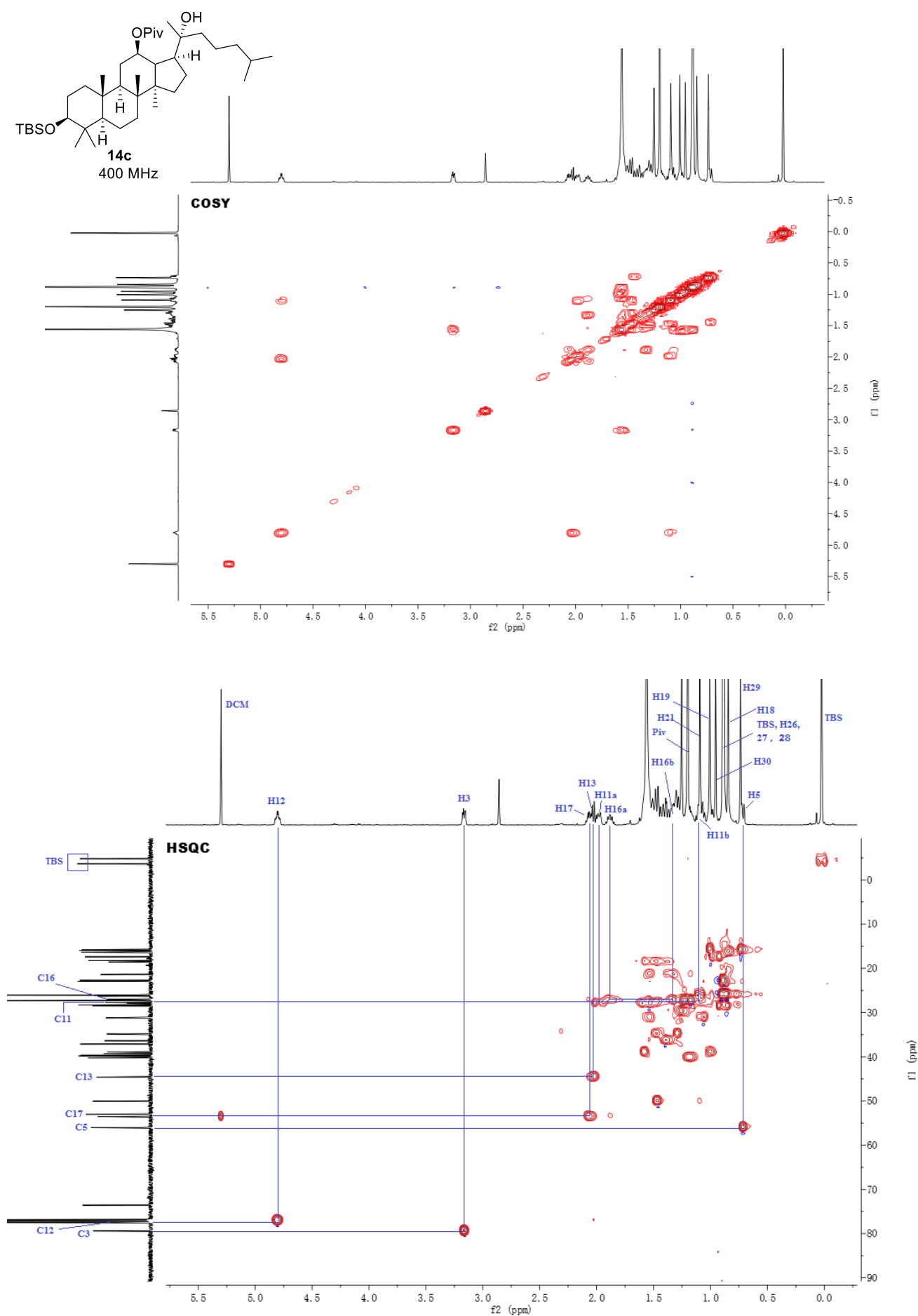
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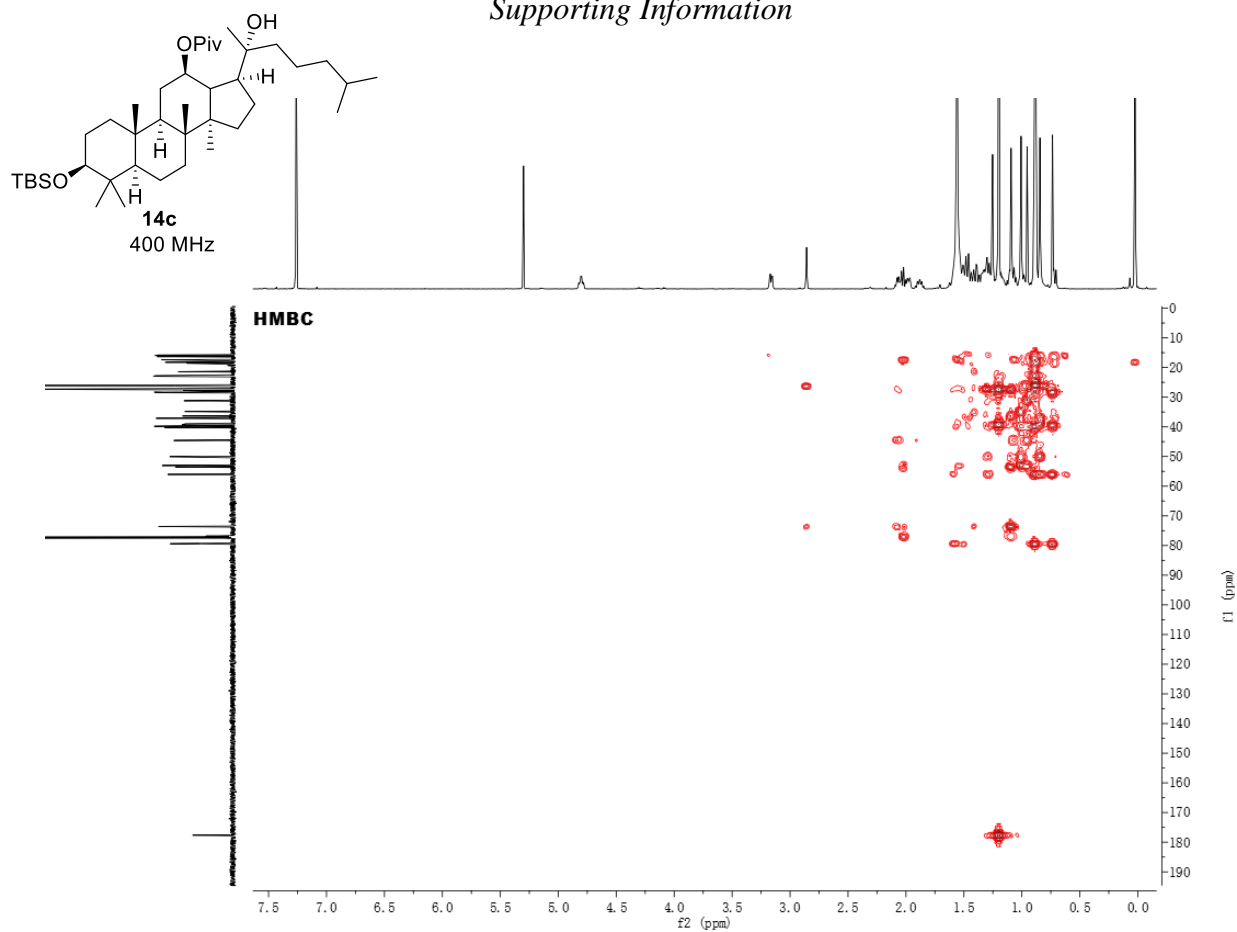
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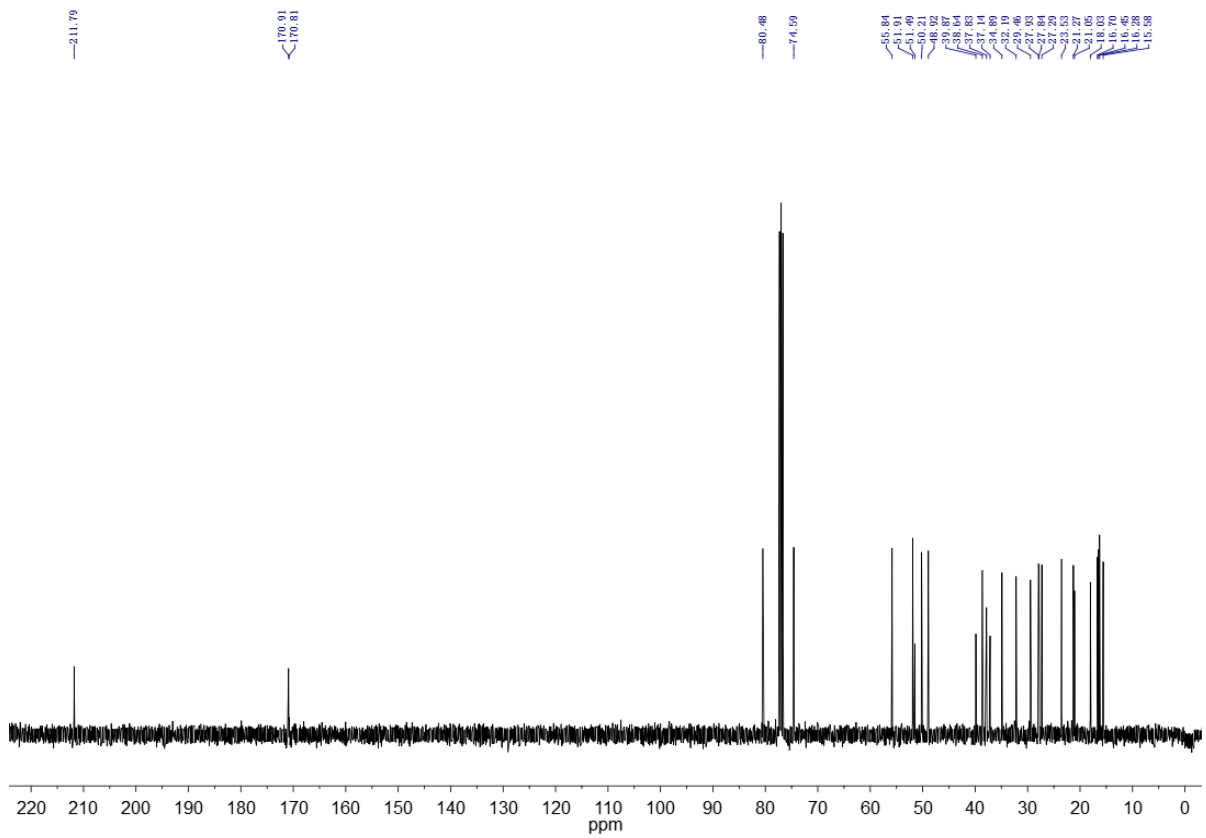
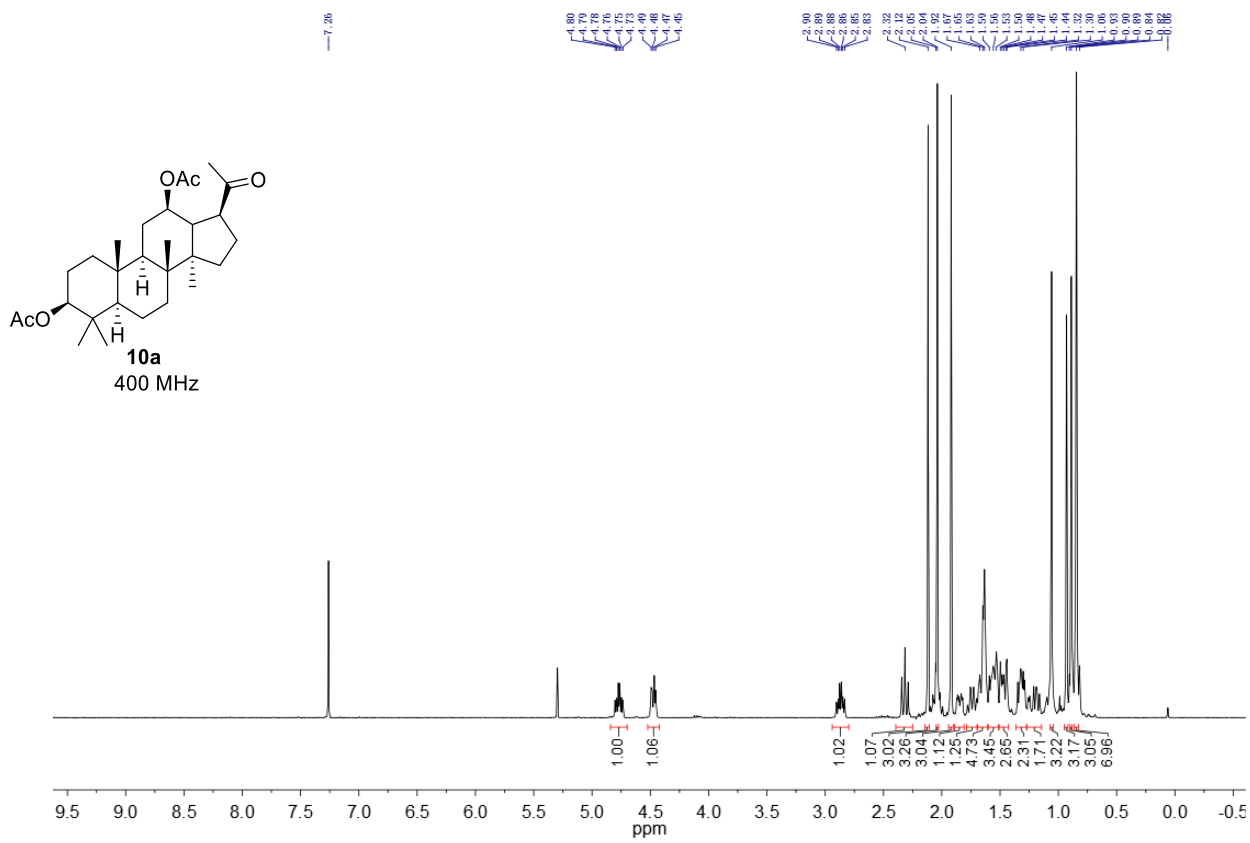
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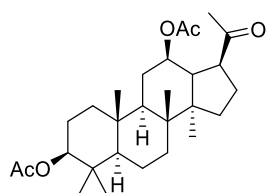
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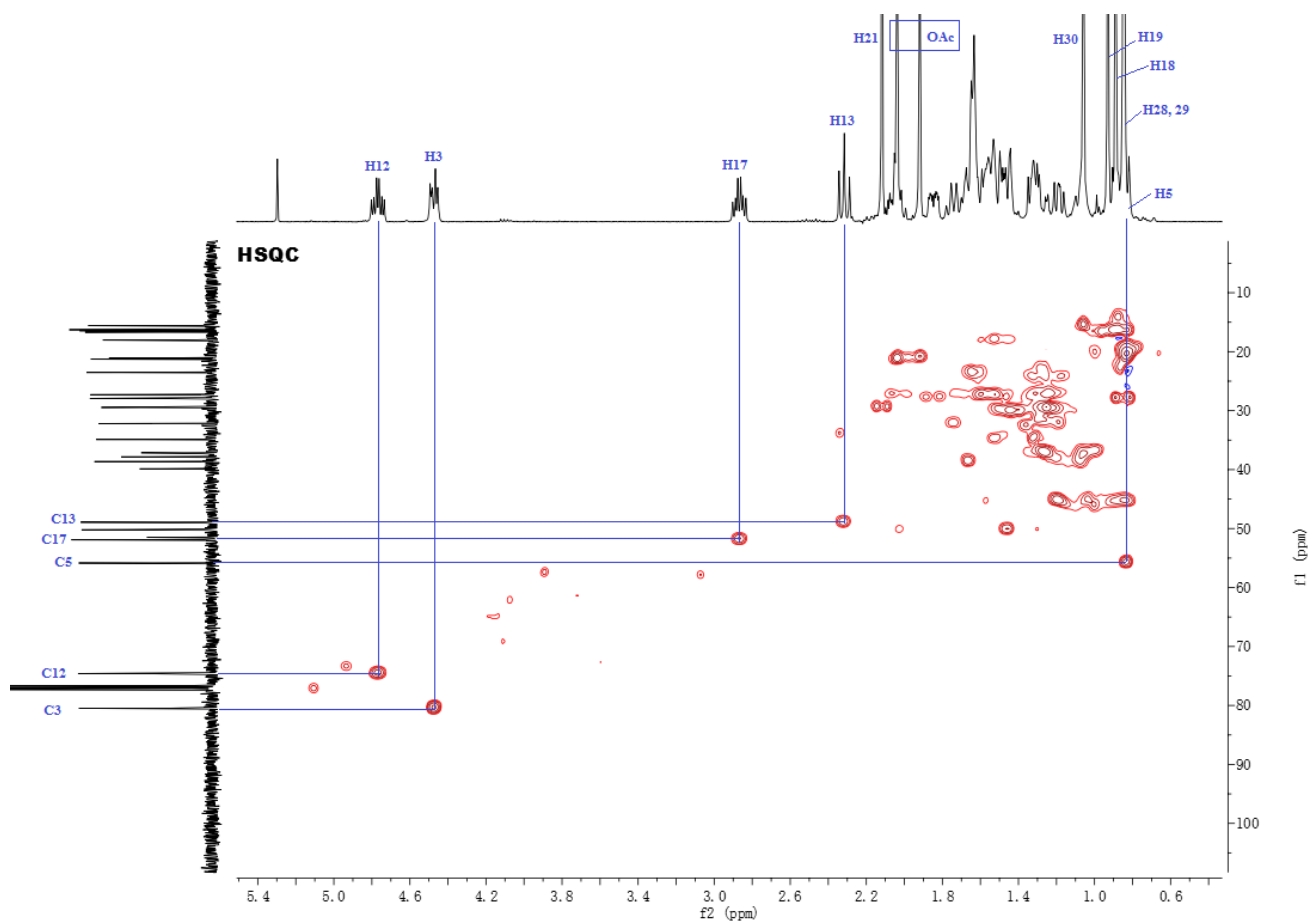
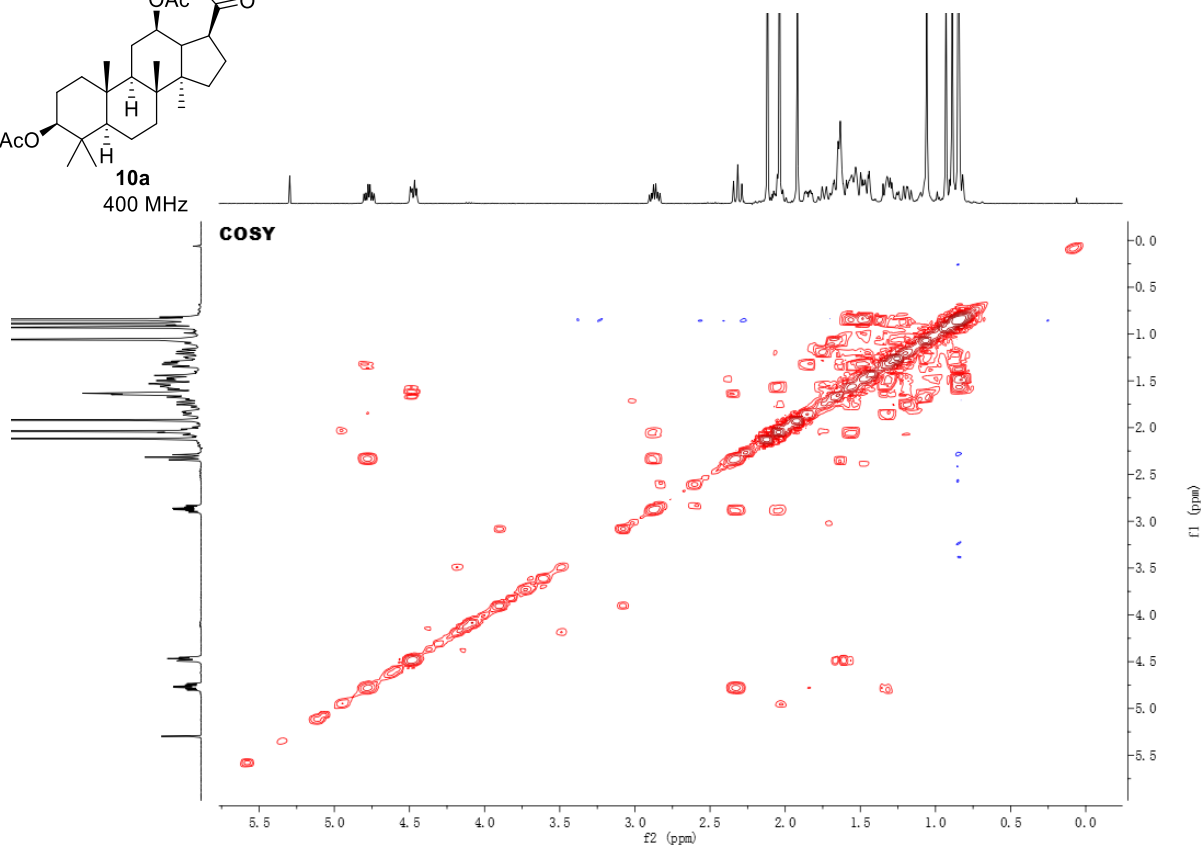


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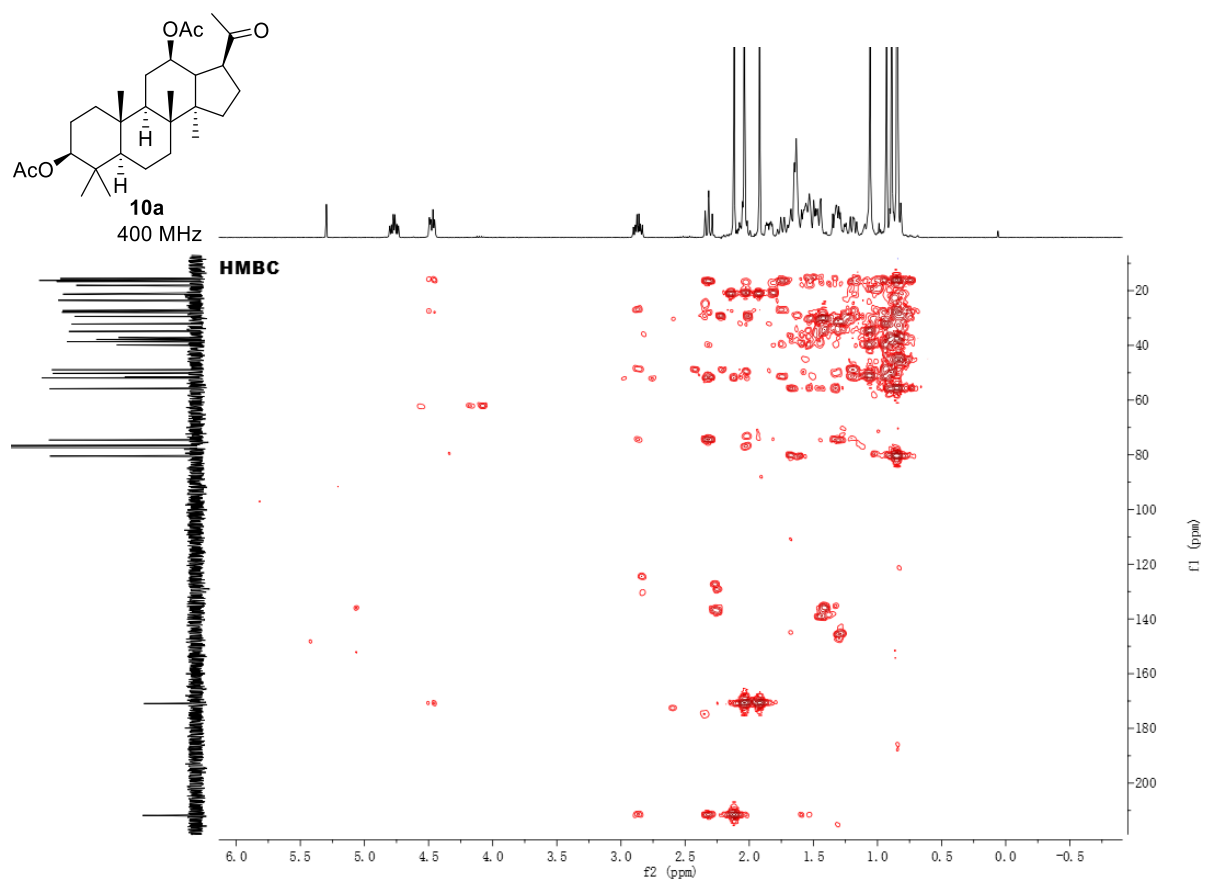


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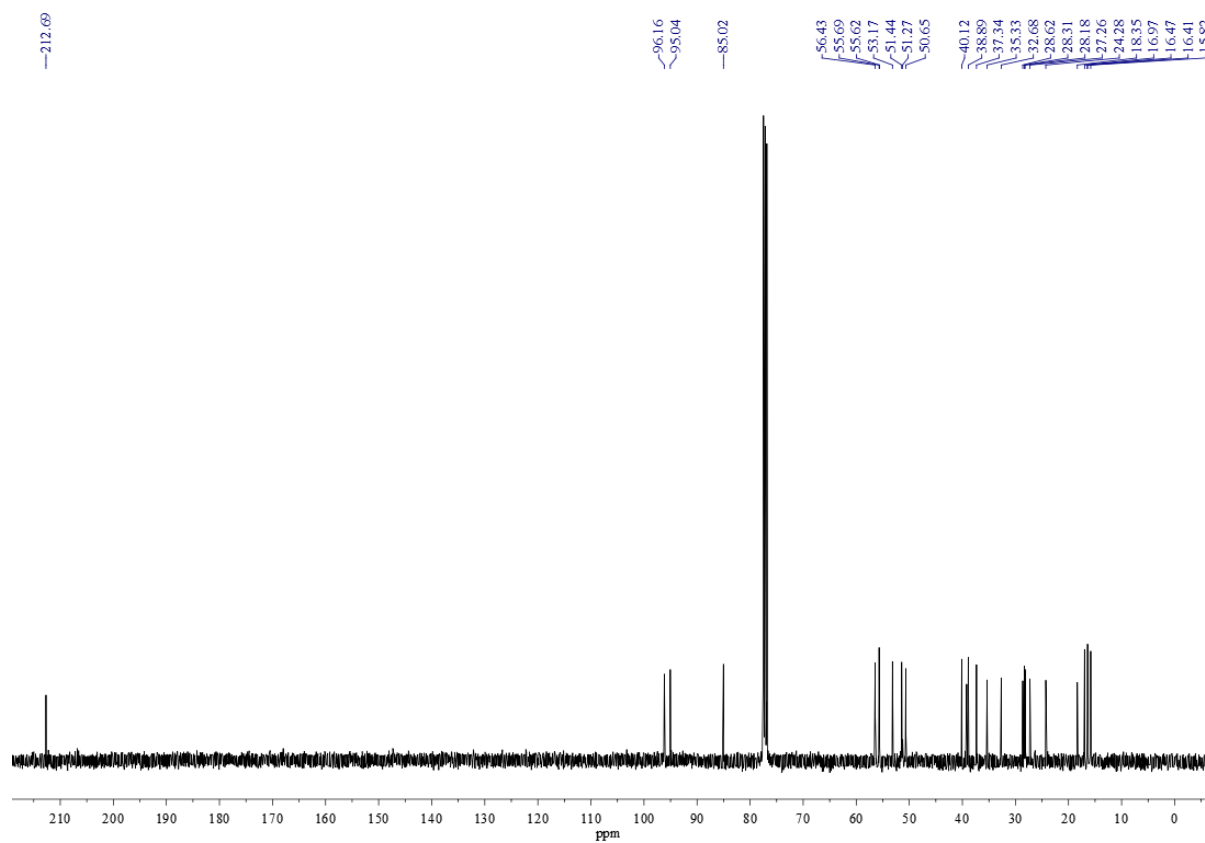
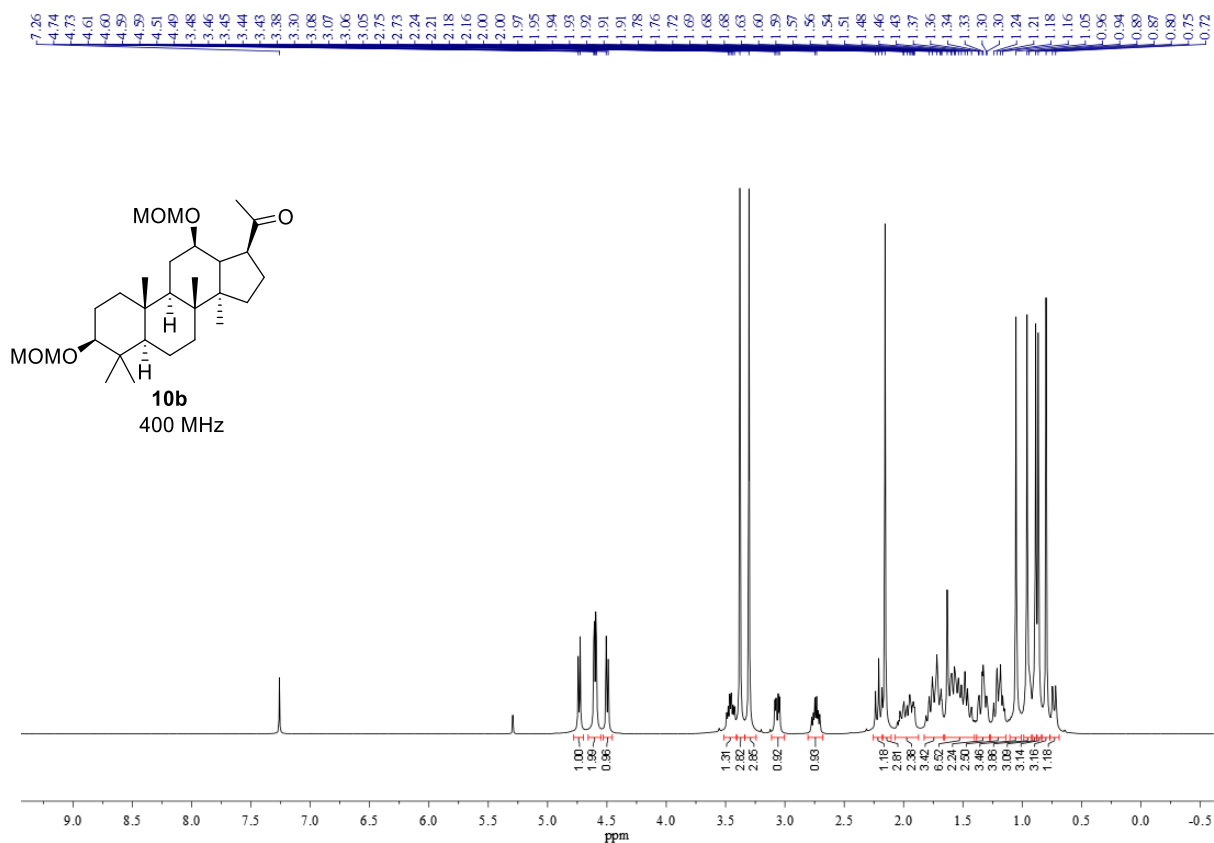
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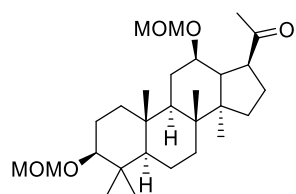
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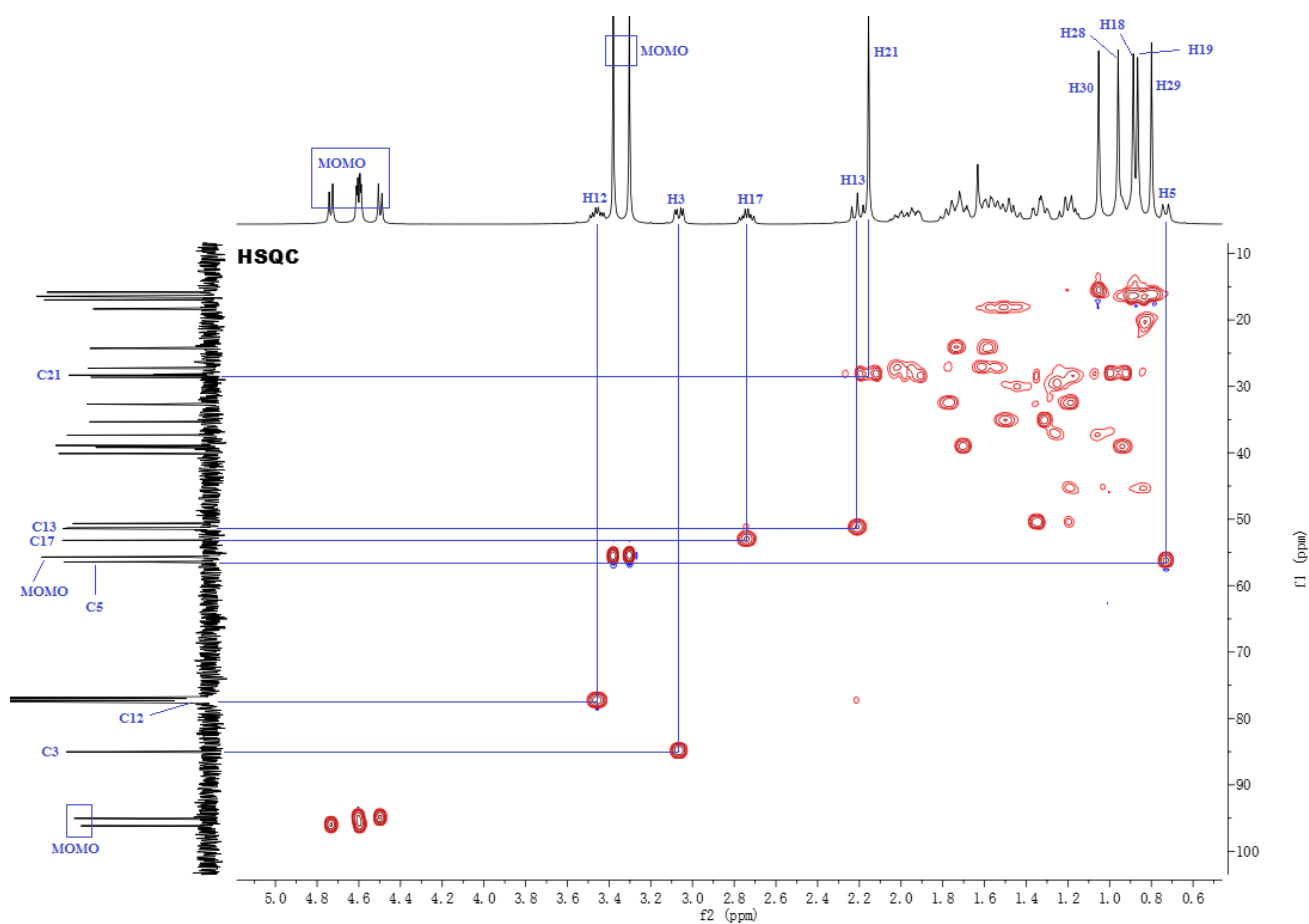
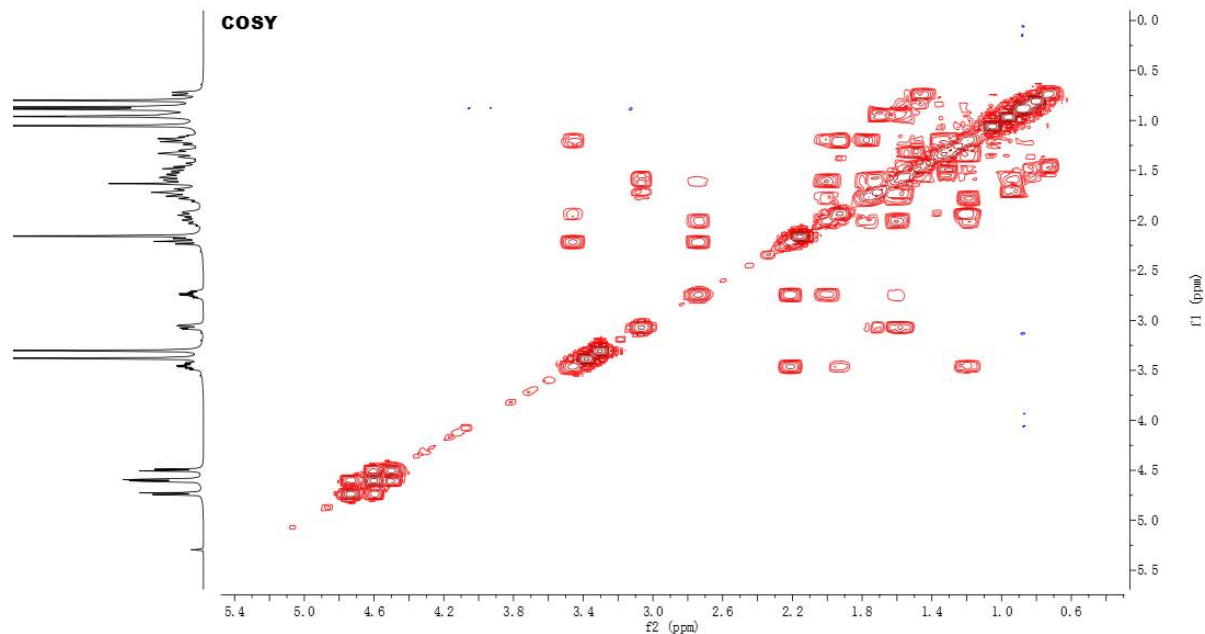
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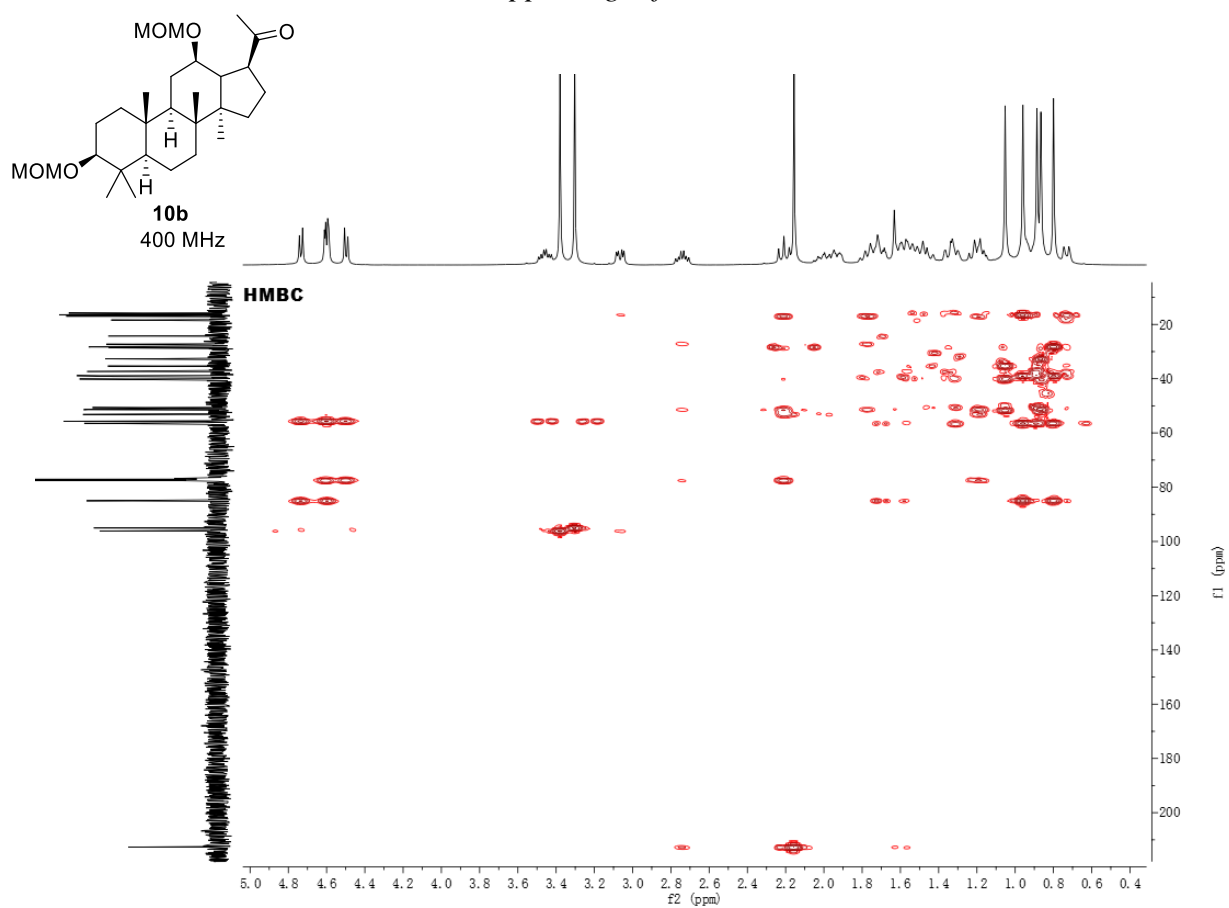
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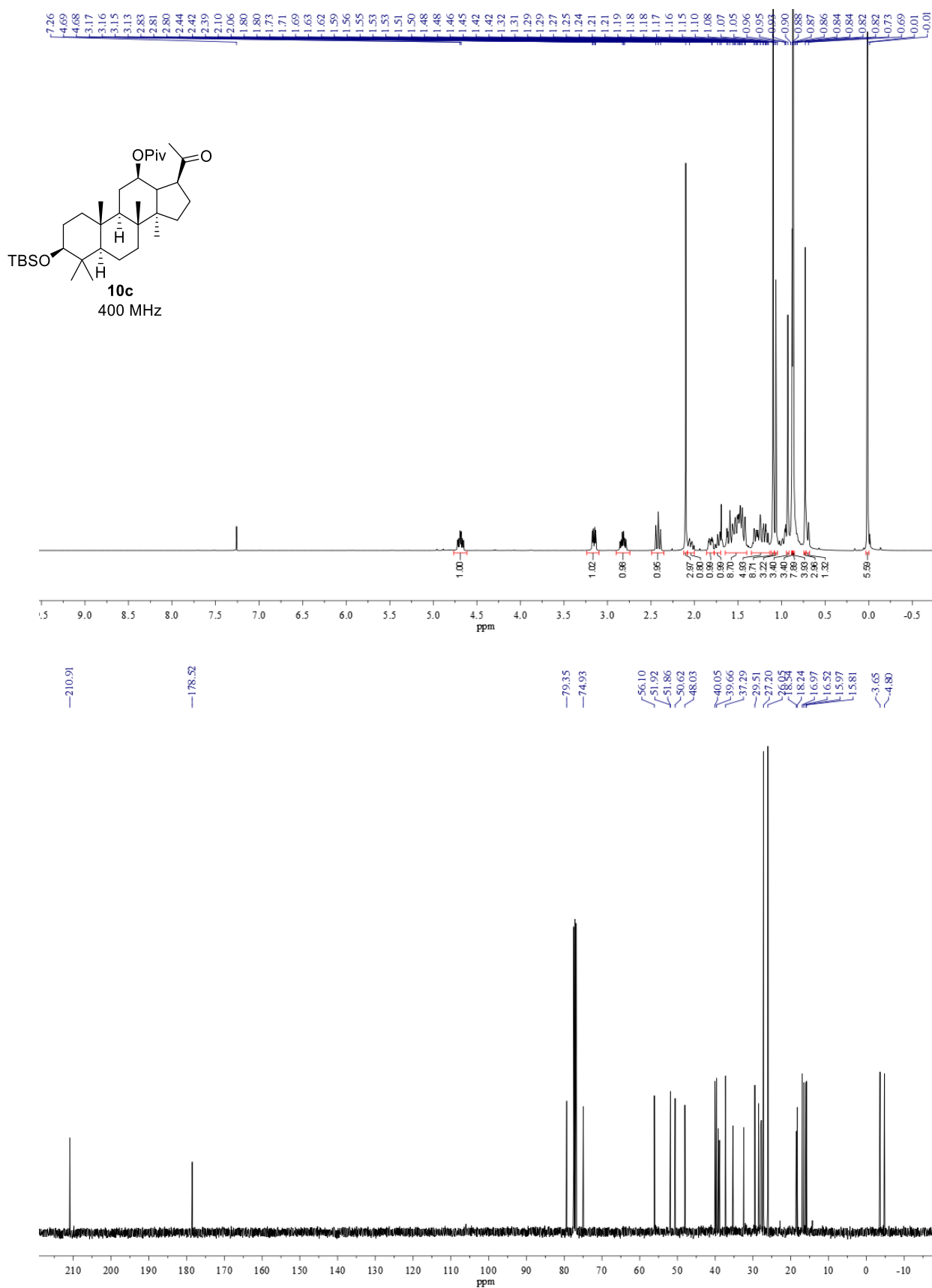
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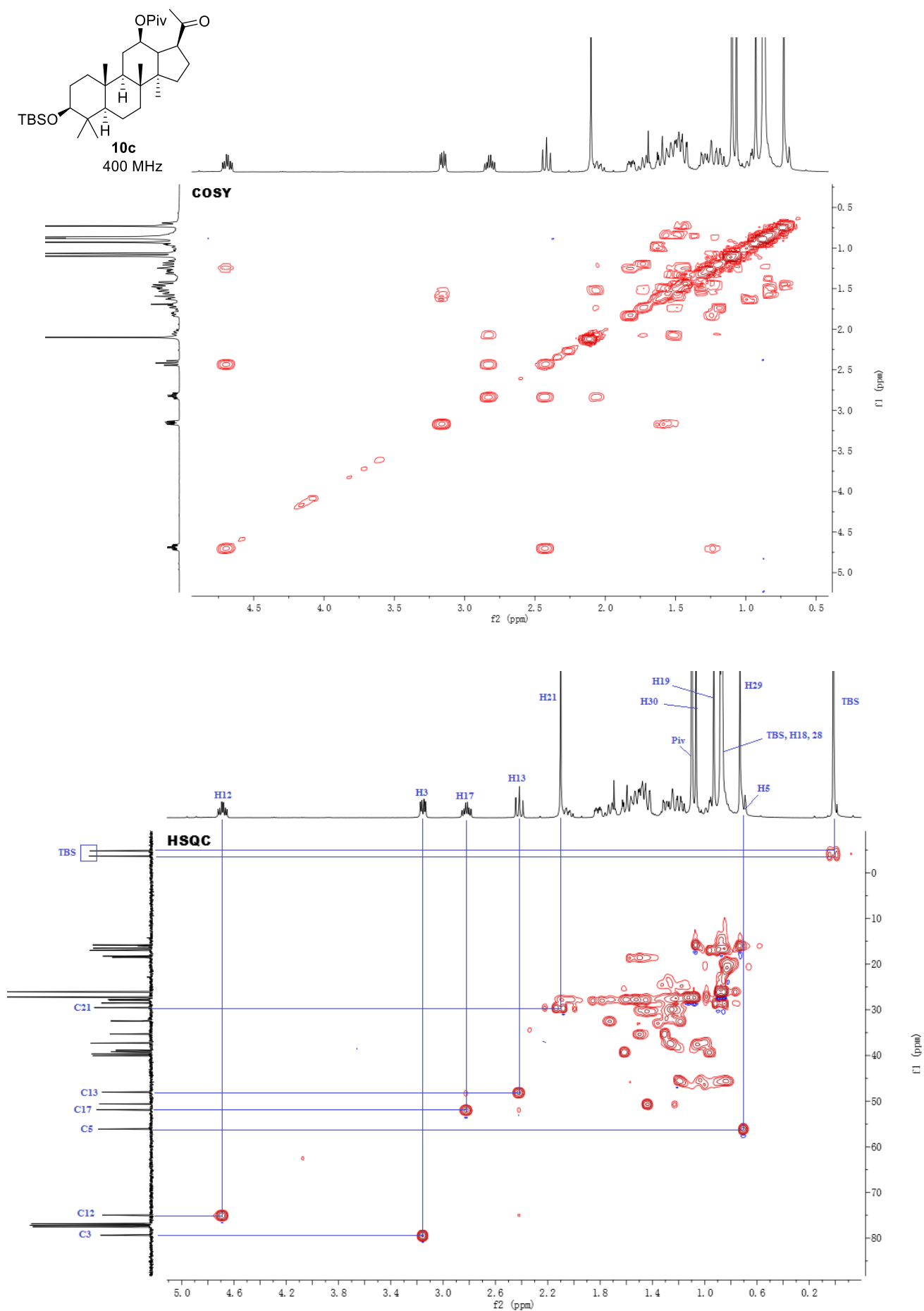
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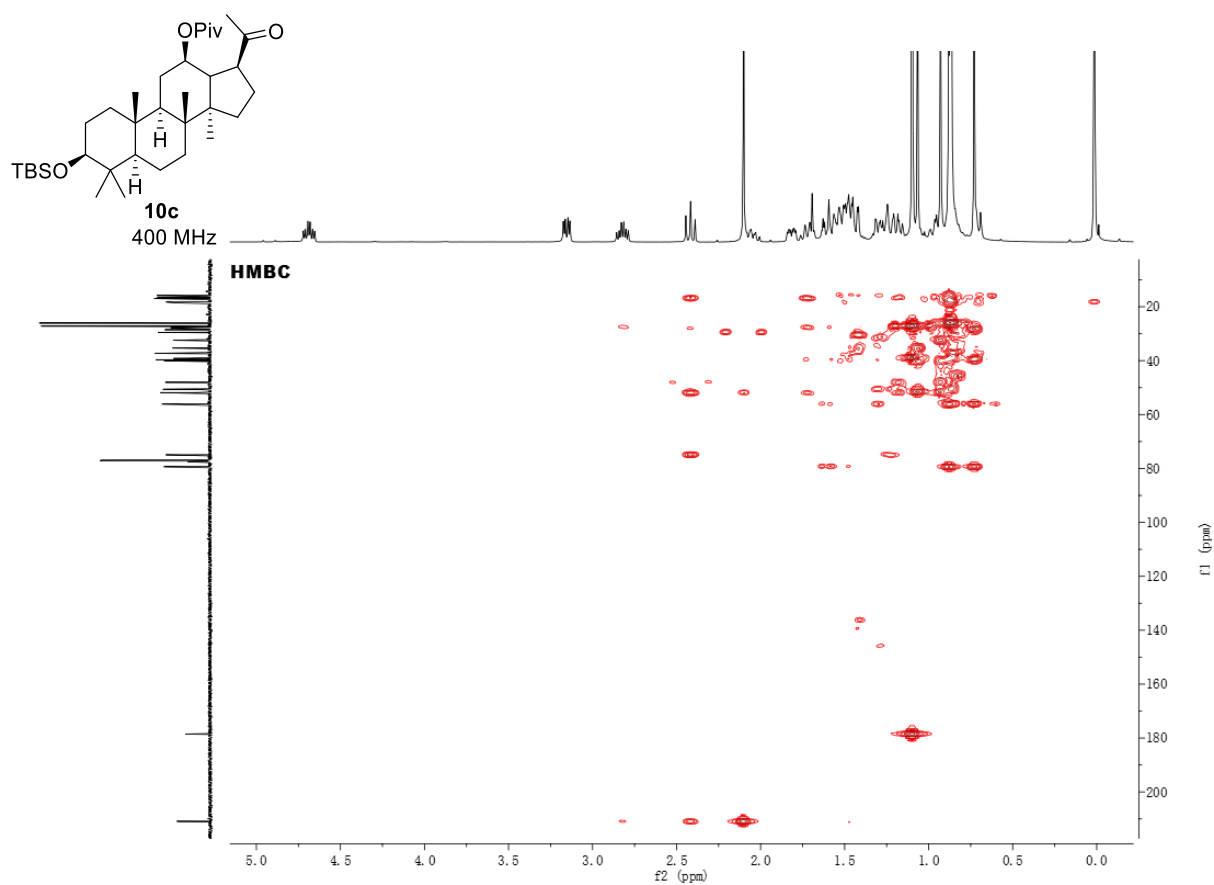
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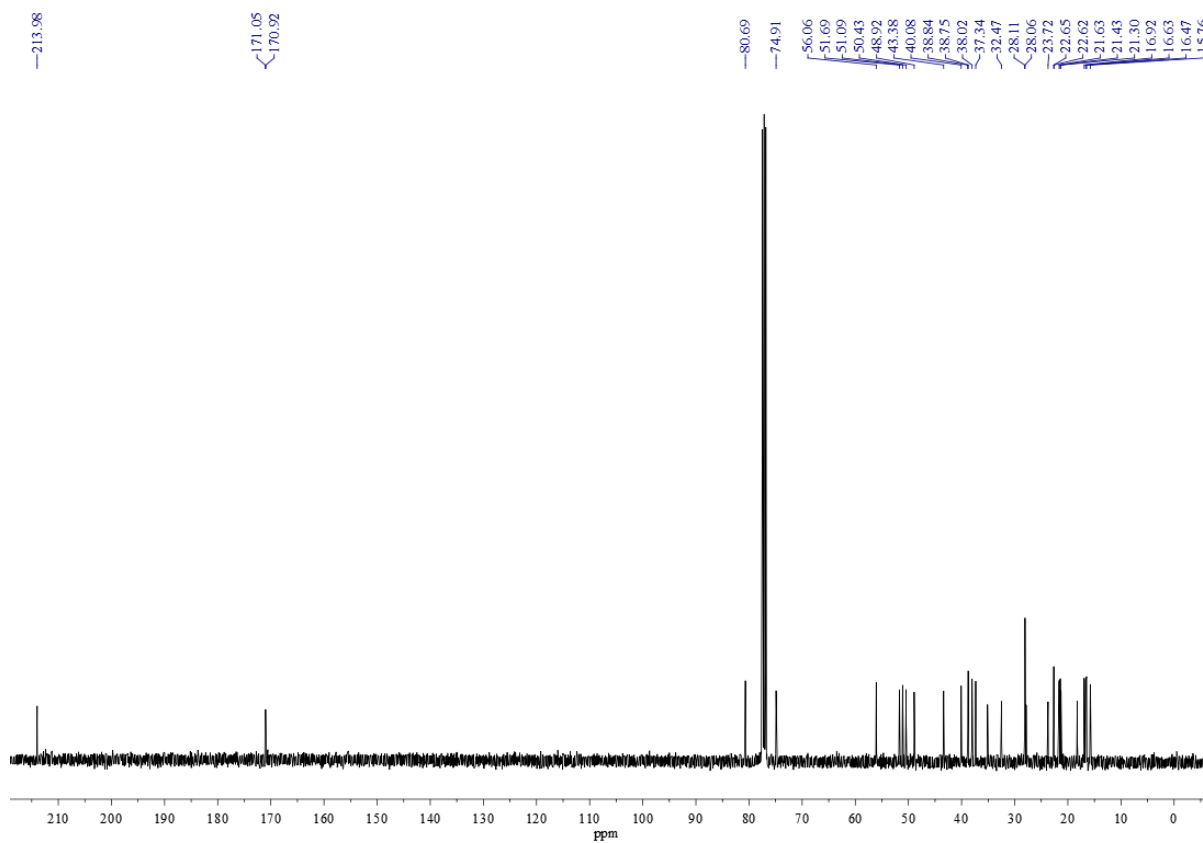
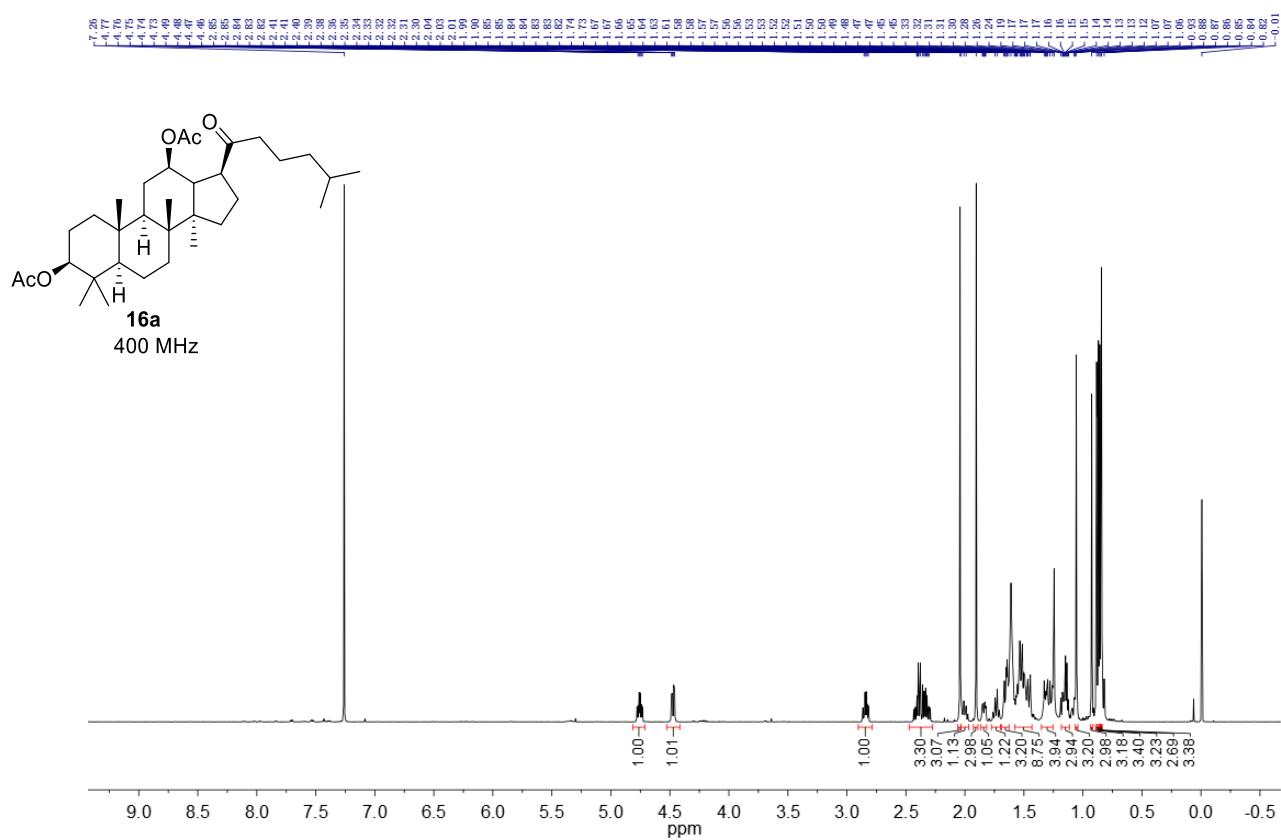
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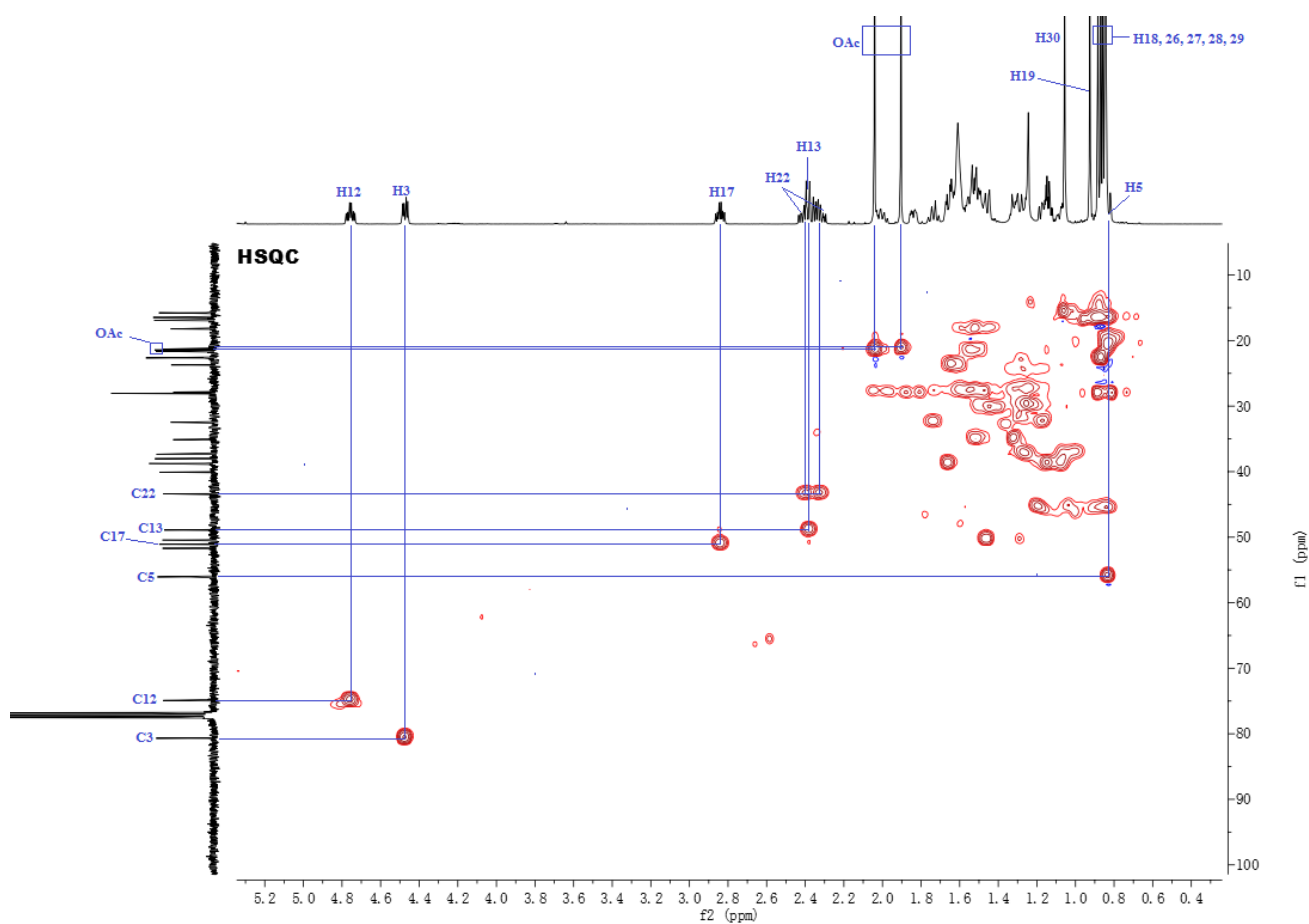
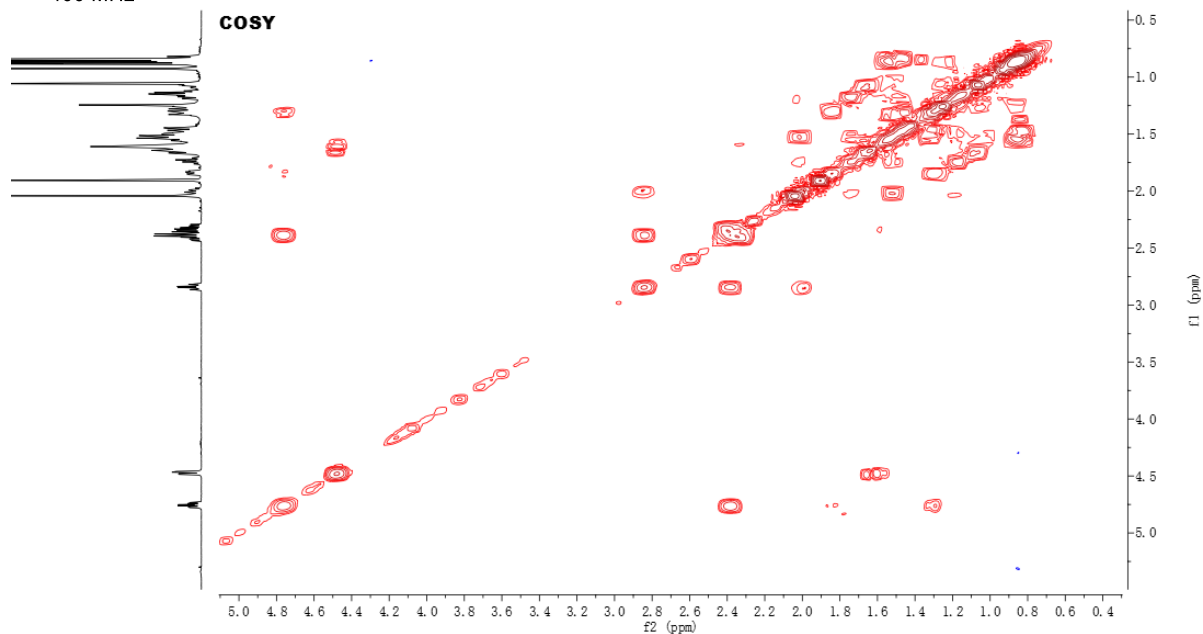
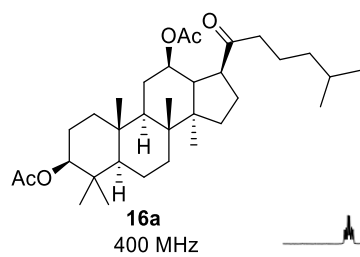
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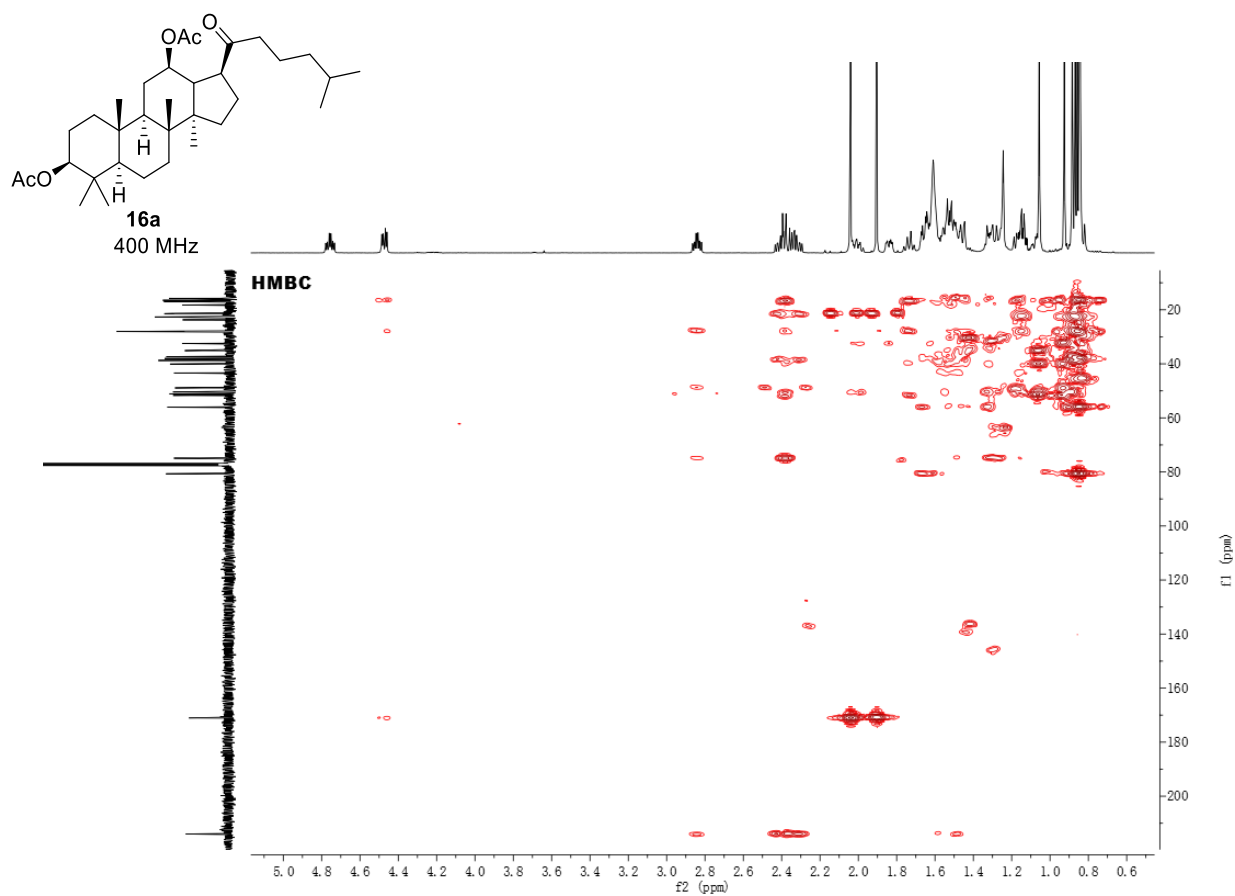
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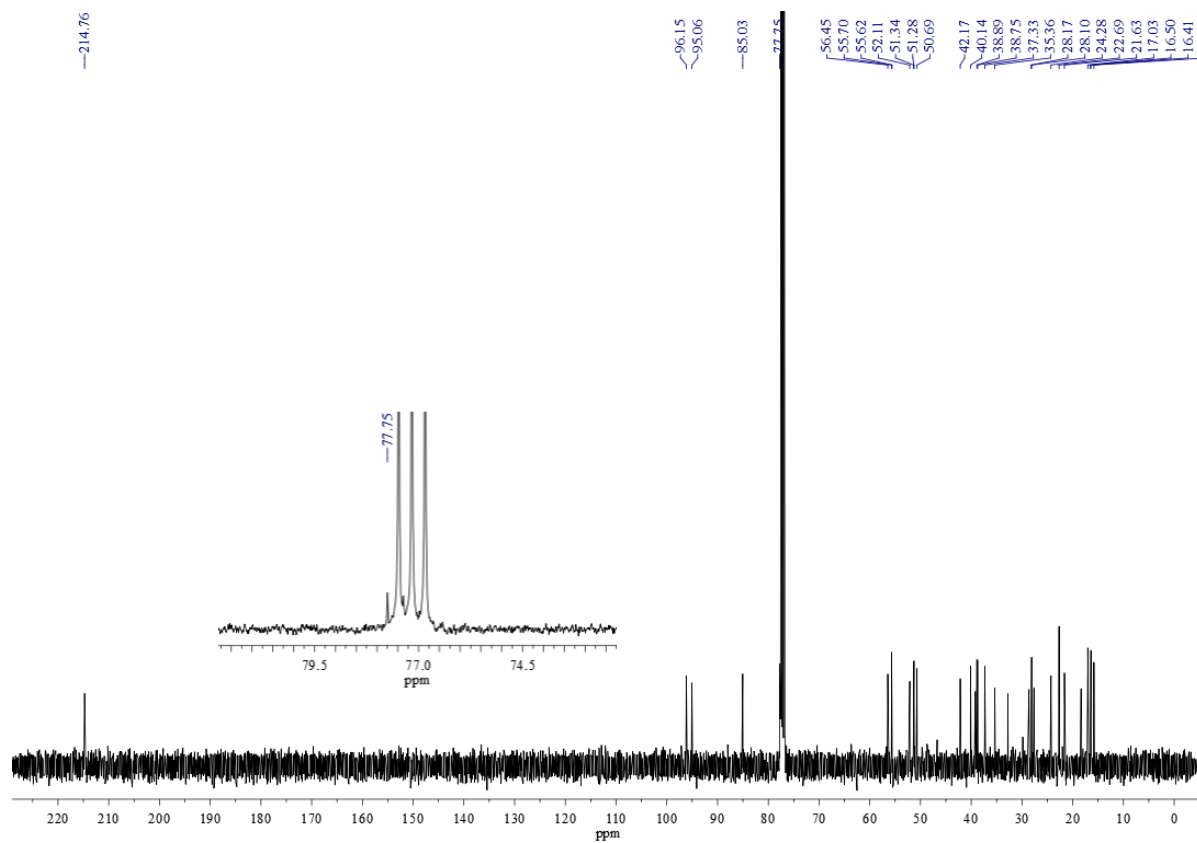
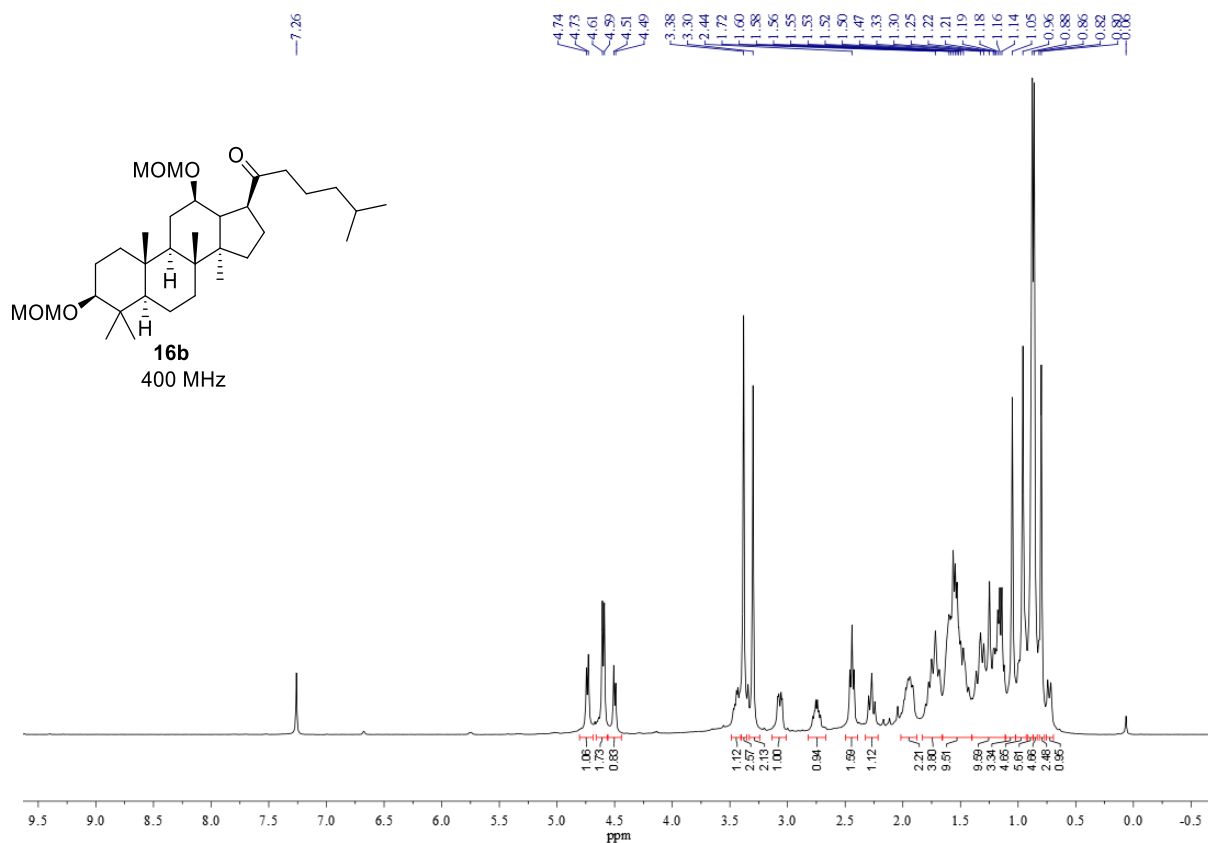
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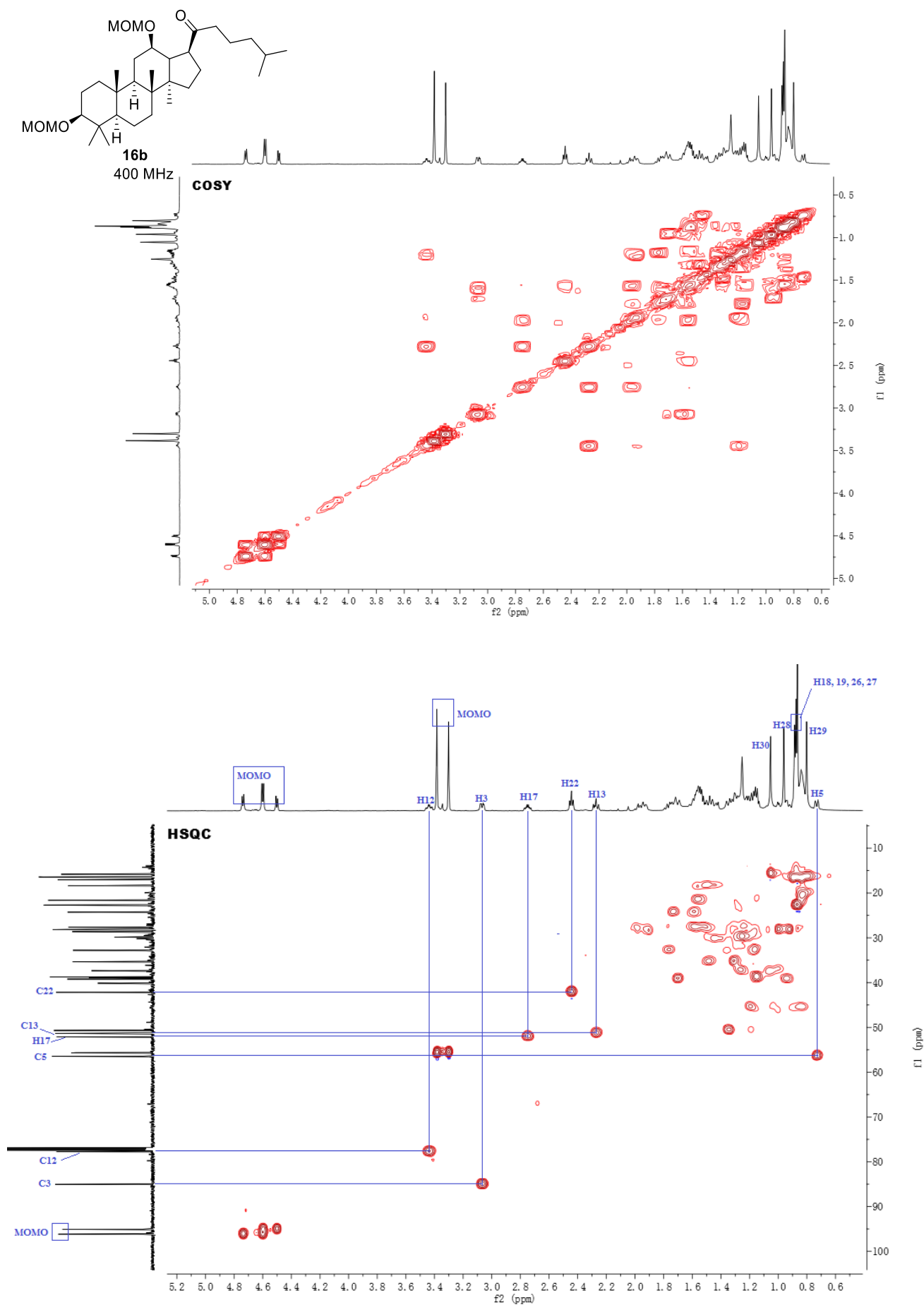
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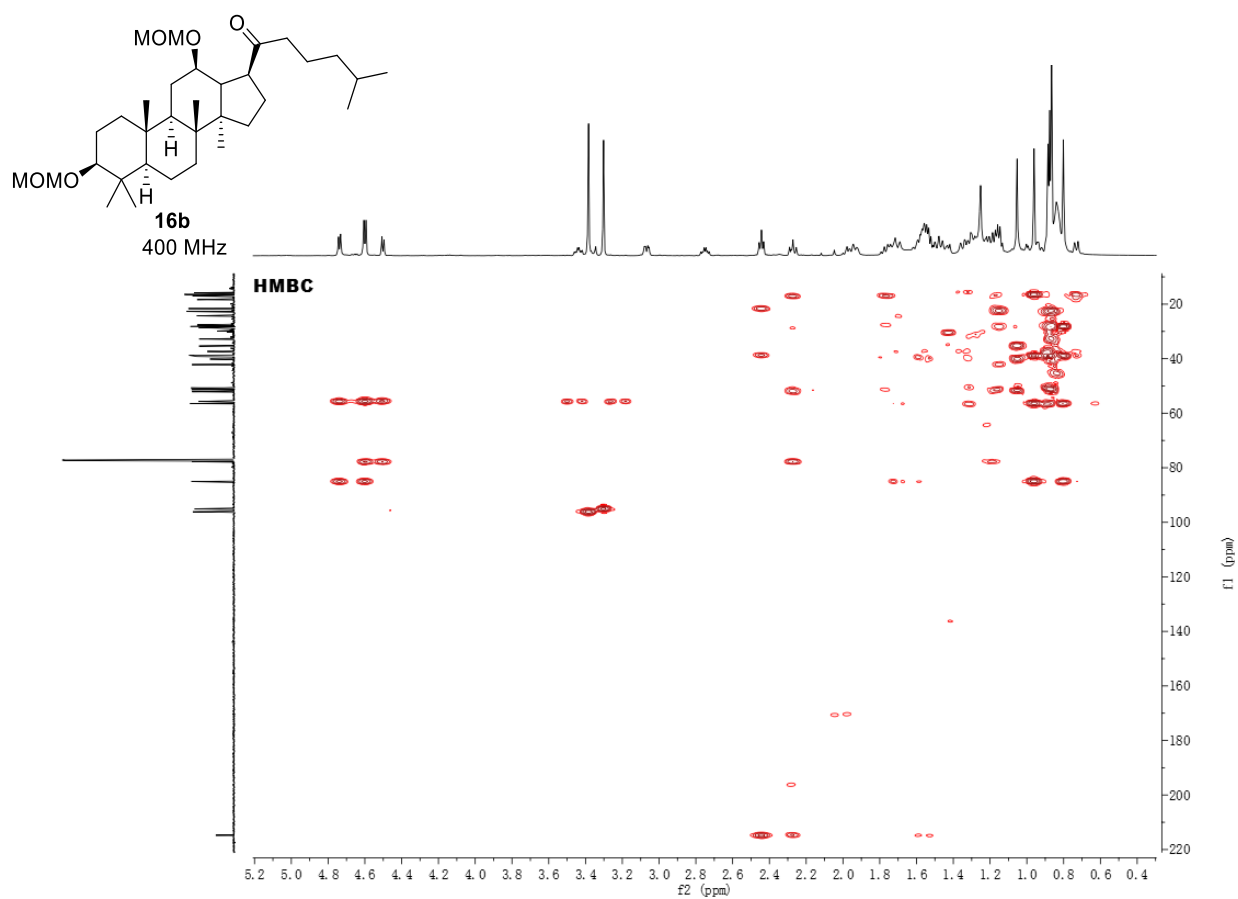
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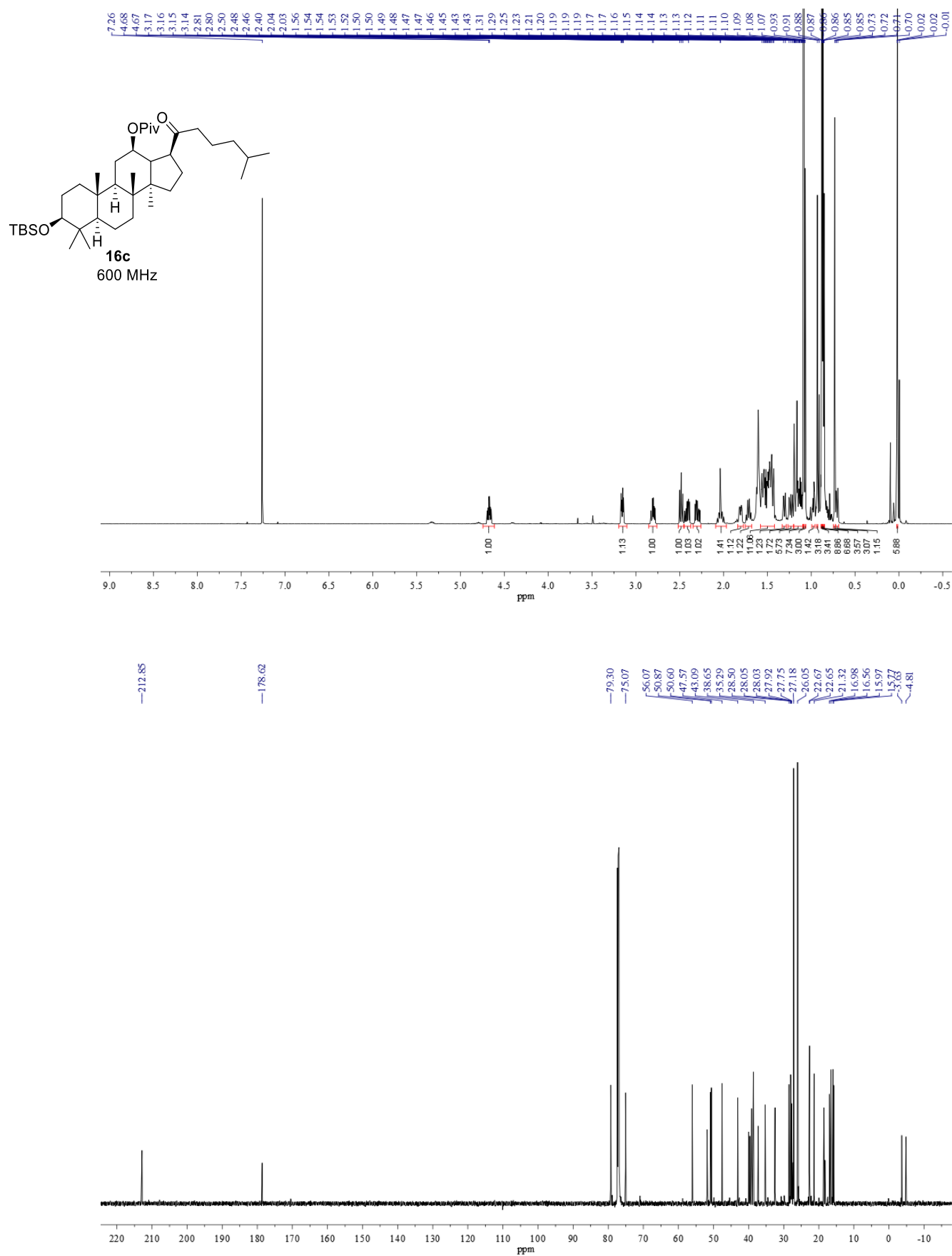
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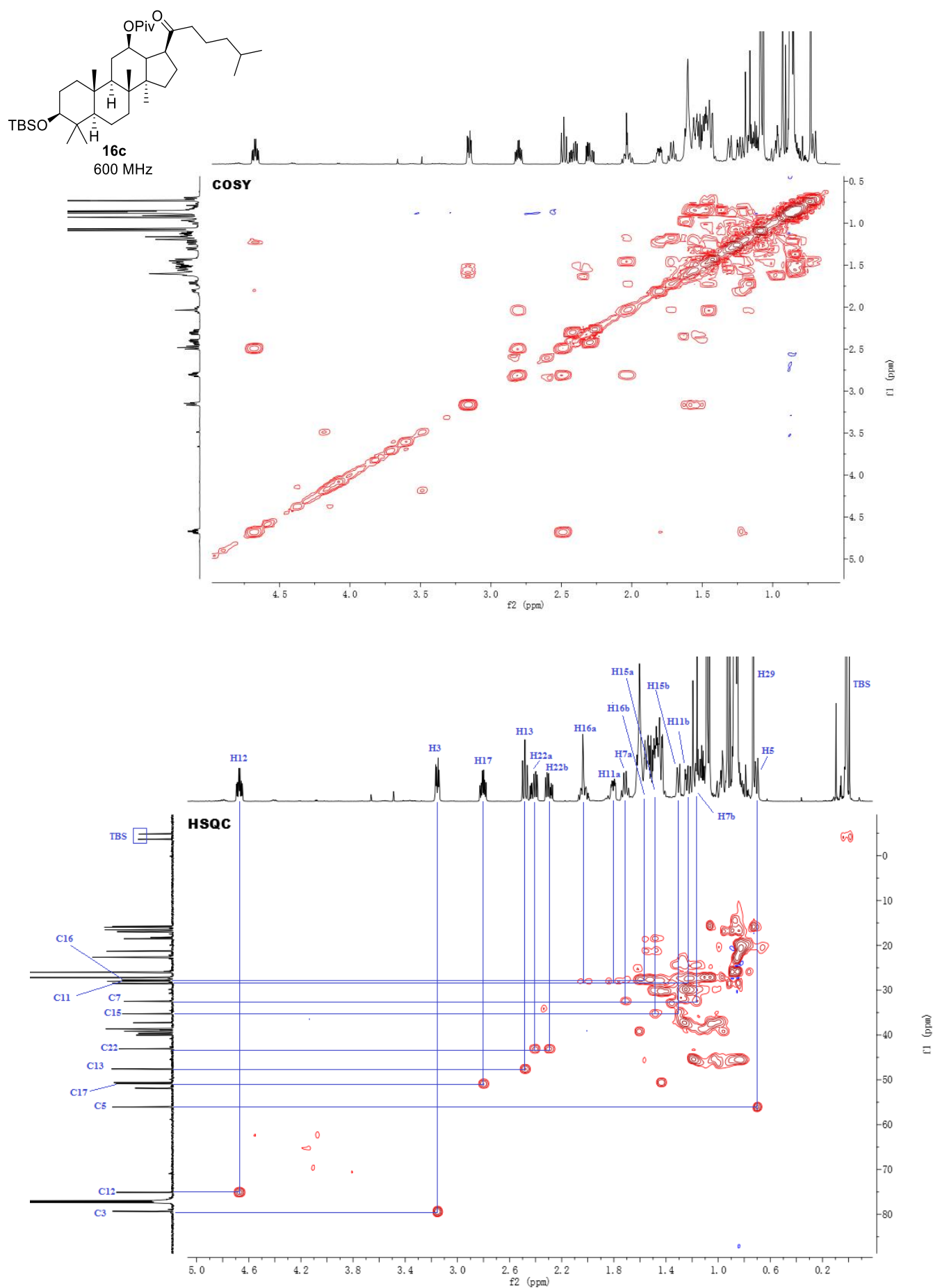
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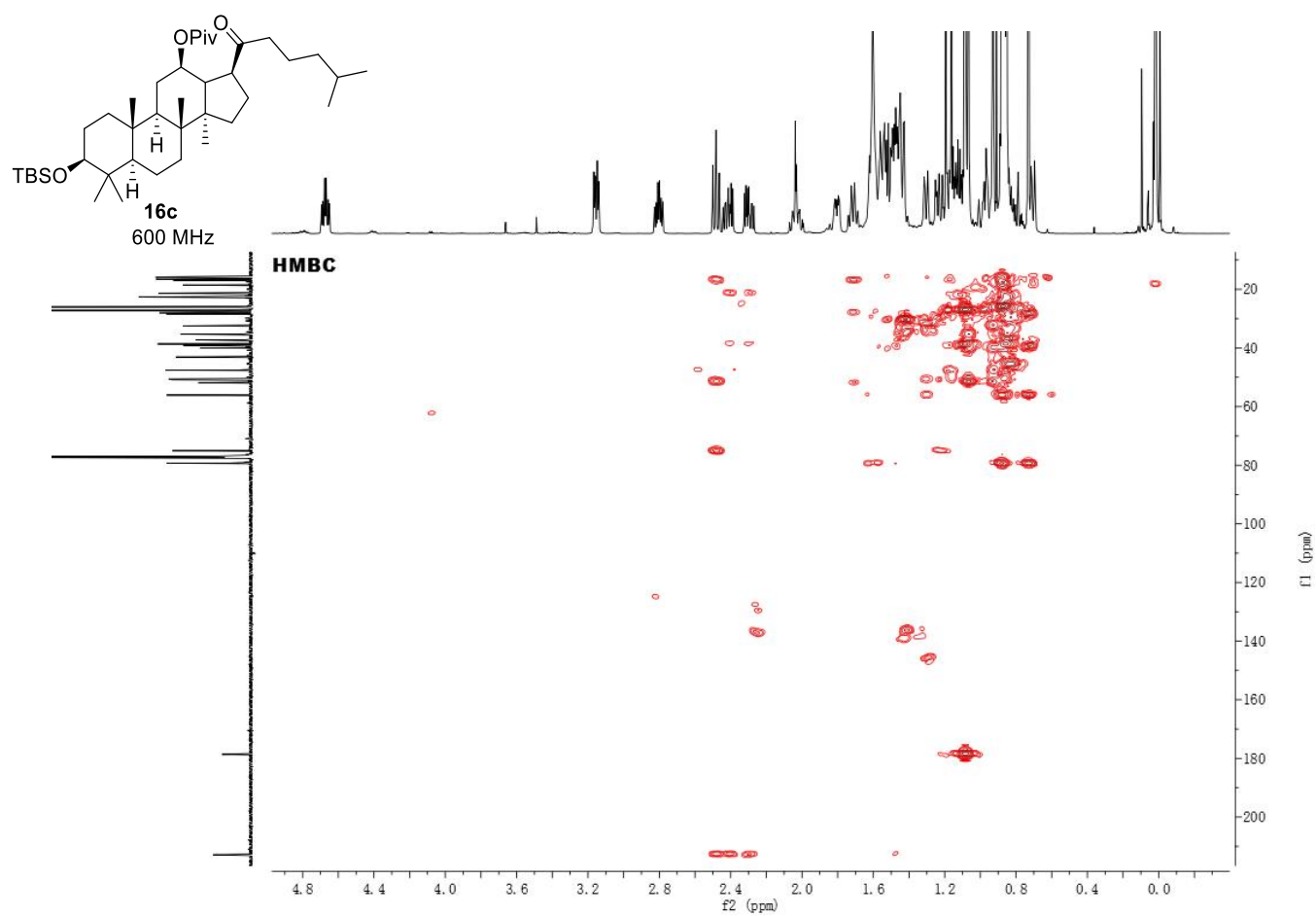
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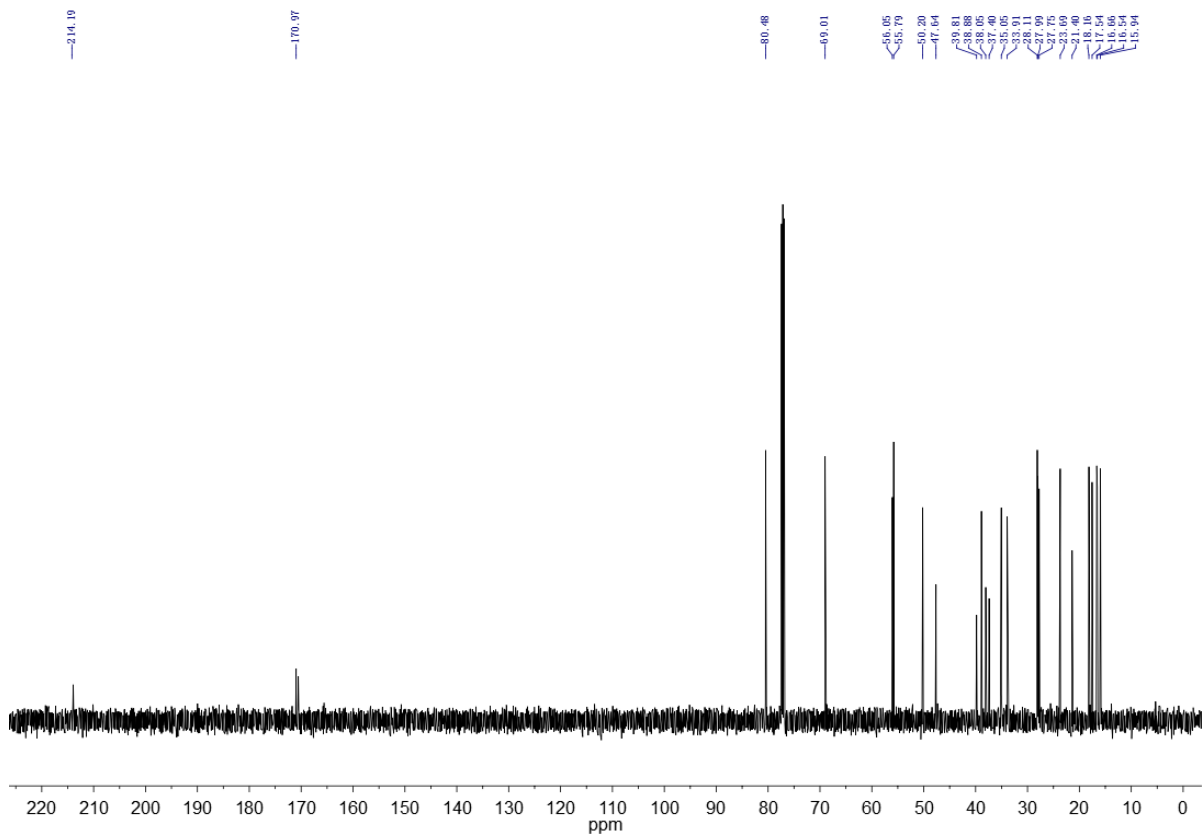
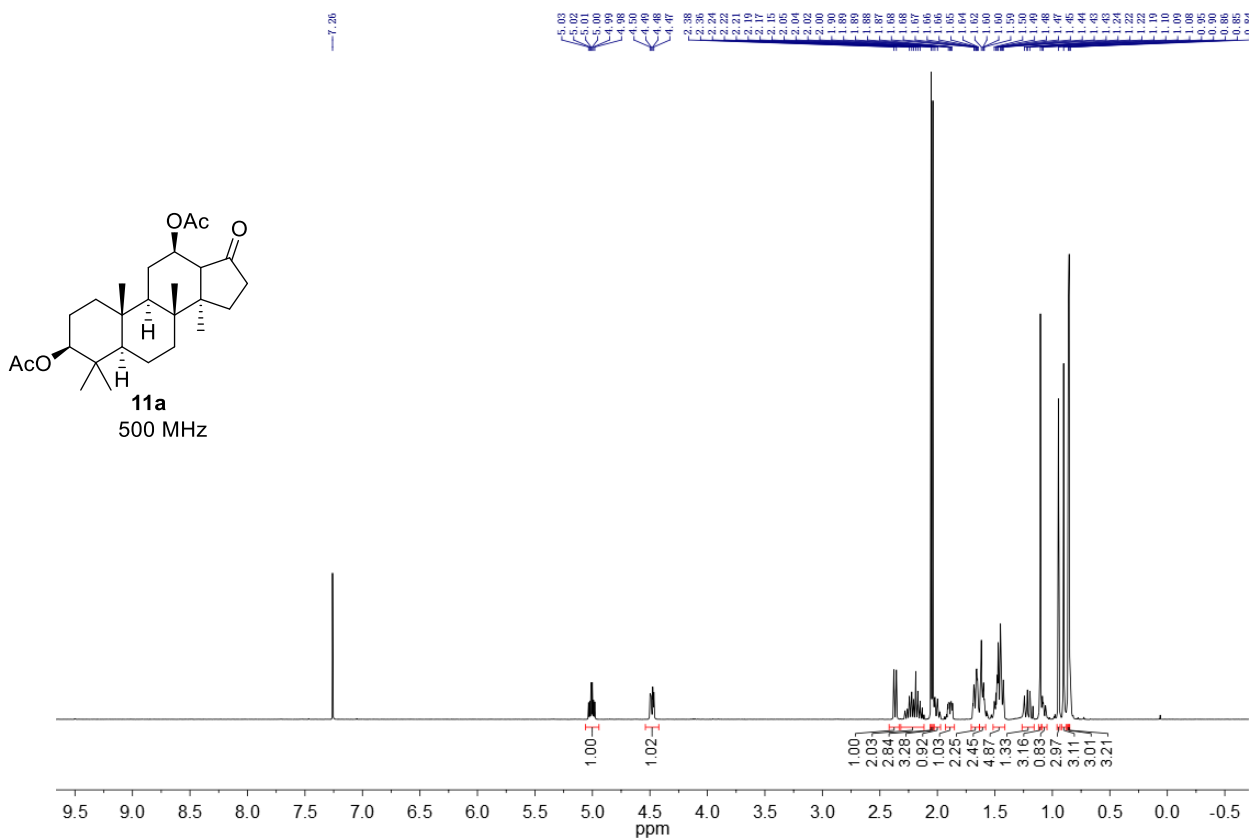
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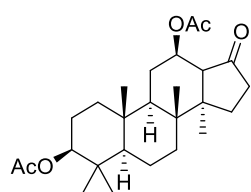
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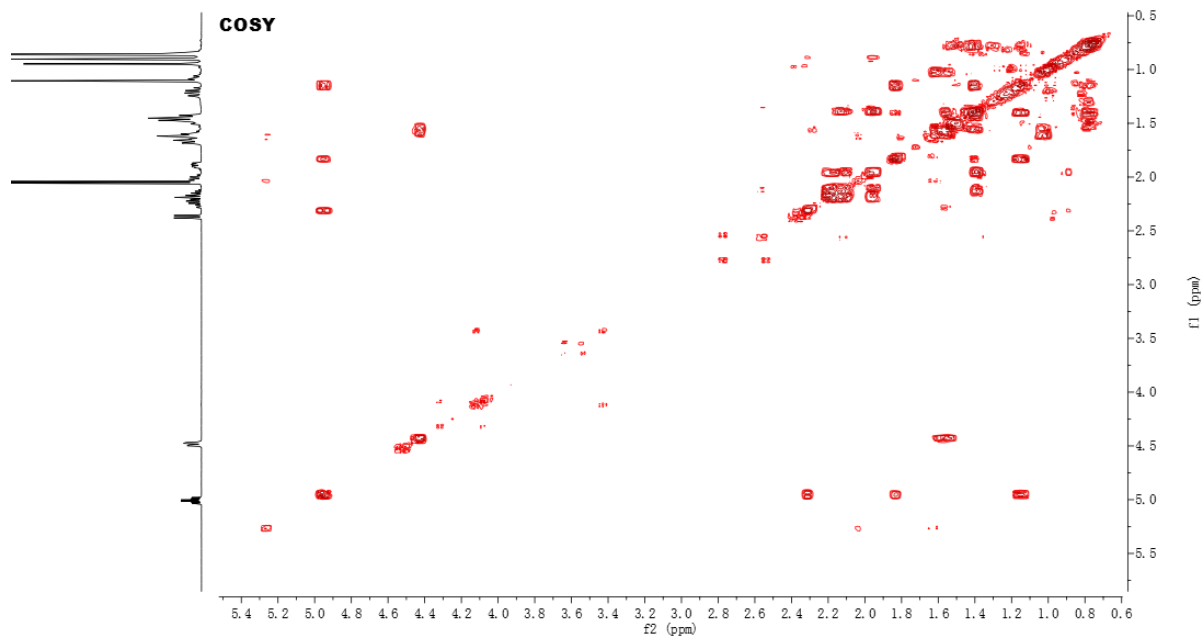


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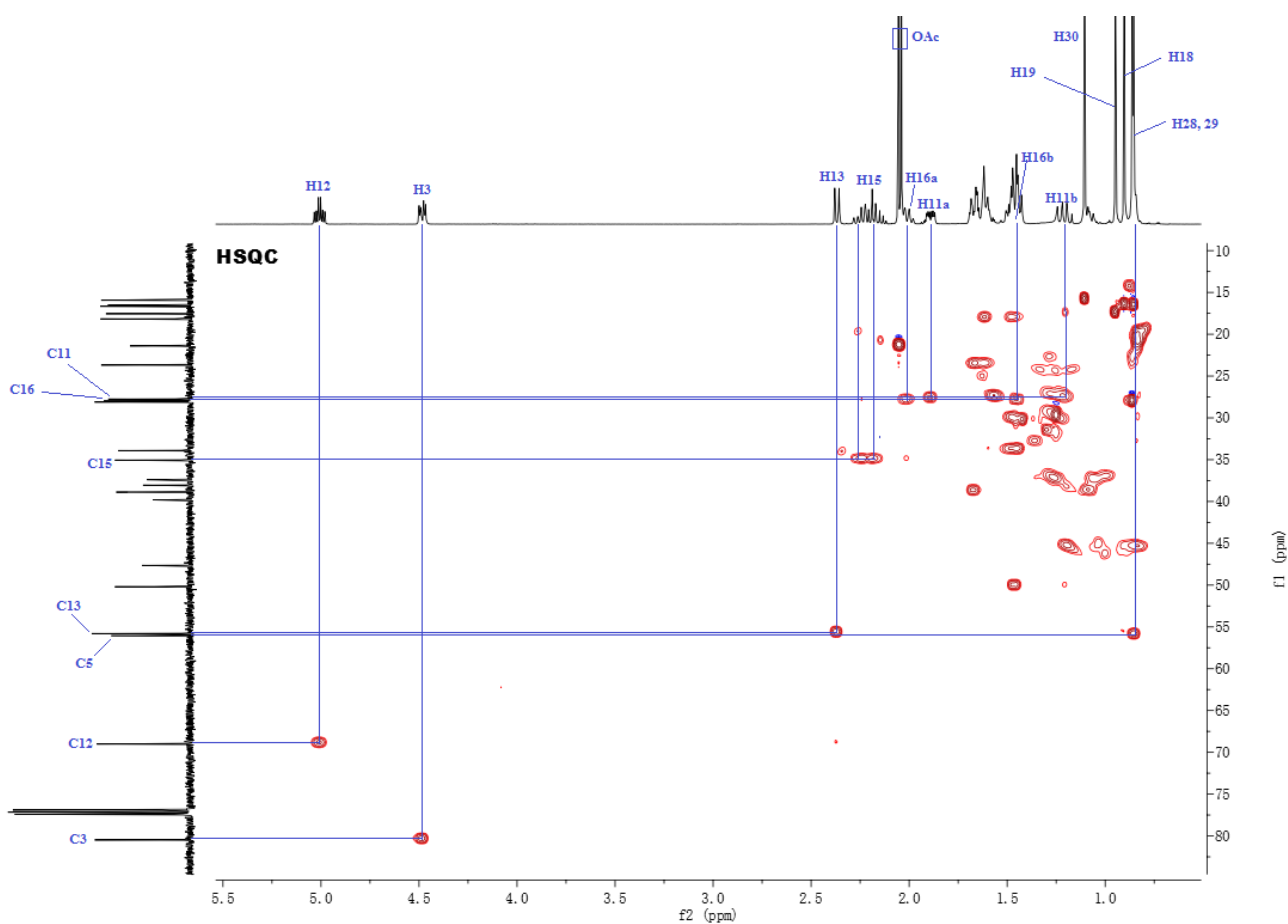


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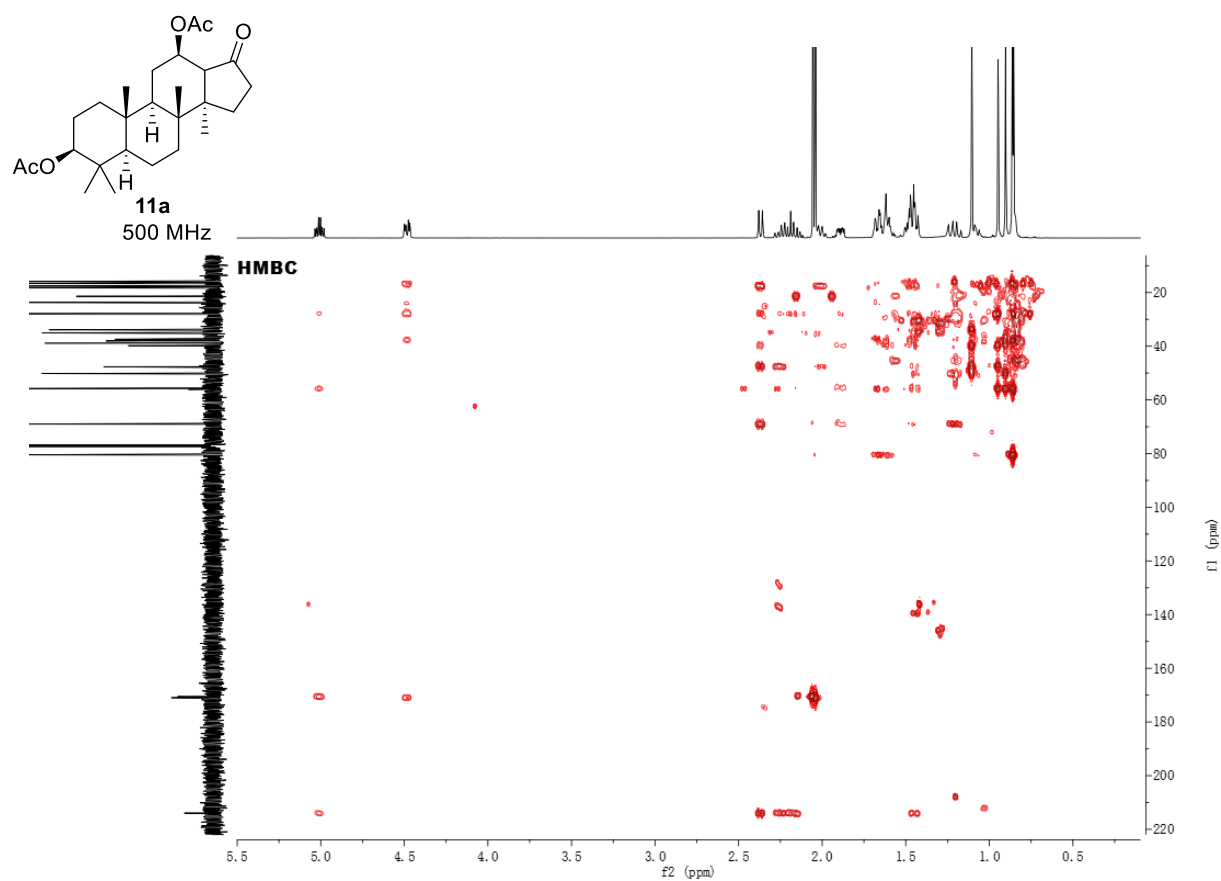
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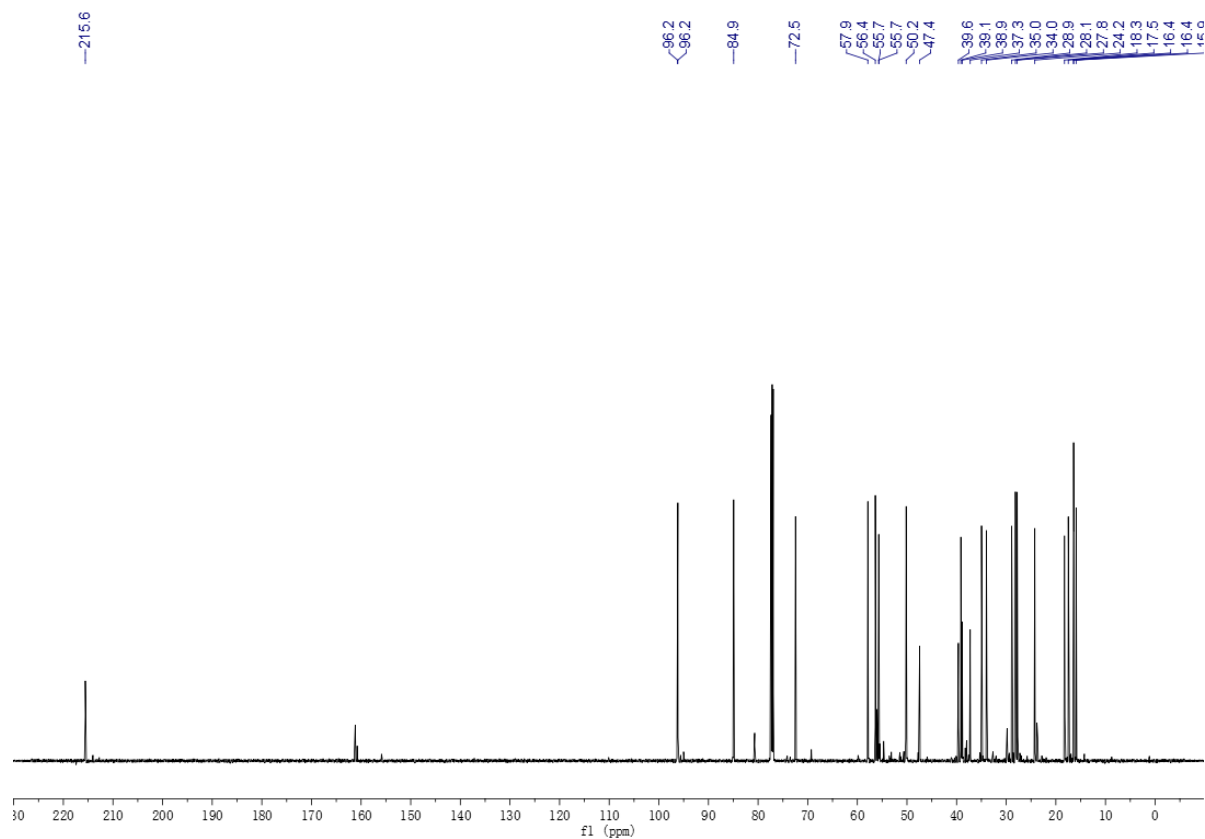
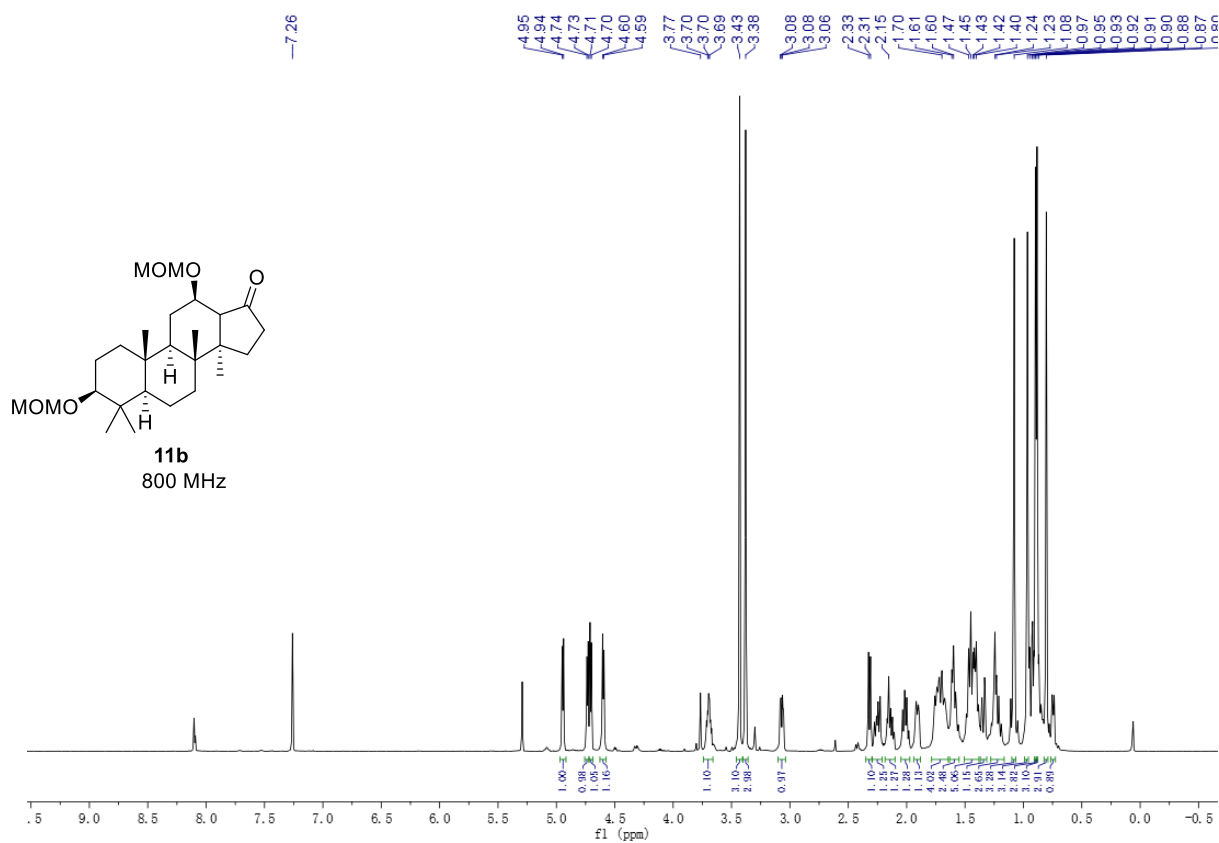
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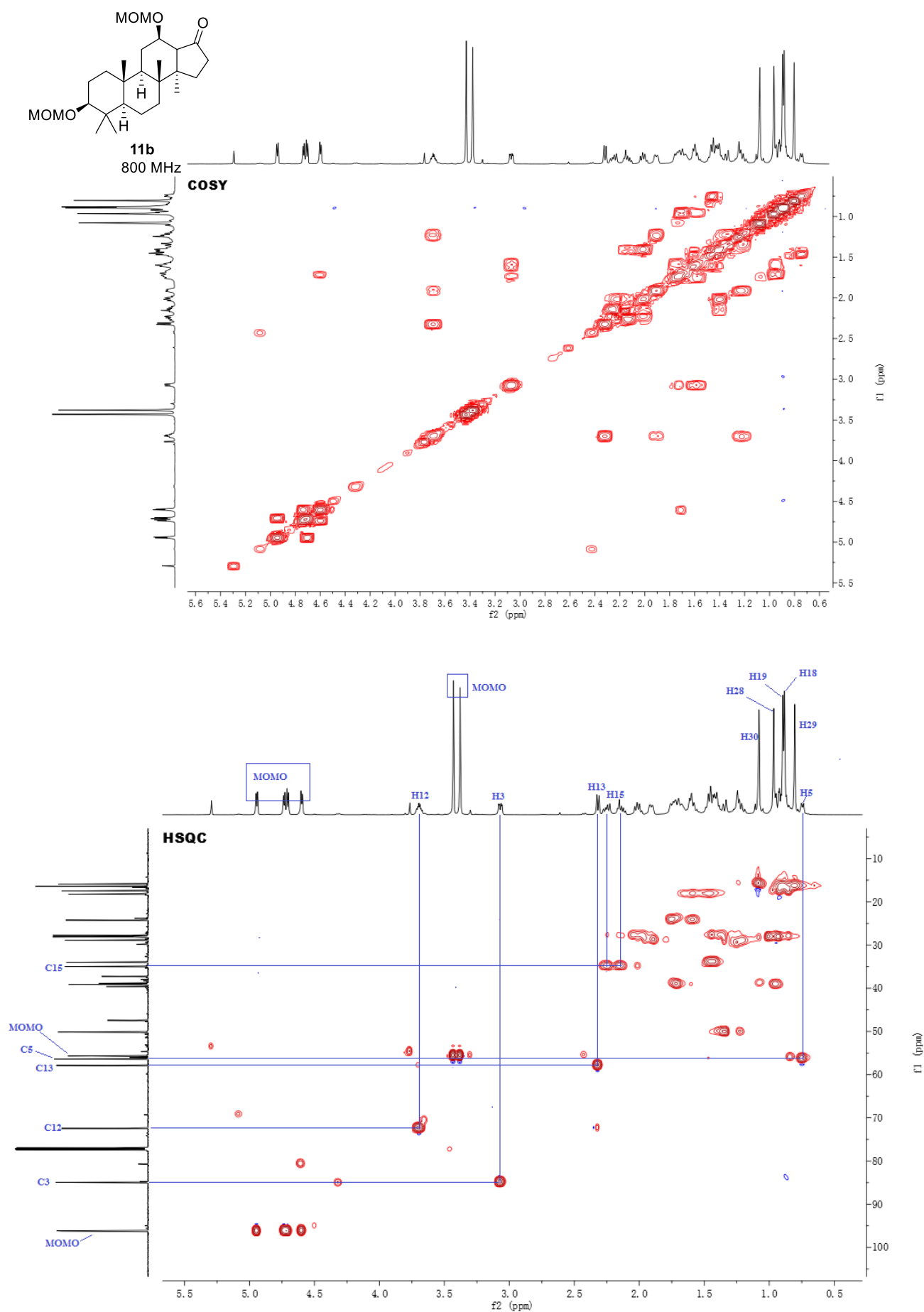
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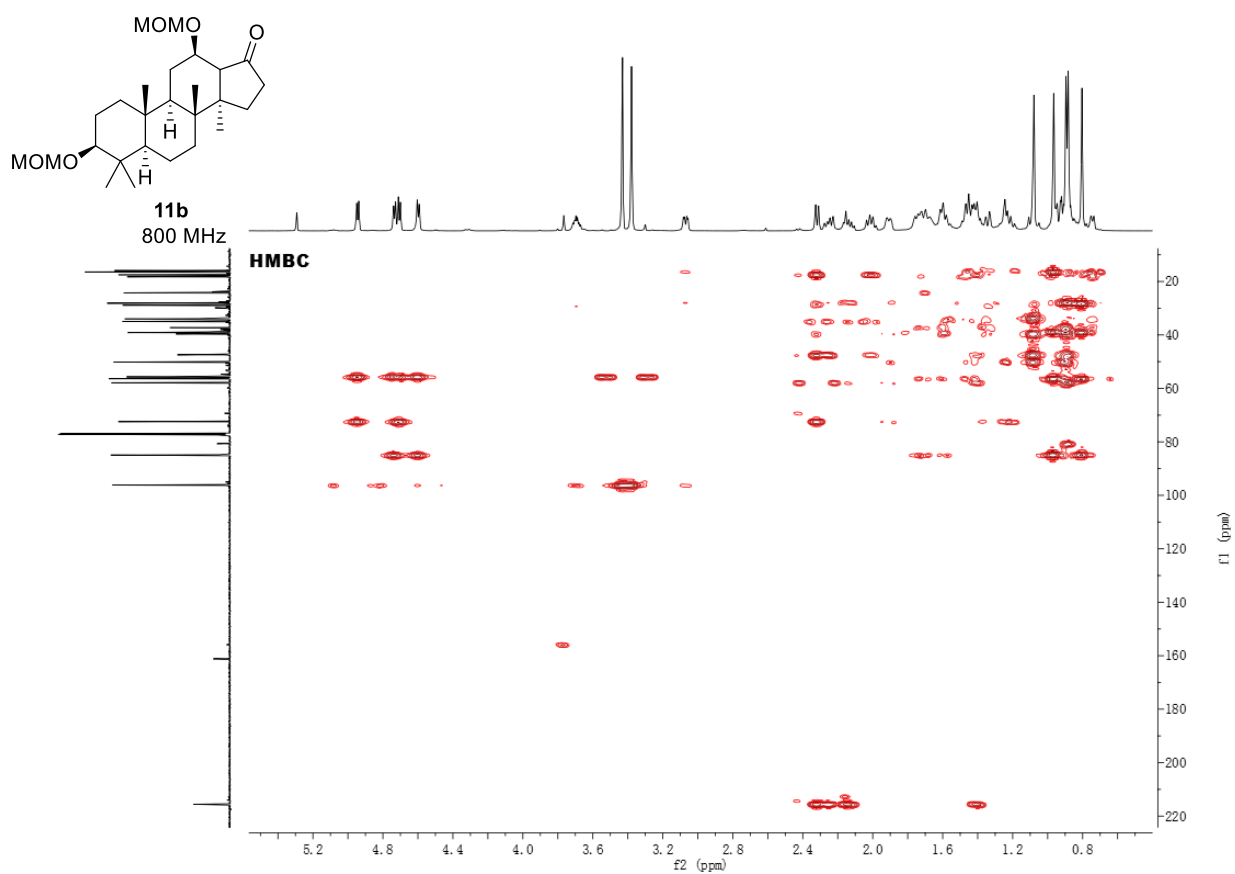
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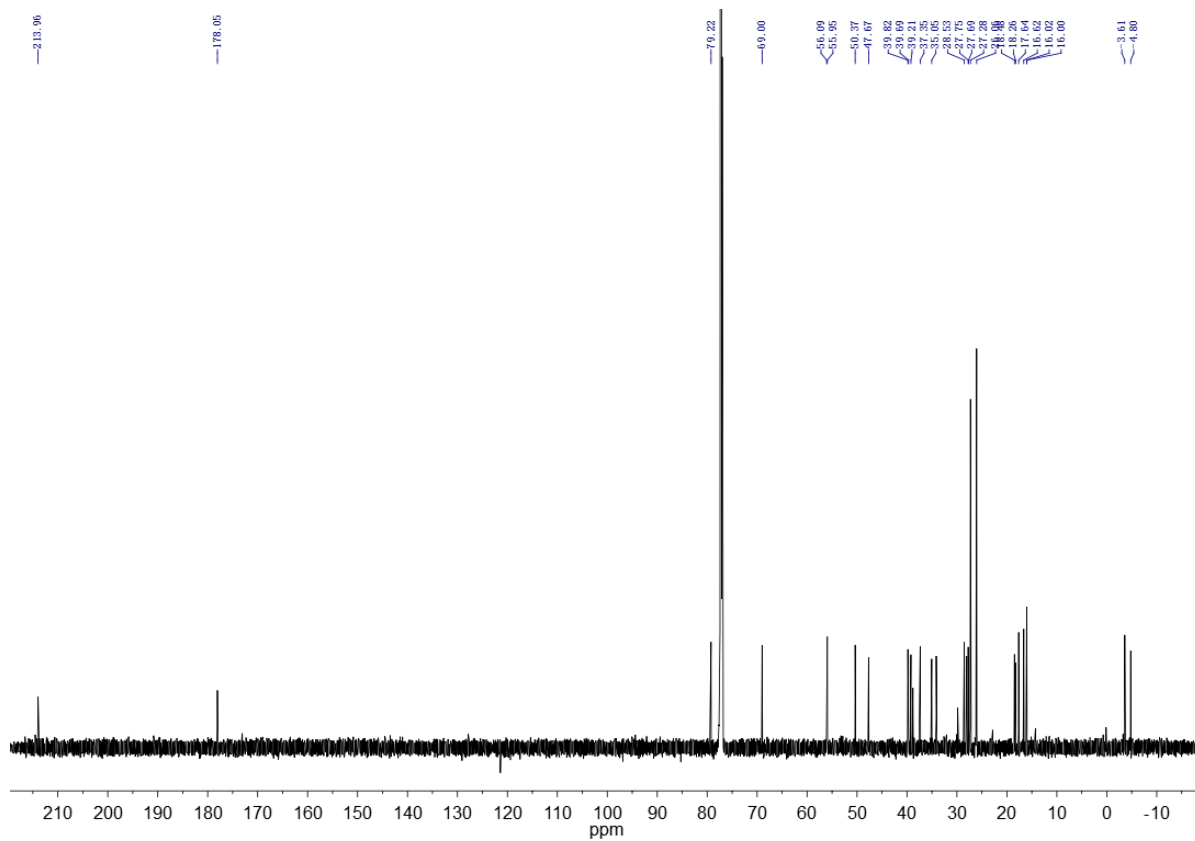
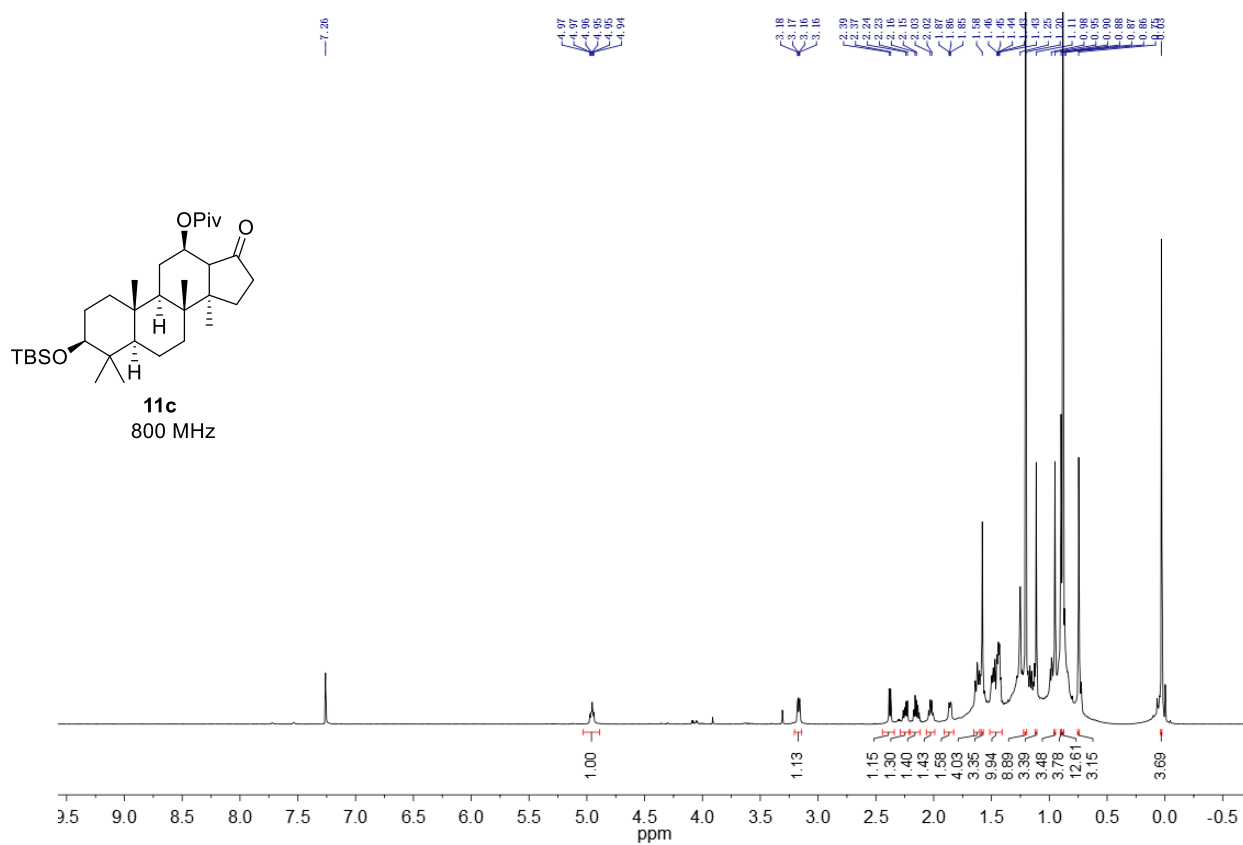
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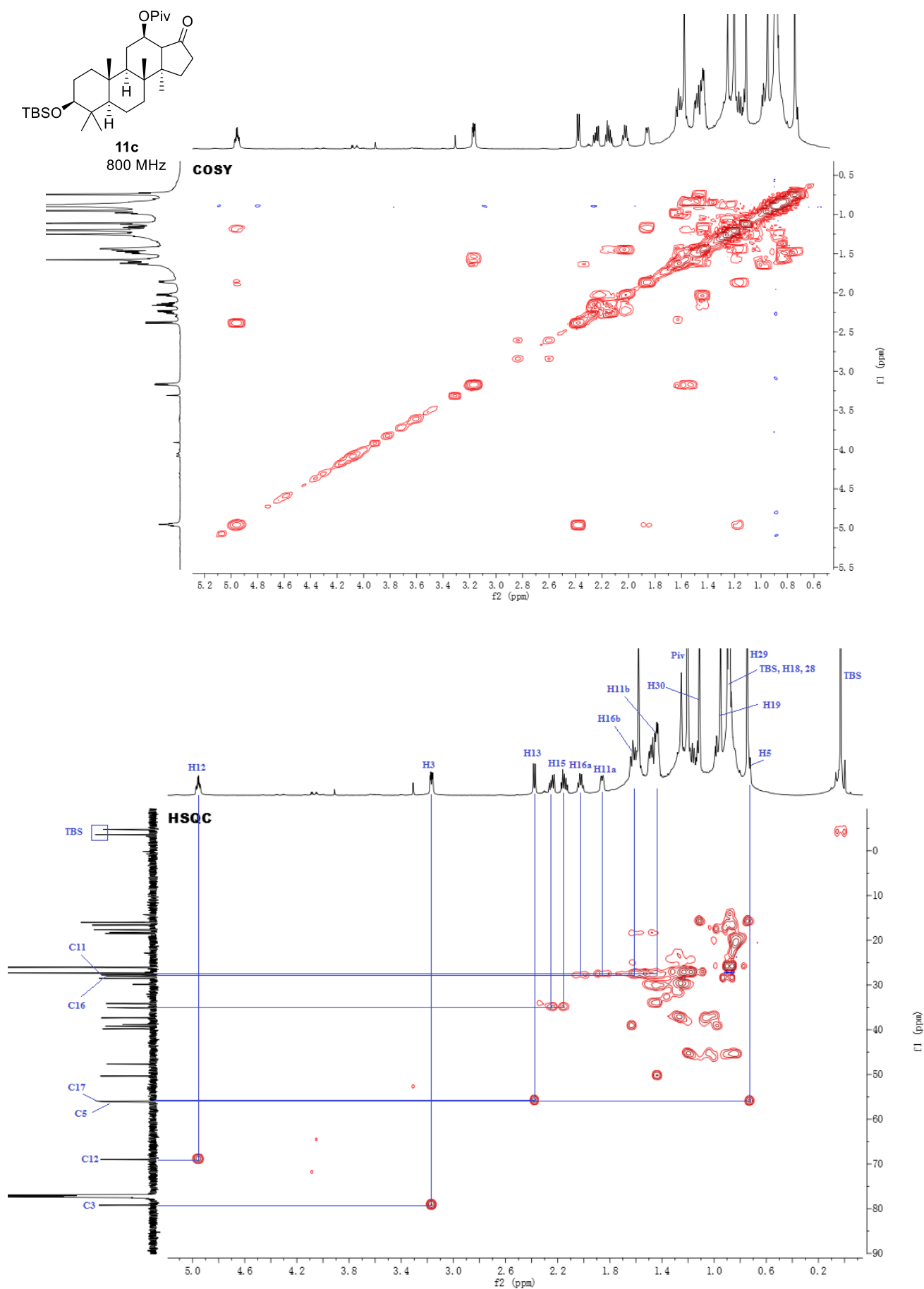
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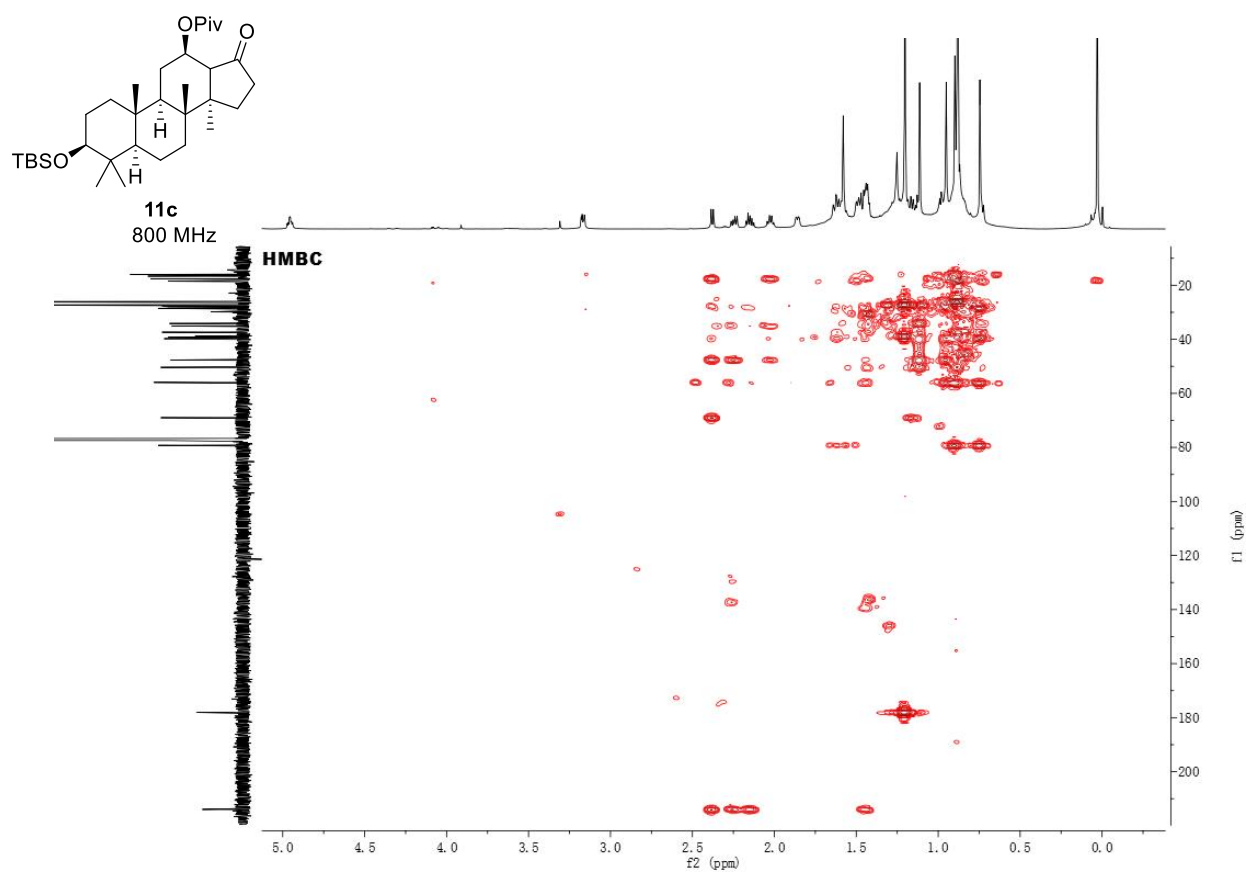
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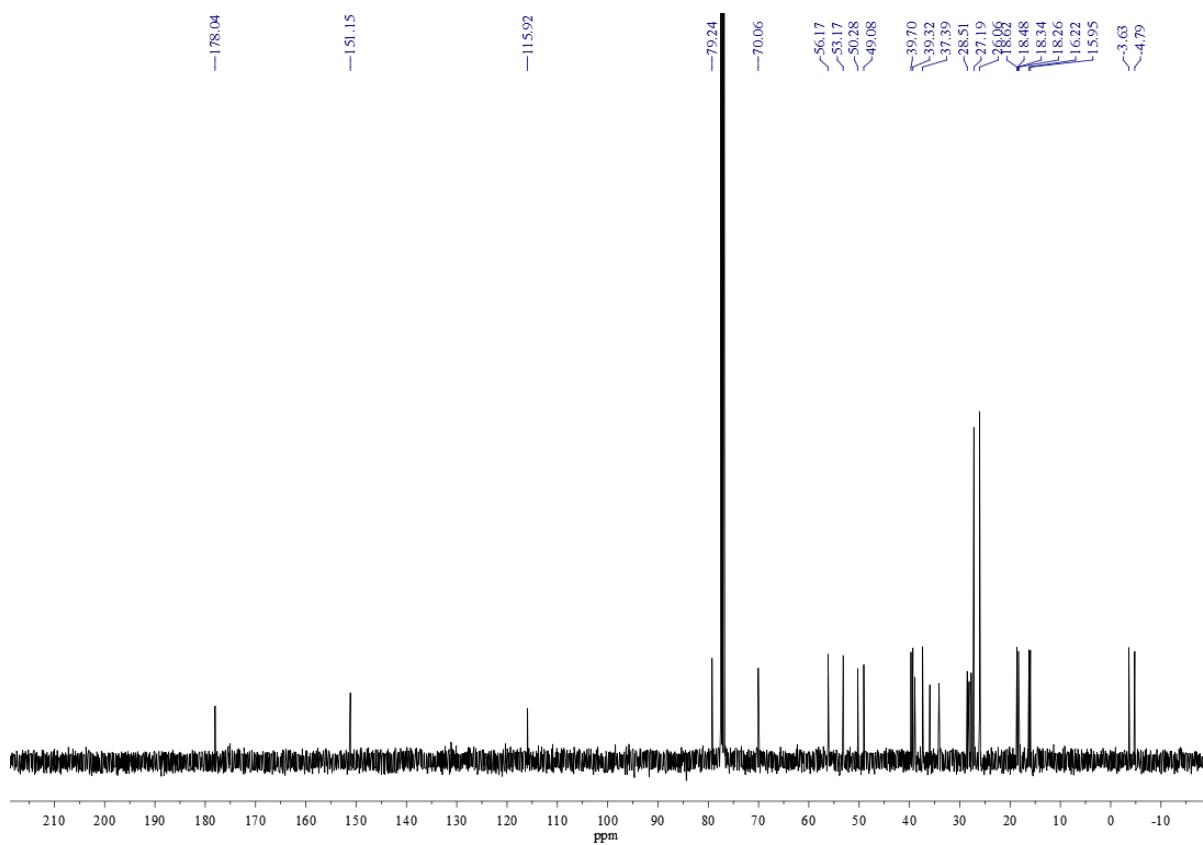
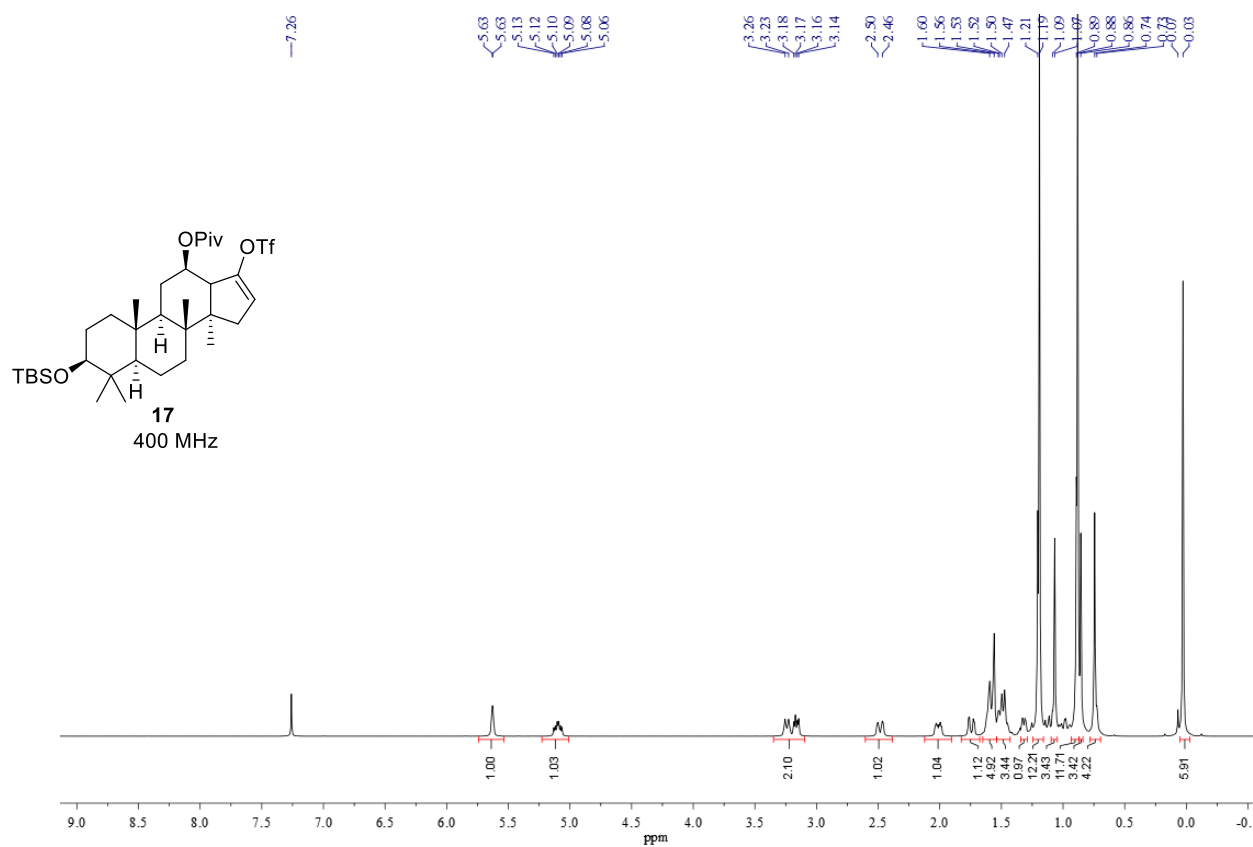
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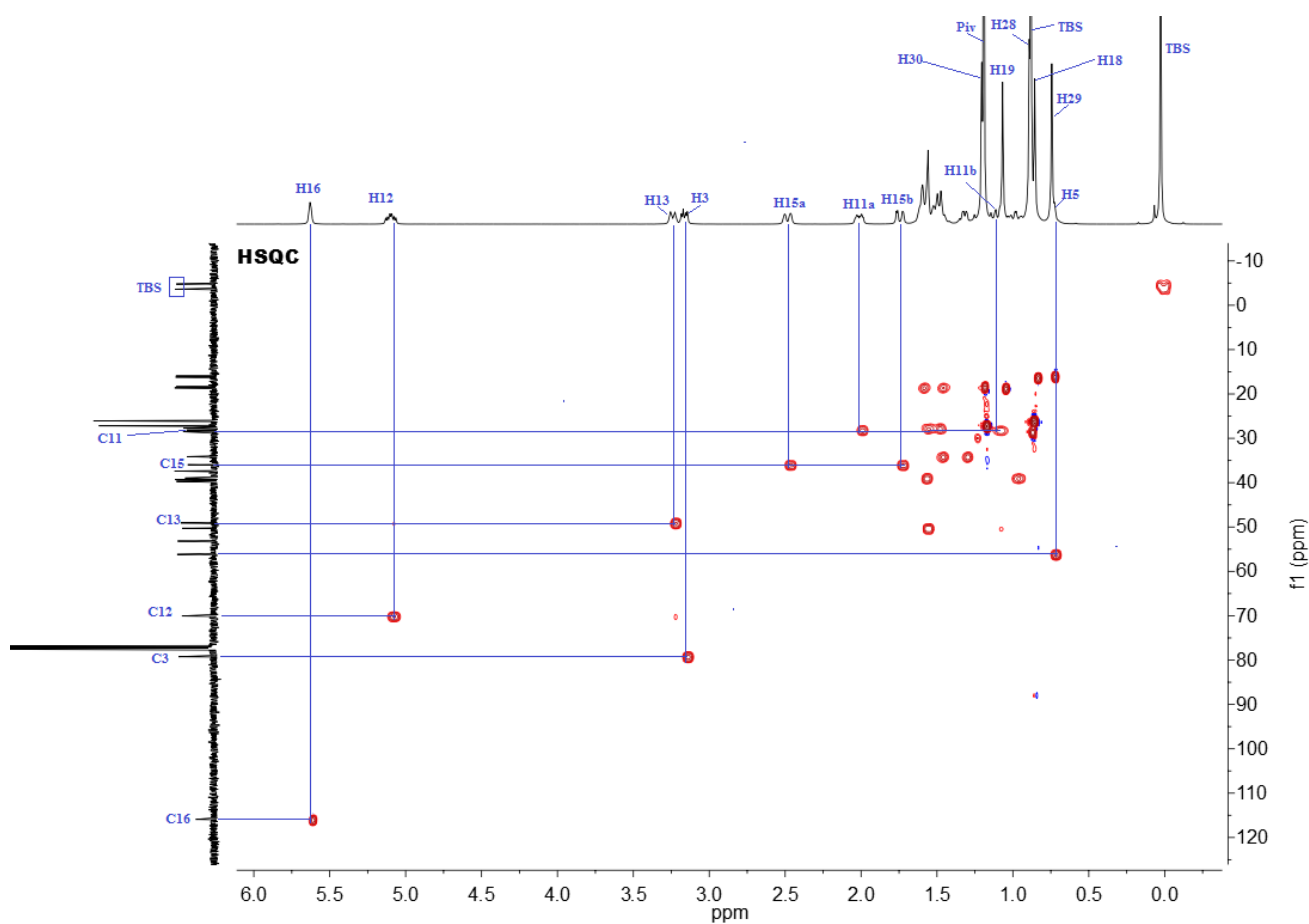
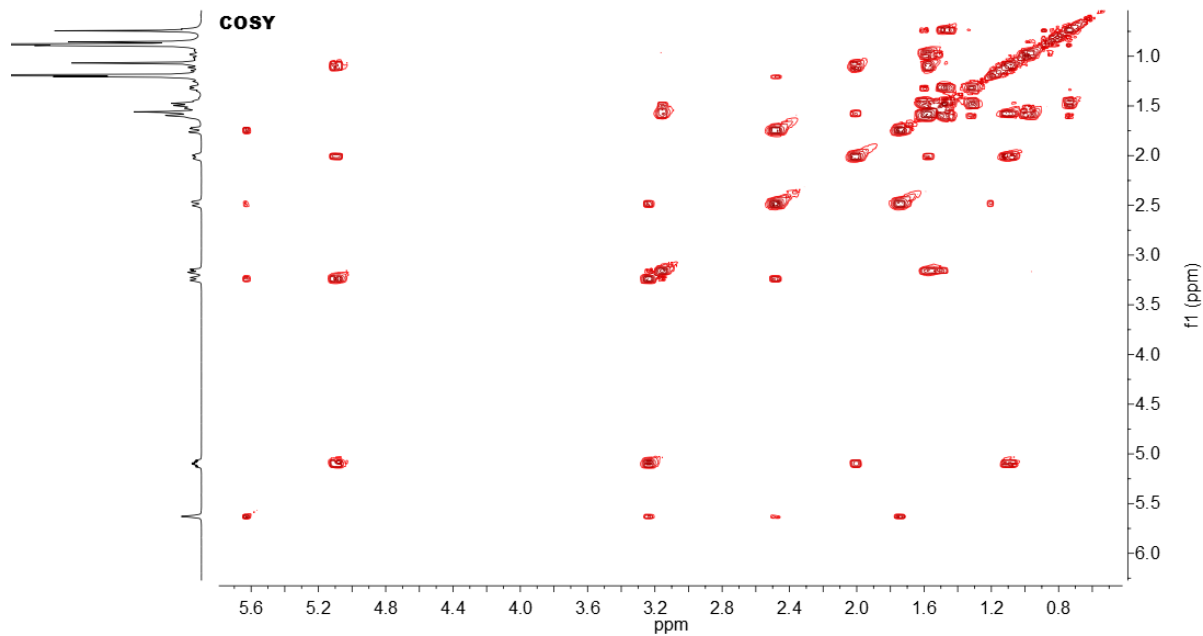
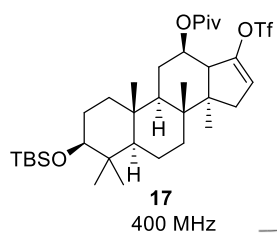
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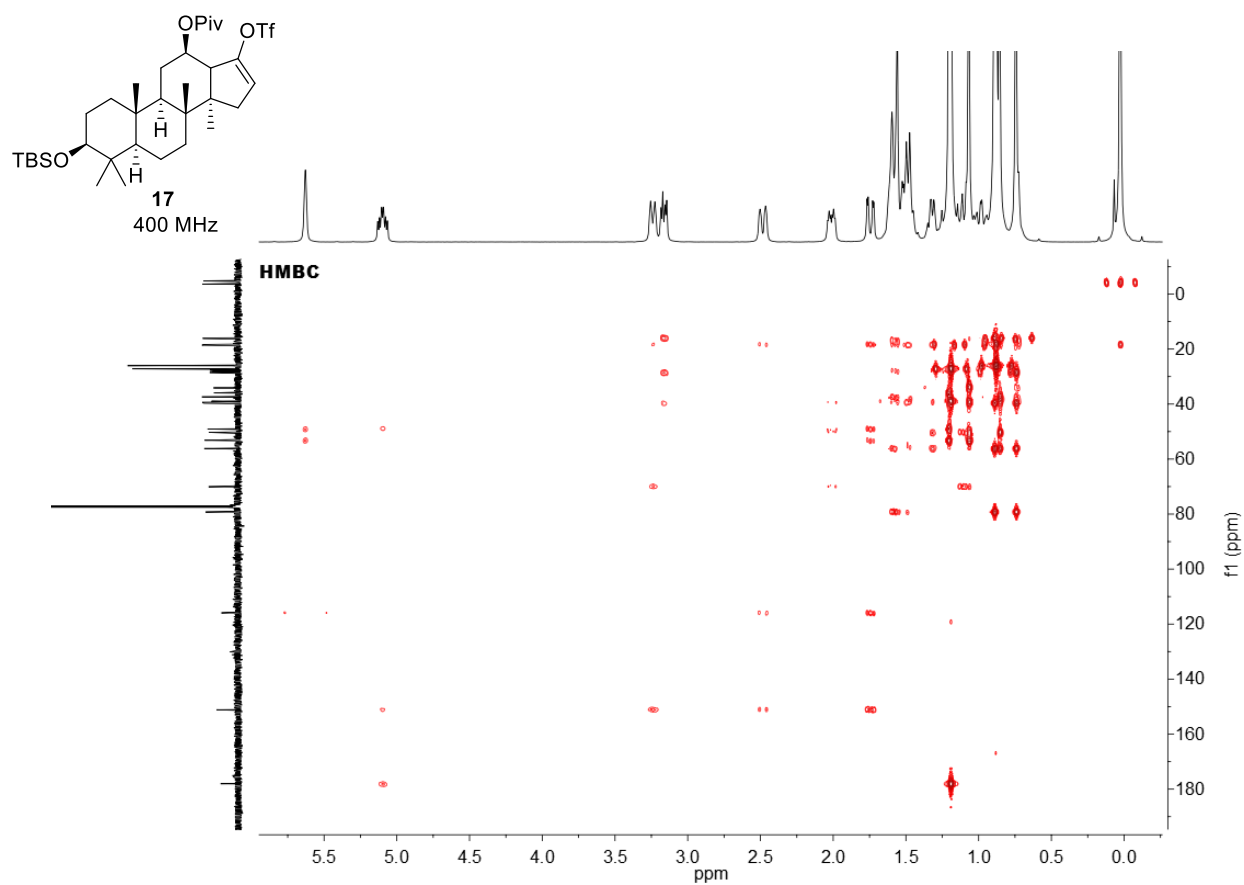
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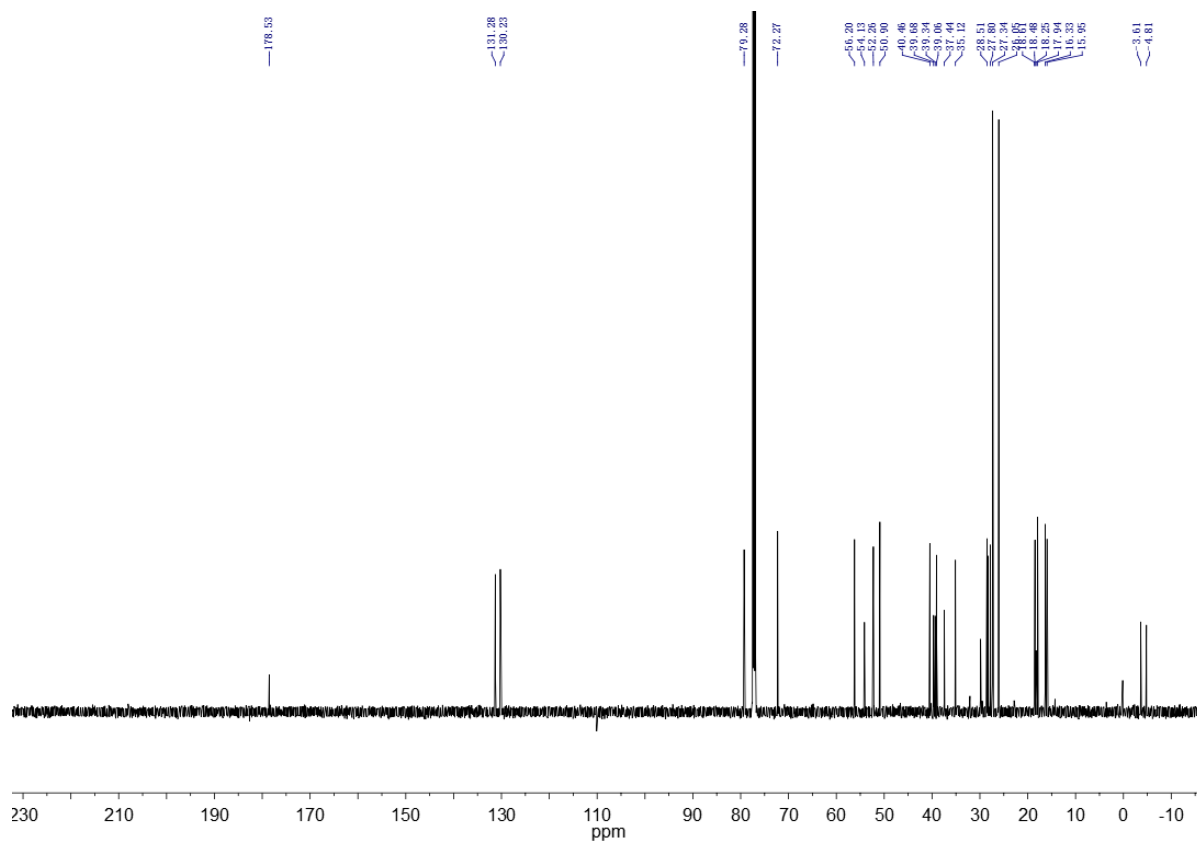
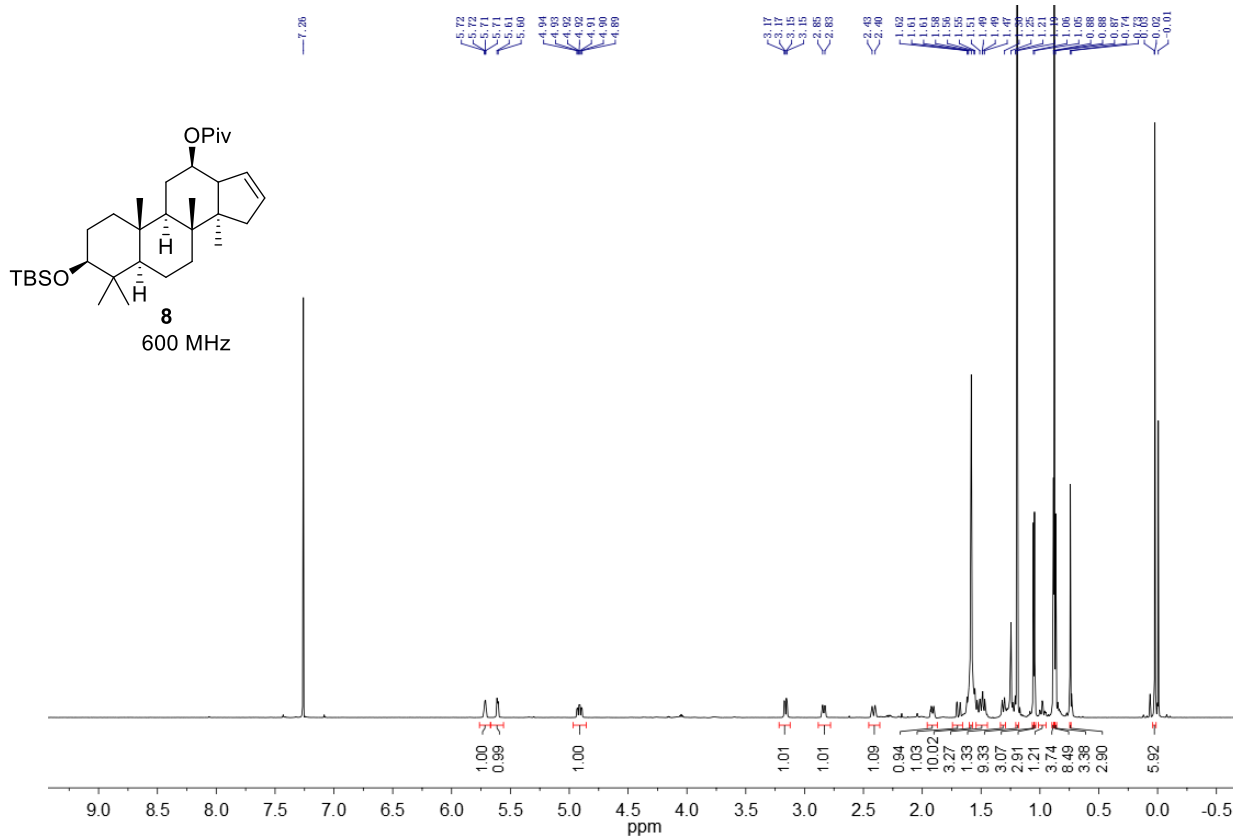
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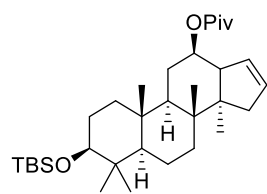
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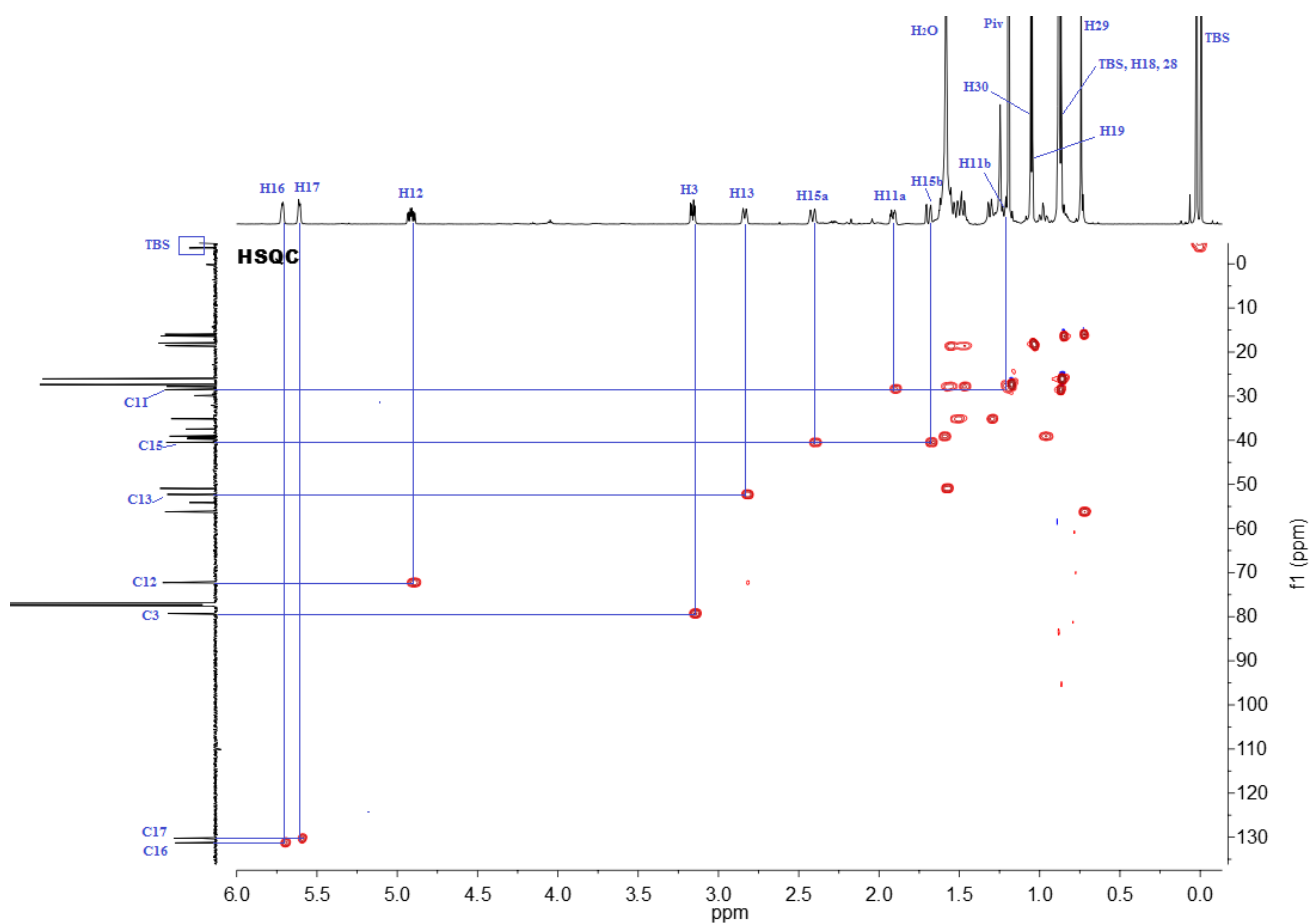
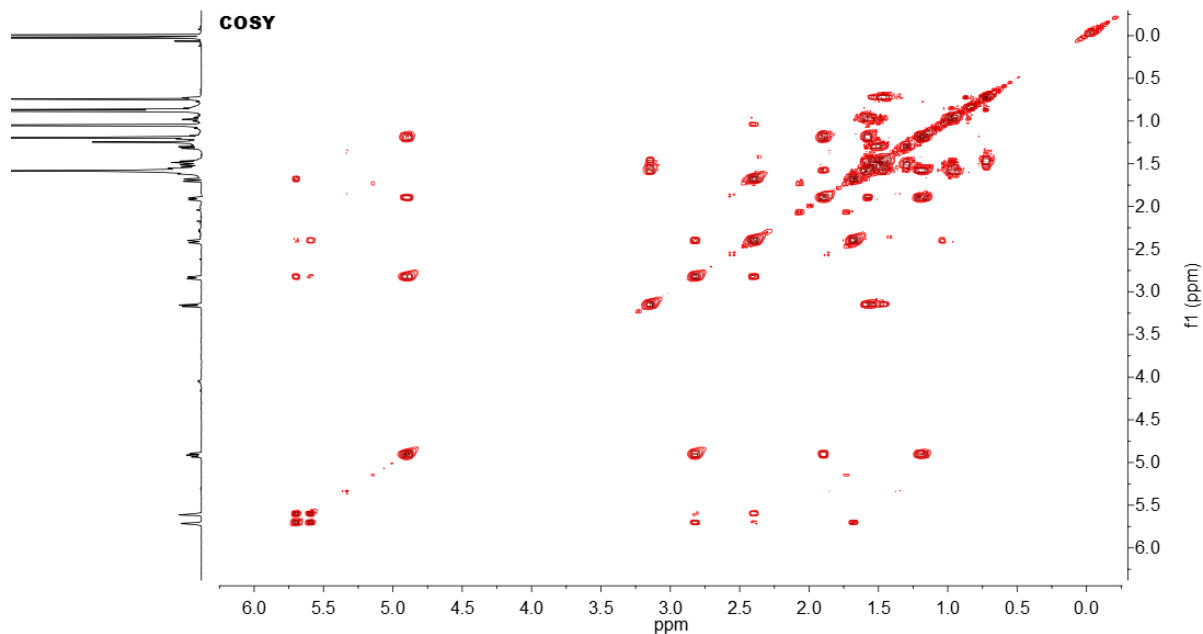
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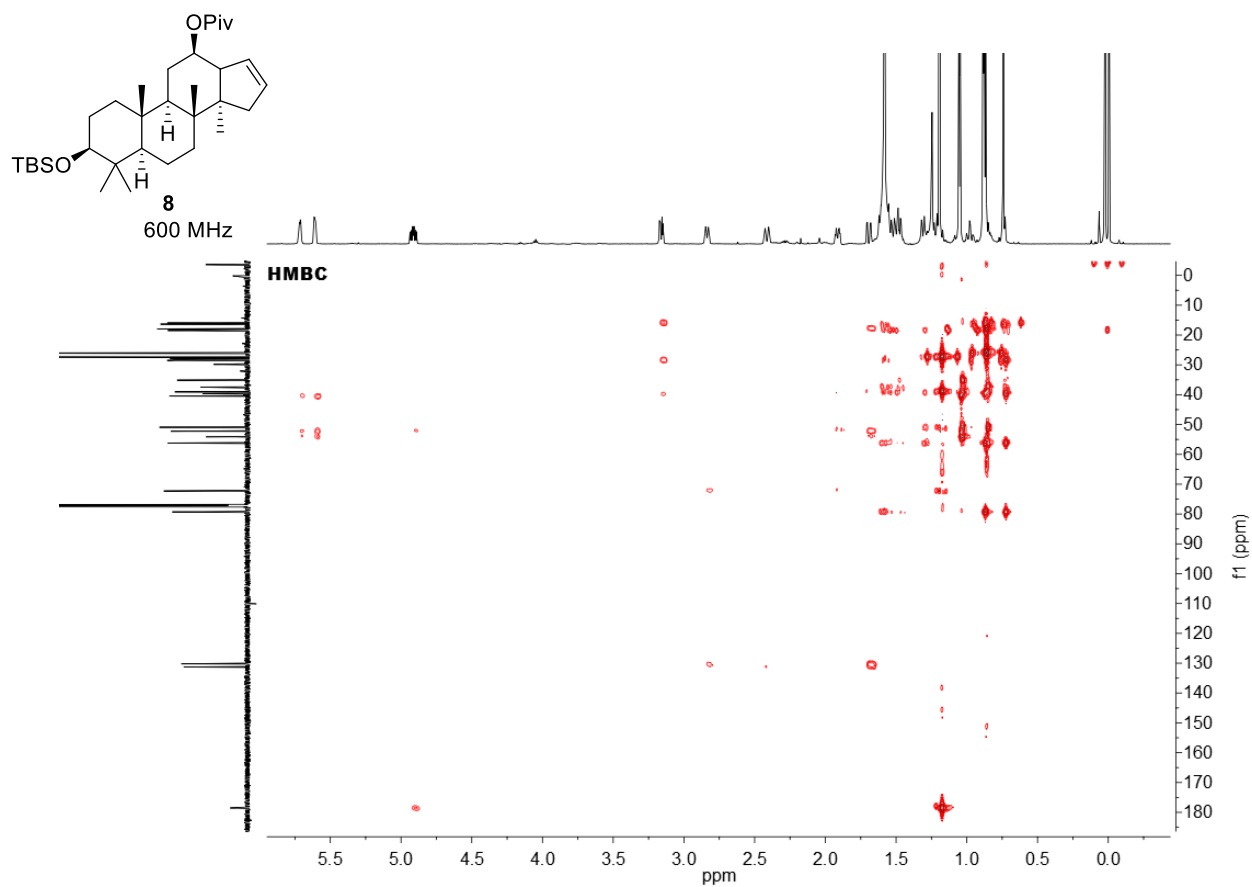
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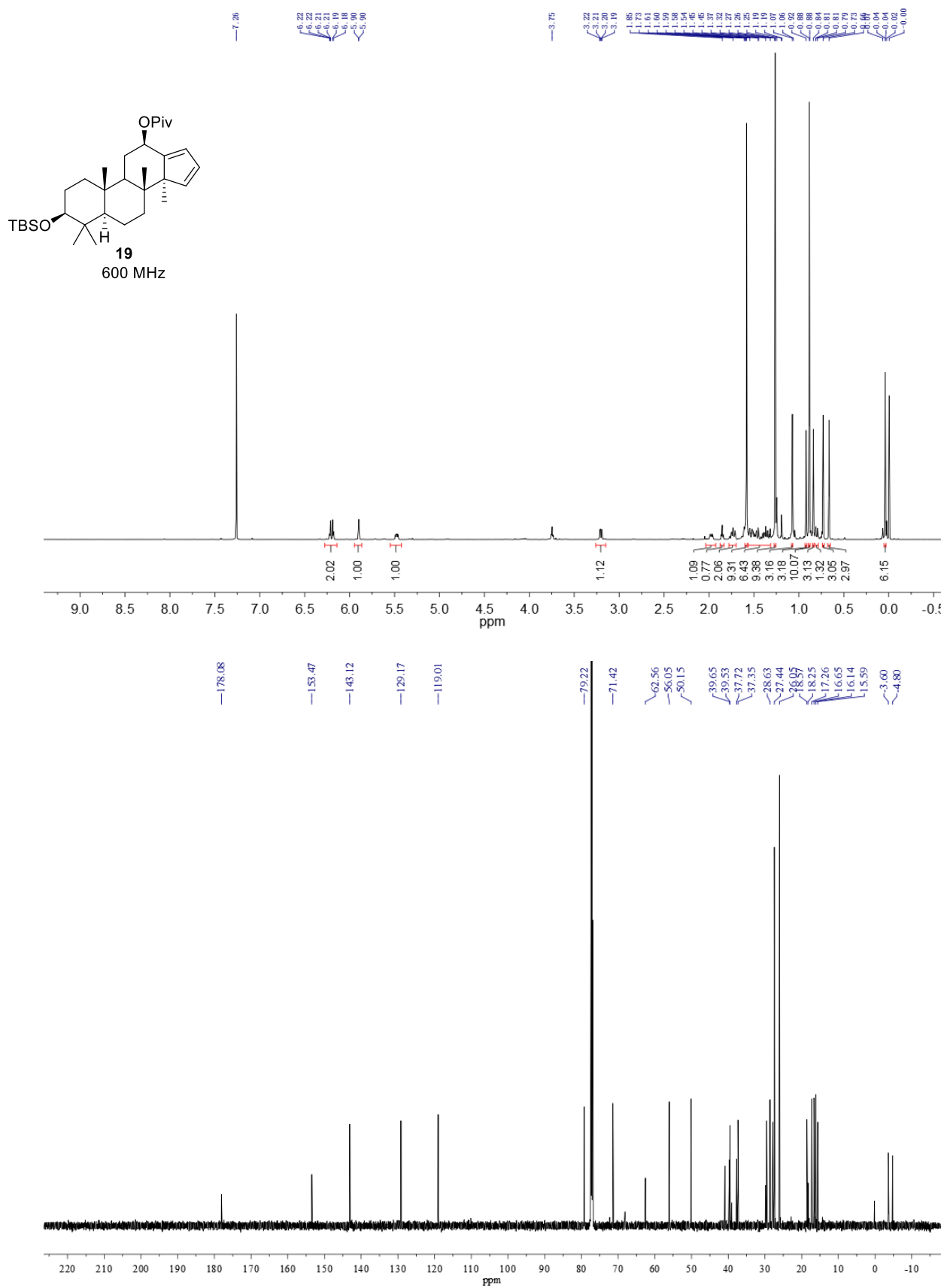
8
600 MHz



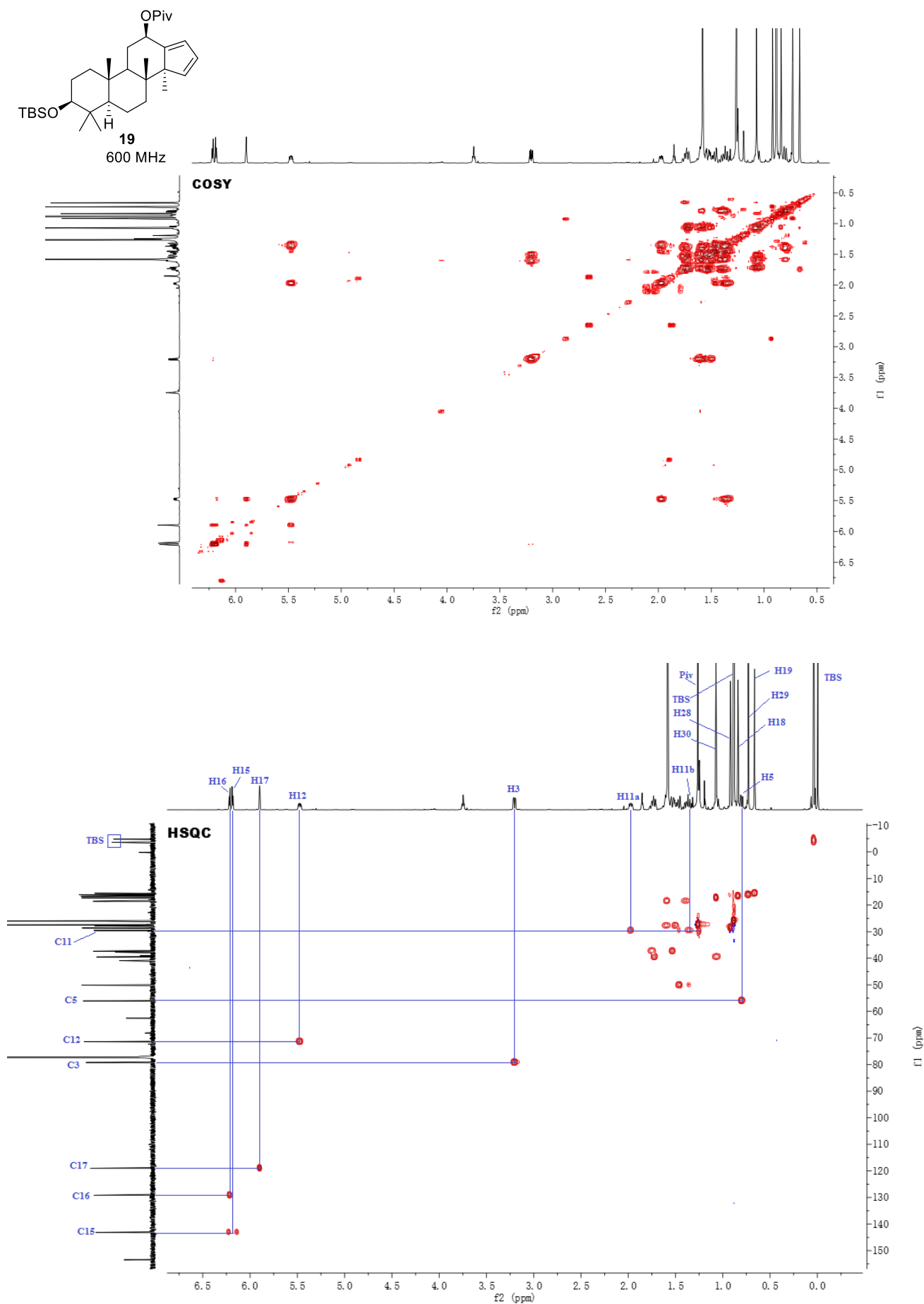
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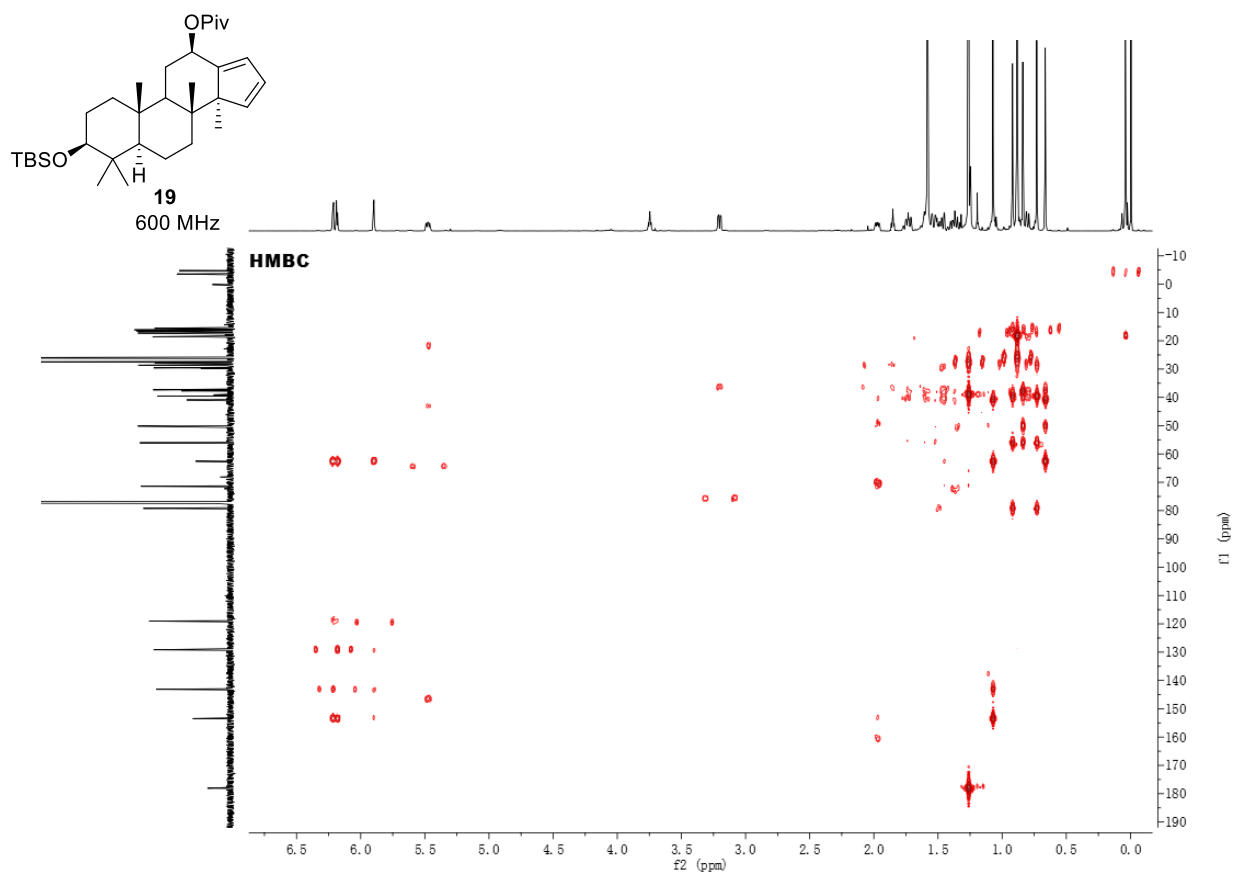
S54



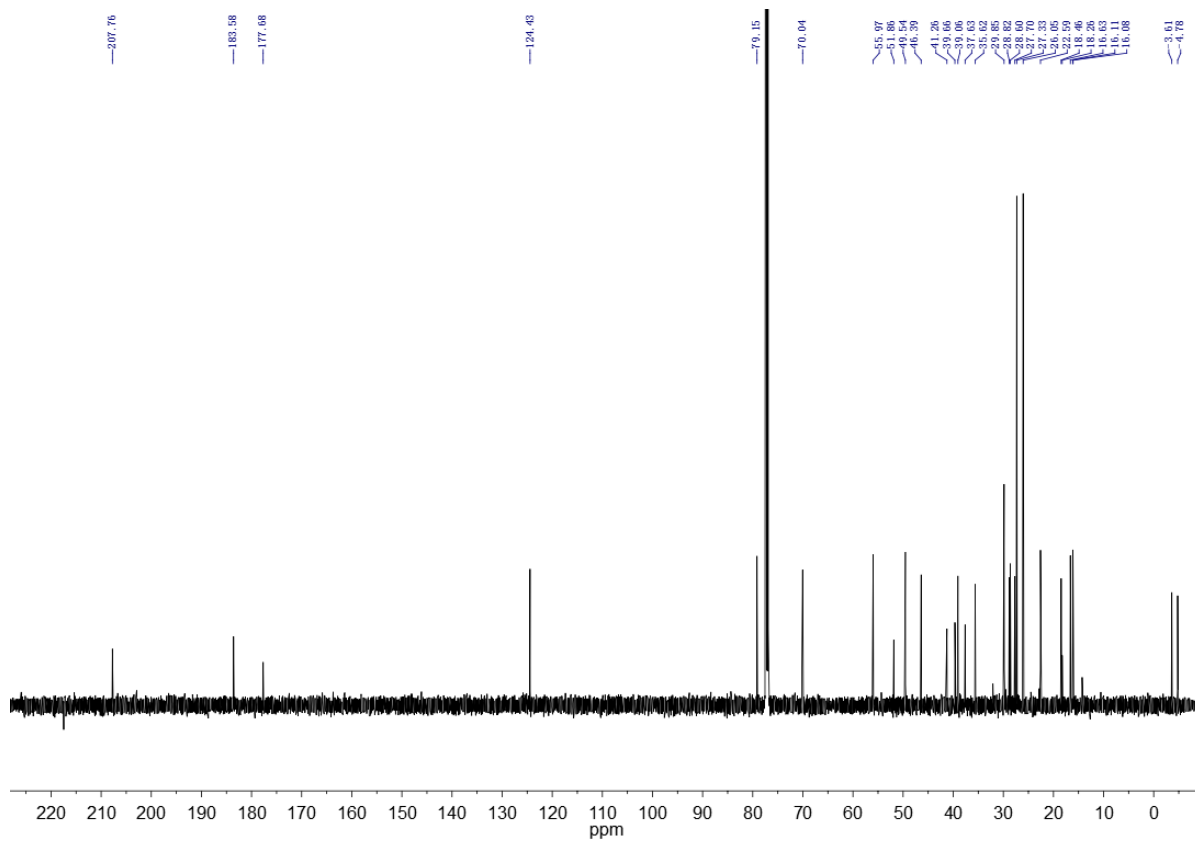
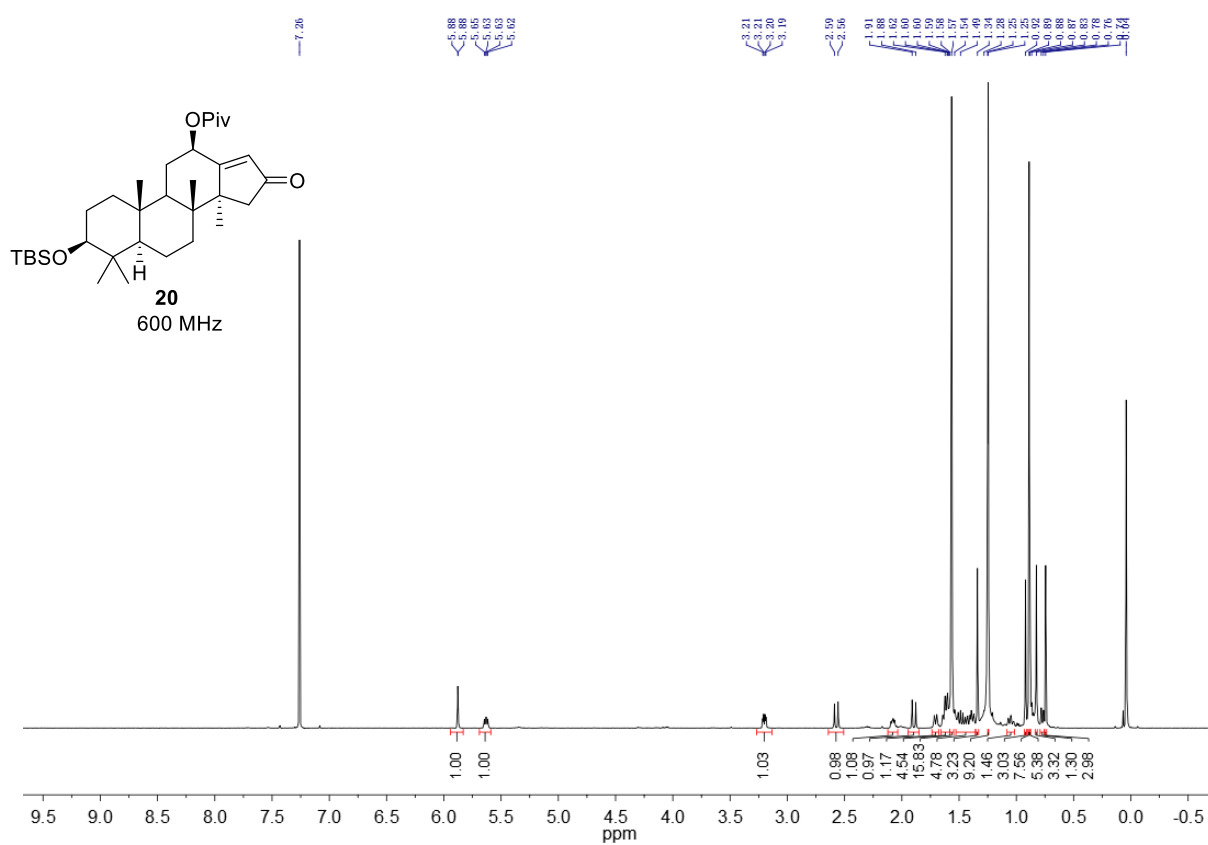
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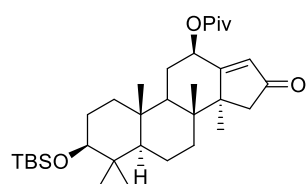
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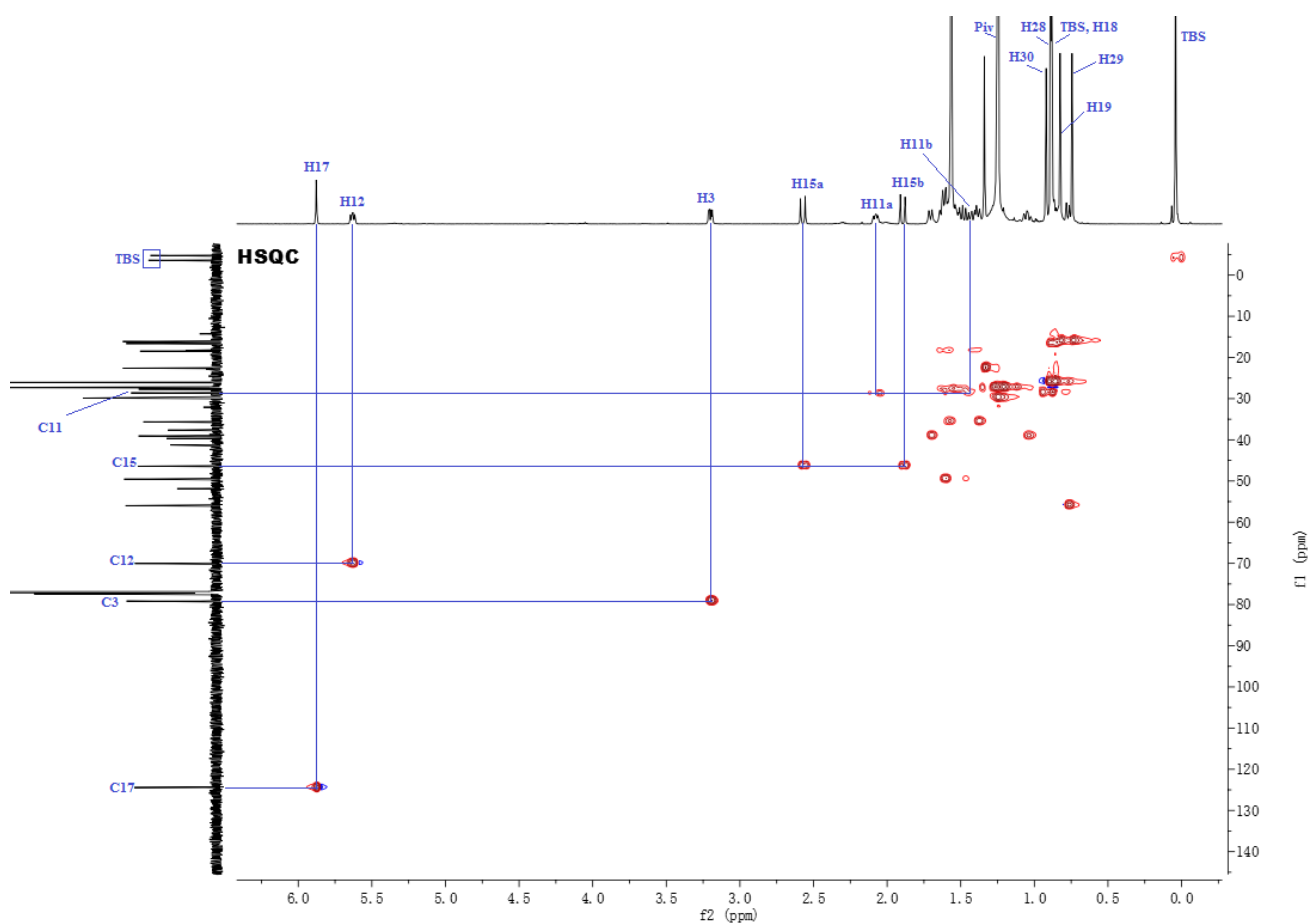
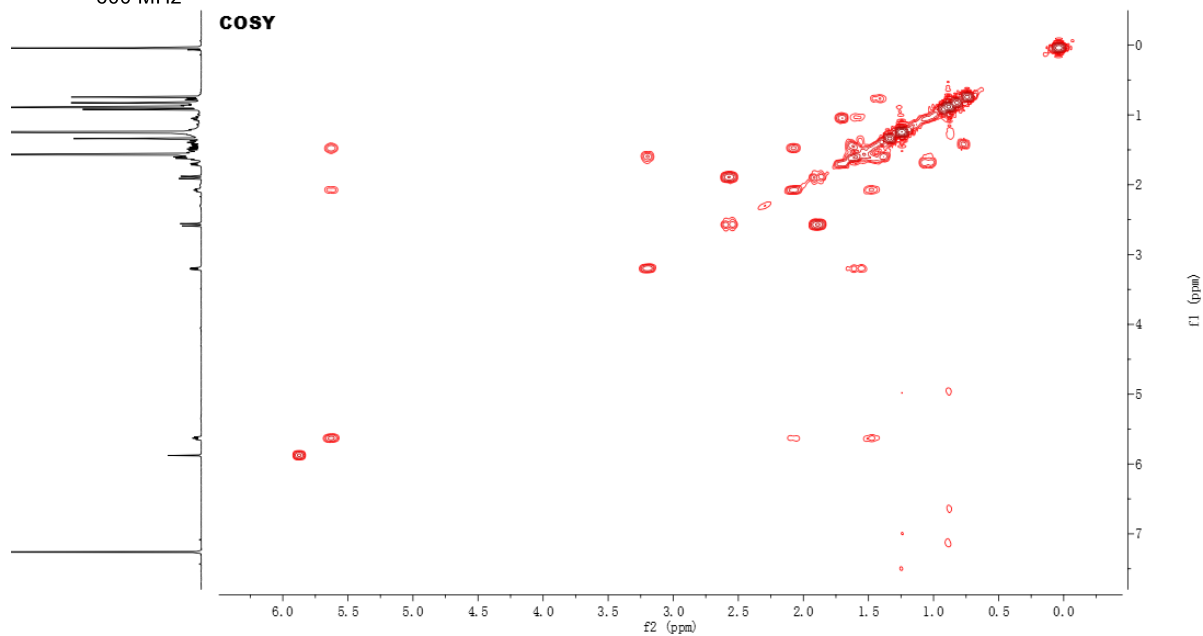
S57



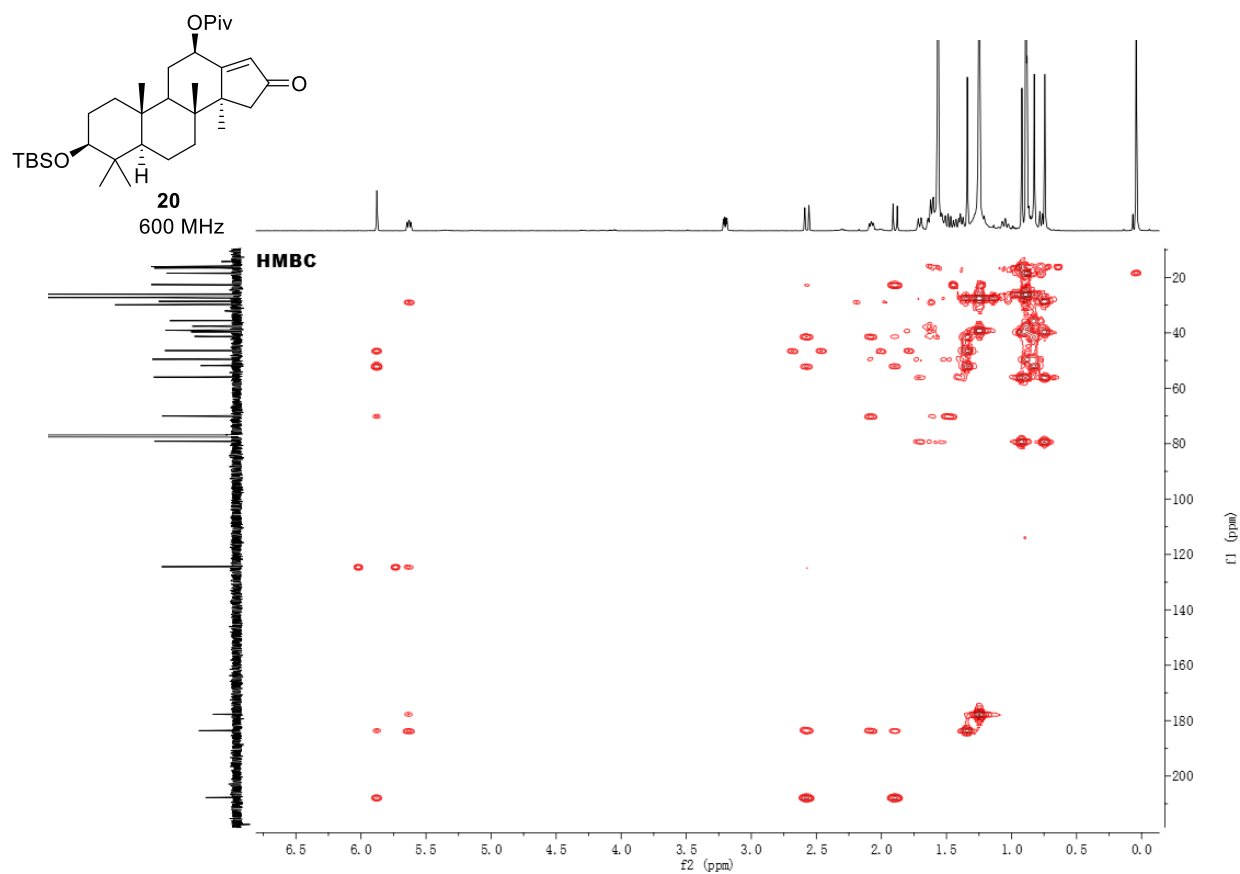
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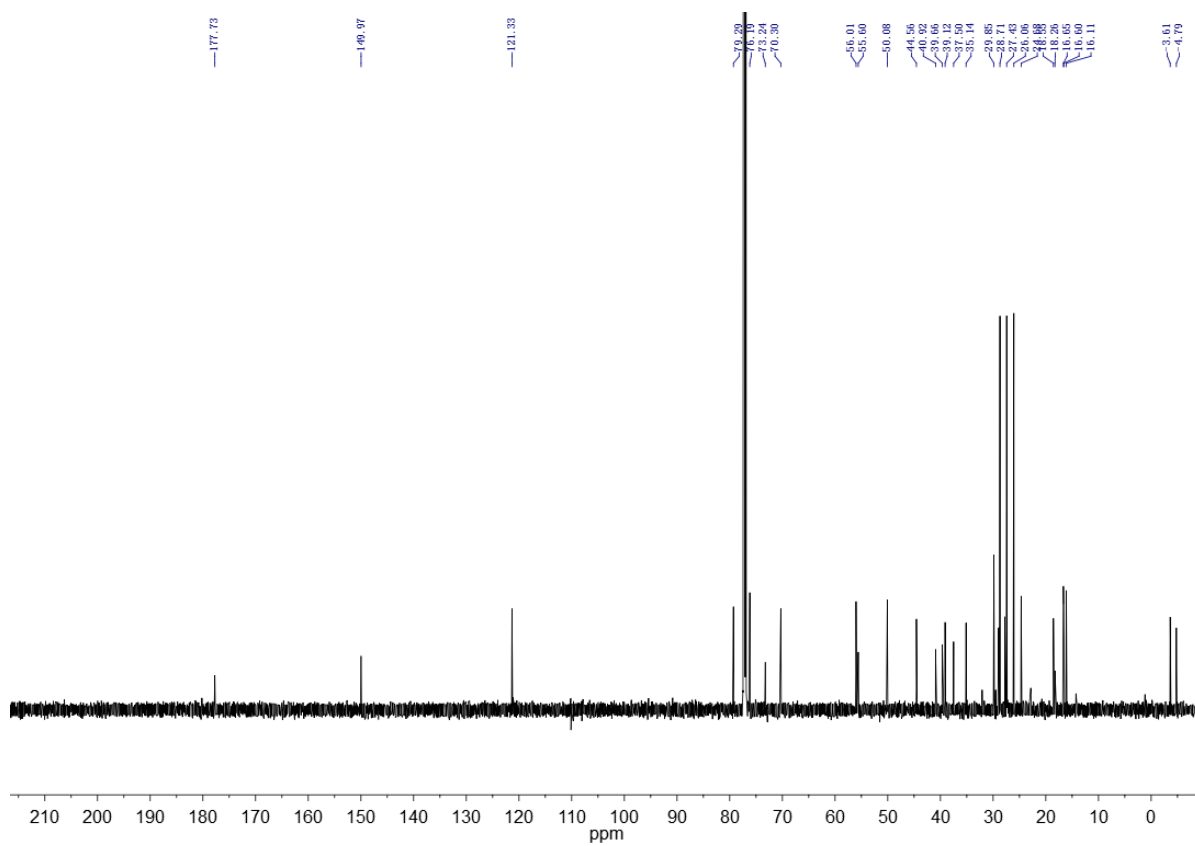
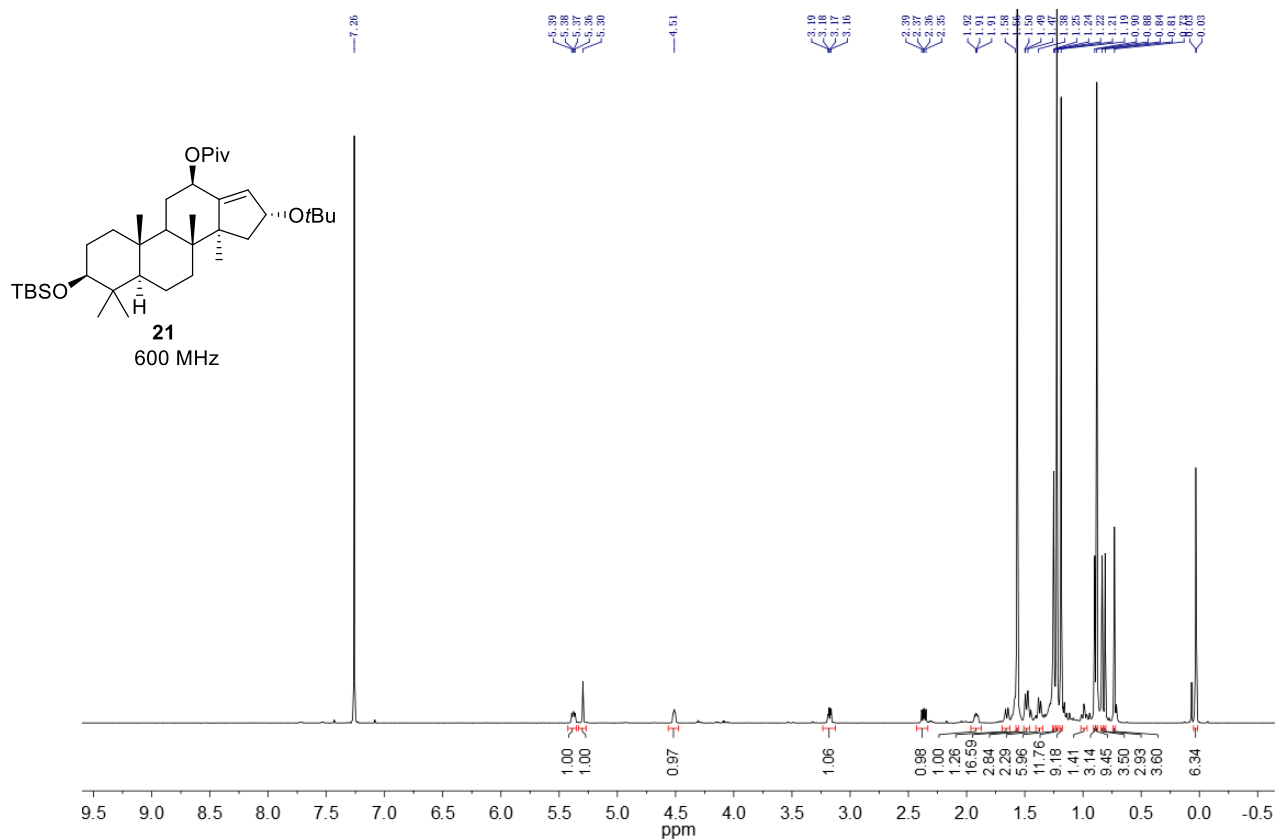
20
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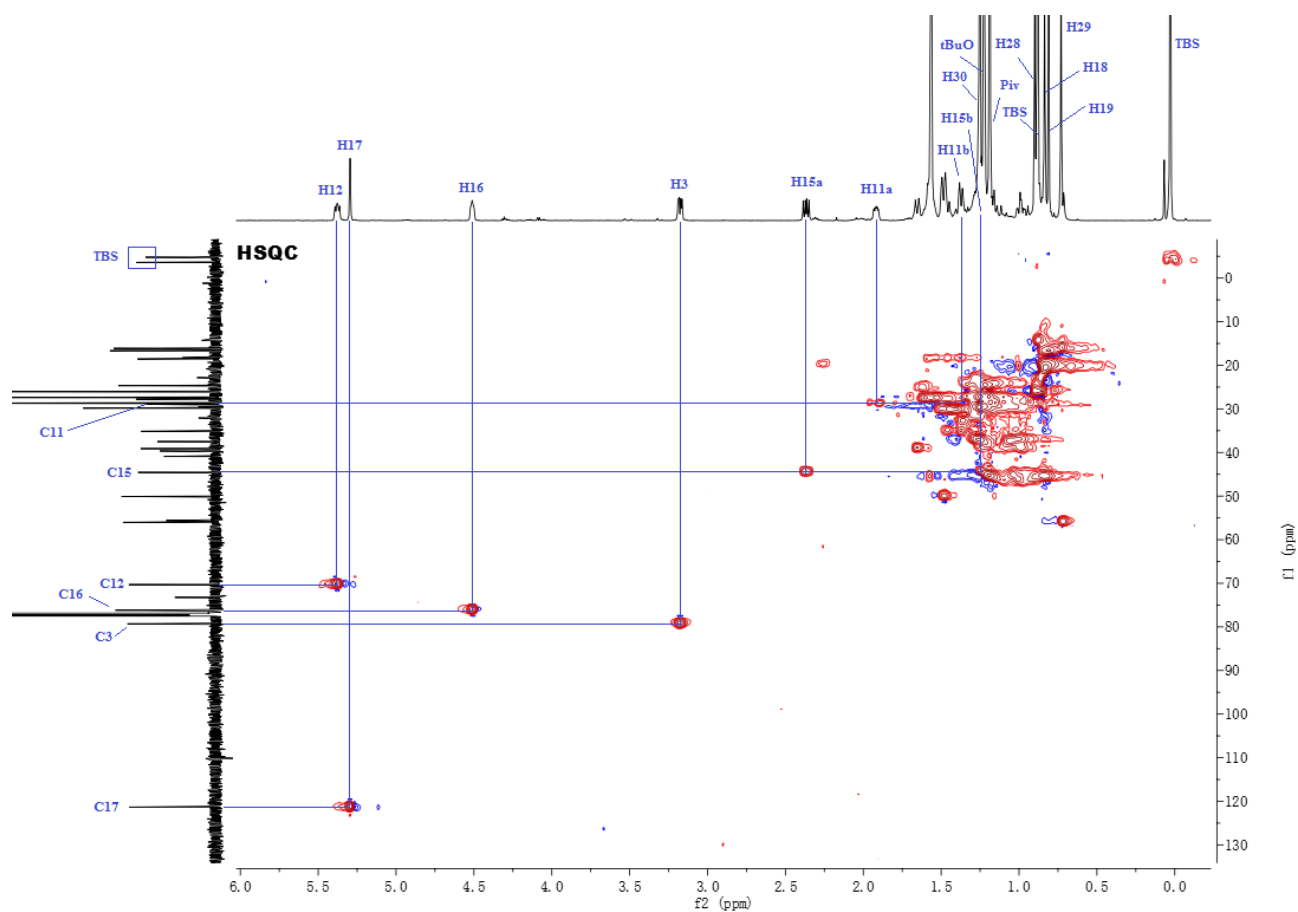
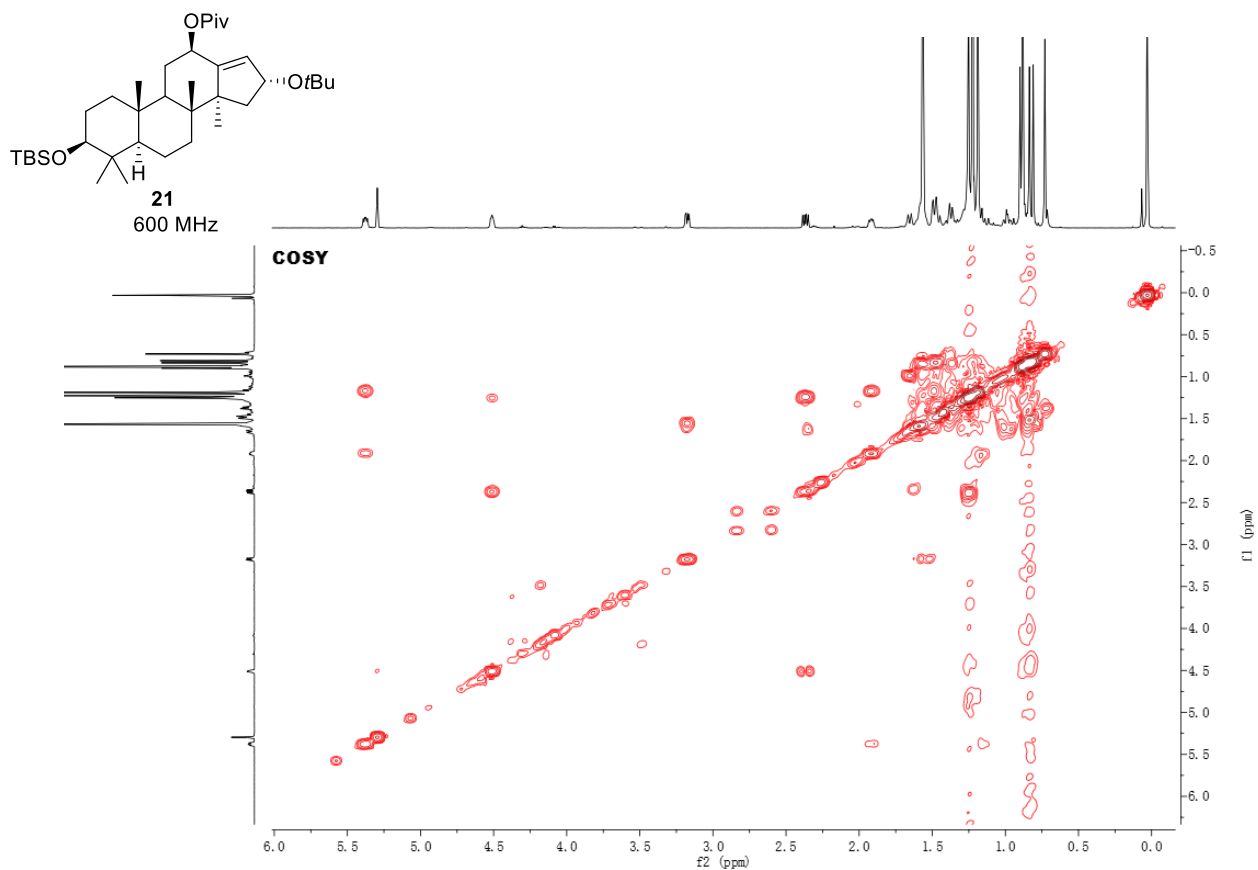
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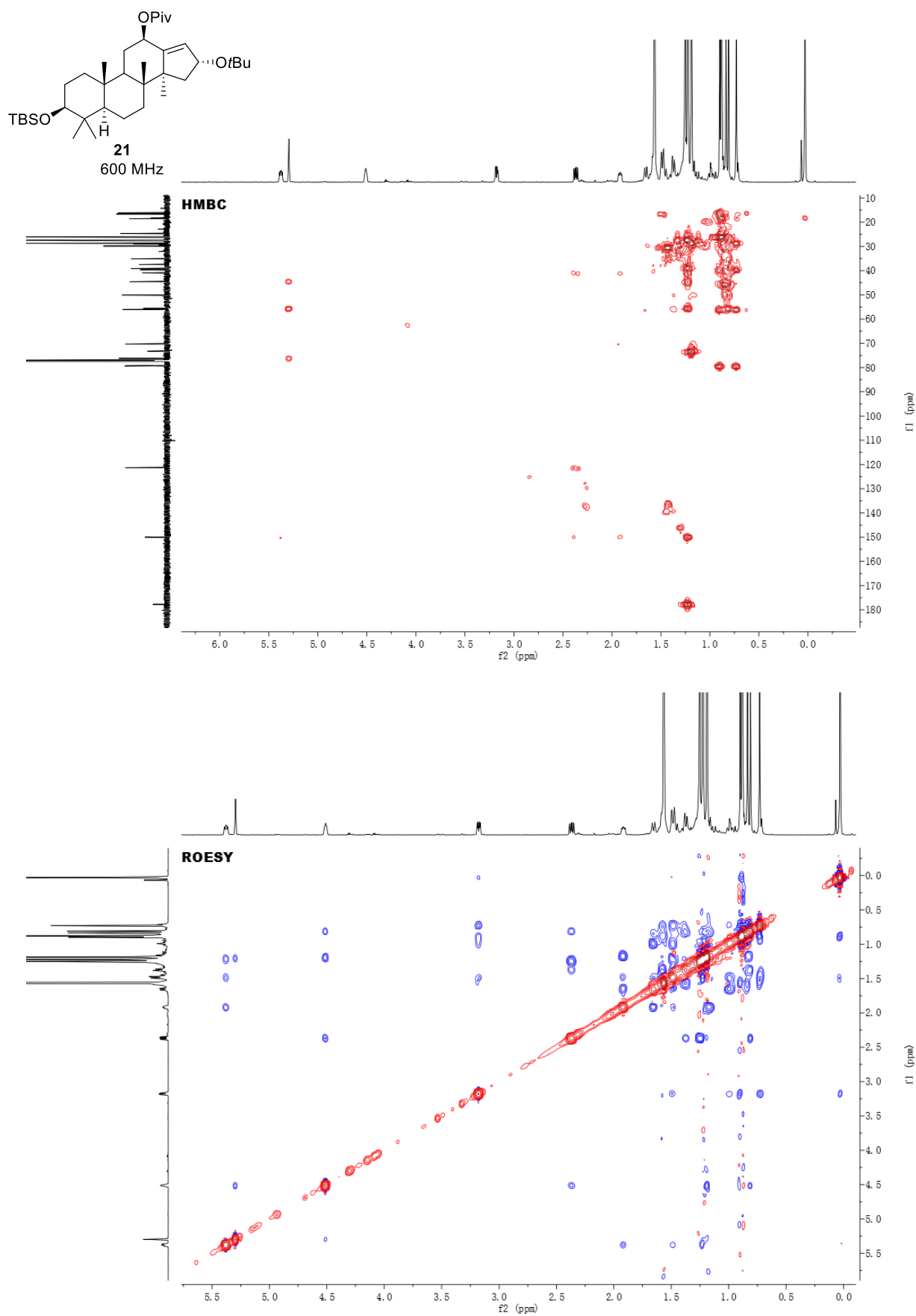
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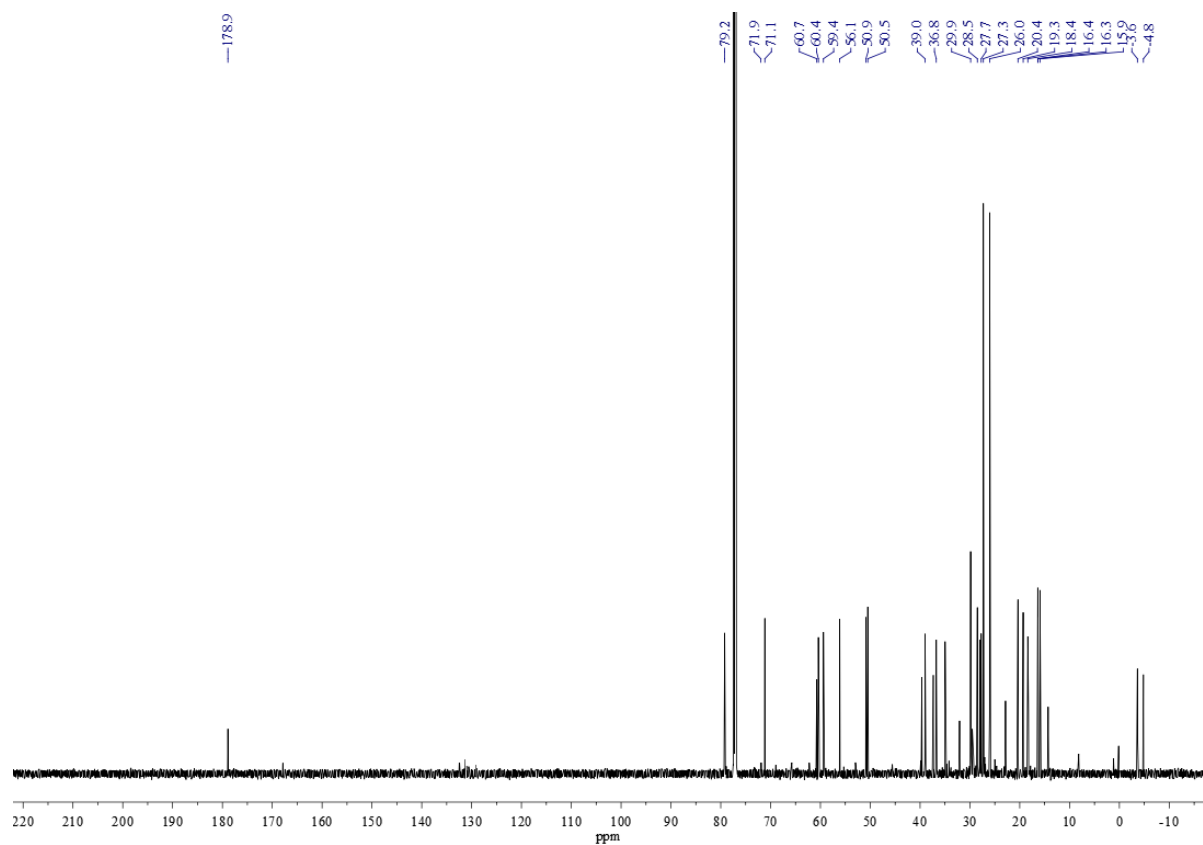
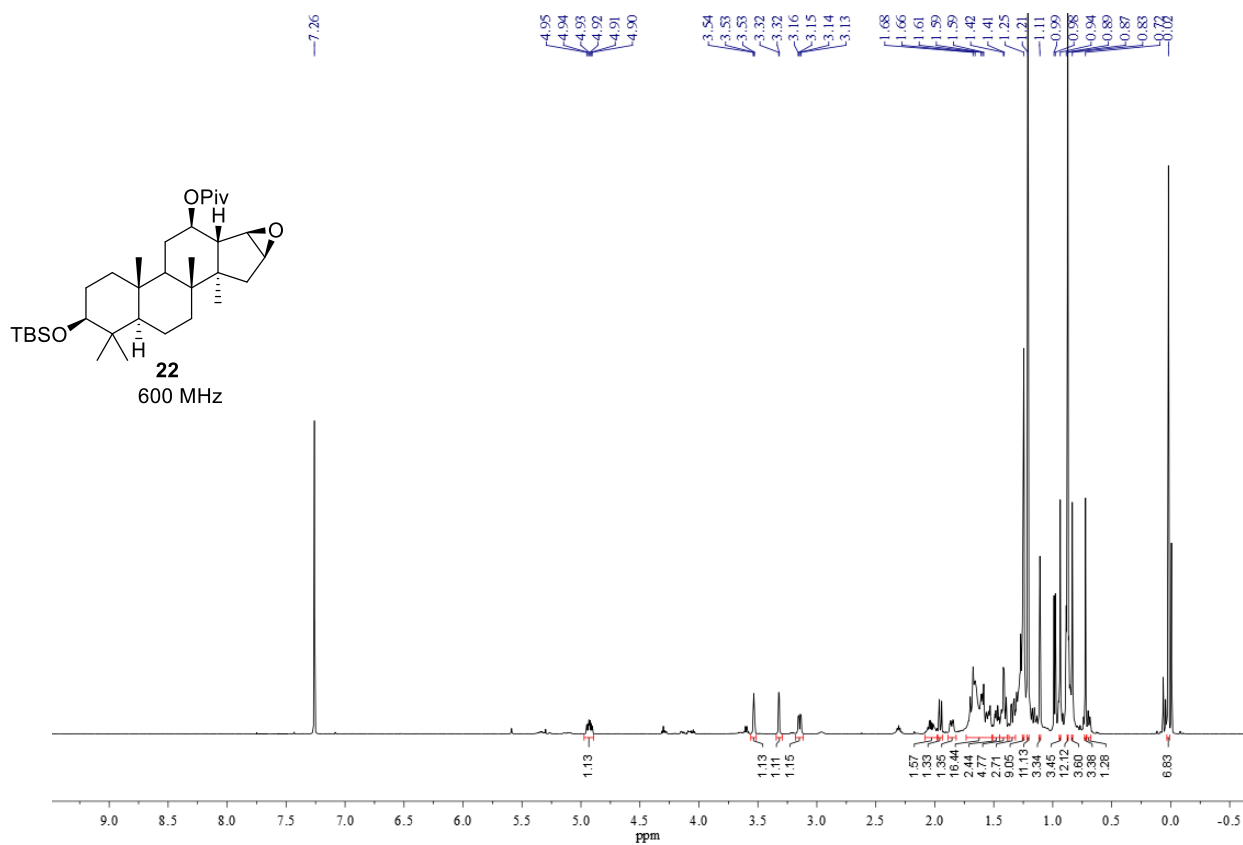
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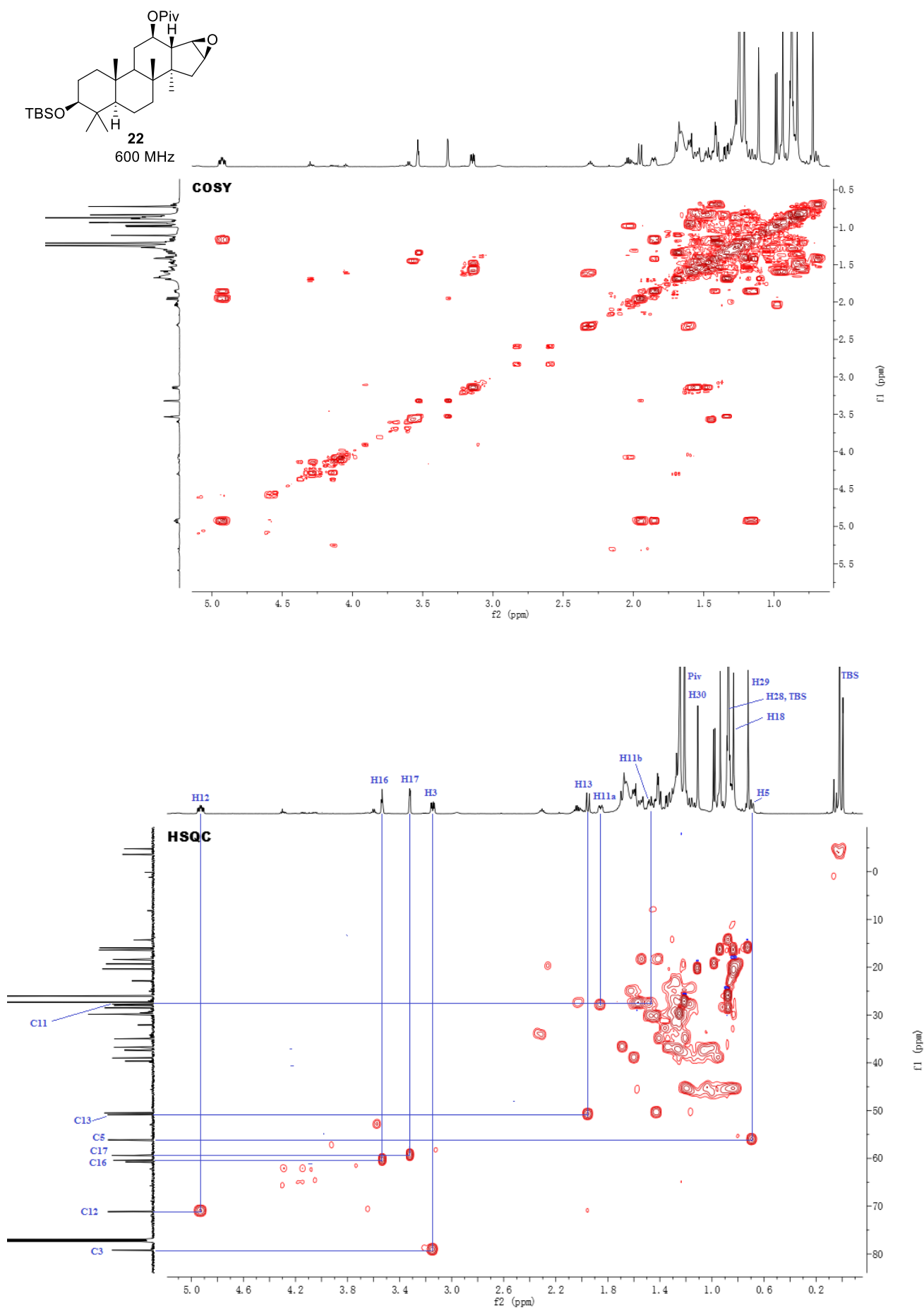
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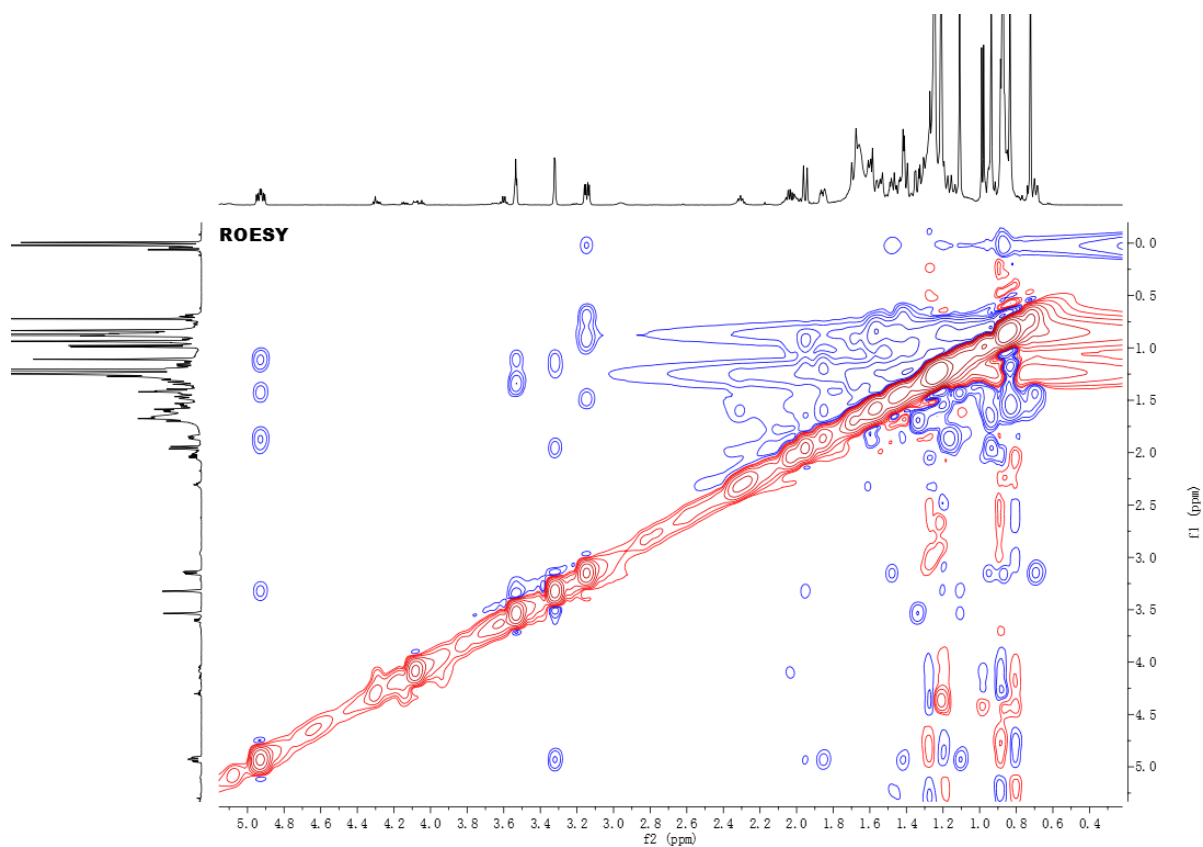
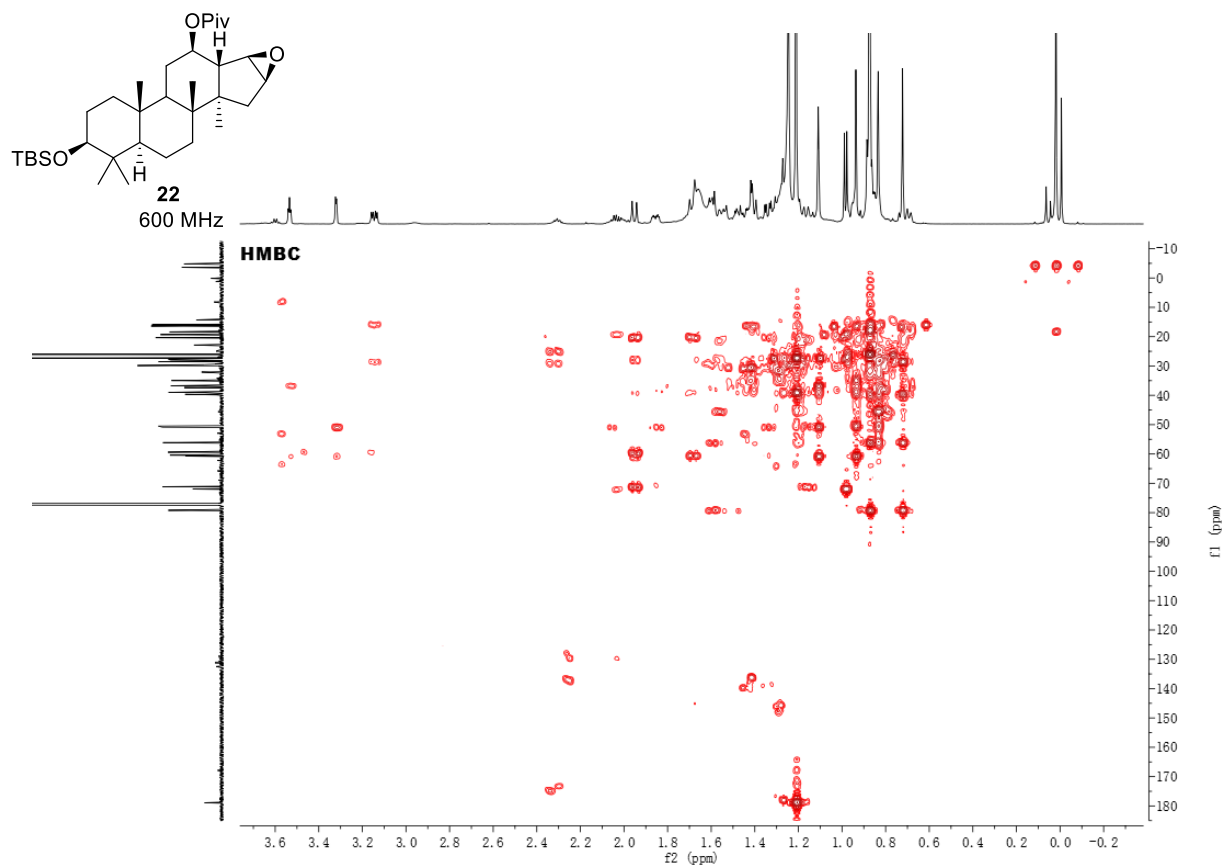
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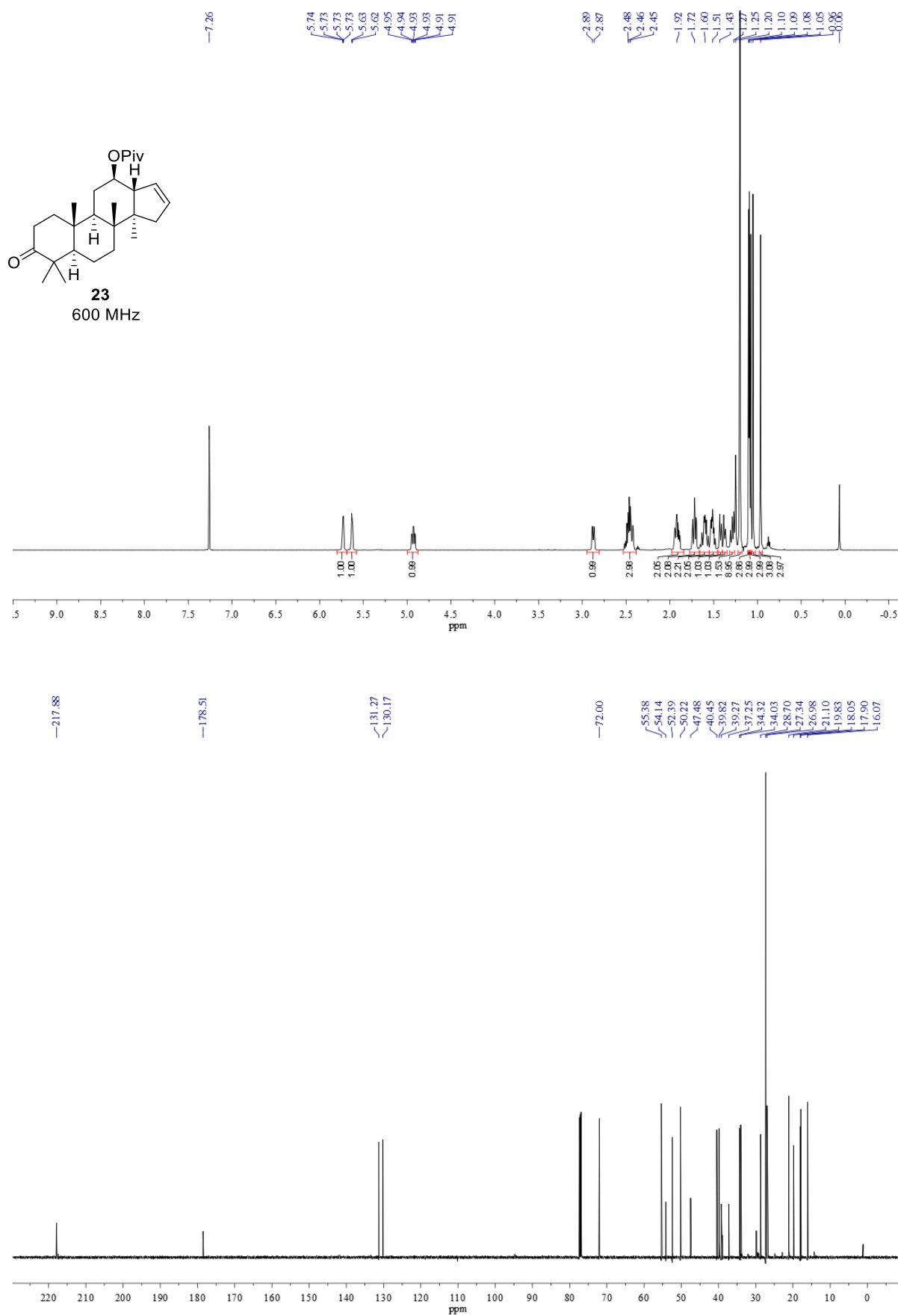
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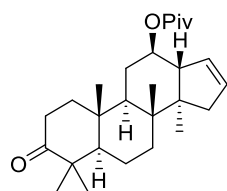
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S66

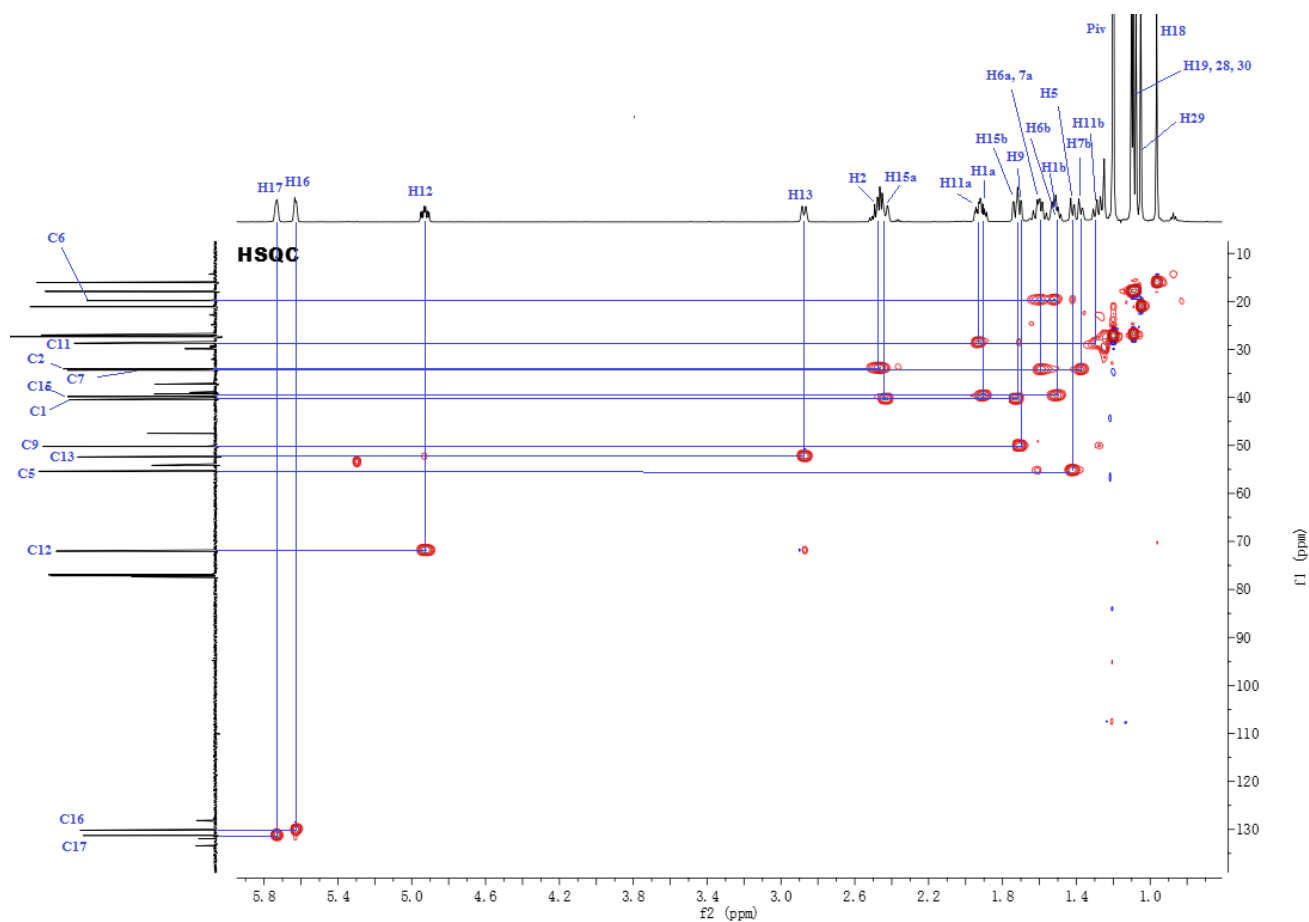
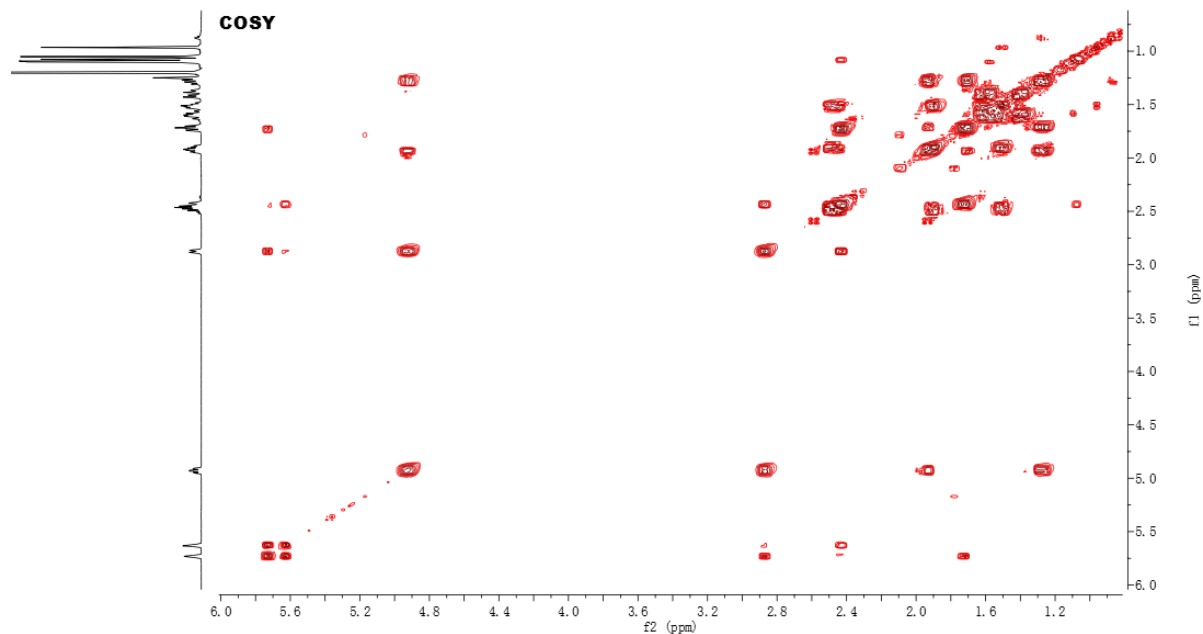


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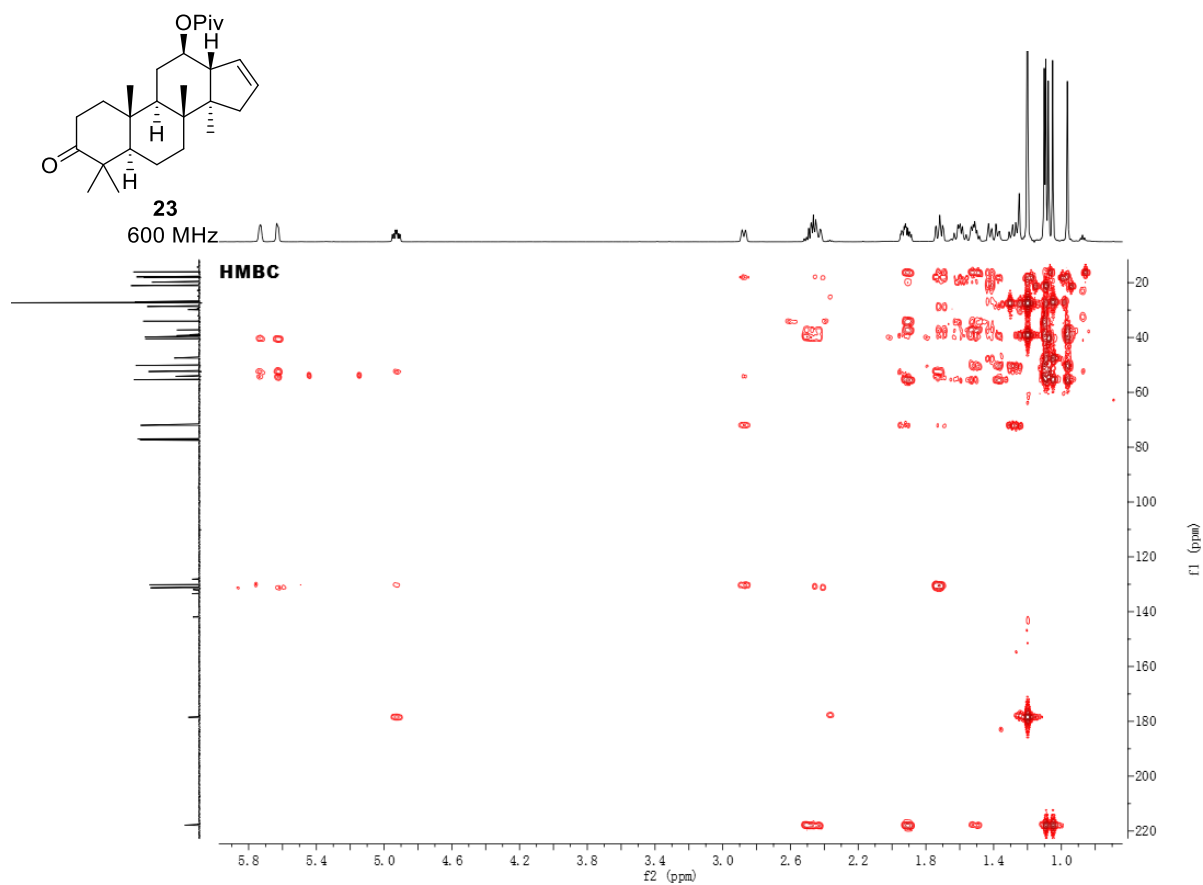


23

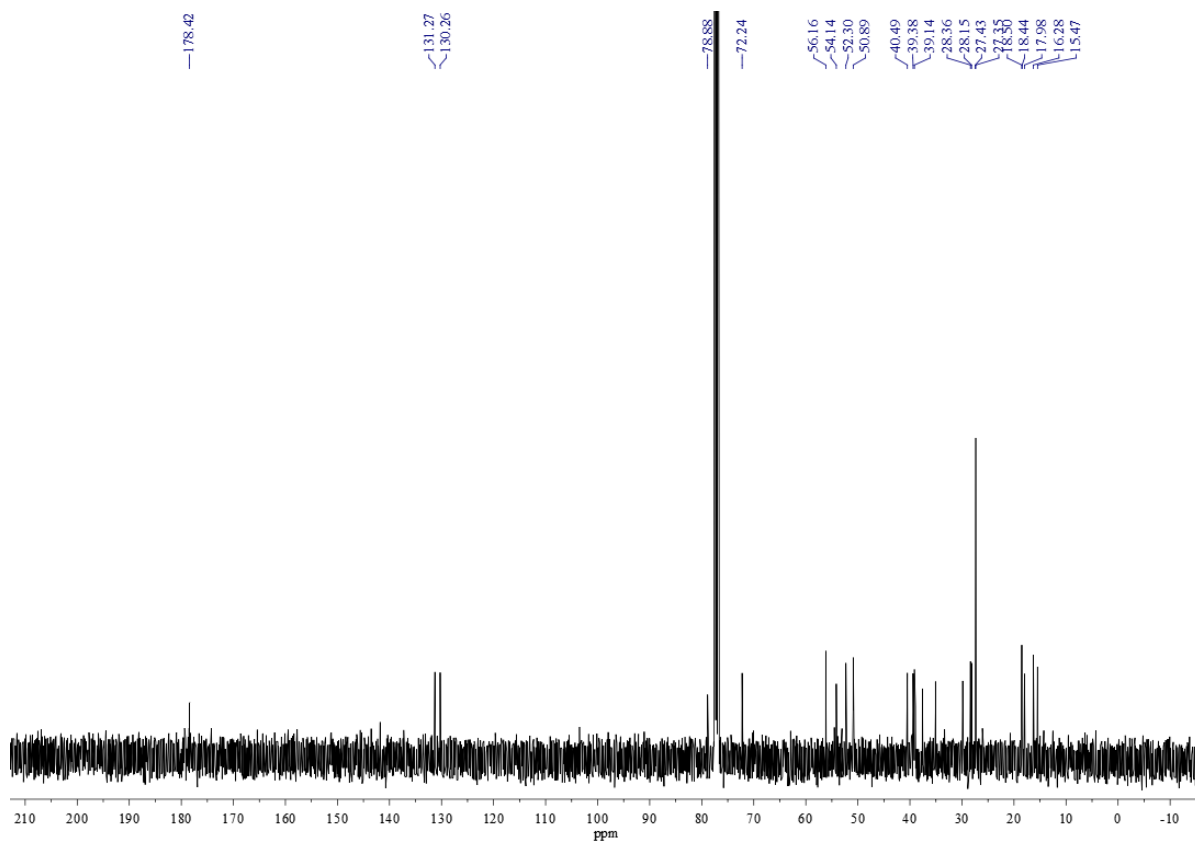
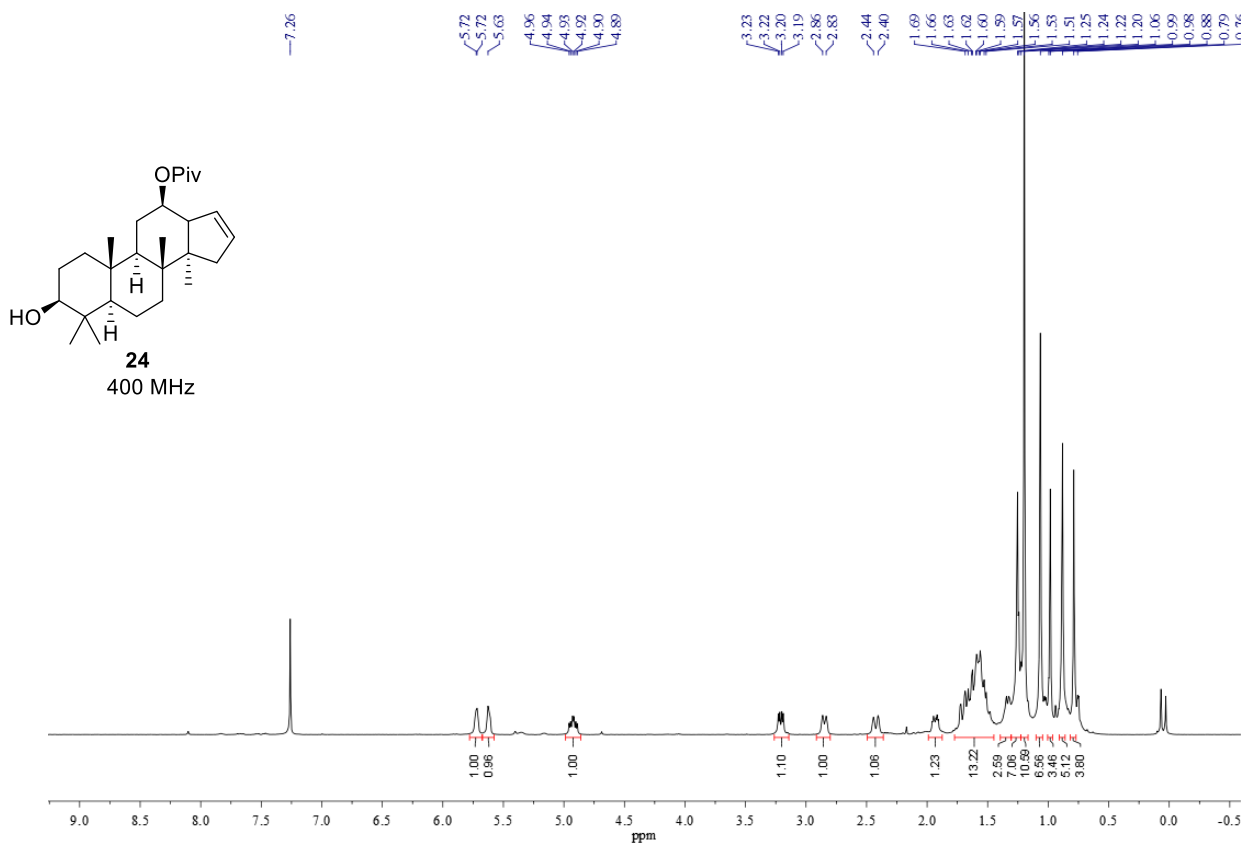
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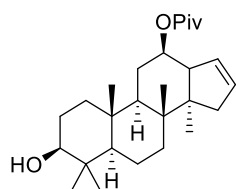
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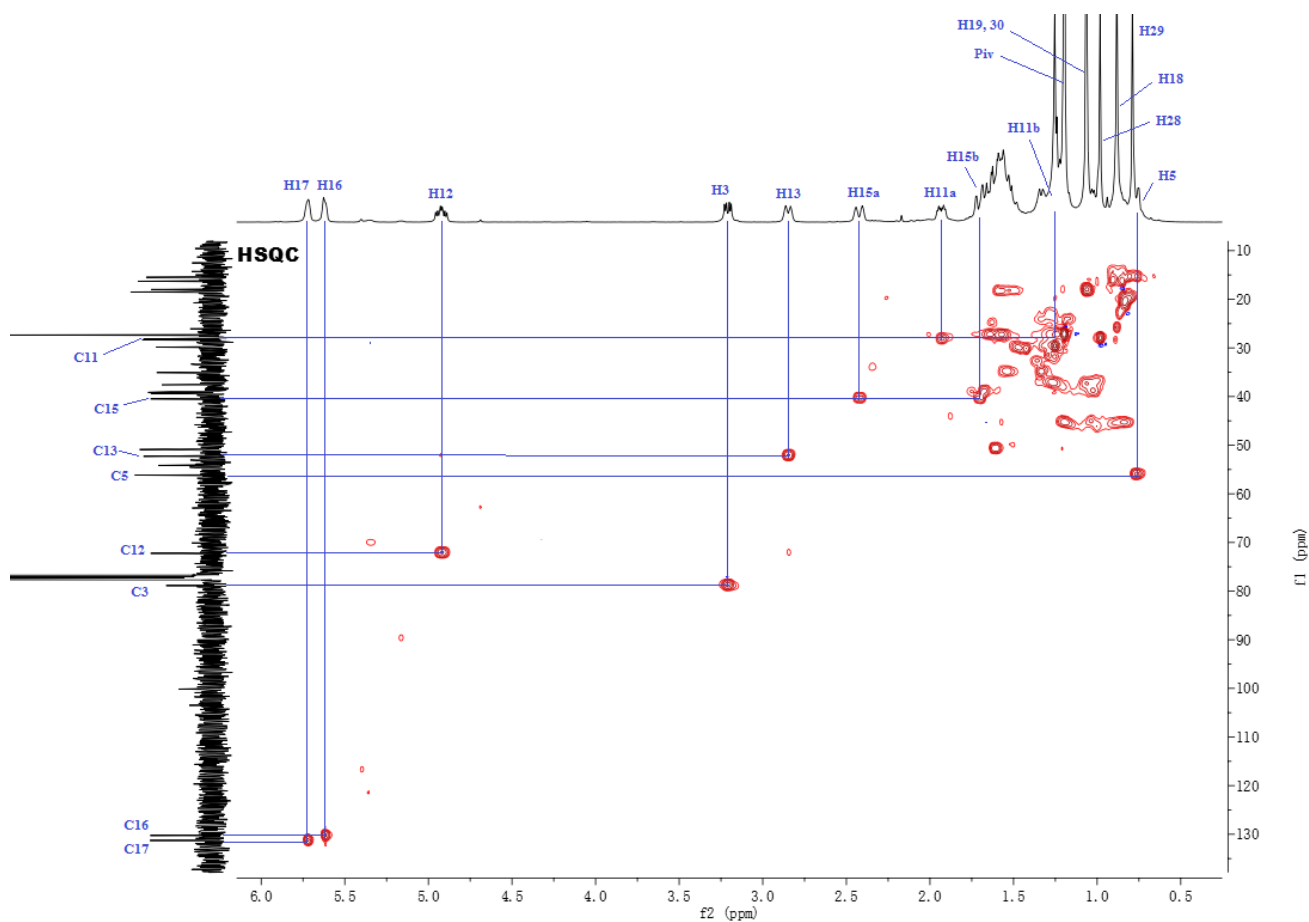
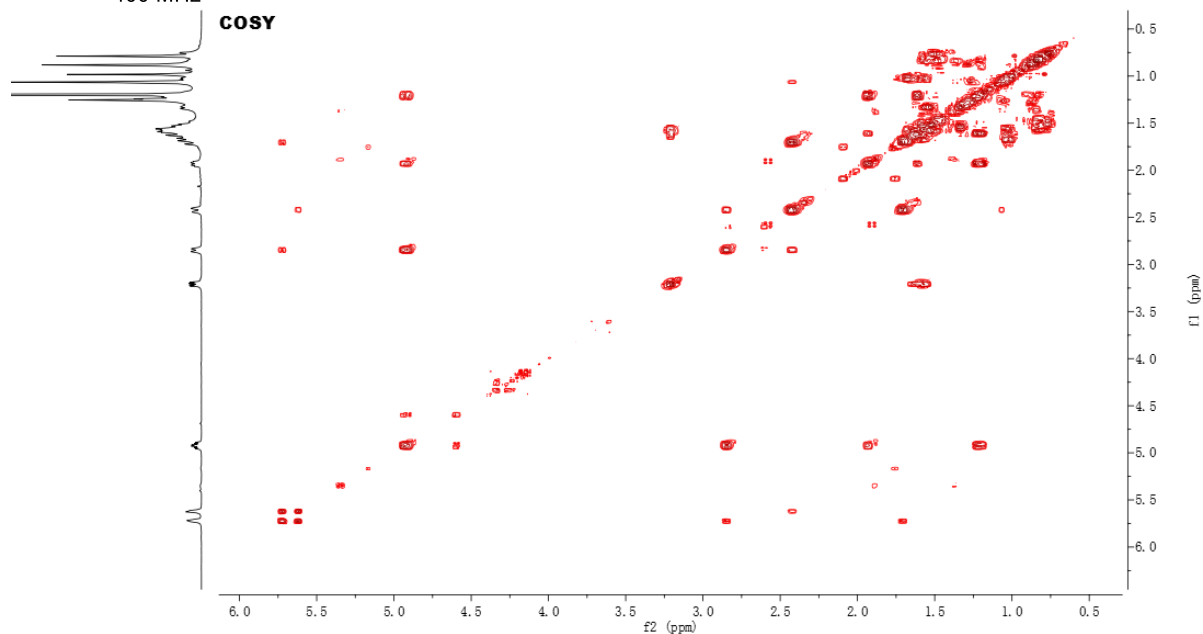
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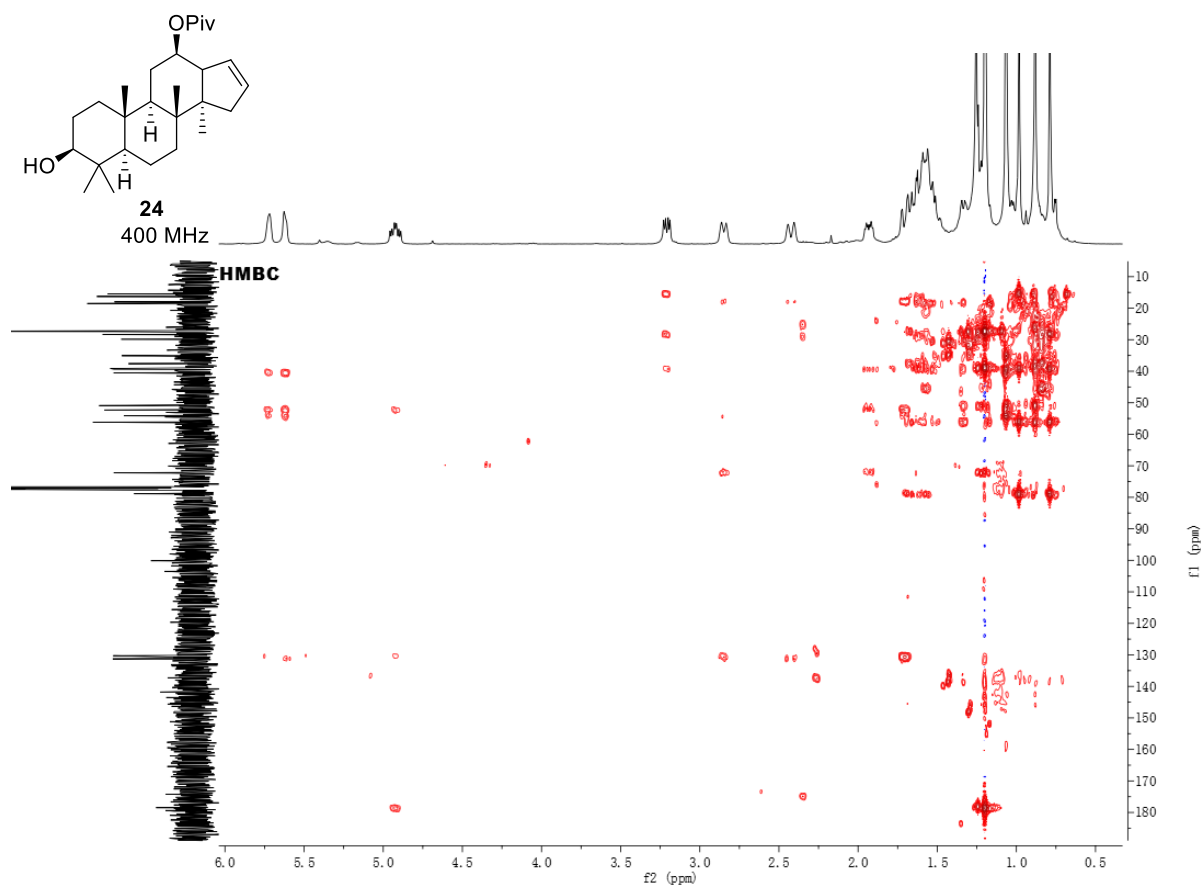
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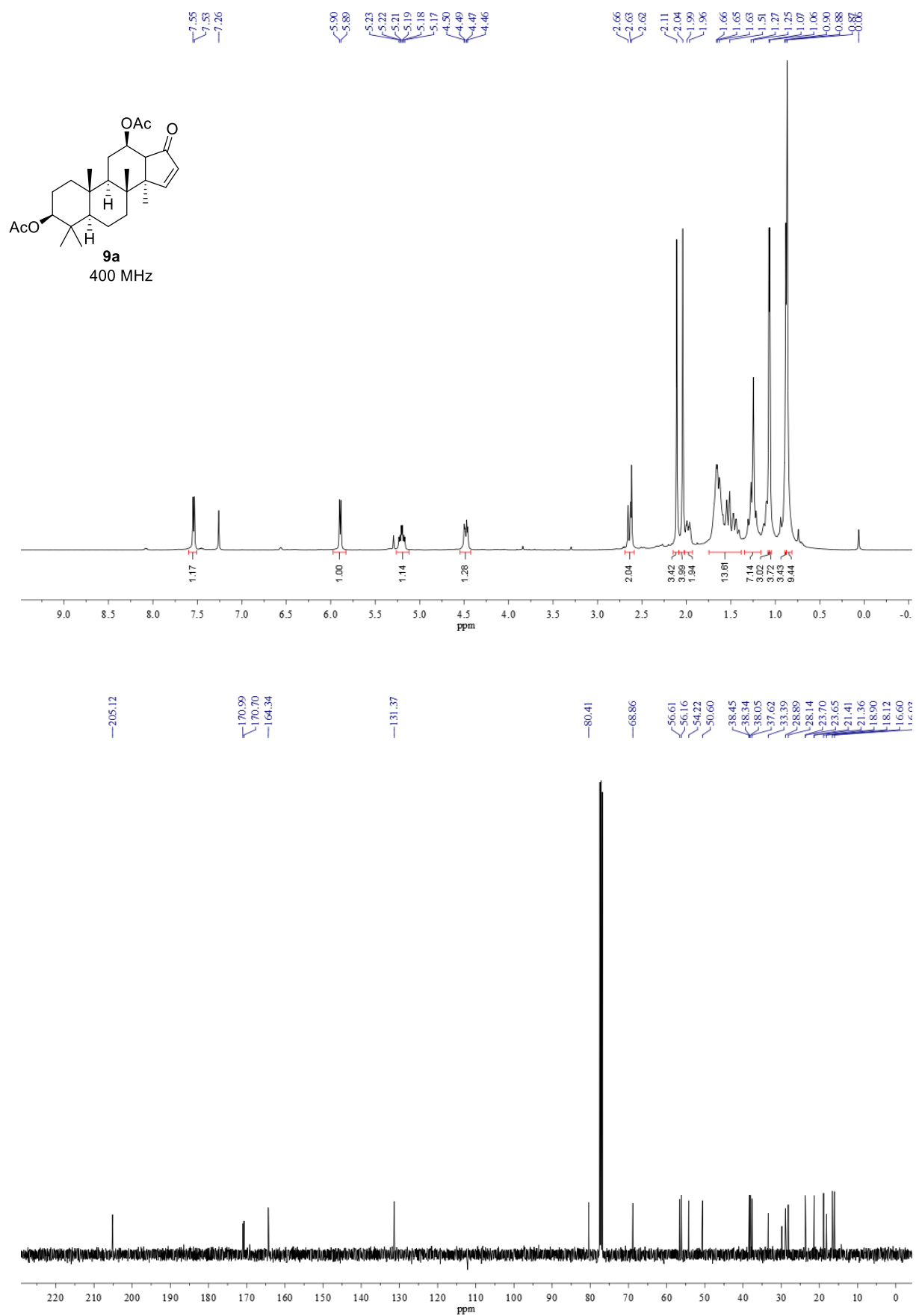
24
400 MHz



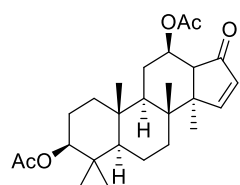
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Supporting Information

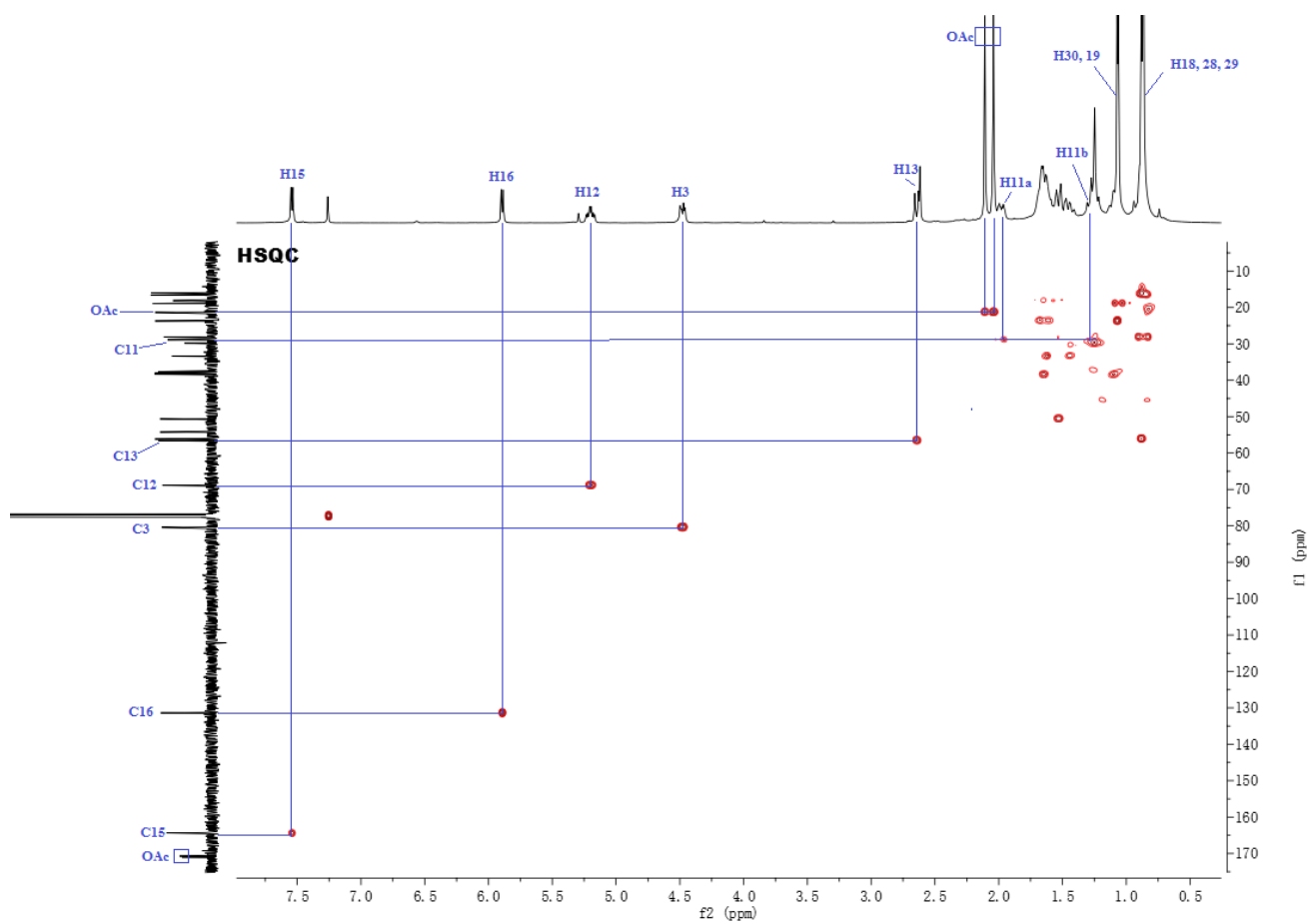
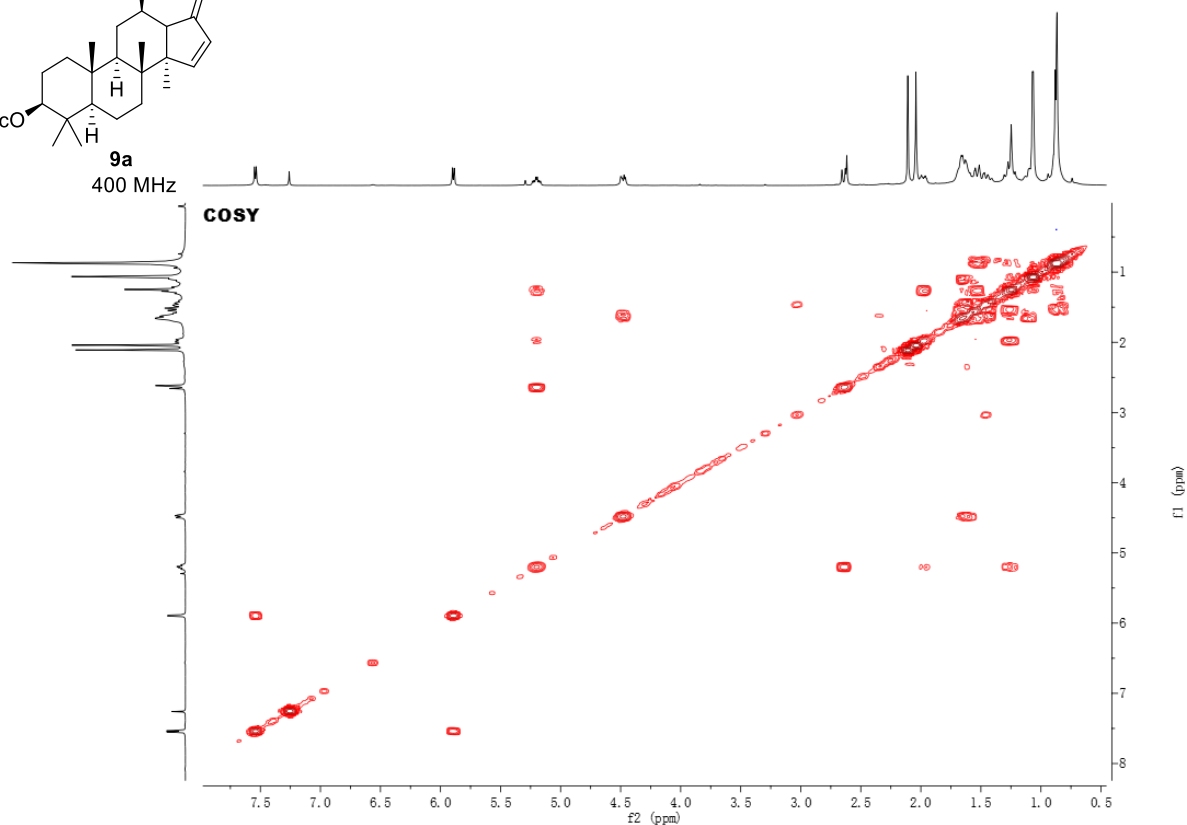


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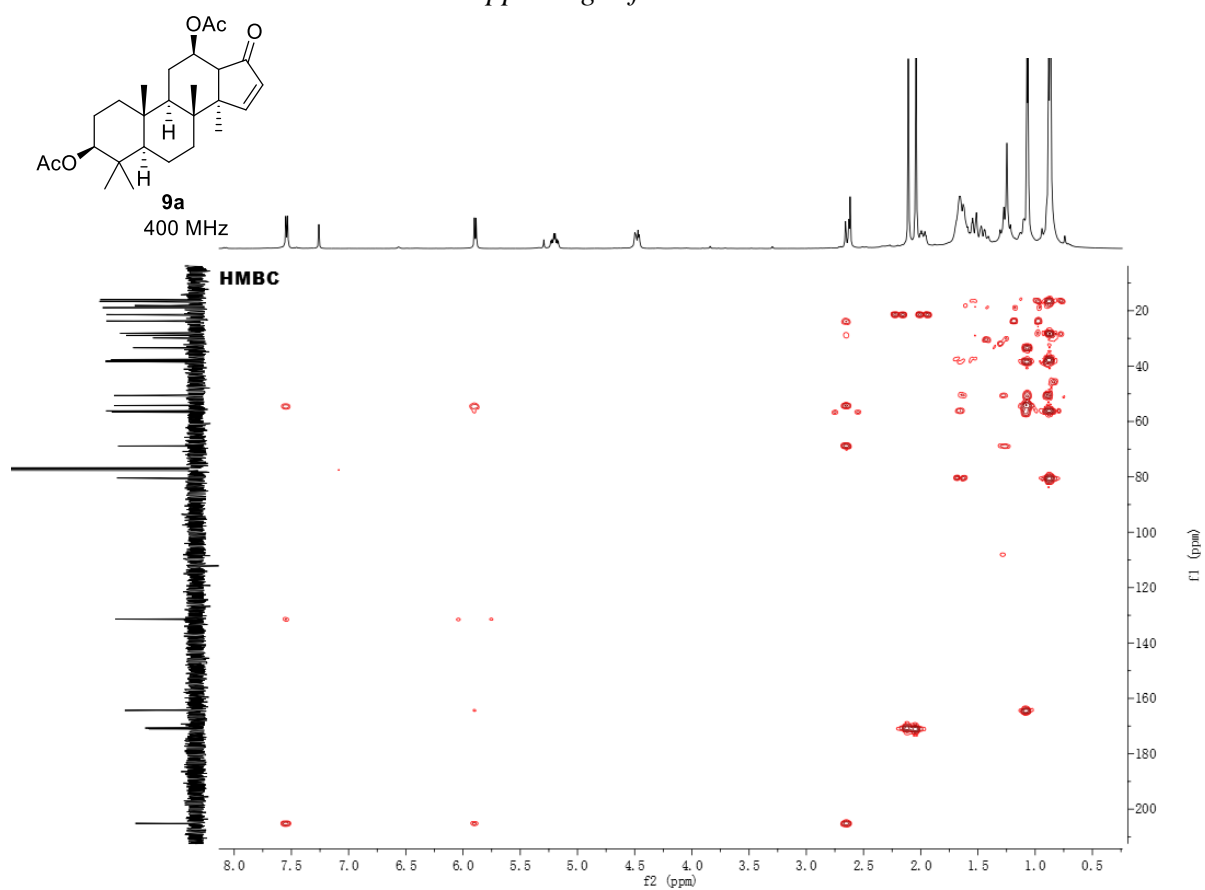


9a
400 MHz

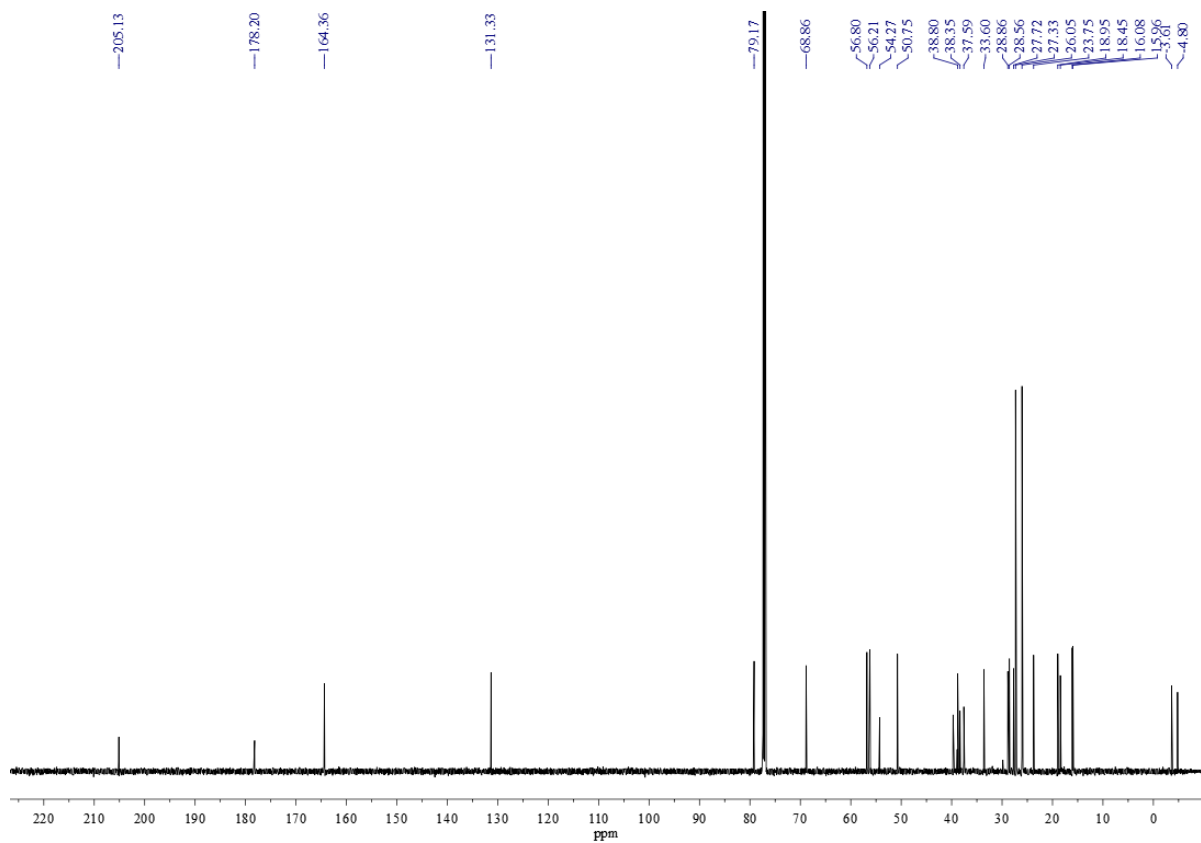
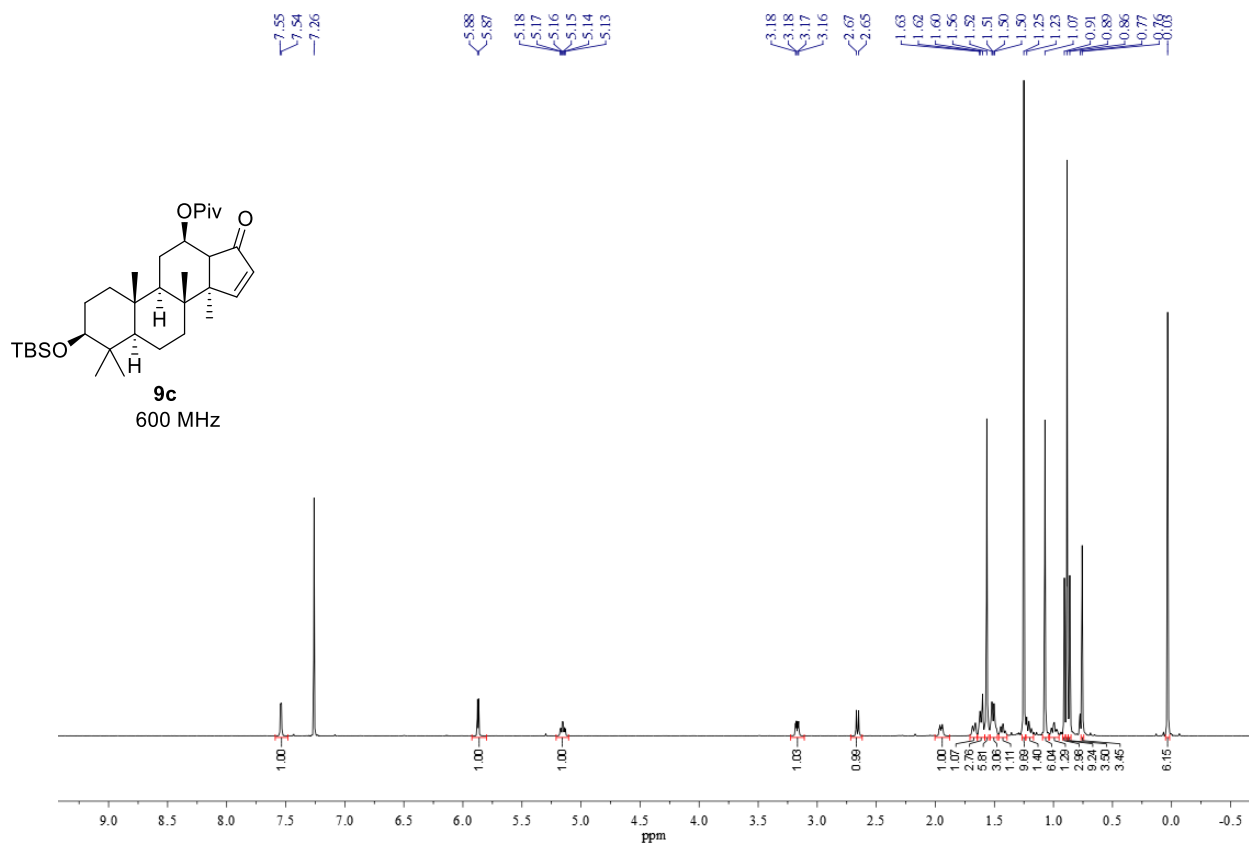
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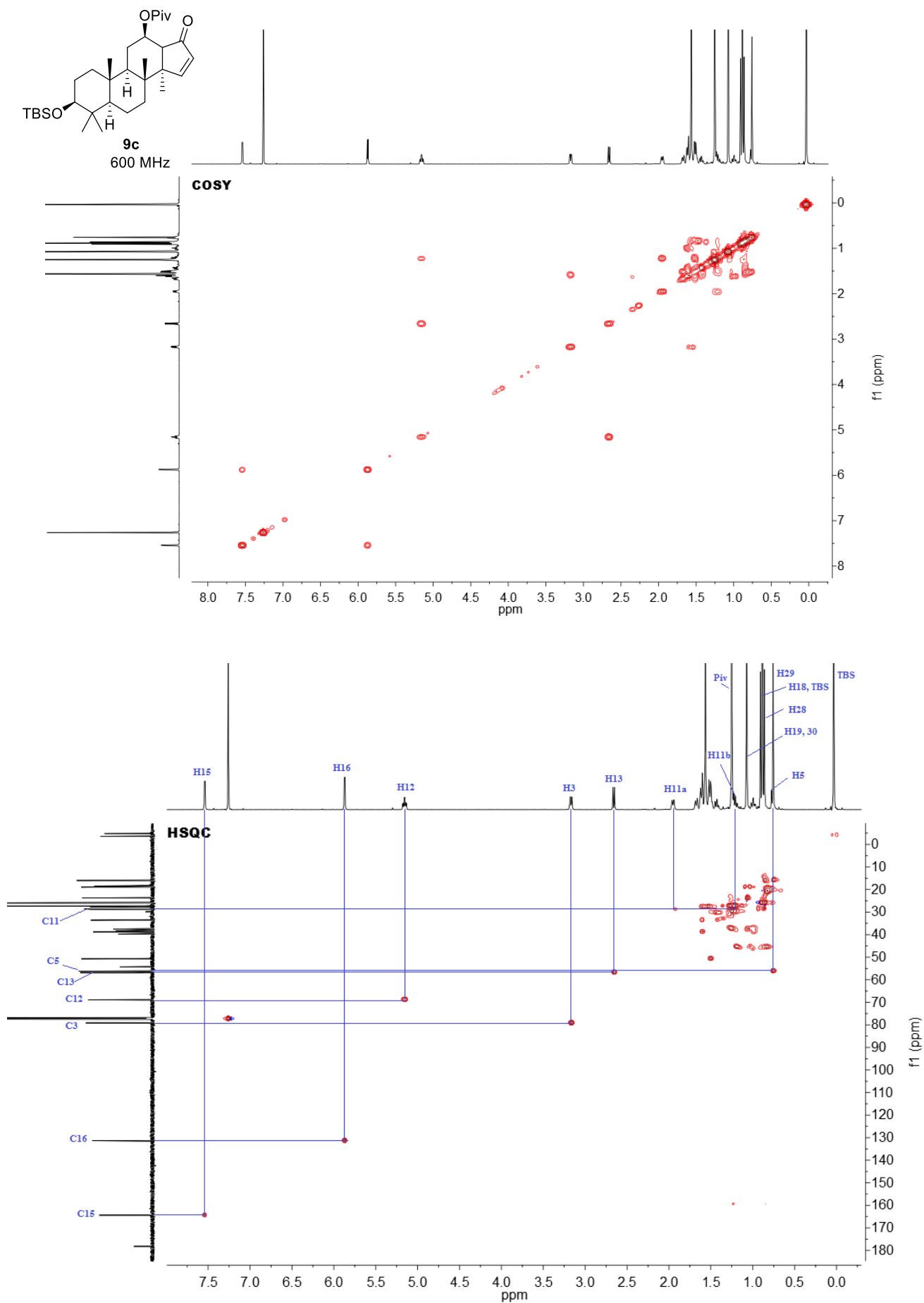
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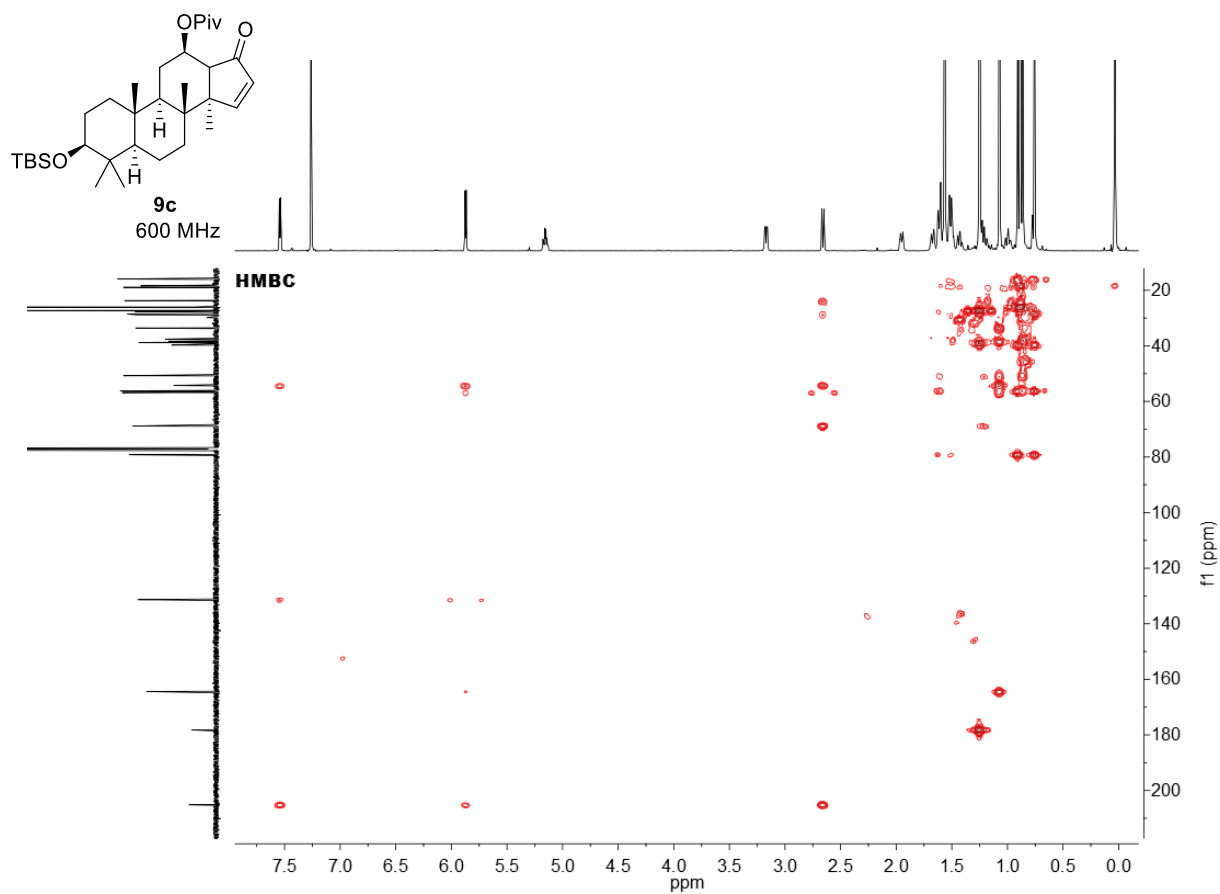
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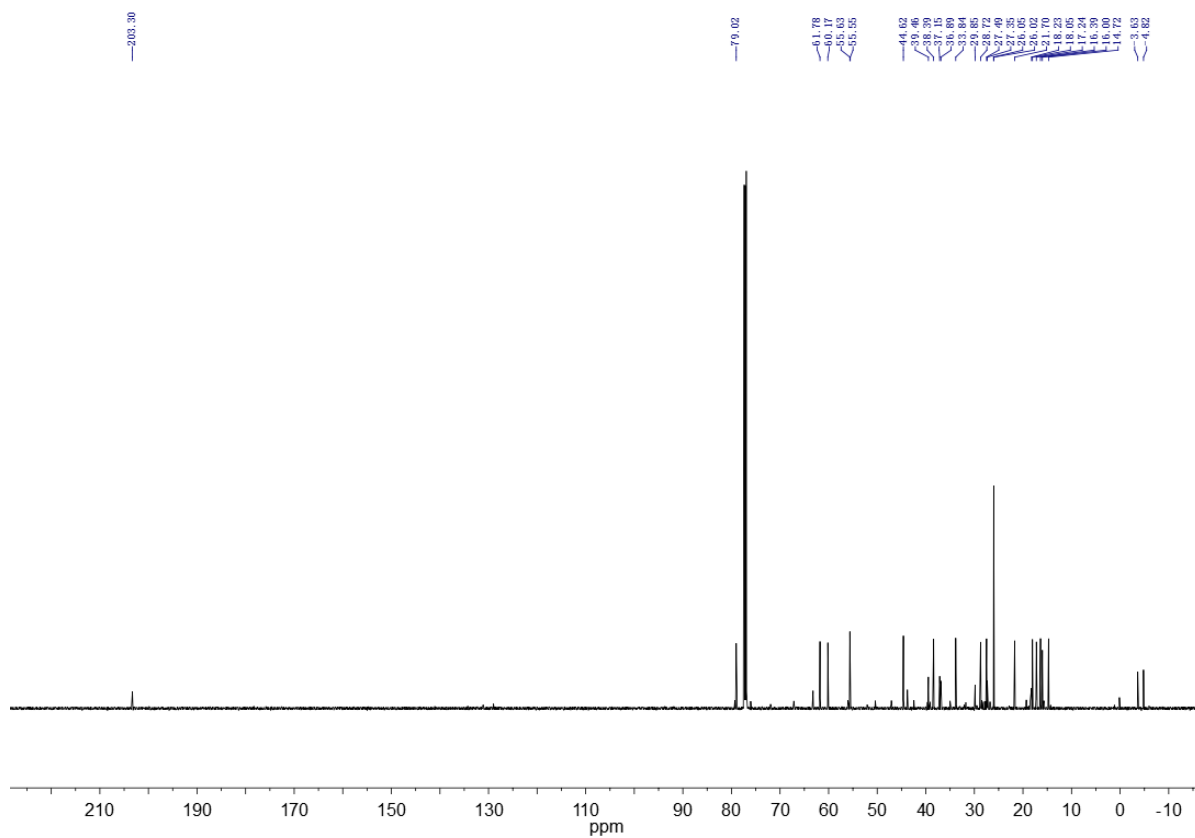
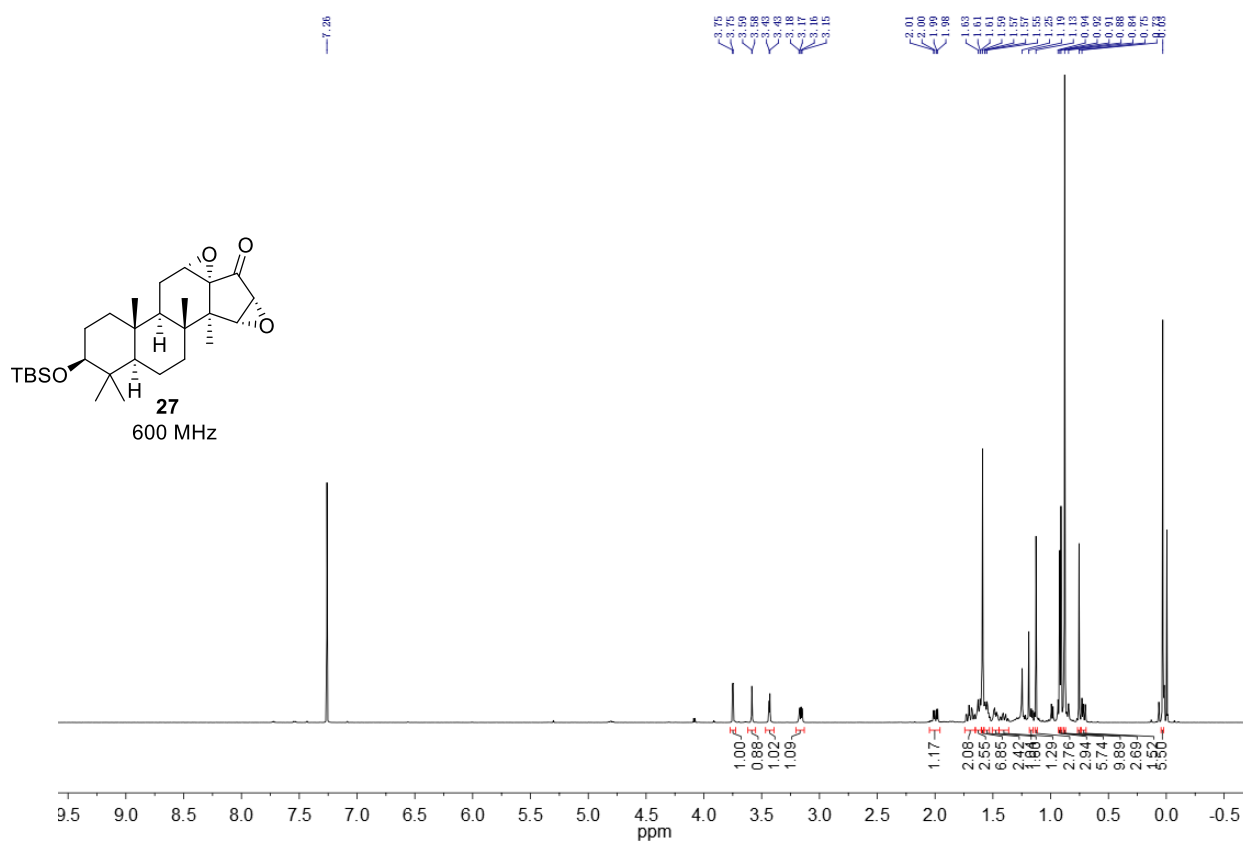
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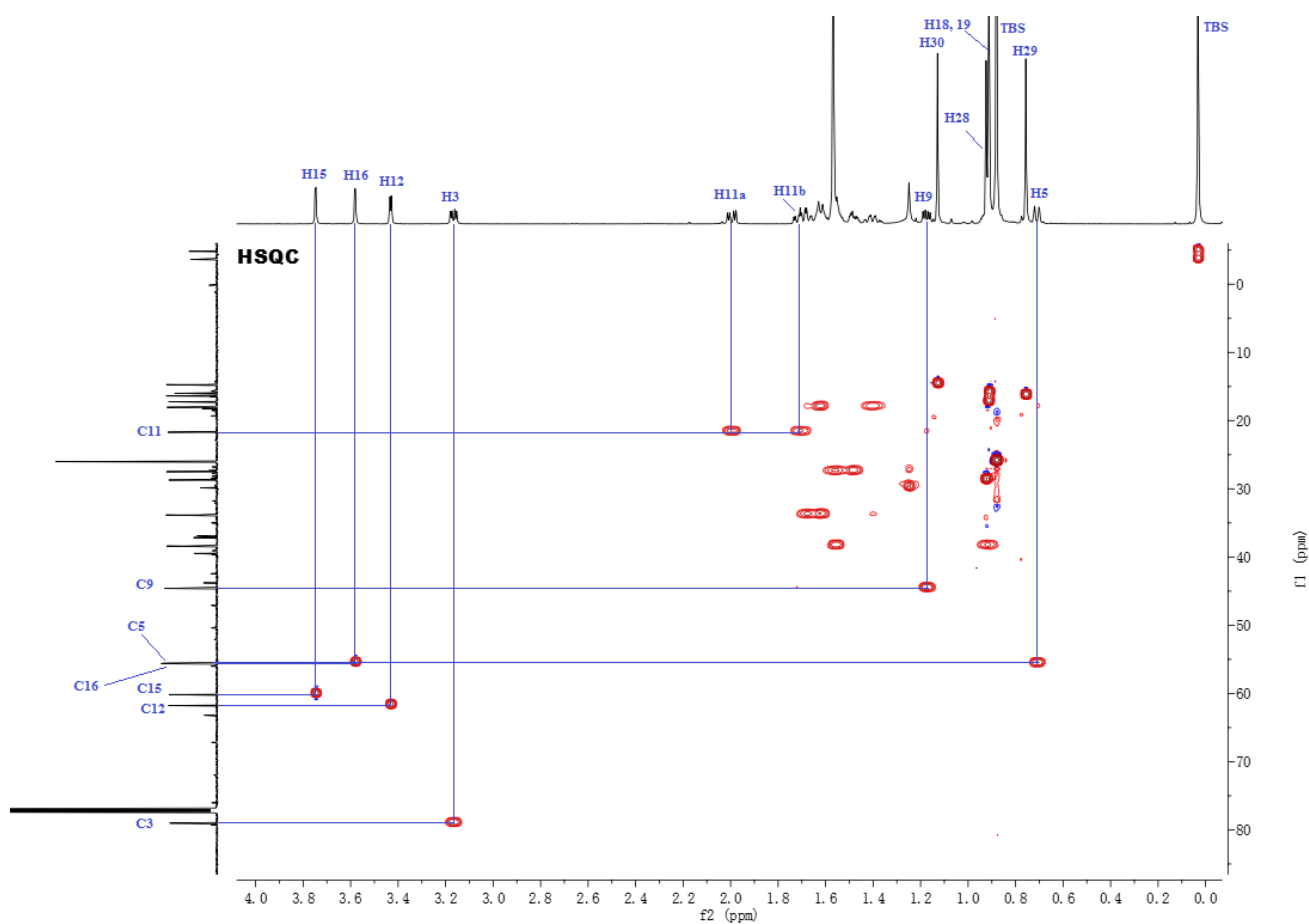
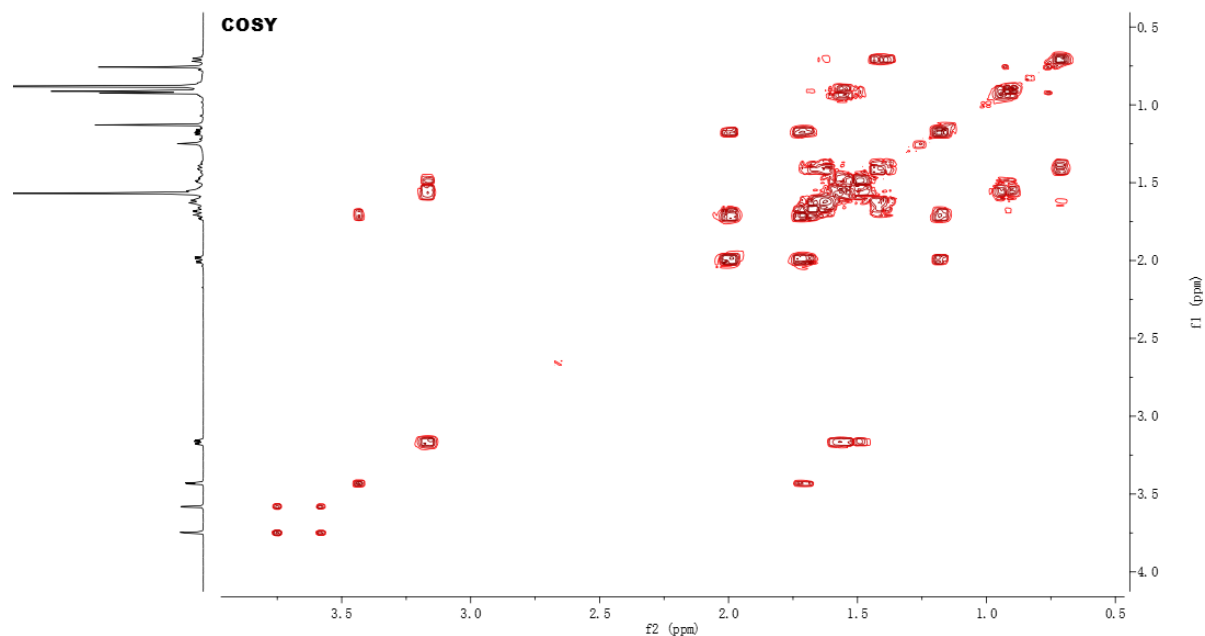
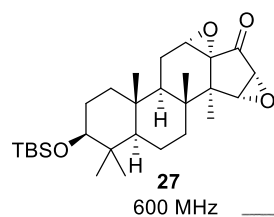
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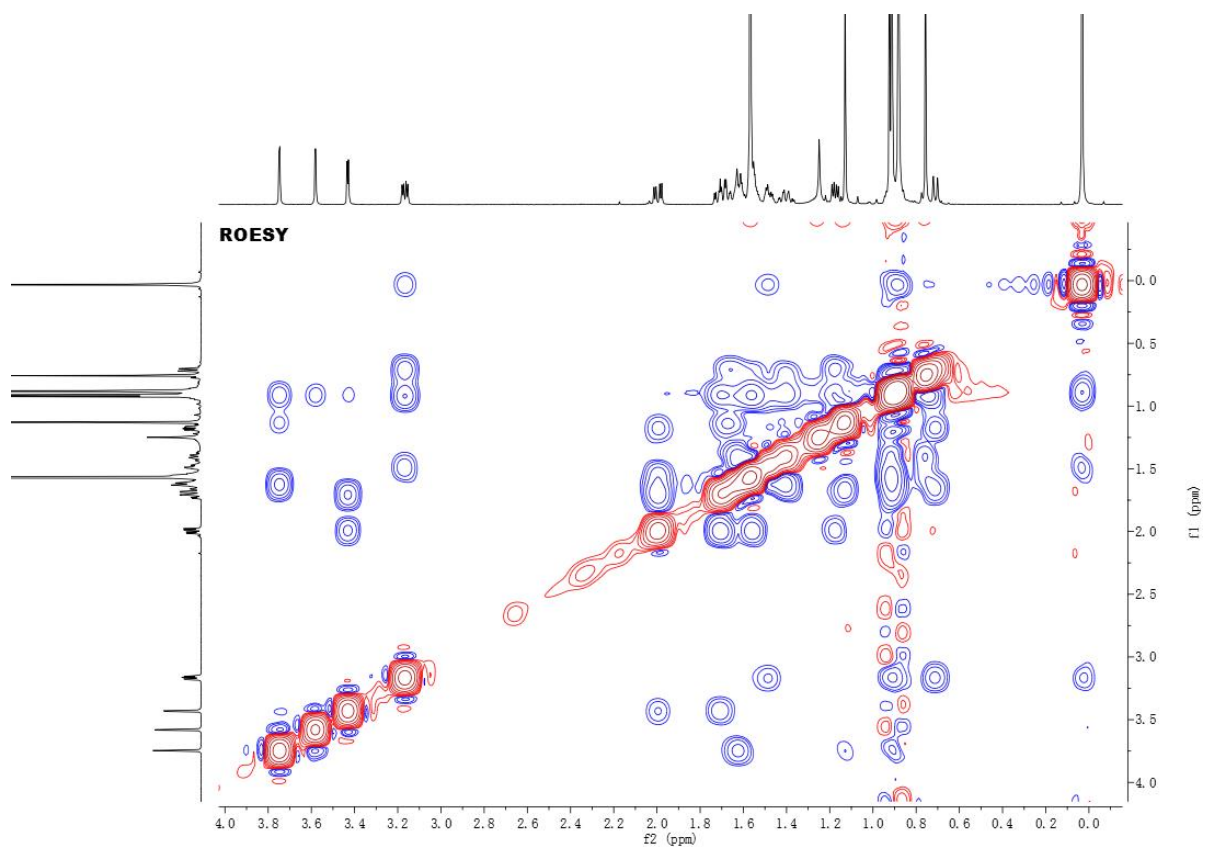
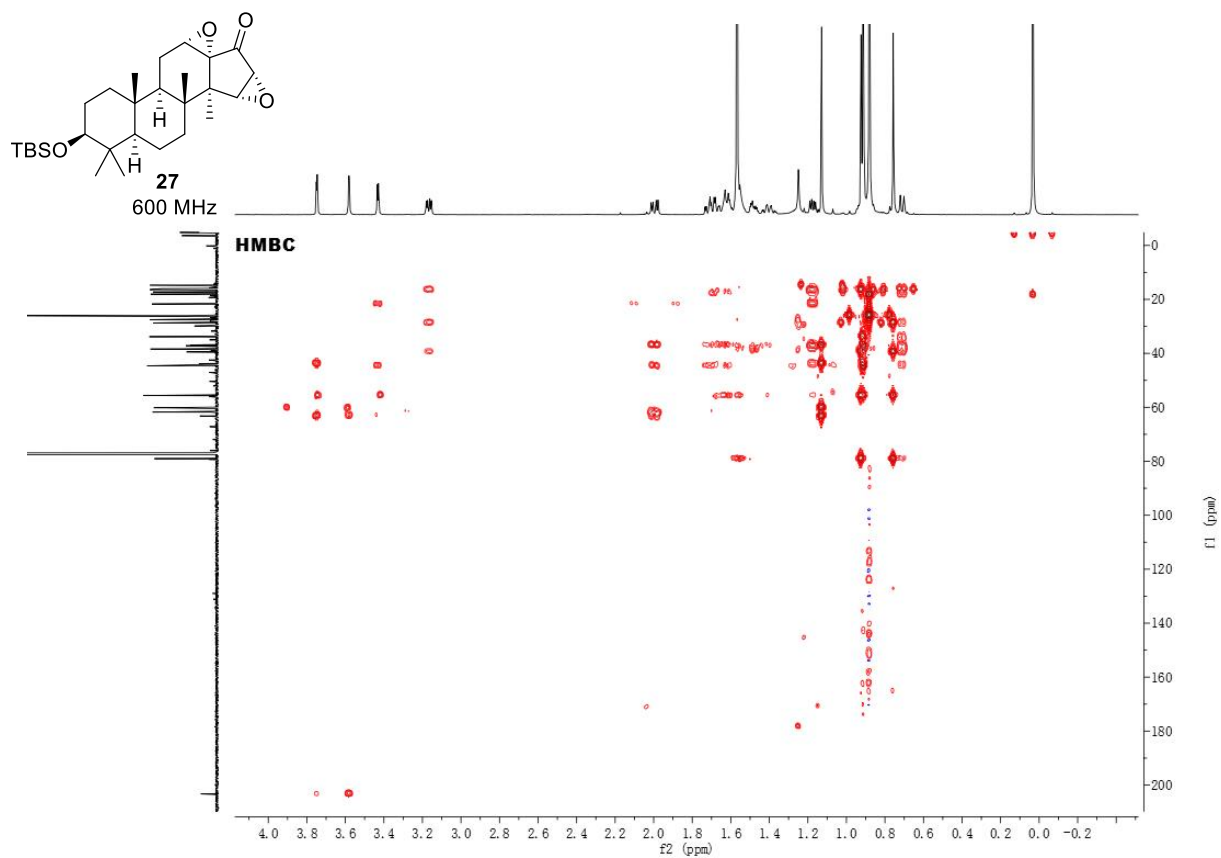
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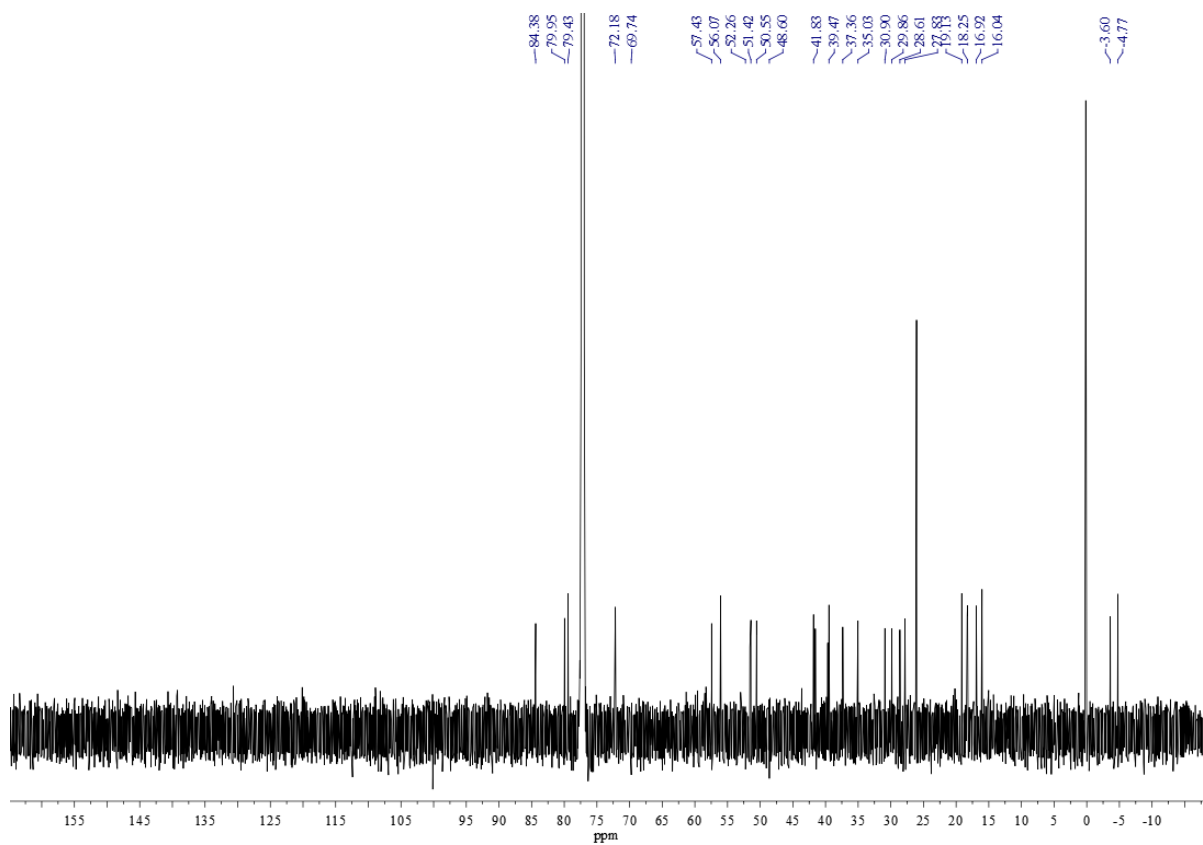
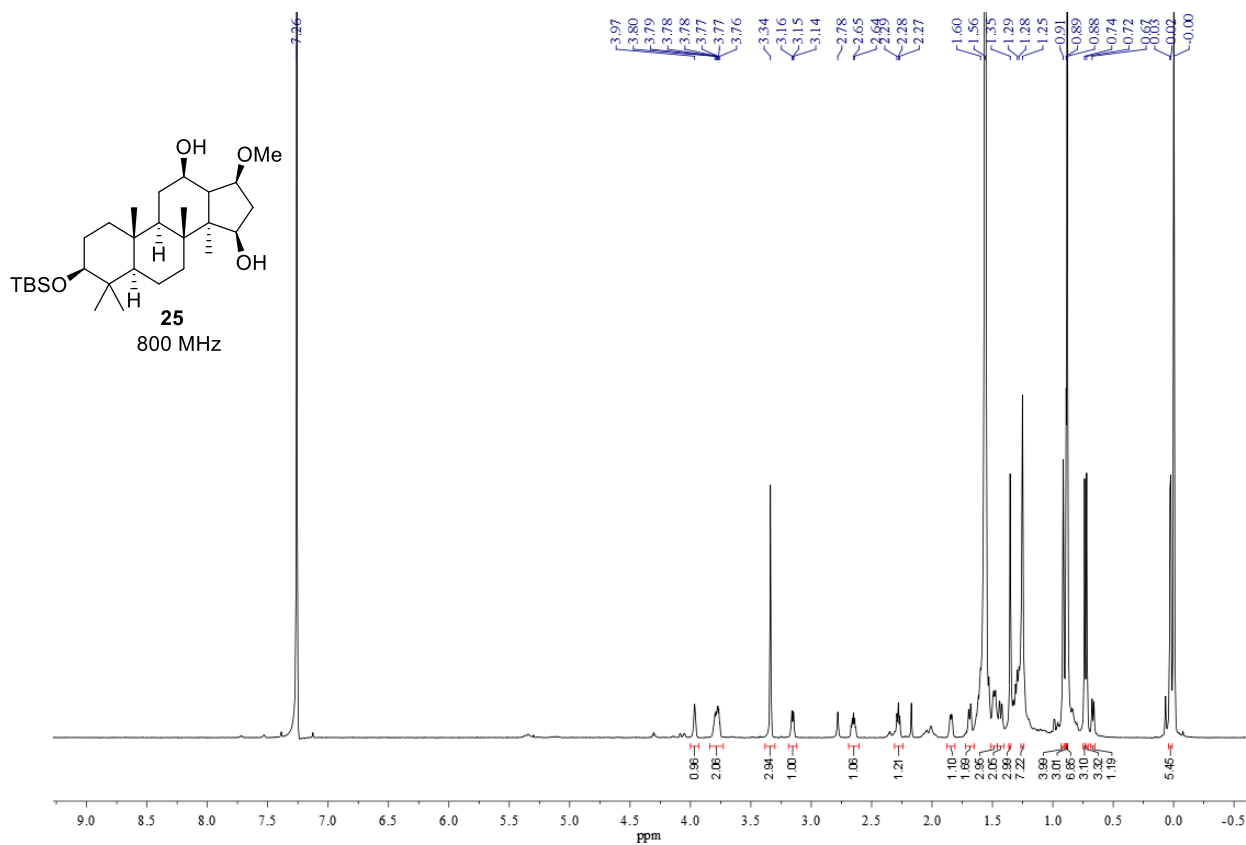
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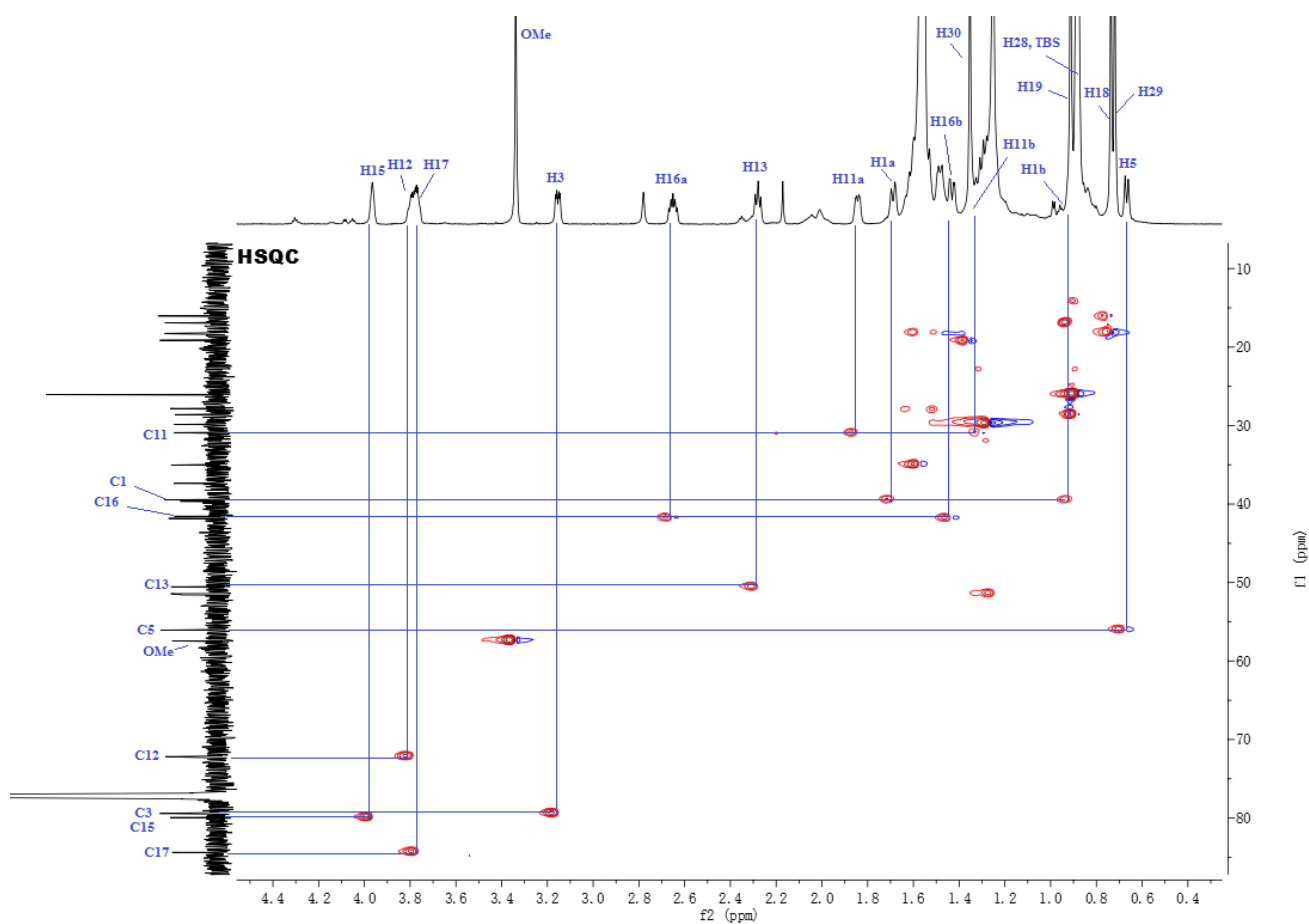
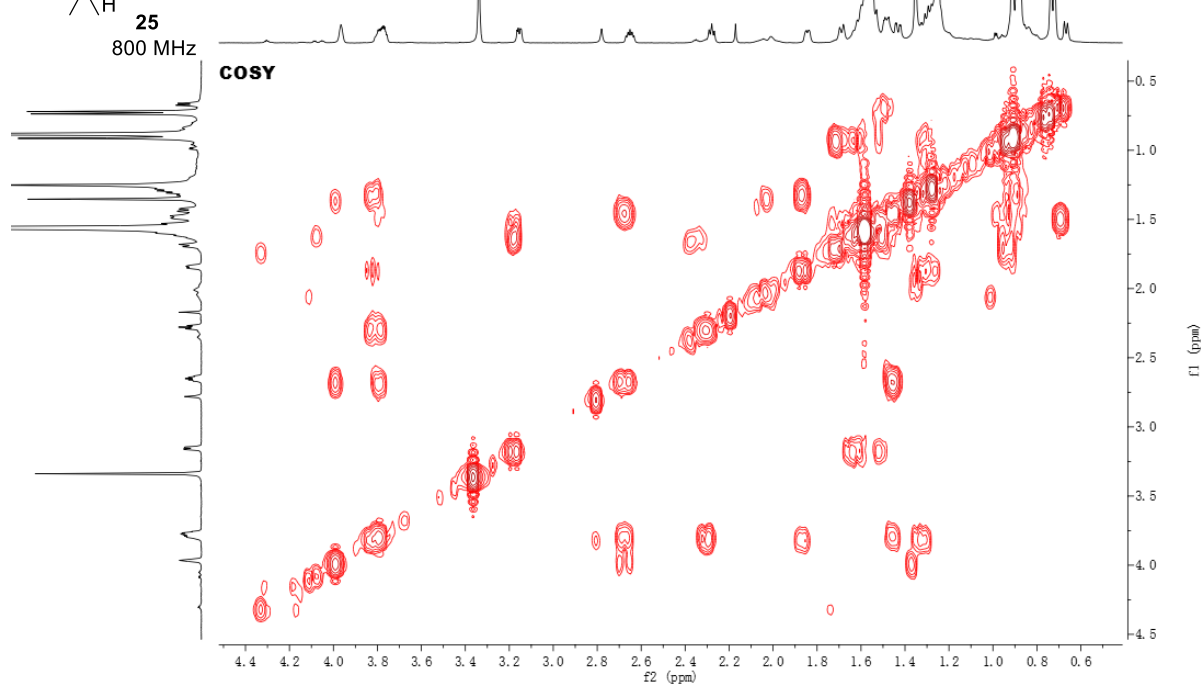
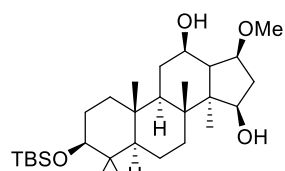
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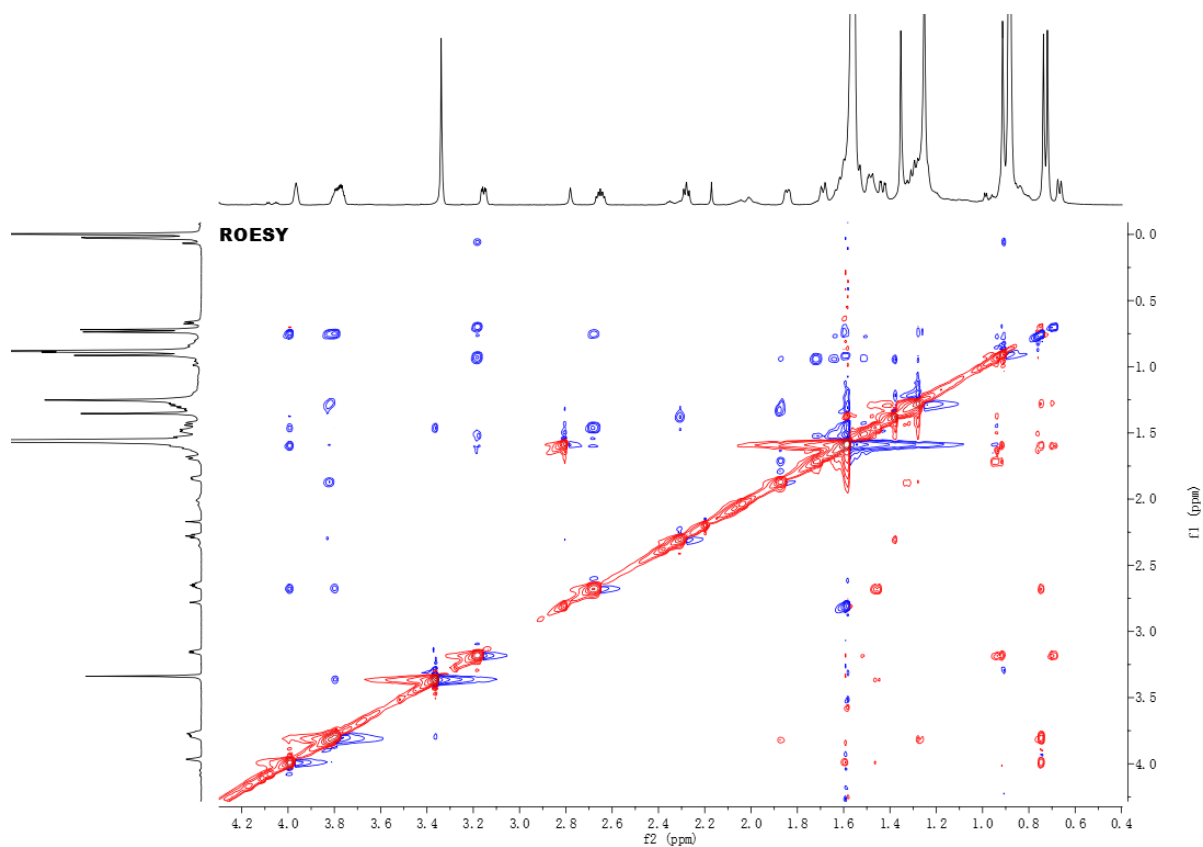
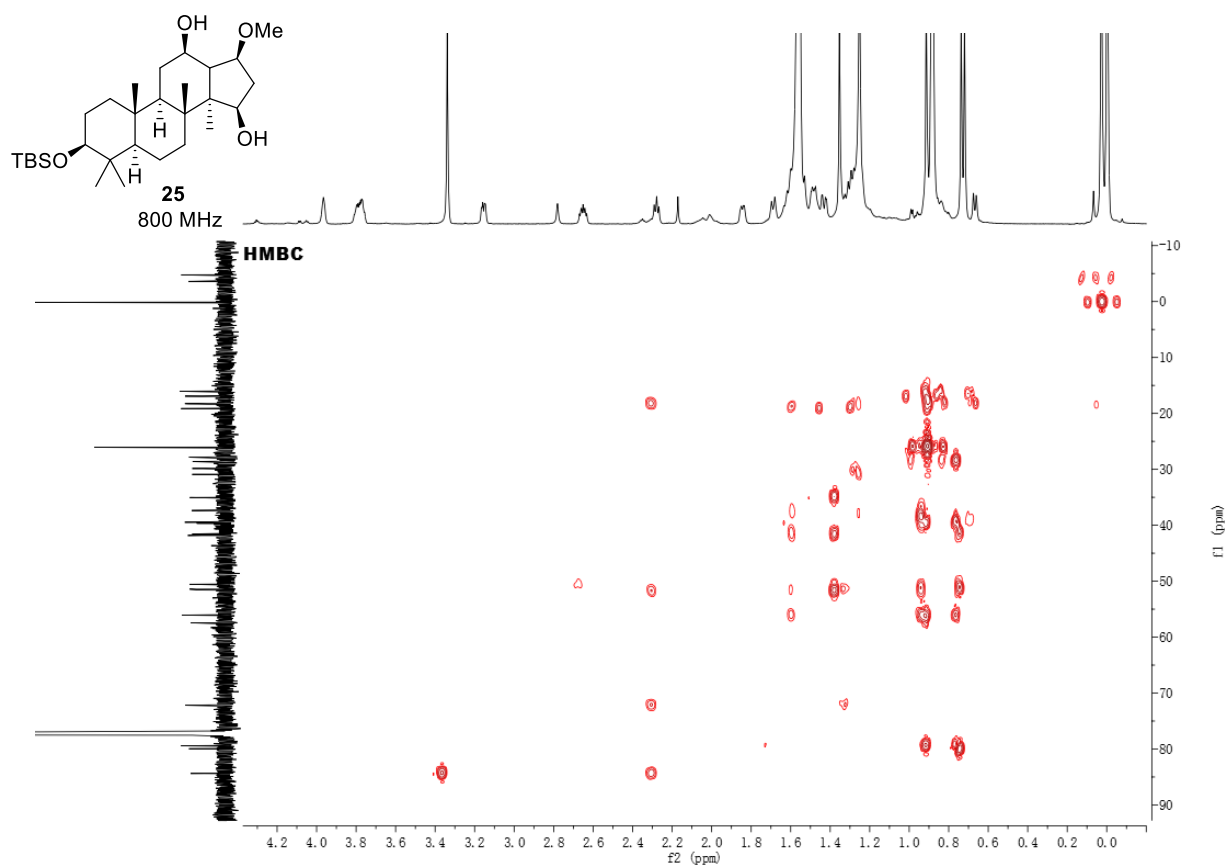
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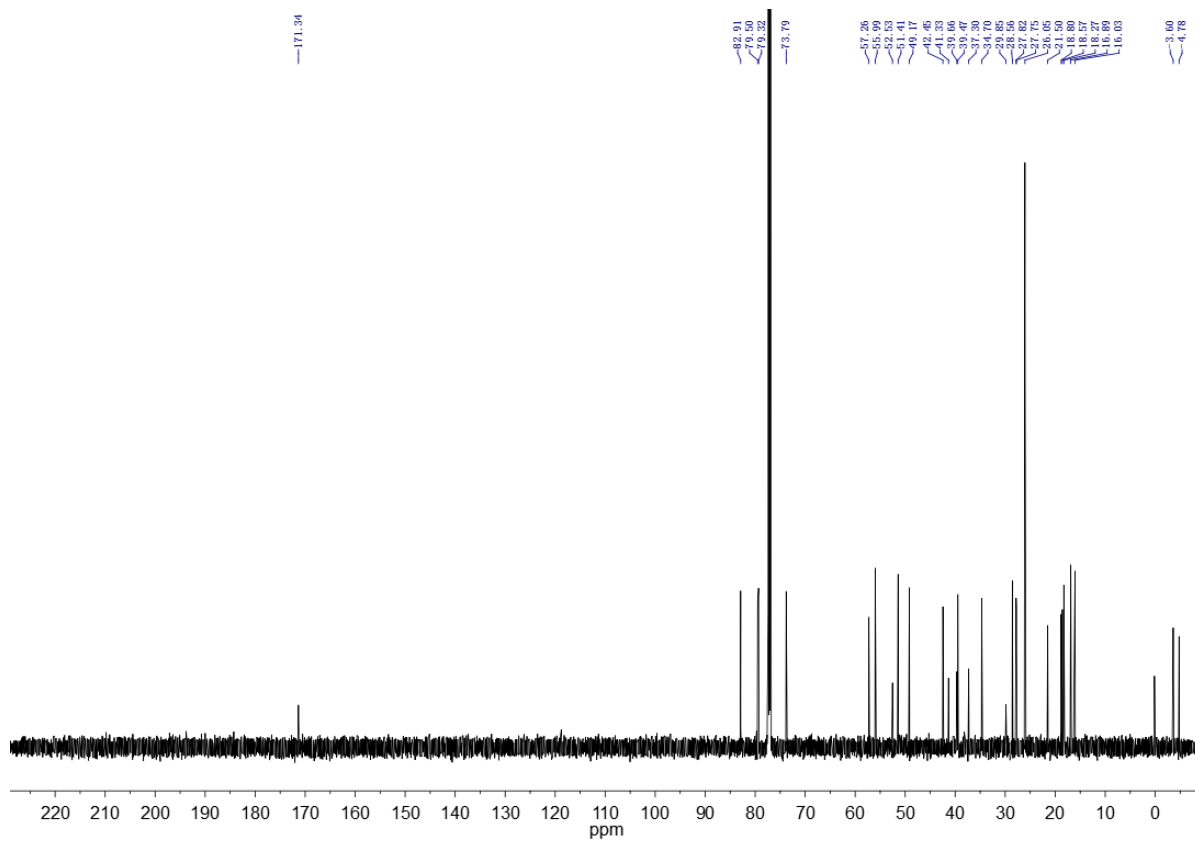
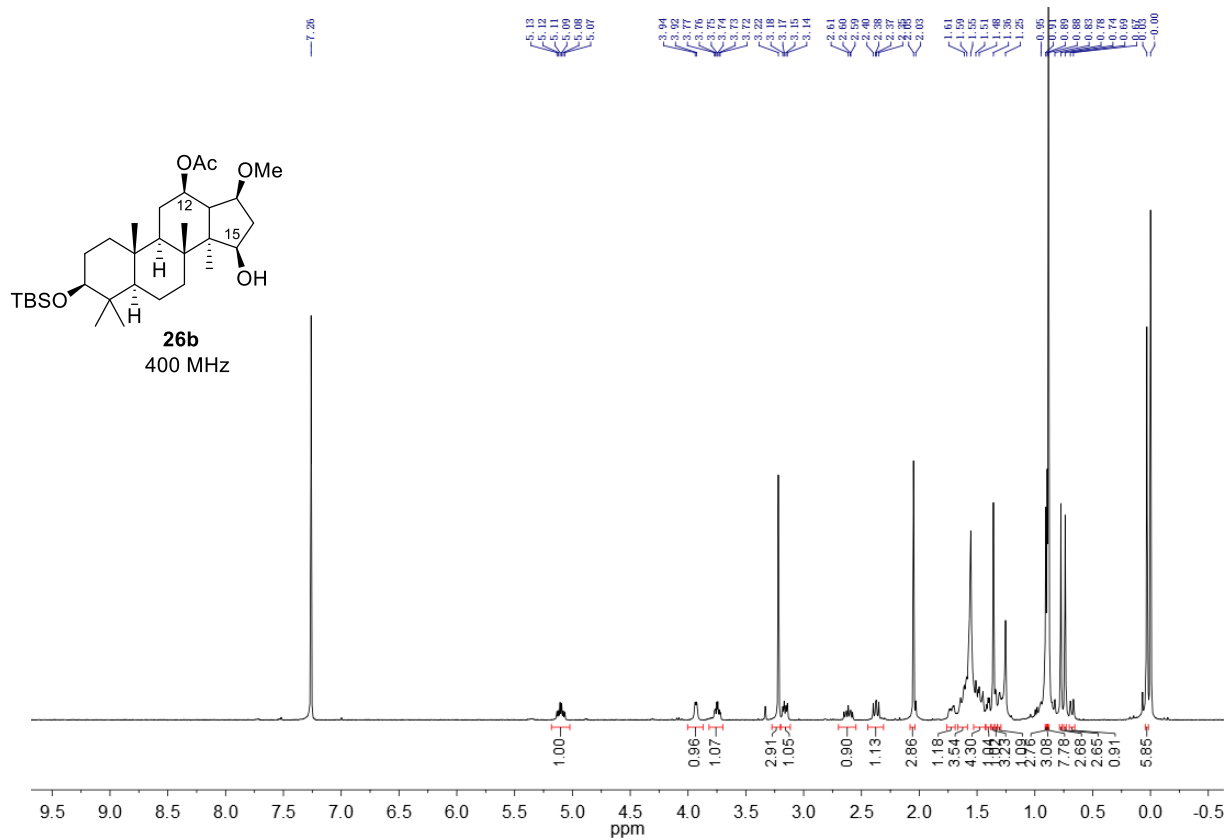
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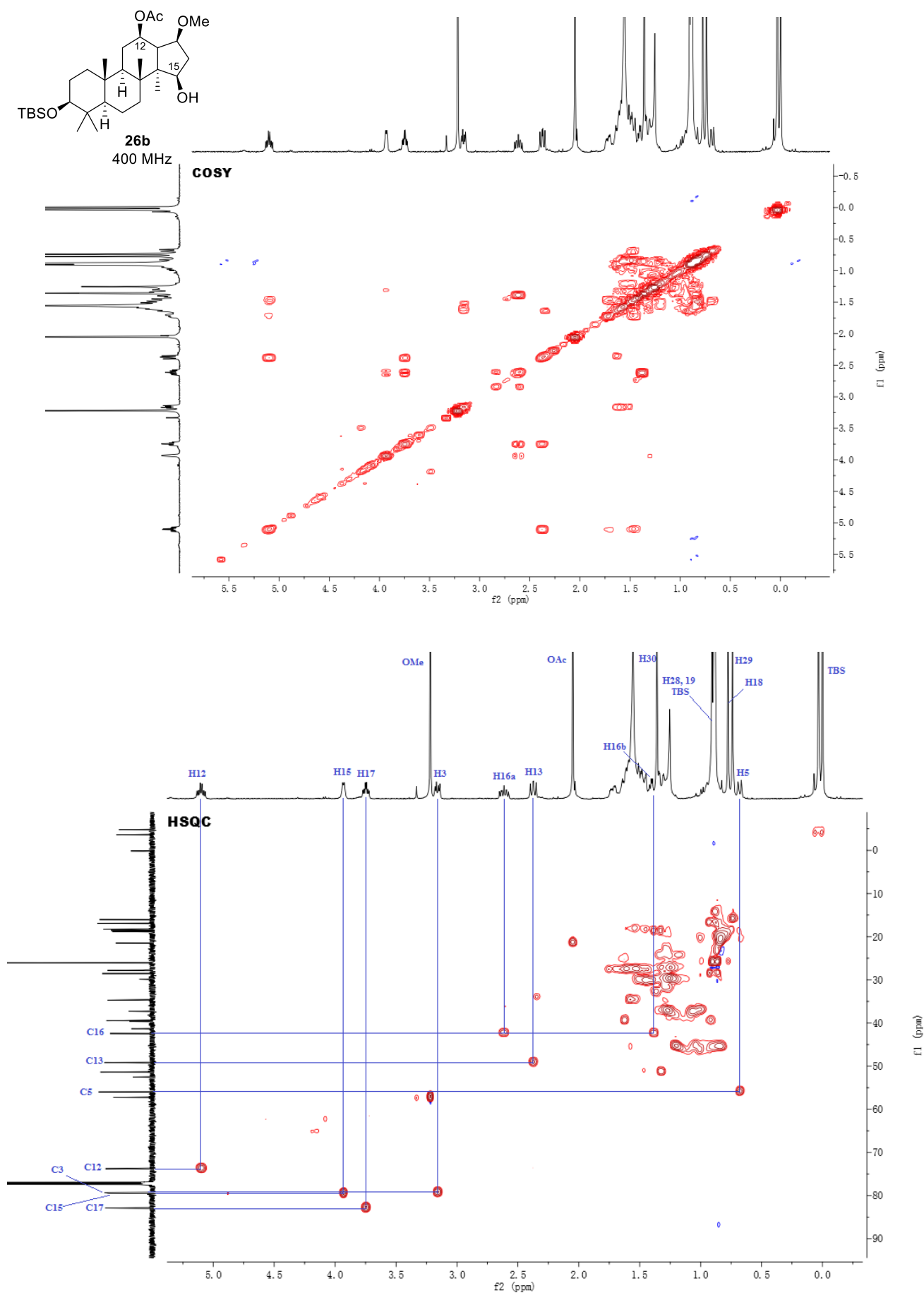
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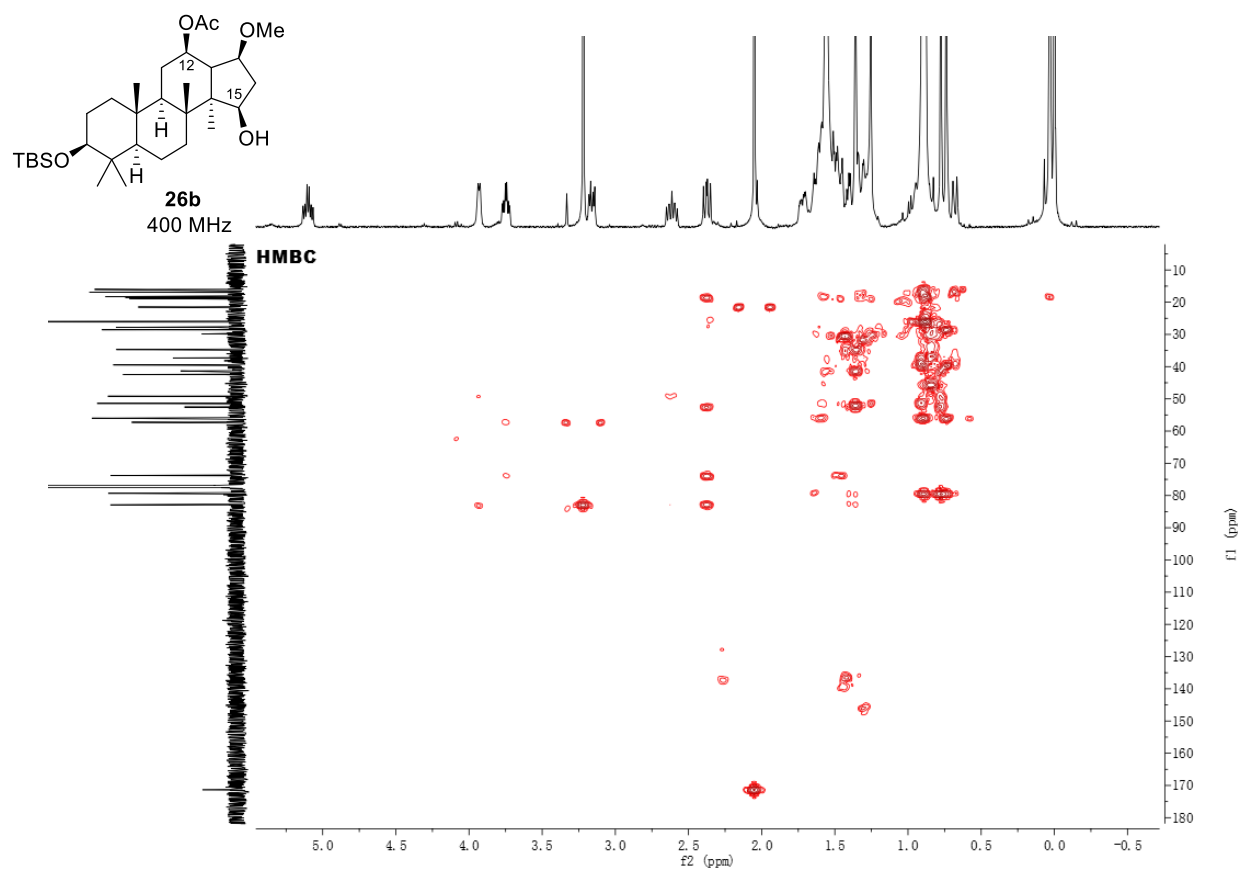
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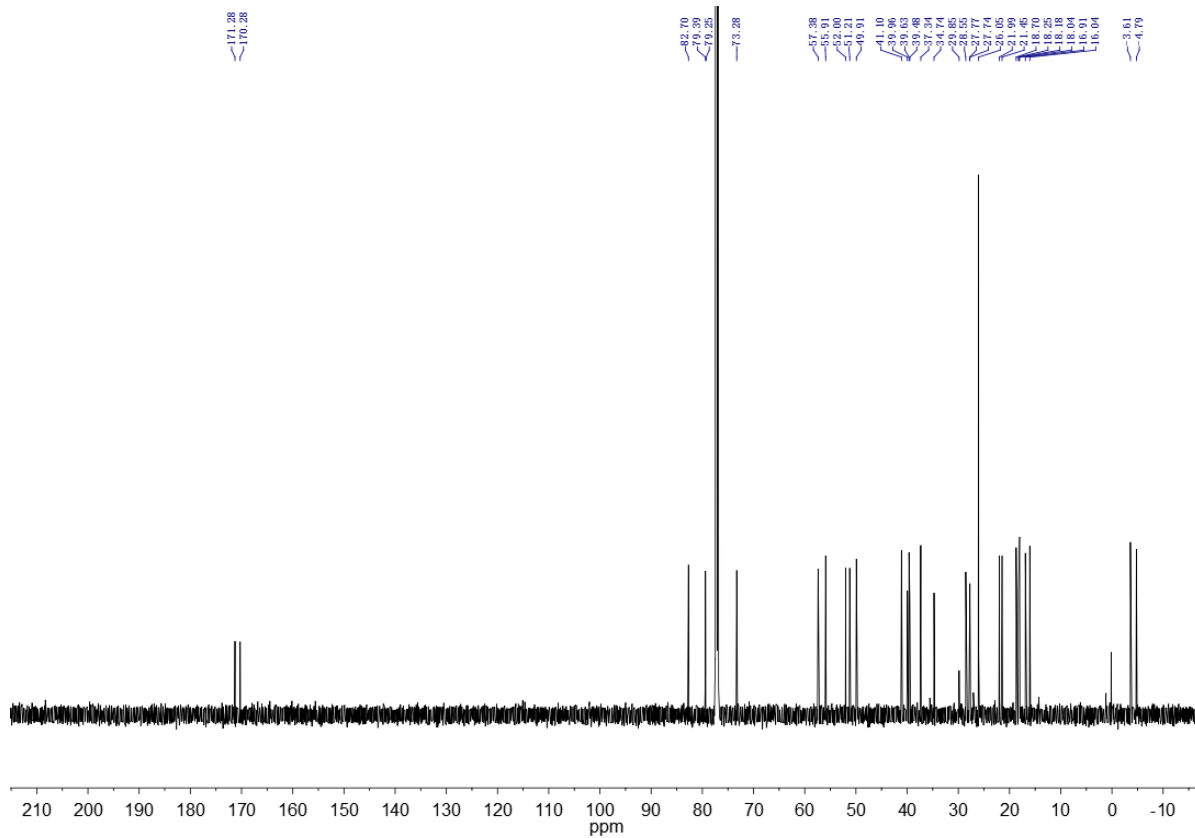
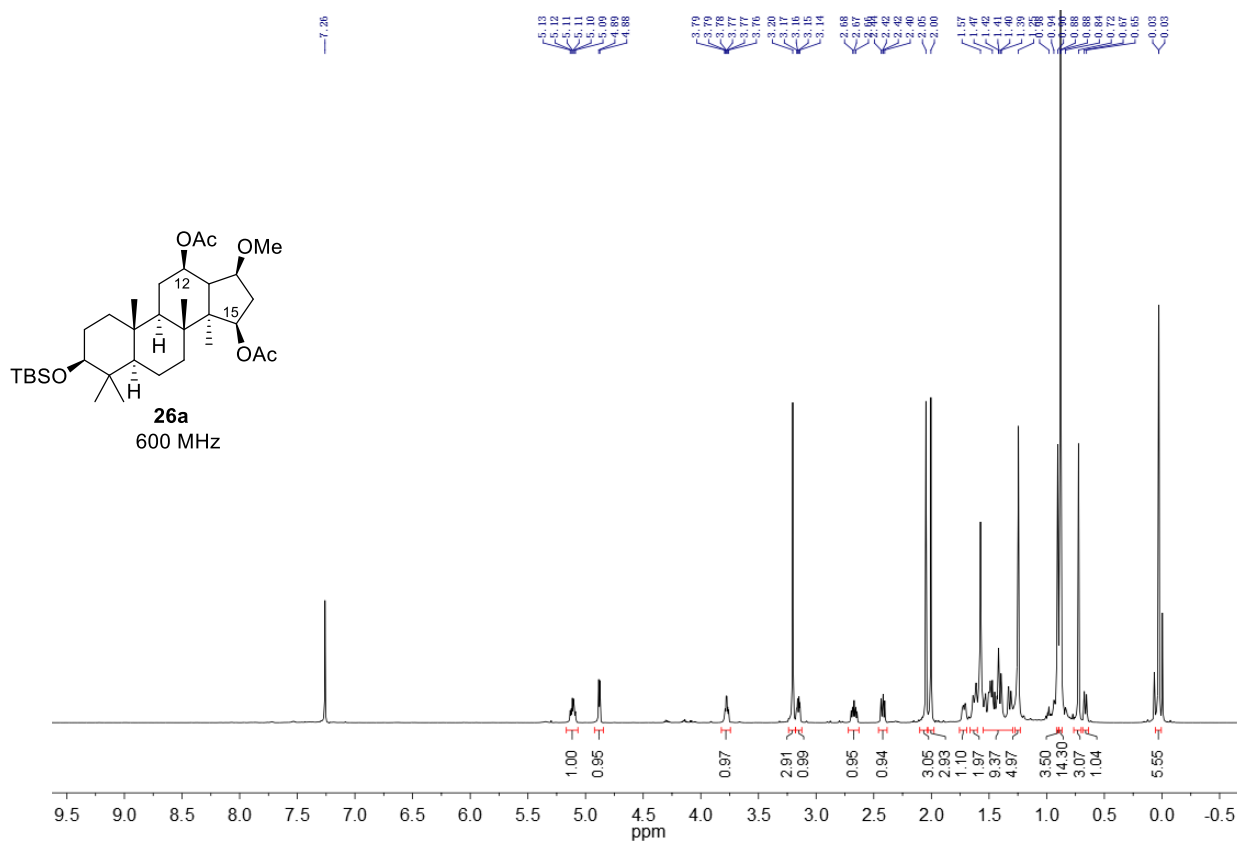
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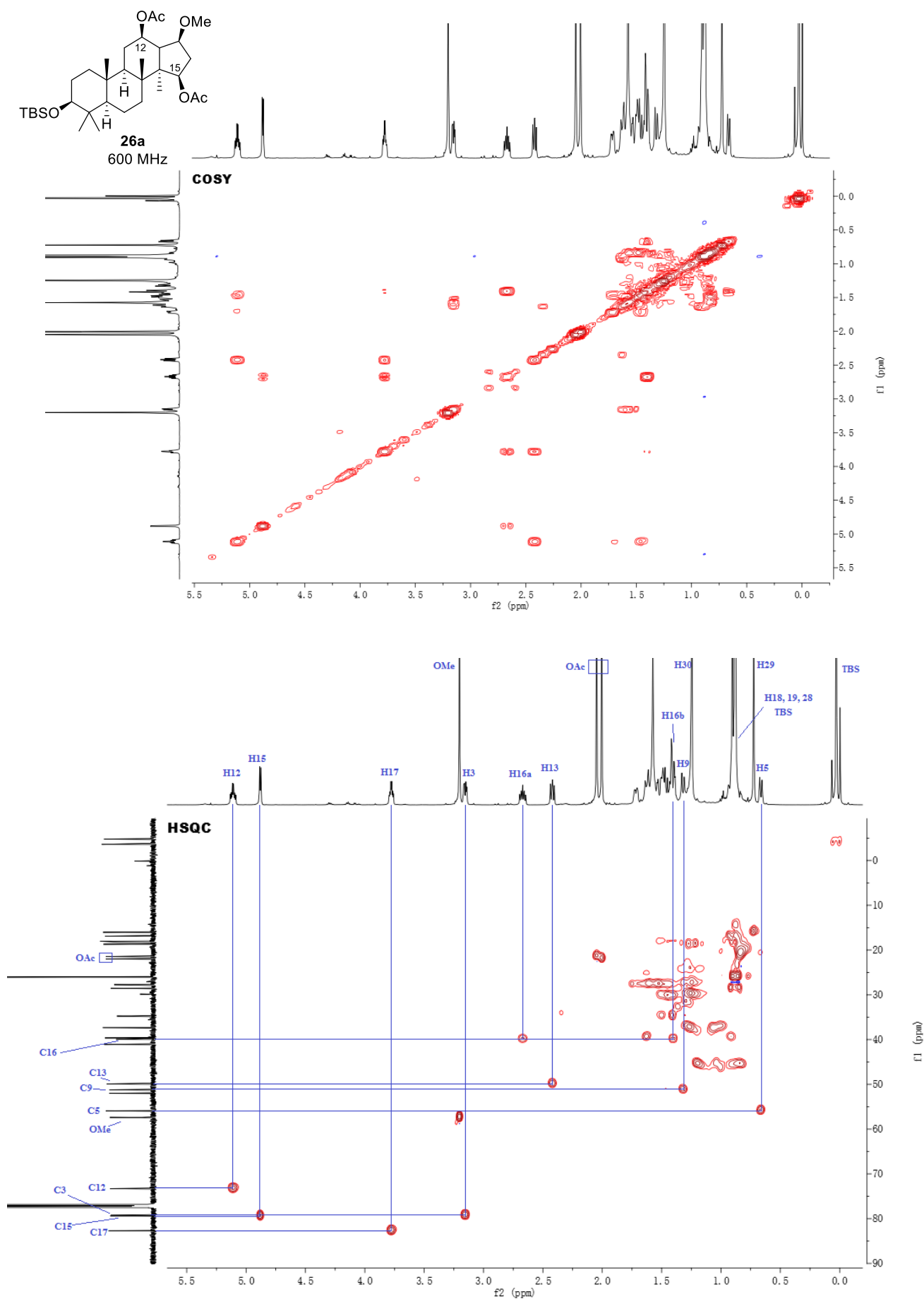
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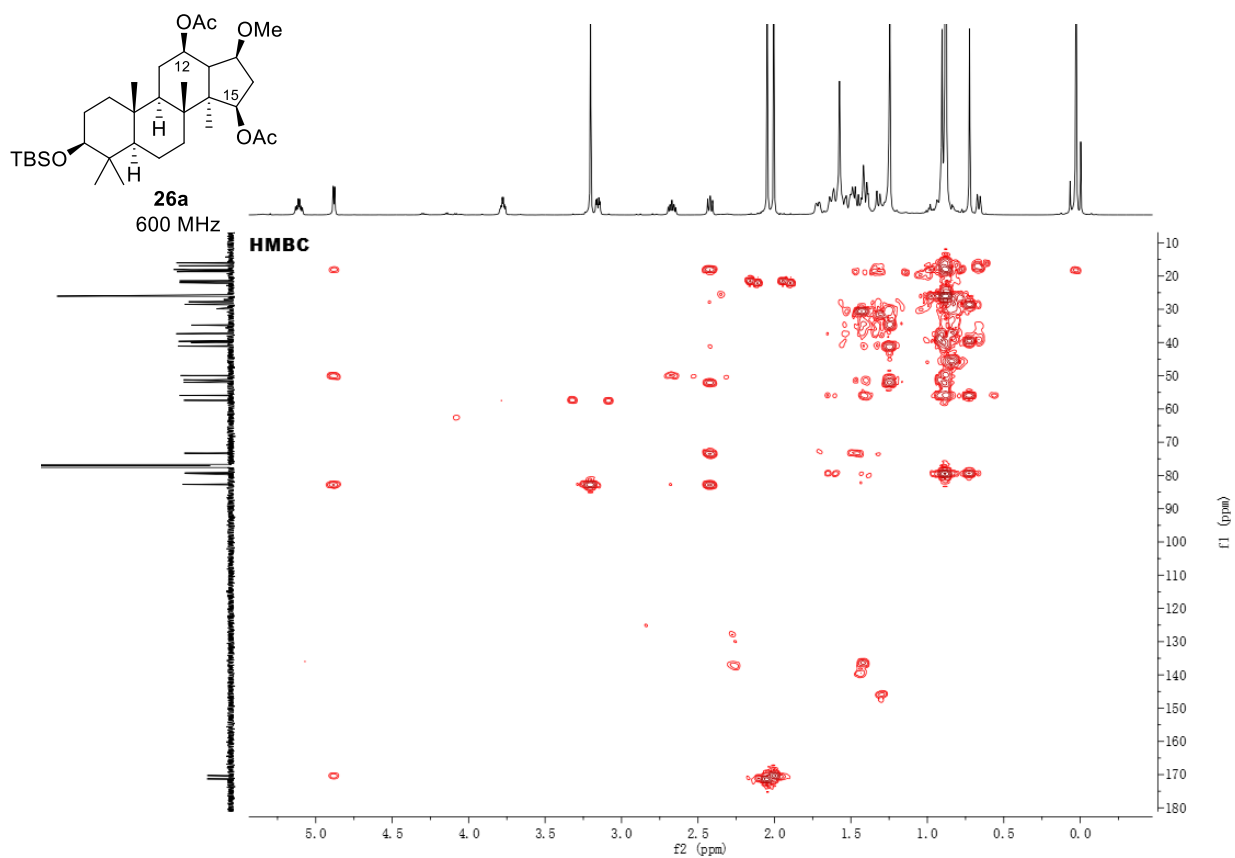
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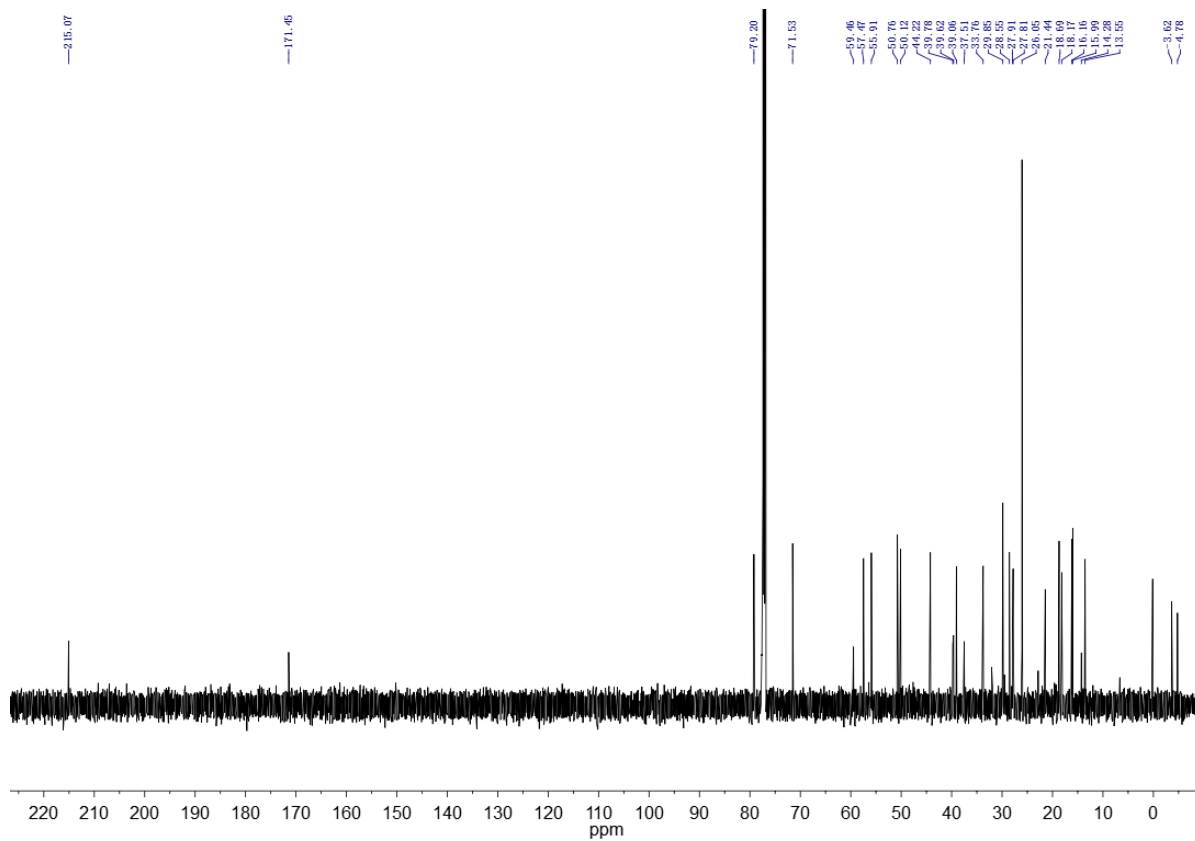
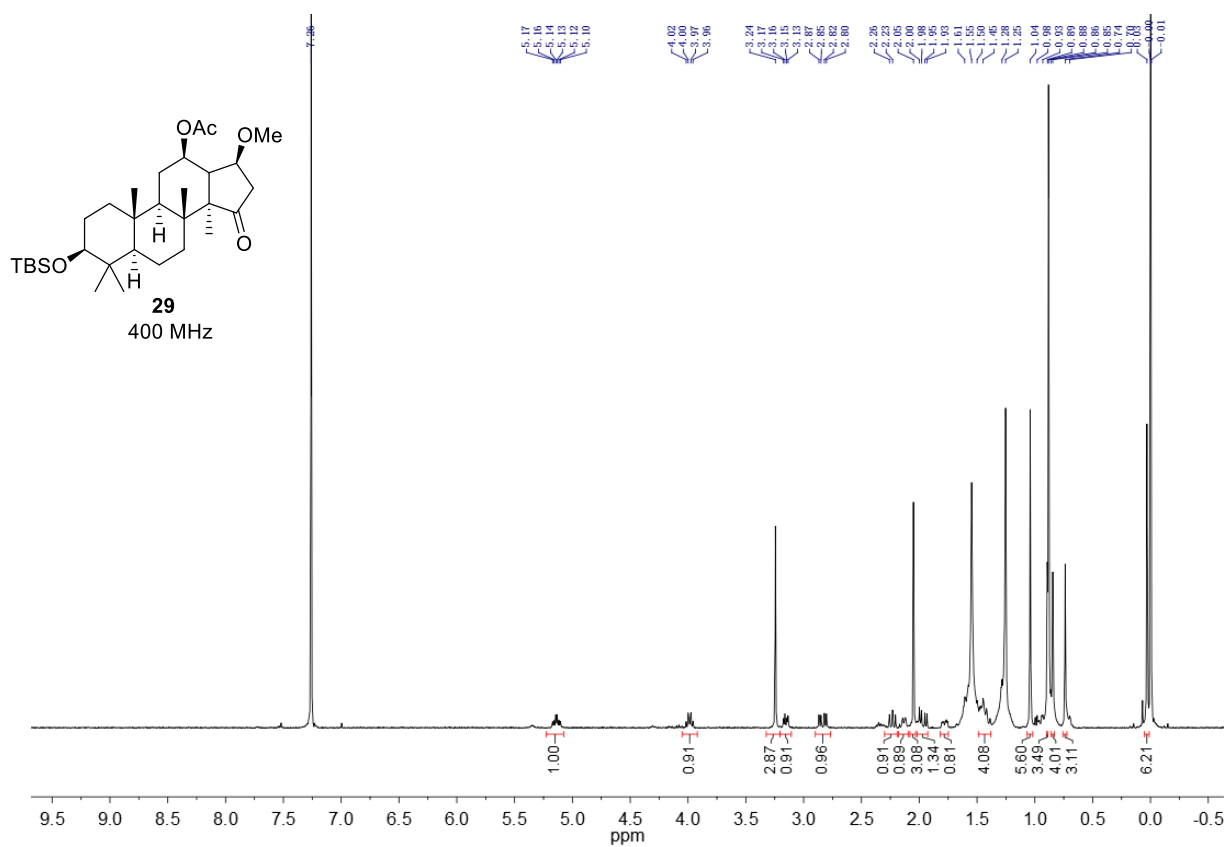
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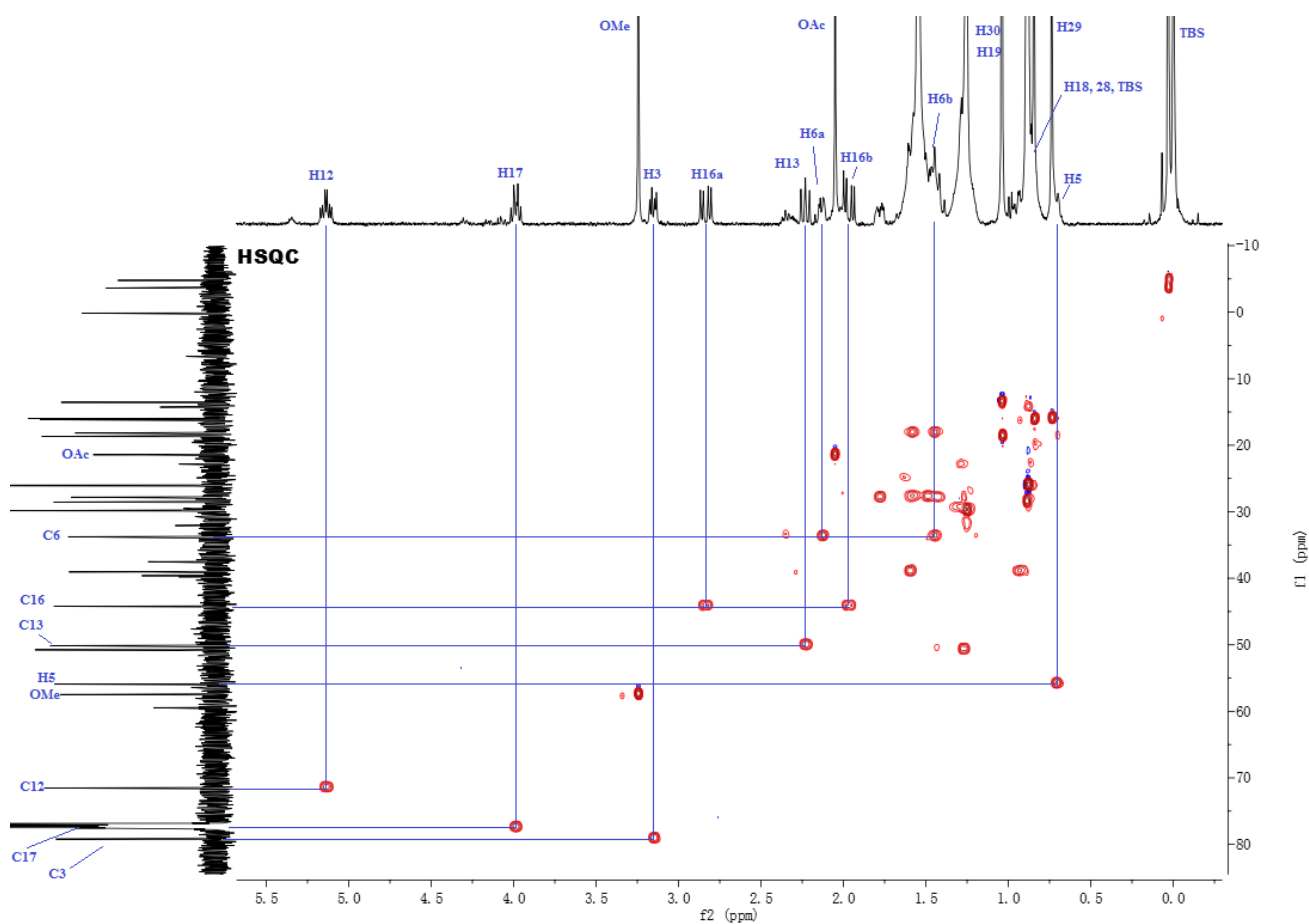
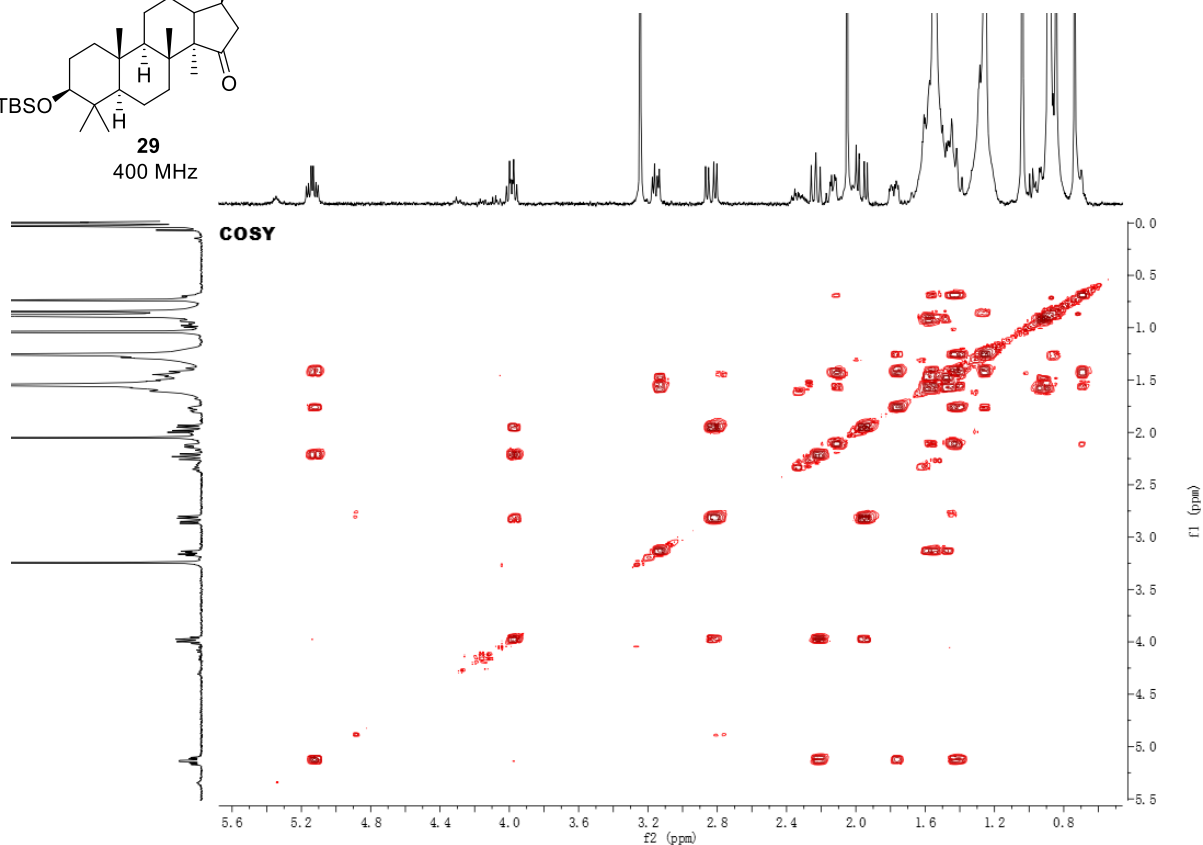
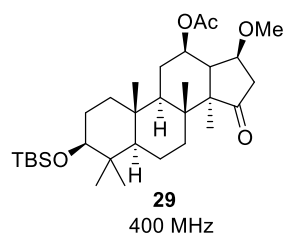
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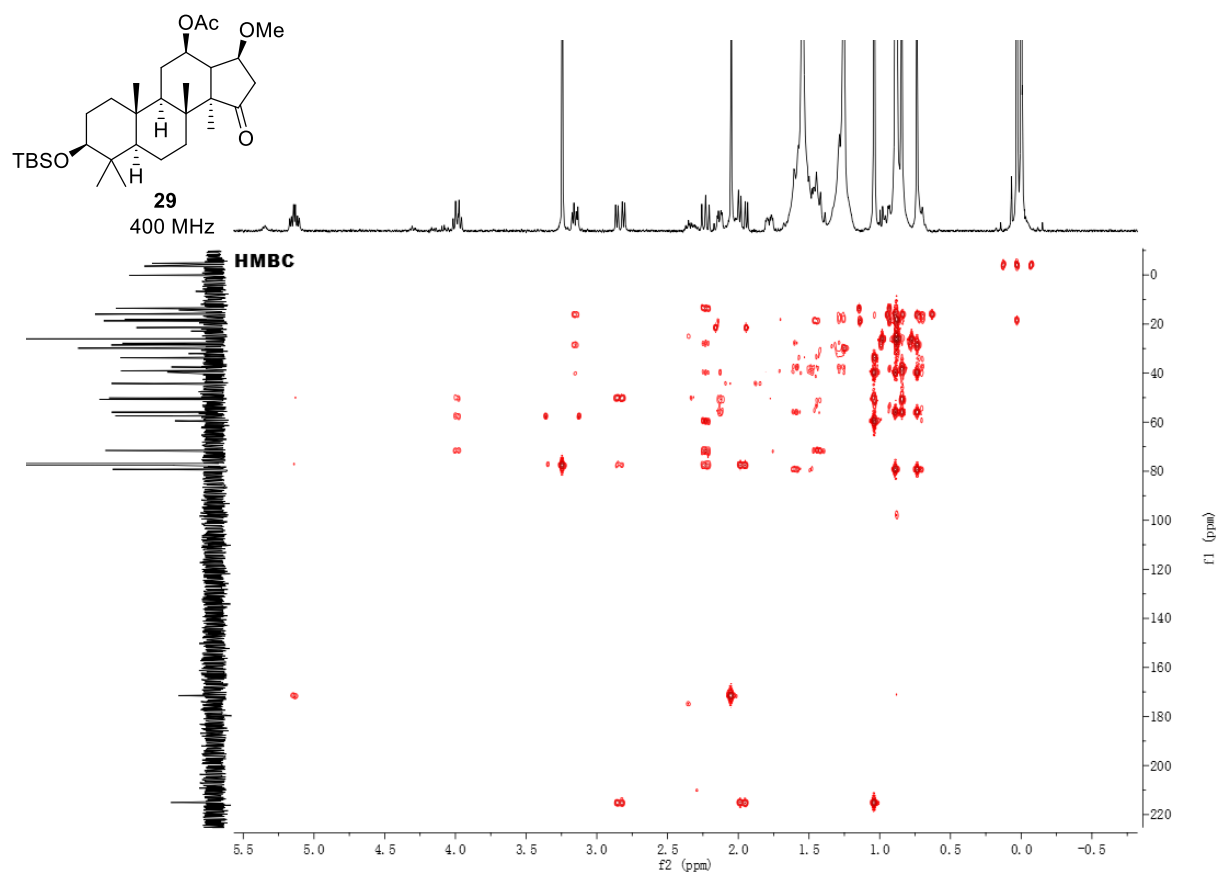
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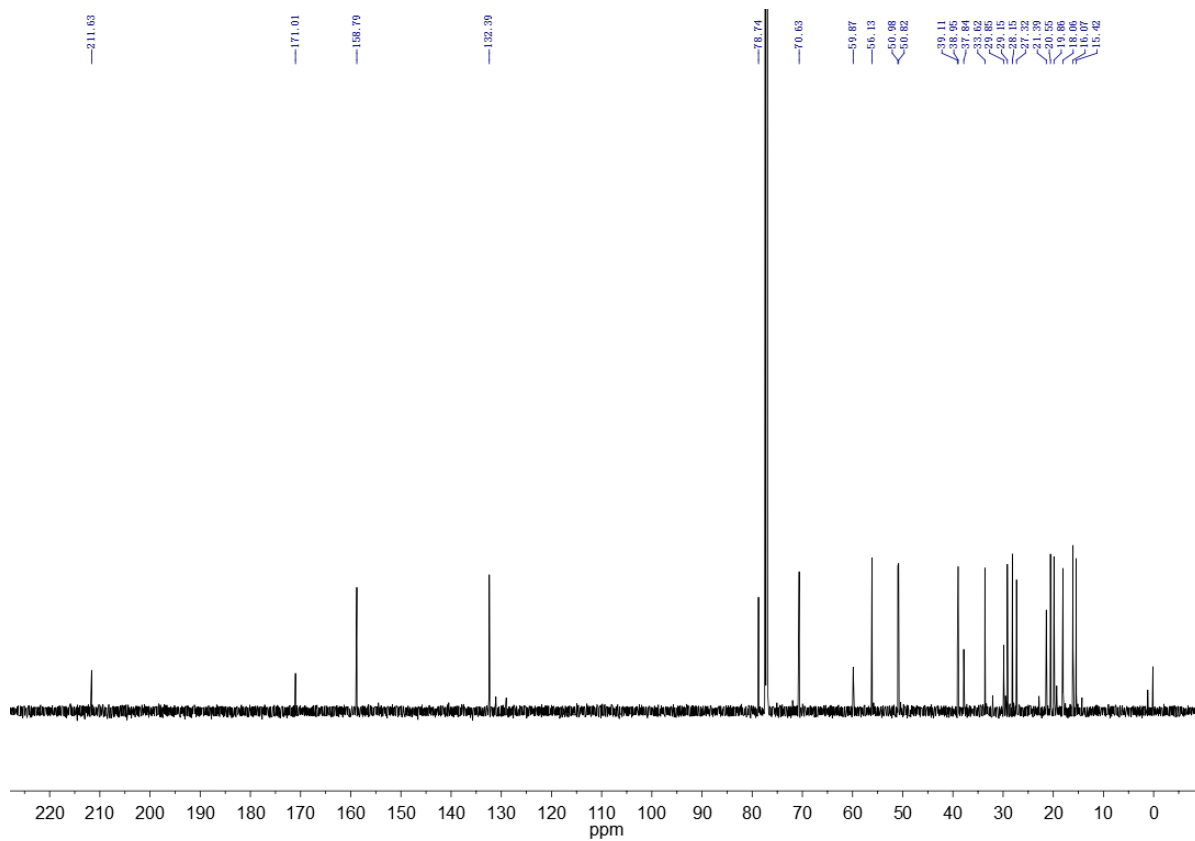
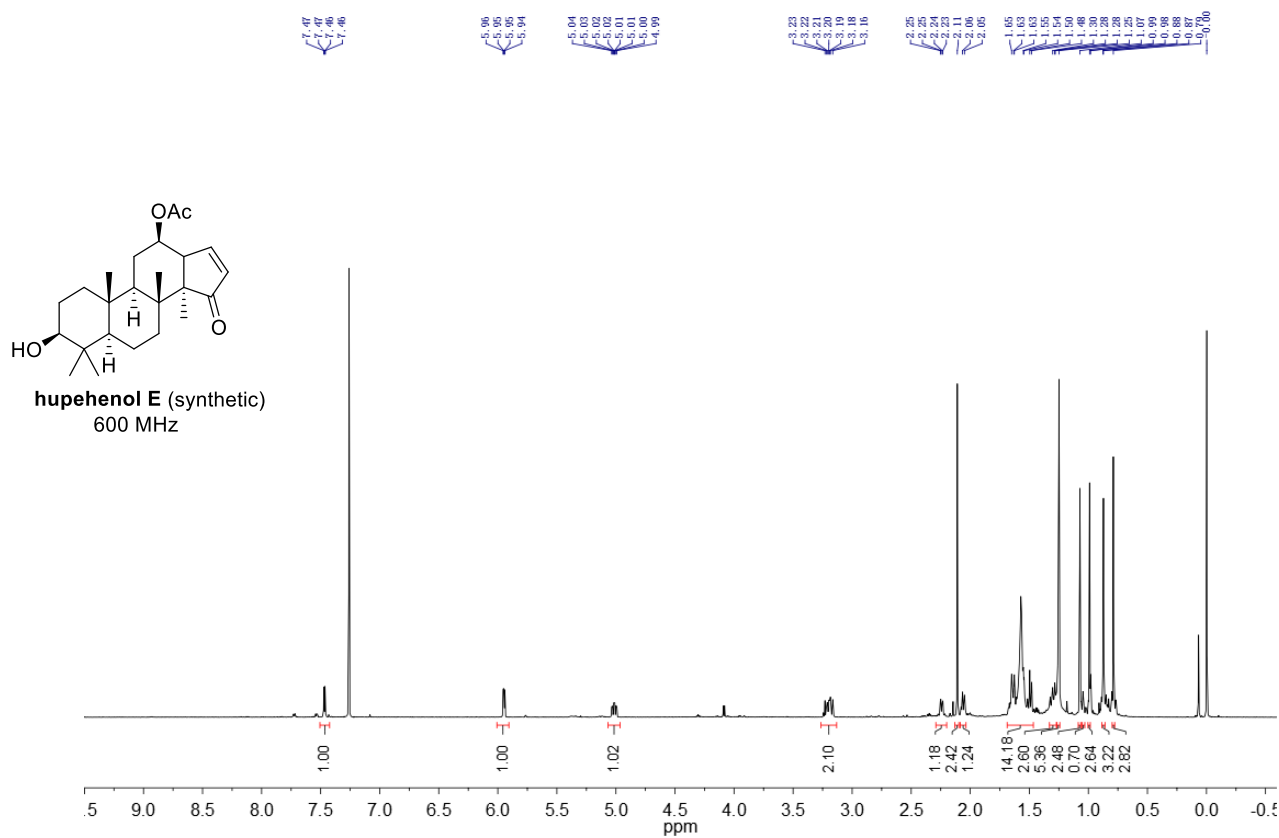
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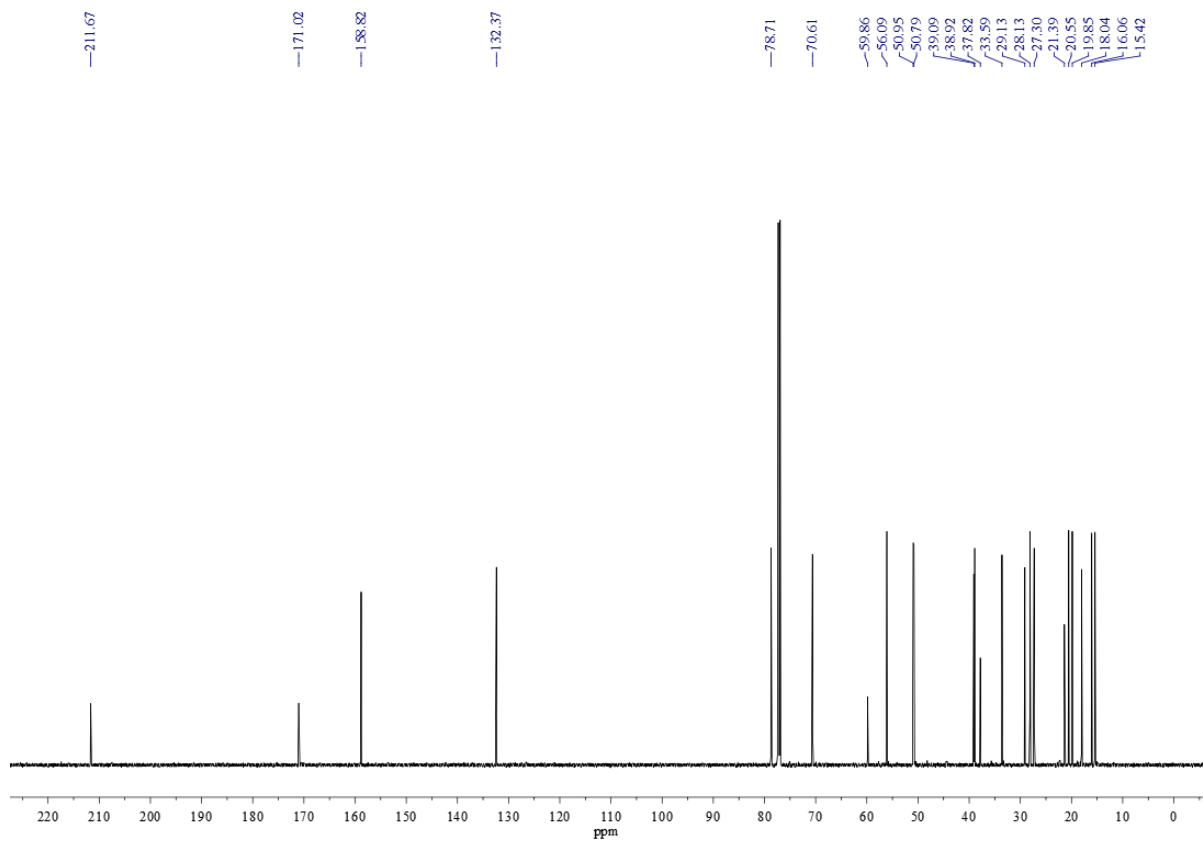
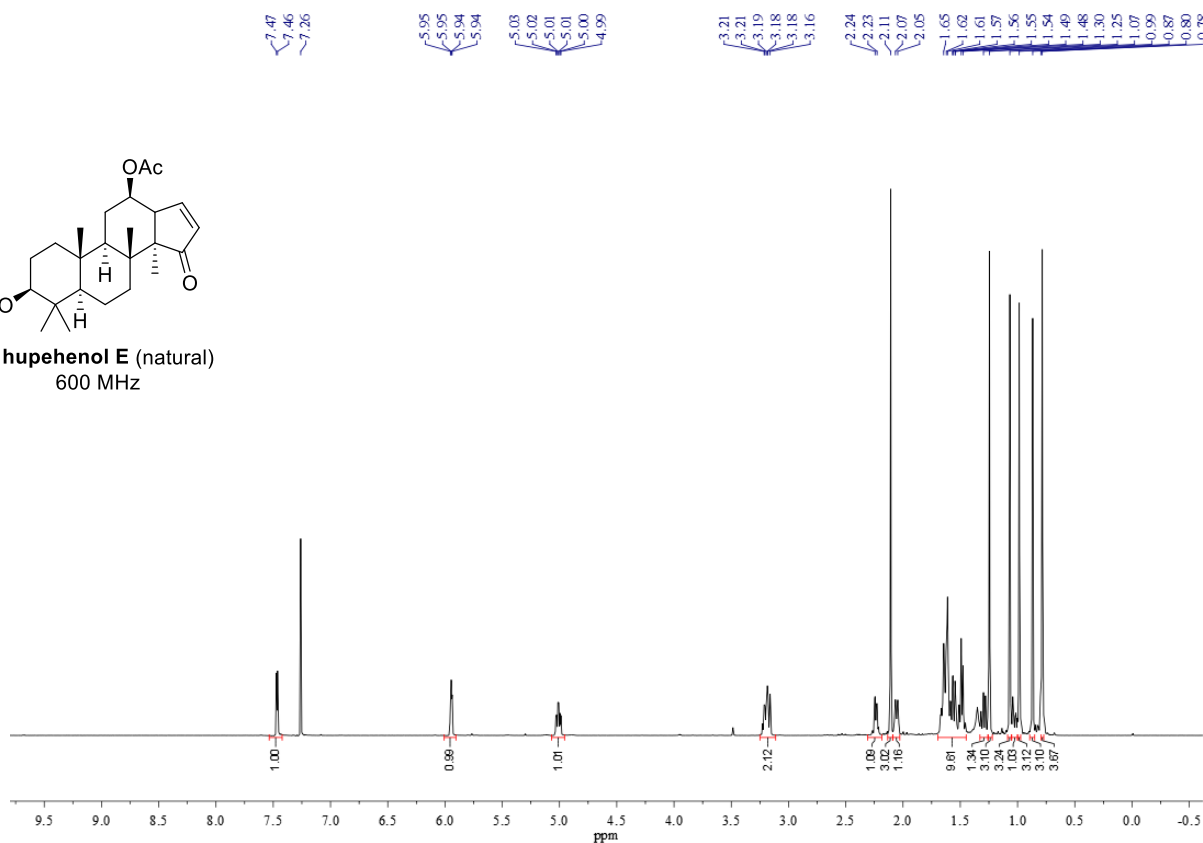
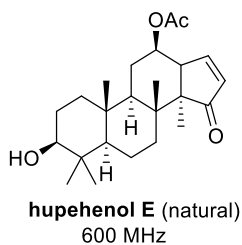
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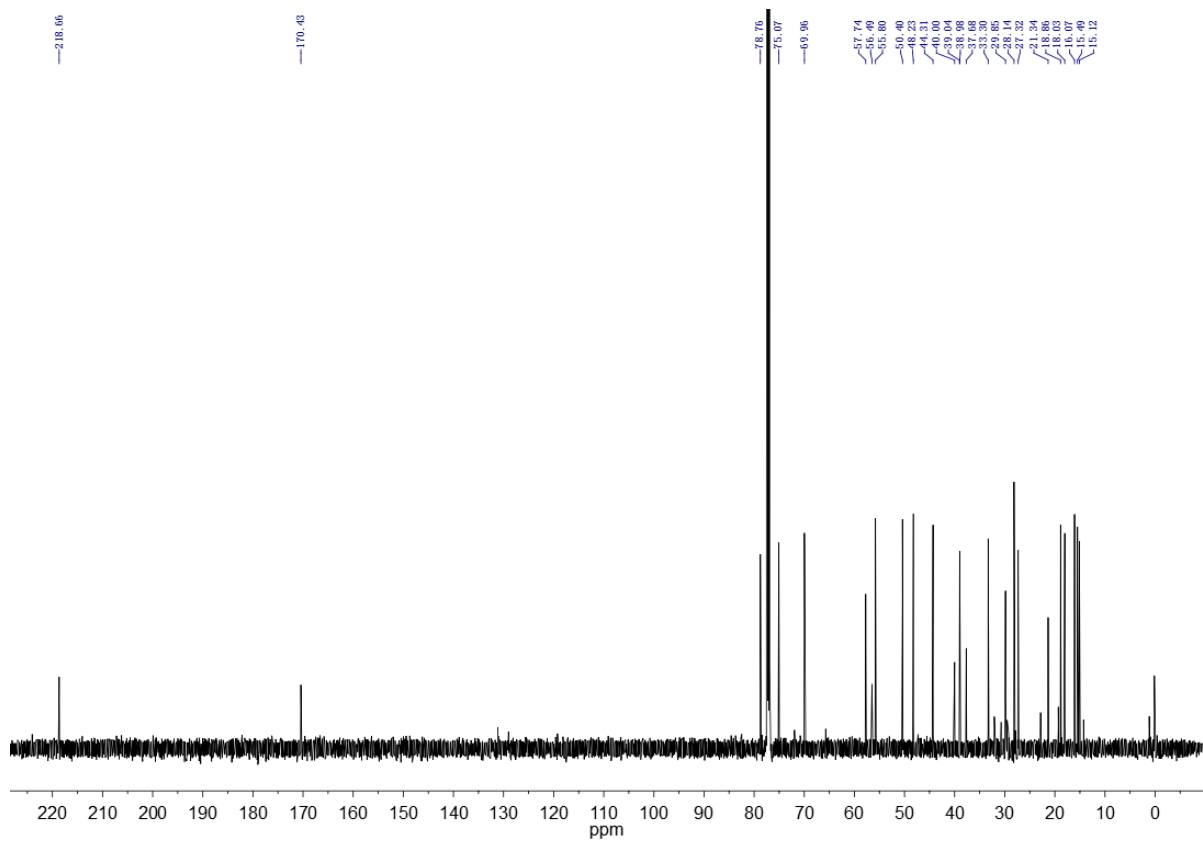
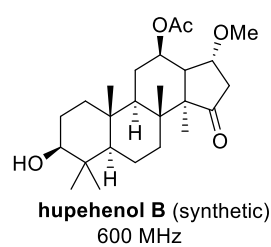


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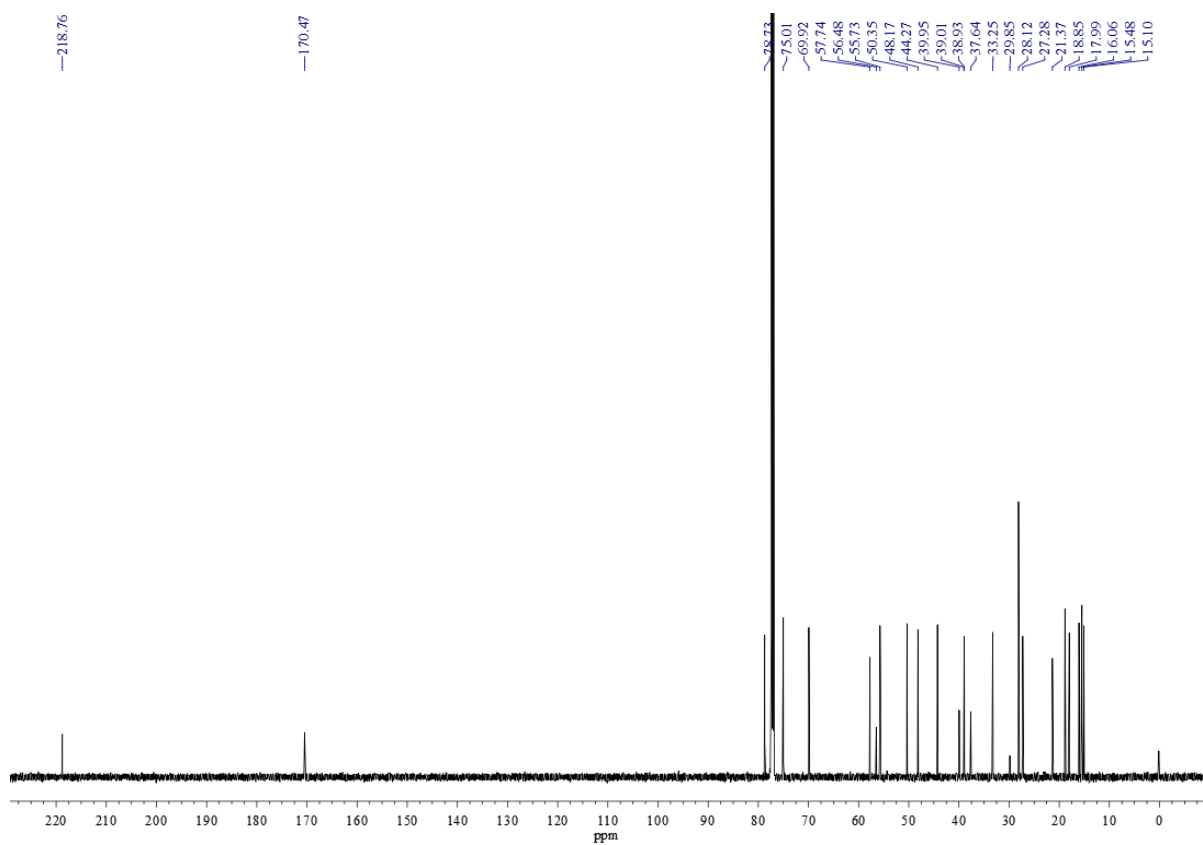
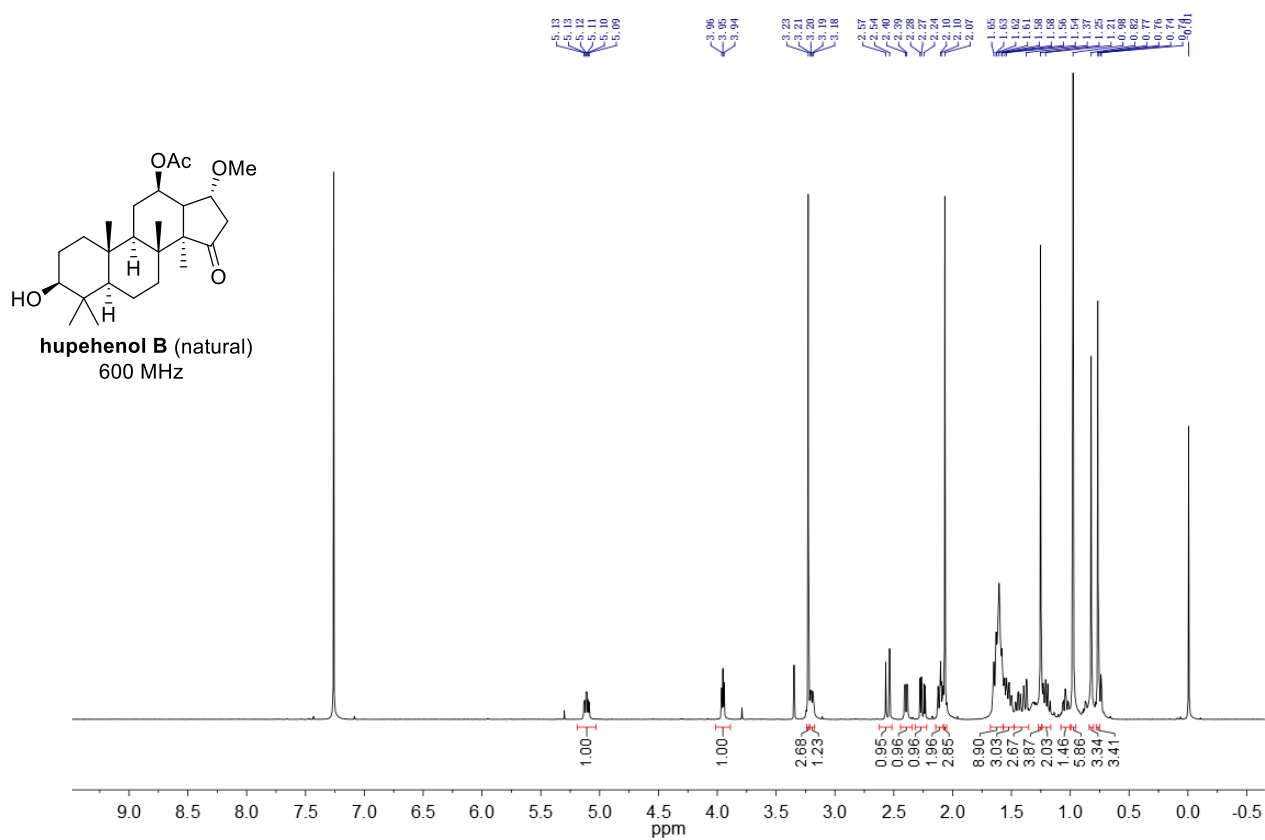


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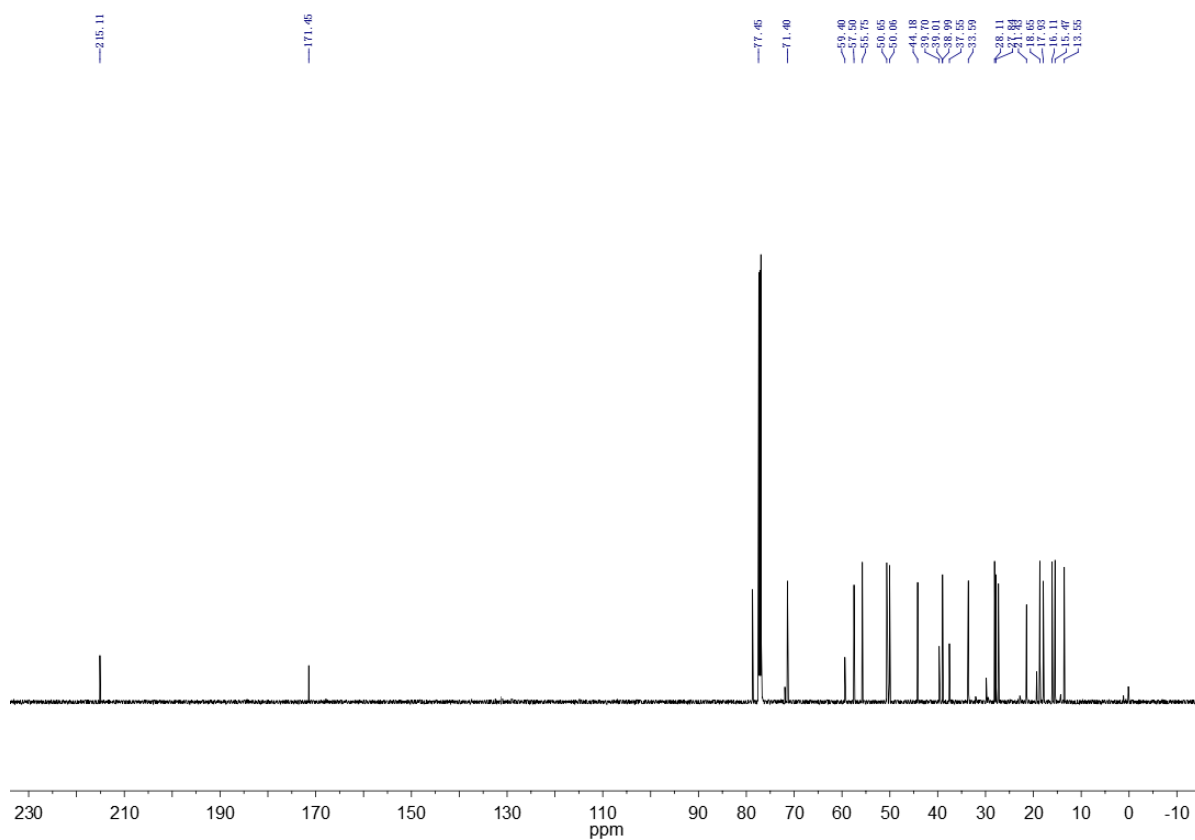
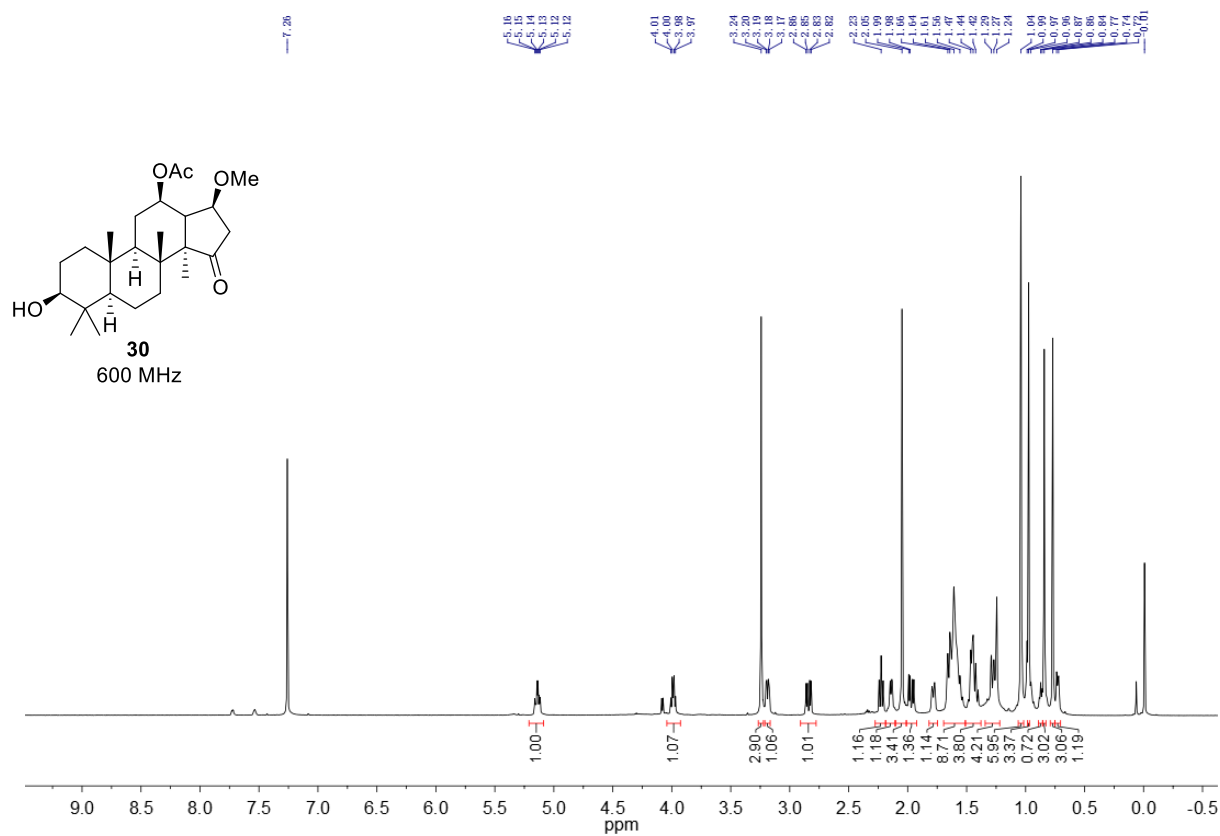




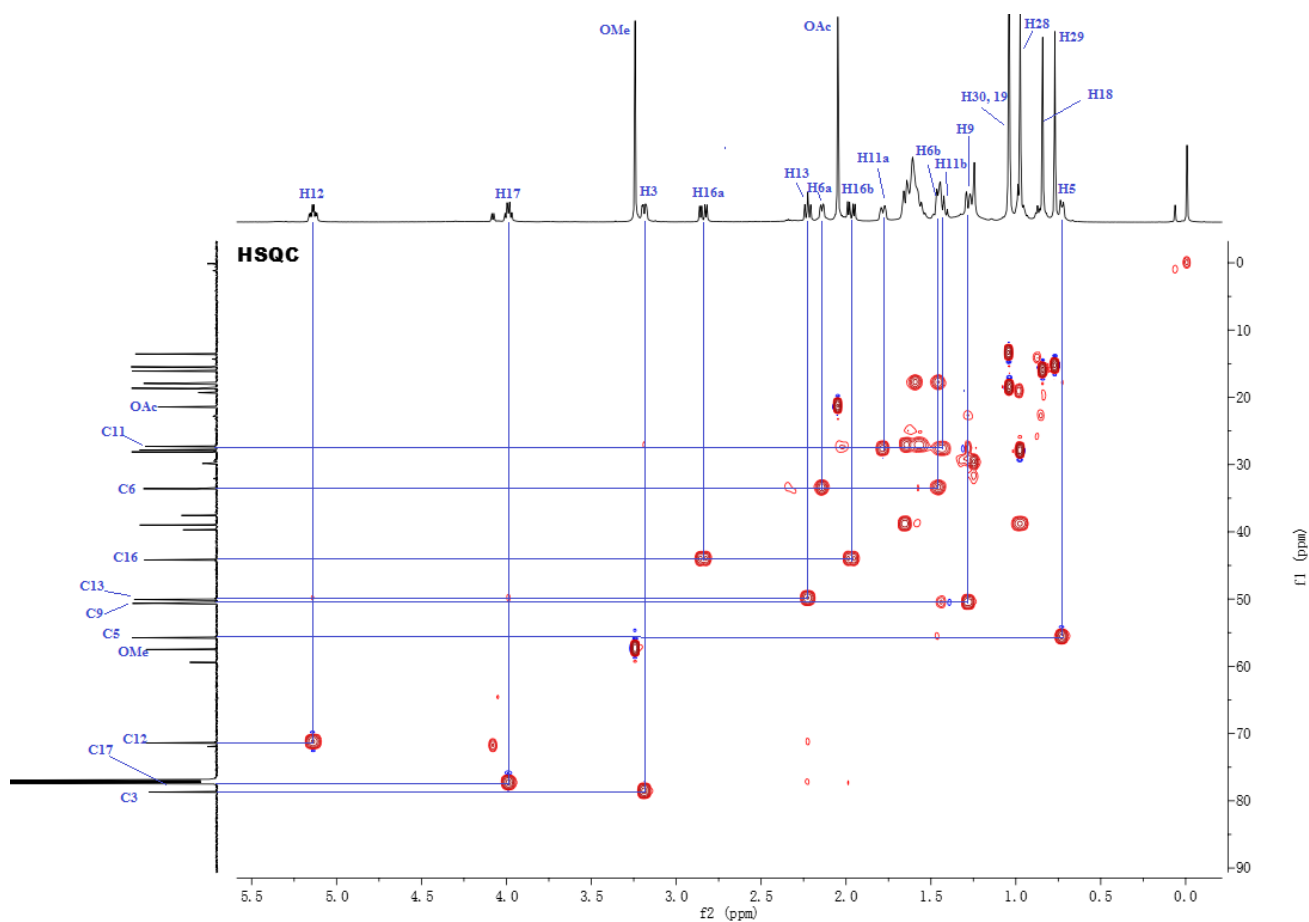
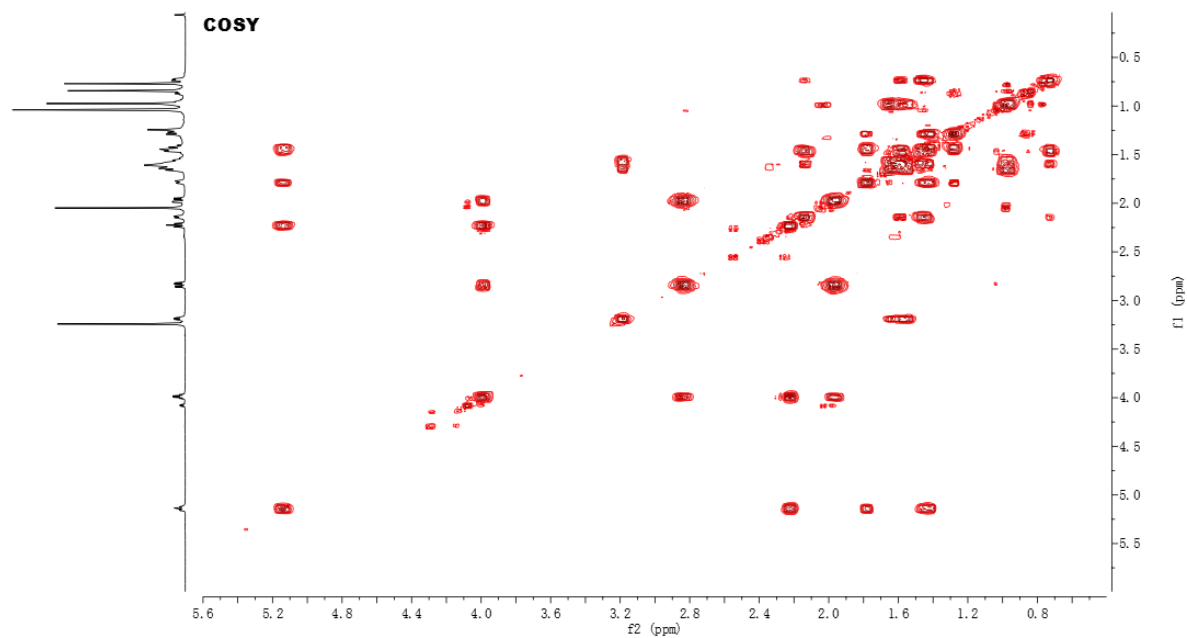
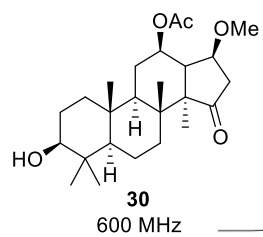
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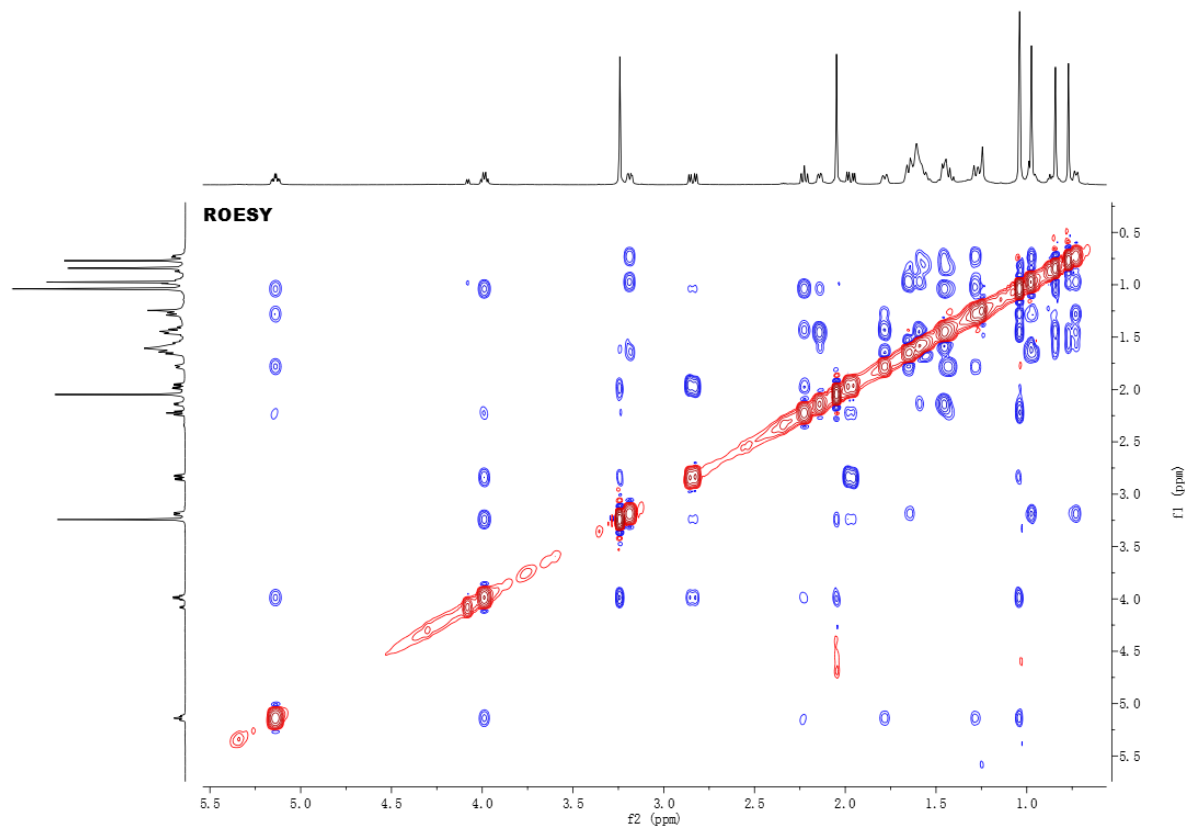
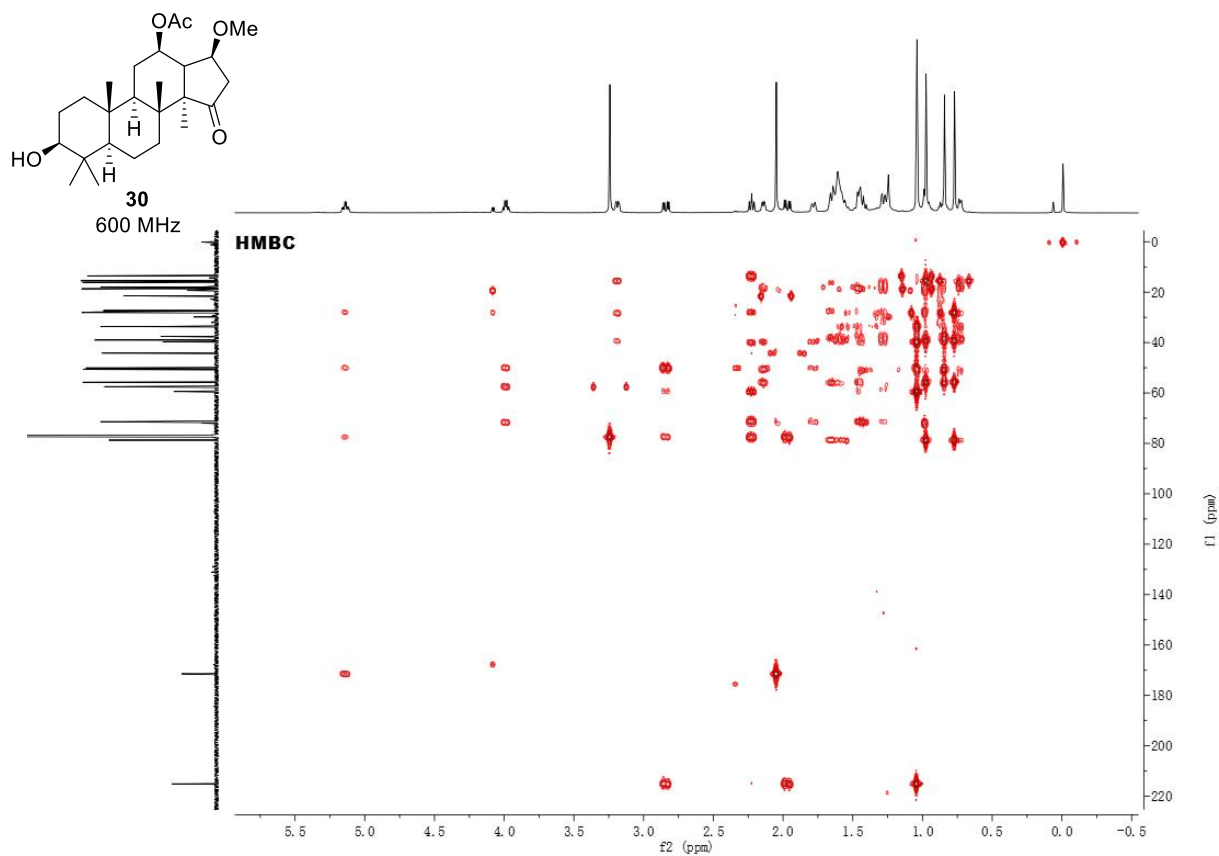
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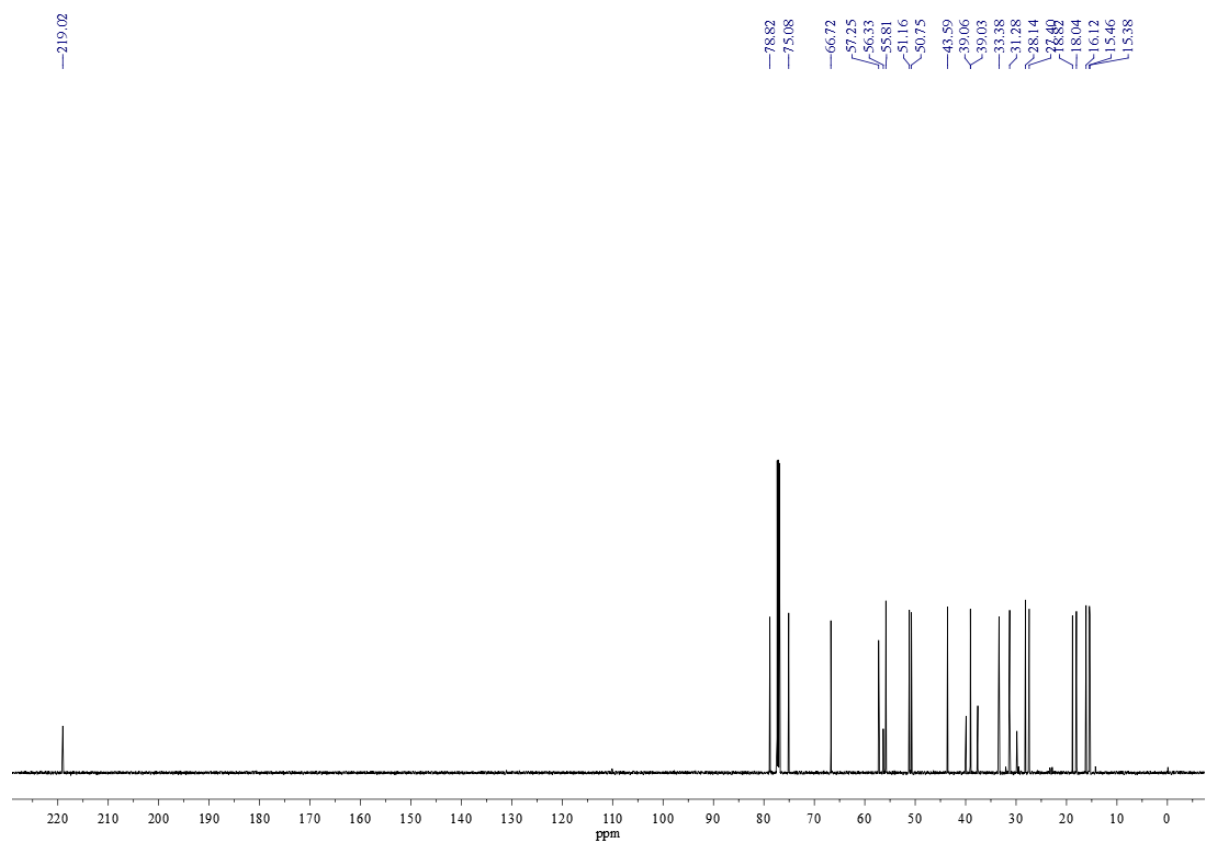
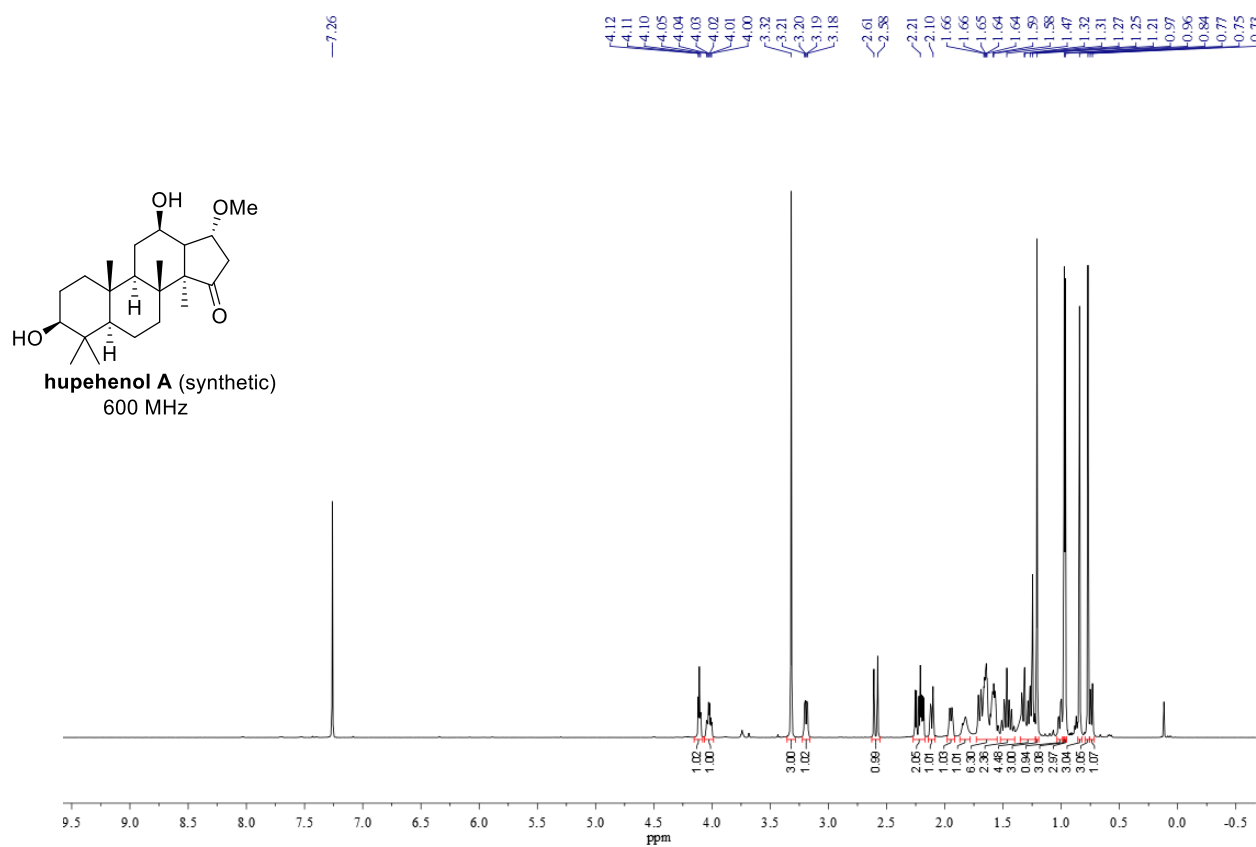
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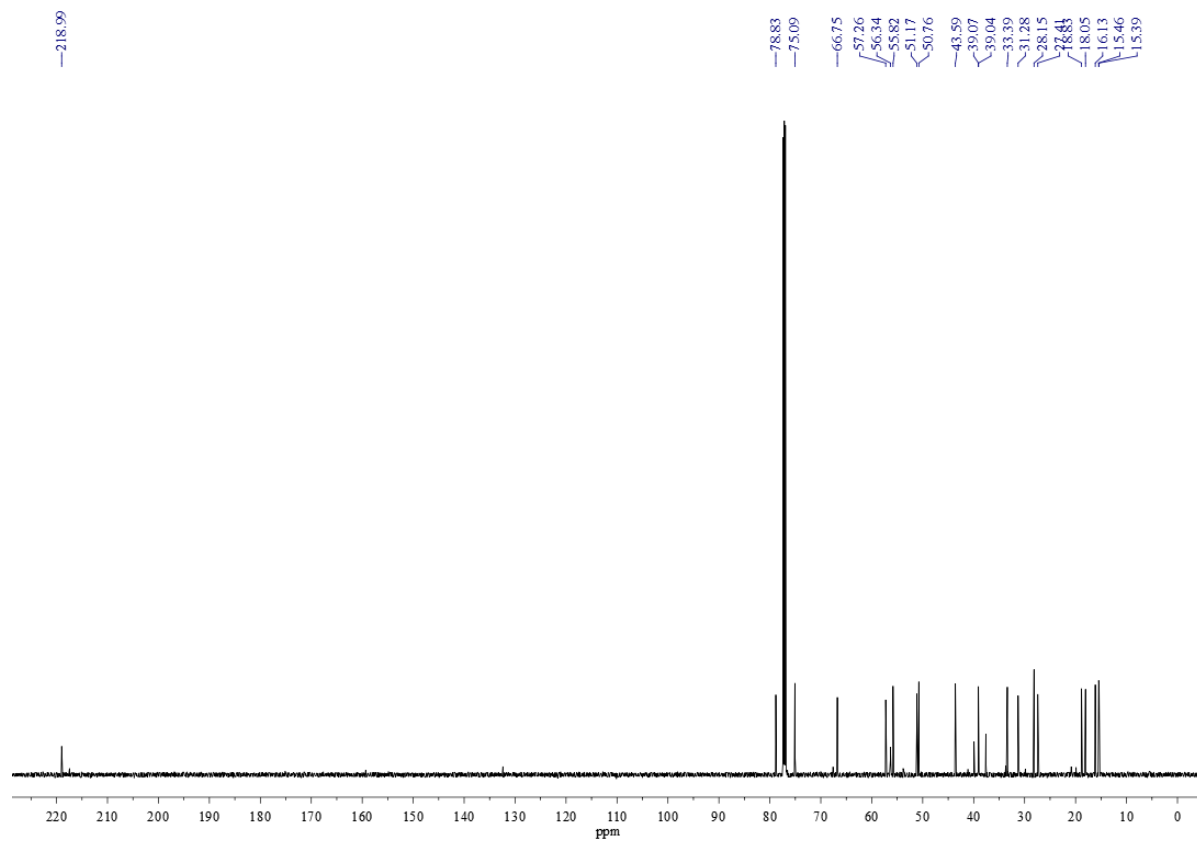
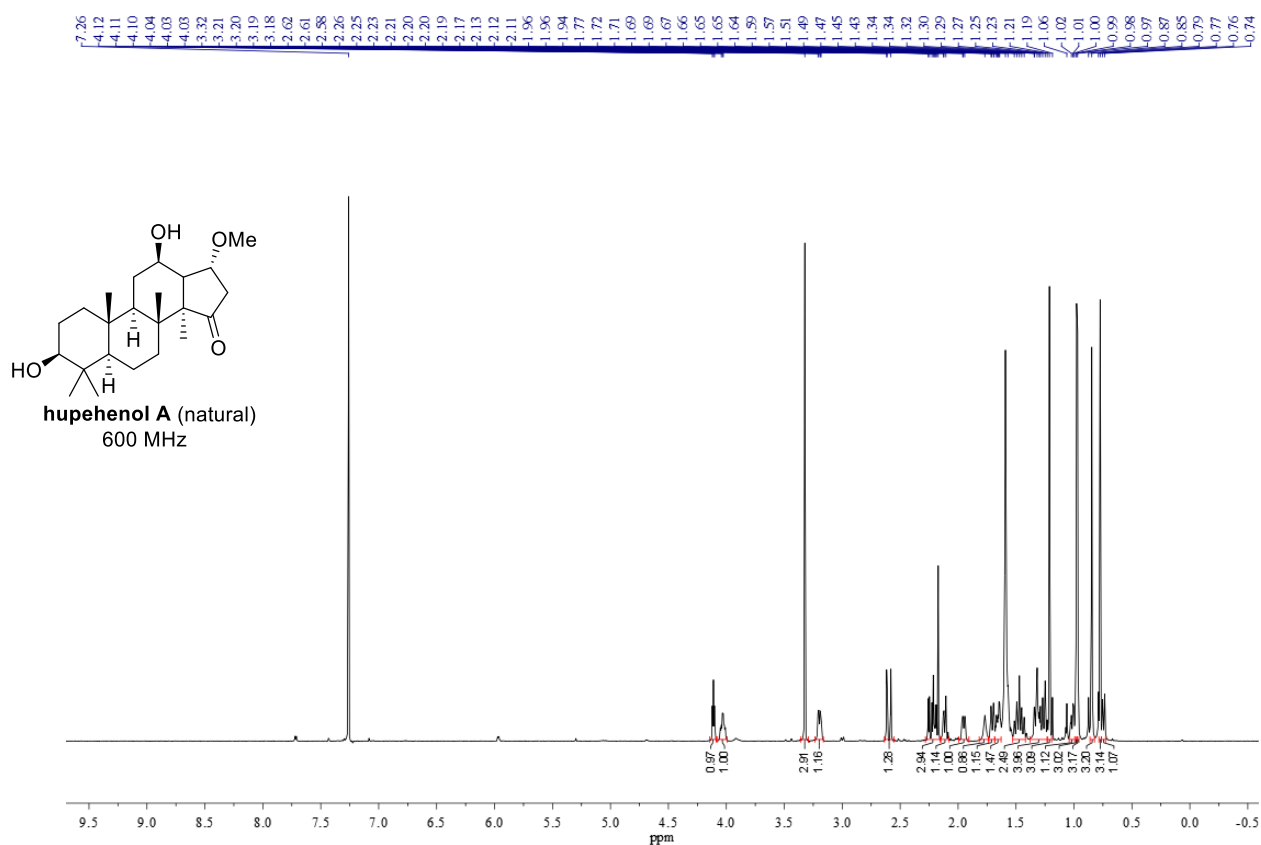
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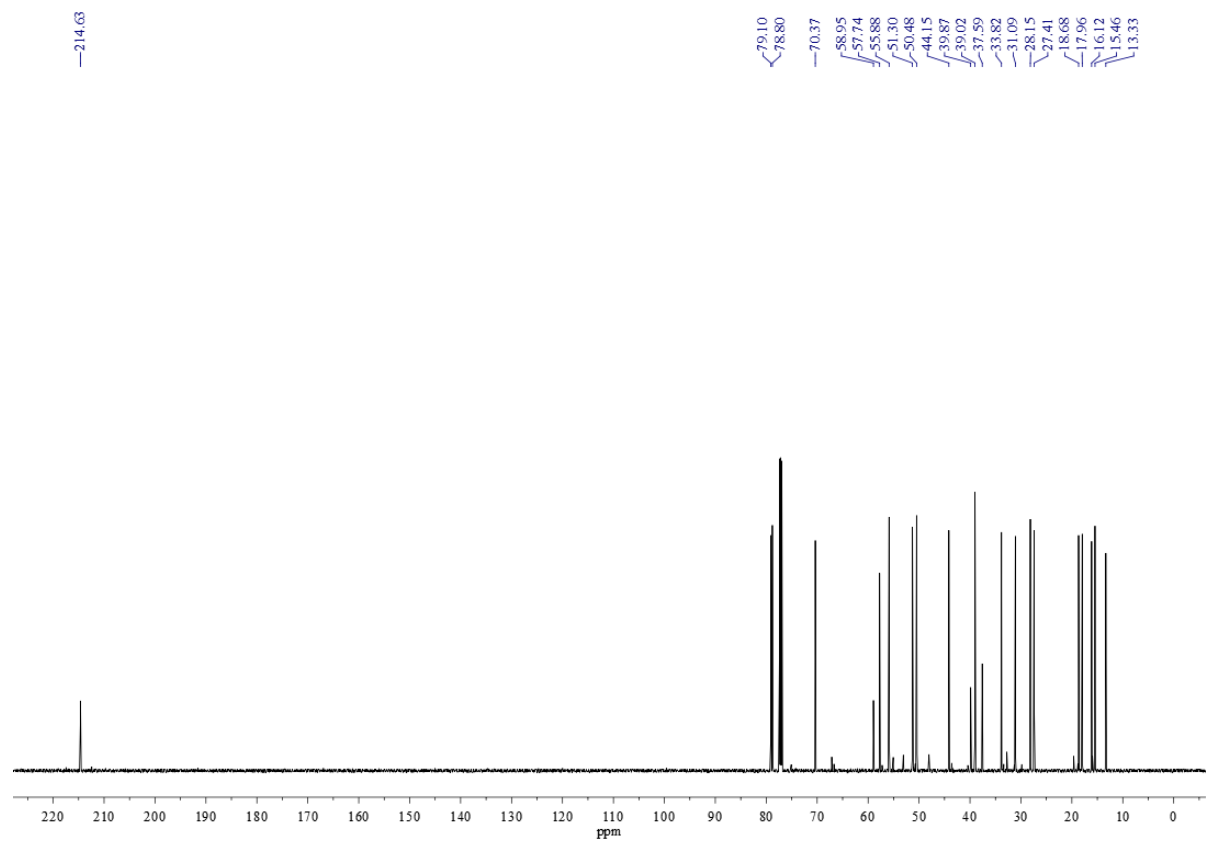
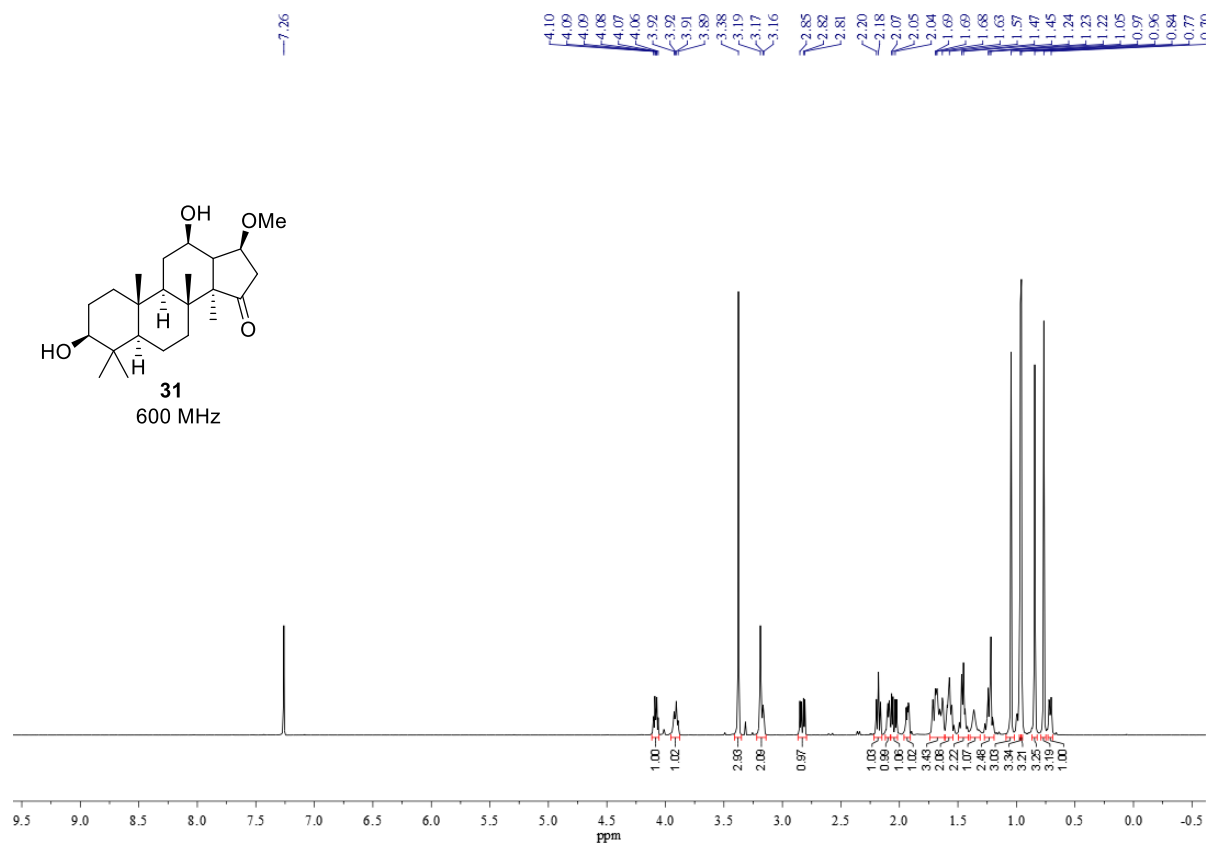
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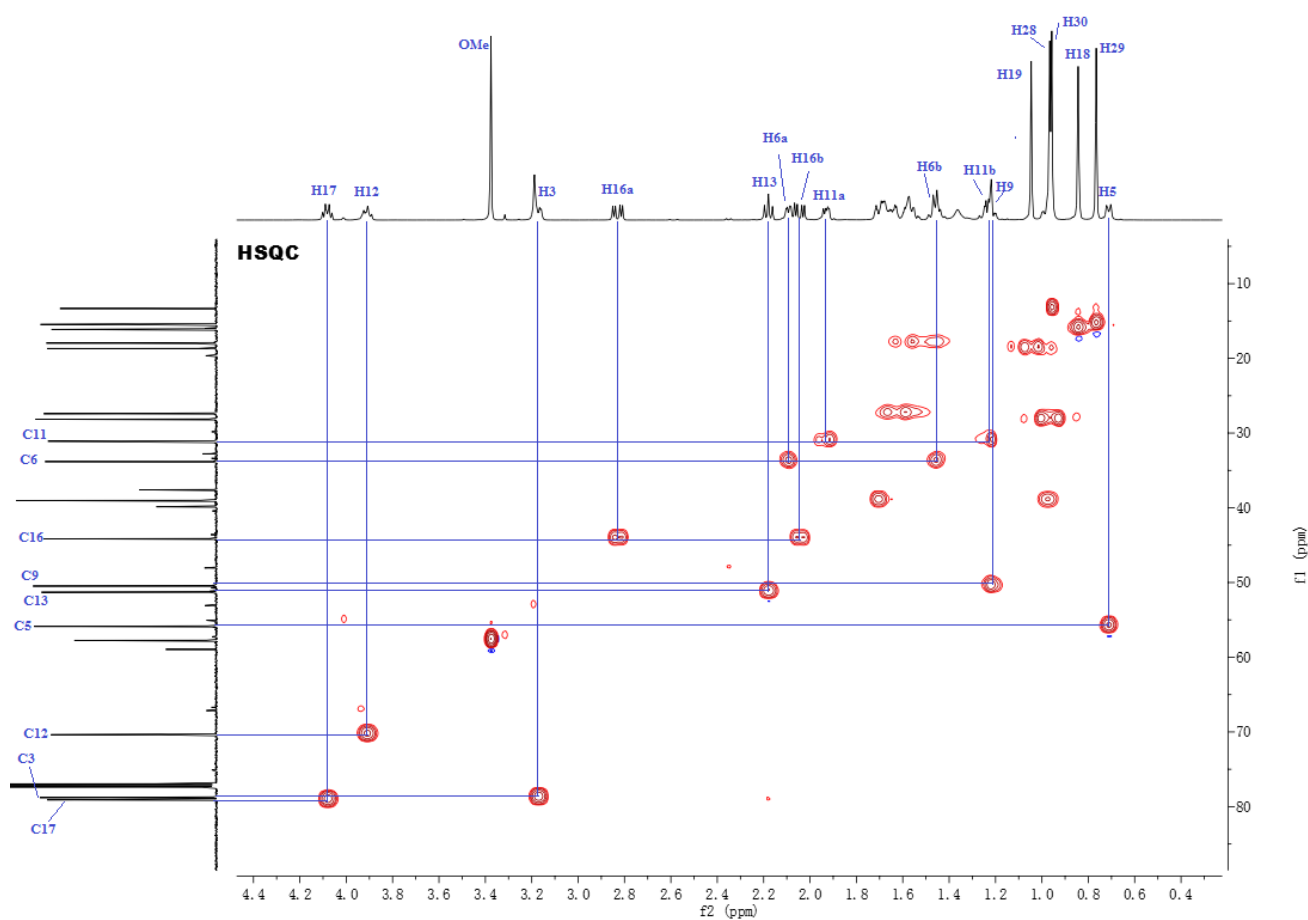
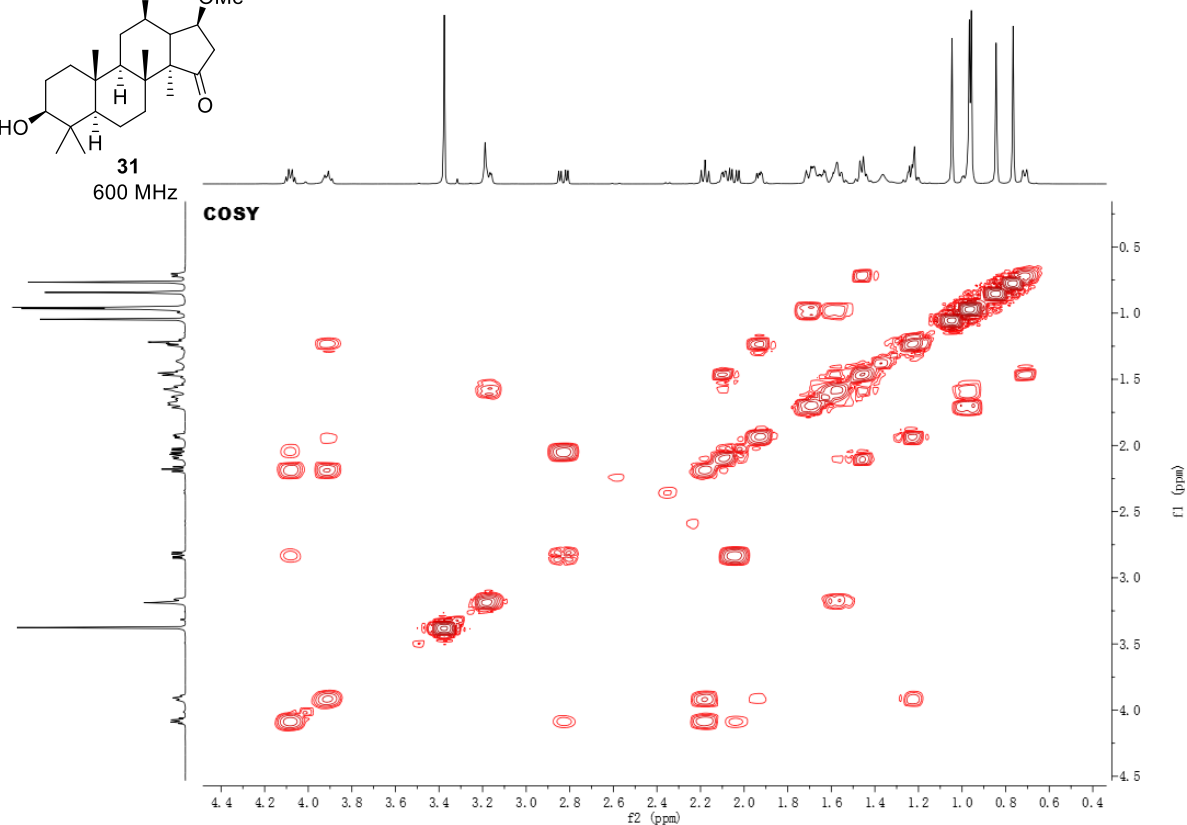
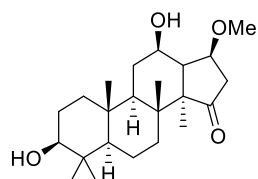
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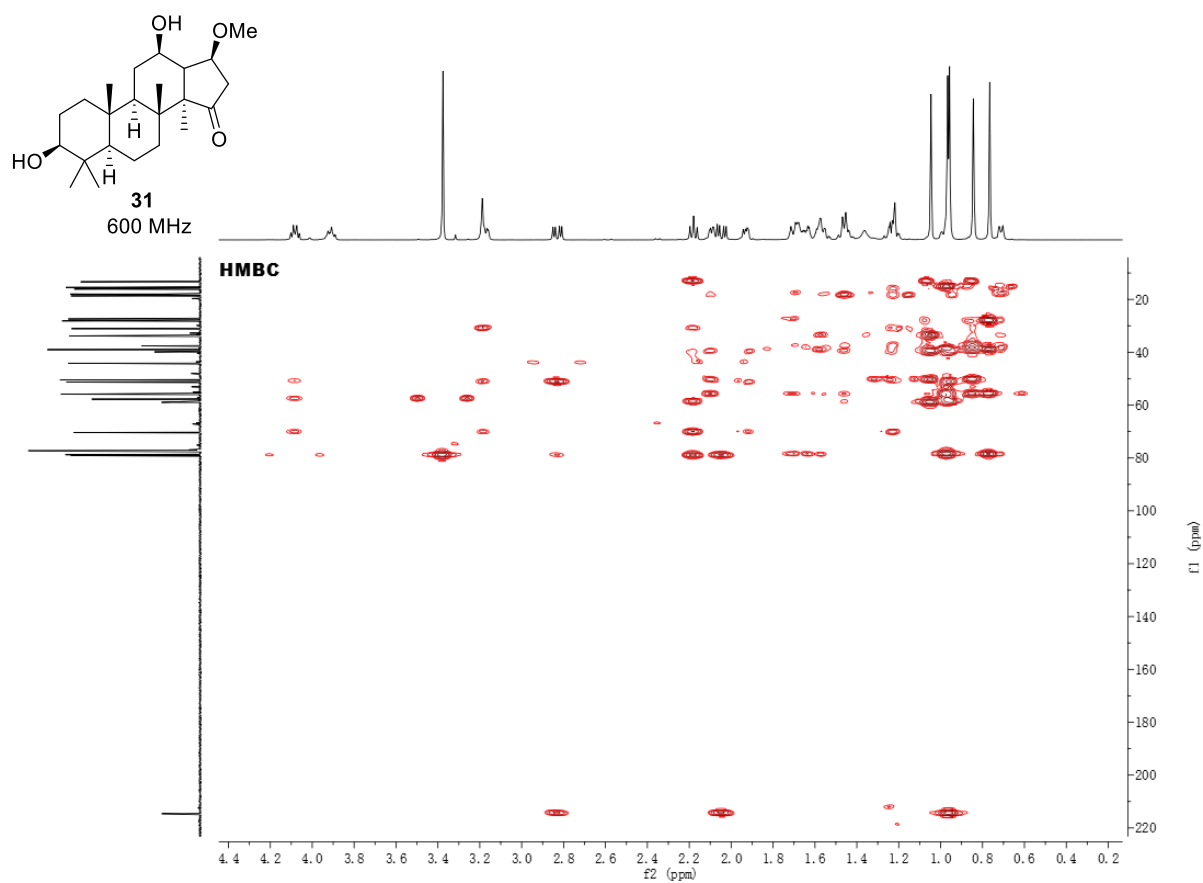
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Supporting Information

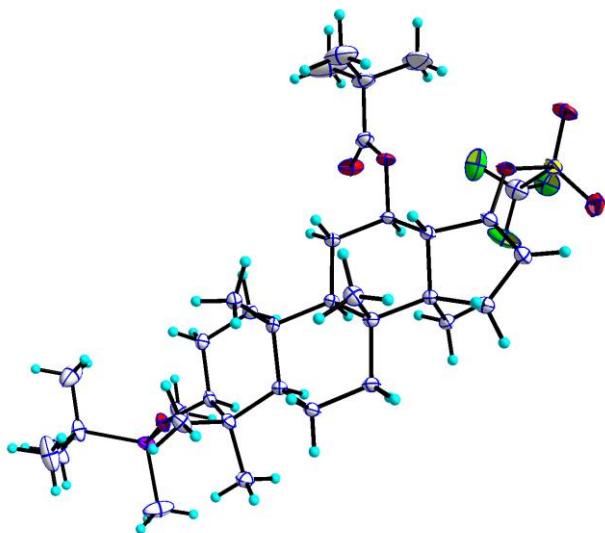


Supporting Information



Supporting Information

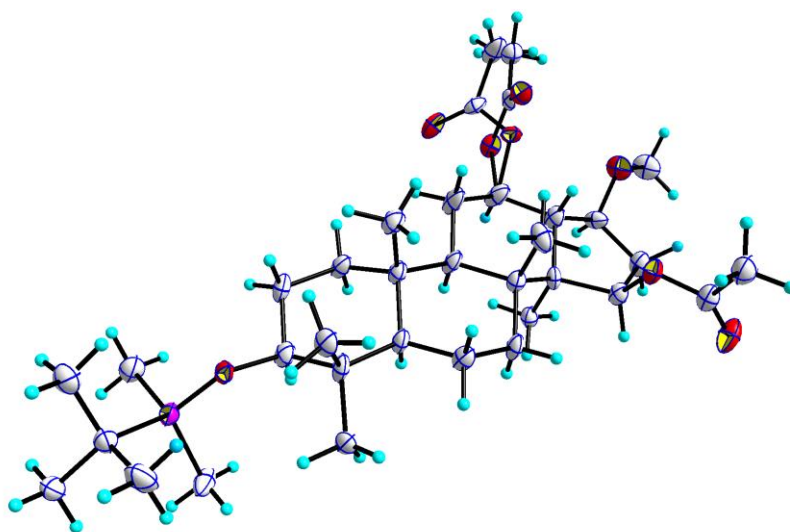
Crystal data for compound **17**: $C_{34}H_{57}F_3O_6SSi$, $M = 678.95$, orthorhombic, $a = 9.526(2) \text{ \AA}$, $b = 15.182(3) \text{ \AA}$, $c = 25.702(5) \text{ \AA}$, $\alpha = 90.00^\circ$, $\beta = 90.00^\circ$, $\gamma = 90.00^\circ$, $V = 3717.2(13) \text{ \AA}^3$, $T = 100(2) \text{ K}$, space group $P212121$, $Z = 4$, $\mu(\text{MoK}\alpha) = 0.174 \text{ mm}^{-1}$, 36539 reflections measured, 9281 independent reflections ($R_{\text{int}} = 0.0567$). The final R_I values were 0.0449 ($I > 2\sigma(I)$). The final $wR(F^2)$ values were 0.1104 ($I > 2\sigma(I)$). The final R_I values were 0.0546 (all data). The final $wR(F^2)$ values were 0.1154 (all data). The goodness of fit on F^2 was 1.050. Flack parameter = $-0.02(6)$. (CCDC 1405681)



Displacement ellipsoids are drawn at the 50% probability level.

Supporting Information

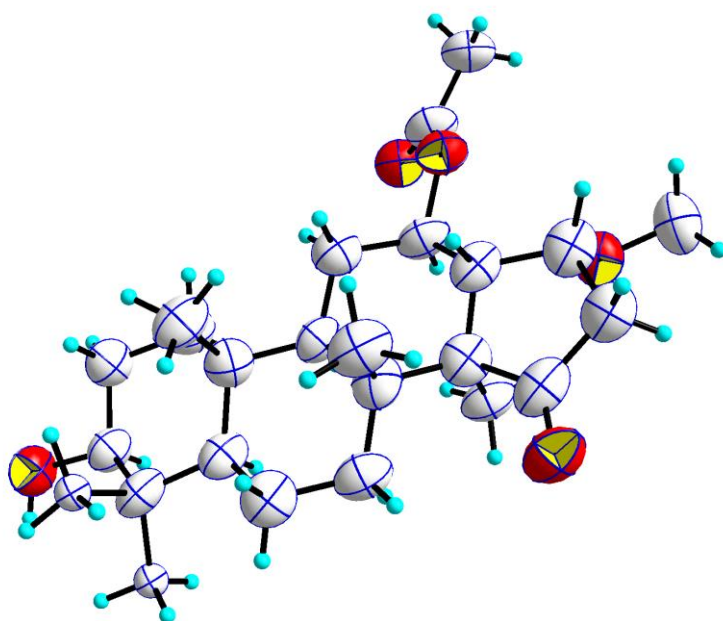
Crystal data for compound **26a**: $C_{33}H_{58}O_6Si$, $M = 578.88$, monoclinic, $a = 11.1824(8) \text{ \AA}$, $b = 12.1736(10) \text{ \AA}$, $c = 12.1396(9) \text{ \AA}$, $\alpha = 90.00^\circ$, $\beta = 100.485(3)^\circ$, $\gamma = 90.00^\circ$, $V = 1625.0(2) \text{ \AA}^3$, $T = 100(2) \text{ K}$, space group $P21$, $Z = 2$, $\mu(\text{CuK}\alpha) = 0.960 \text{ mm}^{-1}$, 12191 reflections measured, 4693 independent reflections ($R_{int} = 0.0555$). The final R_I values were 0.0771 ($I > 2\sigma(I)$). The final $wR(F^2)$ values were 0.2346 ($I > 2\sigma(I)$). The final R_I values were 0.0793 (all data). The final $wR(F^2)$ values were 0.2370 (all data). The goodness of fit on F^2 was 1.163. Flack parameter = 0.11(6). The Hooft parameter is 0.127(18) for 1812 Bijvoet pairs. (CCDC 1405682)



Displacement ellipsoids are drawn at the 50% probability level.

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Crystal data for compound **4**: $C_{25}H_{40}O_5$, $M = 420.57$, orthorhombic, $a = 7.3472(5)$ Å, $b = 11.4681(8)$ Å, $c = 26.6223(19)$ Å, $\alpha = 90.00^\circ$, $\beta = 90.00^\circ$, $\gamma = 90.00^\circ$, $V = 2243.2(3)$ Å³, $T = 100(2)$ K, space group $P212121$, $Z = 4$, $\mu(\text{CuK}\alpha) = 0.676$ mm⁻¹, 11376 reflections measured, 3830 independent reflections ($R_{\text{int}} = 0.0912$). The final R_I values were 0.1555 ($I > 2\sigma(I)$). The final $wR(F^2)$ values were 0.3719 ($I > 2\sigma(I)$). The final R_I values were 0.2829 (all data). The final $wR(F^2)$ values were 0.4569 (all data). The goodness of fit on F^2 was 1.582. Flack parameter = 0.3(9). (**CCDC 1405683**)



Displacement ellipsoids are drawn at the 50% probability level.